

ADVANCE PROGRAM

2 0 1 1
INTERNATIONAL CONFERENCE ON

SOLID STATE

DEVICES AND MATERIALS

Conference ___ September 28-30, 2011

Place _____ Aichi Industry & Labor Center
(WINC AICHI)

Short Course &
Workshop _____ September 27, 2011

Sponsored by
The Japan Society of Applied Physics
Technical-Cosponsored by
IEEE Electron Devices Society
in cooperation with

The Electrochemical Society of Japan

IEEE EDS Japan Chapter

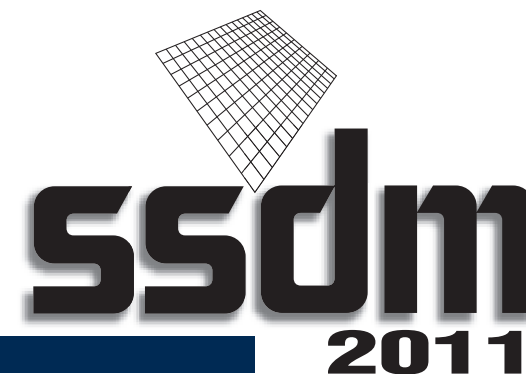
The Institute of Electrical Engineers of Japan

The Institute of Electronics, Information and Communication Engineers

The Institute of Image Information and Television Engineers

Japan Institute of Electronics Packaging

Web Site : <http://www.ssdm.jp>

The logo for the 2011 International Conference on Solid State Devices and Materials (SSDM 2011). It features a stylized grid pattern above the lowercase letters 'ssdm' in a bold, sans-serif font, with the year '2011' positioned below it.

CONTENTS

PREFACE	3
SUPPORTING COMPANIES, FOUNDATIONS, AND ORGANIZATIONS	5
COMMITTEE MEMBERS	7
GENERAL INFORMATION	10
PLENARY SESSION	12
TECHNICAL PROGRAM	
SEPTEMBER 28 (Wed.)	14
SEPTEMBER 29 (Thu.)	20
SEPTEMBER 30 (Fri.)	34
RUMP SESSIONS	44
SHORT COURSES & WORKSHOPS	45
INSTRUCTION FOR SPEAKERS	47
EXHIBITION	48
AUTHOR INDEX	49
ACCESS MAP	60
FLOOR GUIDE	62
PROGRAM TIME TABLE	66

PREFACE

On behalf of the organizing committee, it is my great pleasure and honor to welcome you to the 43rd International Conference on Solid State Devices and Materials (SSDM 2011), held on September 28–30, 2011 in Nagoya, Japan. SSDM 2011 is sponsored by the Japan Society of Applied Physics and technically co-sponsored by the IEEE Electron Devices Society. This year, the venue for SSDM 2011 is the Aichi Industry & Labor Center (WINC AICHI), Nagoya, which is located at the center of Nagoya City. Nagoya City is a castle town established 400 years ago that today is an industrial core of electronic and automotive fields in Japan.

SSDM is one of the most important large-scale conferences in the field of solid state device technologies and materials, presenting the latest scientific achievements and opportunities to exchange technological information. SSDM has been continuously growing and increasing its significance as a unique conference covering a broad spectrum in the field; SSDM covers a very wide scope and includes the physics and processing technology of electron devices, photonic devices and organic devices, as well as their materials and integration into circuits and systems.

In the plenary session, we are pleased to invite three distinguished speakers, Dr. Masao Fukuma (Semiconductor Industry Research Institute Japan, Japan), Dr. Moritaka Yoshida (Toyota Motor Corporation, Japan) and Prof. Tsu-Jae King Liu (University of California at Berkeley, USA), who will speak on future prospects in the semiconductor industry and the application fields of nanoelectronics, respectively. In addition, SSDM 2011 features short courses and workshops. This year, we have planned two short courses related to advanced CMOS technology and carbon-nanotubes/graphenes, and two workshops related to wide gap semiconductor power devices and organic electronics, for stimulating and encouraging students and young researchers and engineers. These short courses and workshops will be held on September 27, the day before the conference.

Reflecting the international nature of SSDM, 966 high quality abstracts were submitted to SSDM 2011 from 24 countries, a record number of submitted abstracts in SSDM history. Great effort by the technical program committee in selecting the abstracts has resulted in an excellent technical program consisting of 55 invited papers, including the three plenary talks, 390 contributed oral papers, 261 poster papers, and 32 late news papers. The papers have been categorized into 14 sub-areas, covering advanced and important topics. We hope all of the papers presented at SSDM 2011 address in depth nearly all the key issues in the field and provide stimulation and new perspectives to all participants.

We wish to express our sincere appreciation to all the committee members for their tremendously significant contribution to SSDM 2011. We also express our heartfelt gratitude for the financial support provided by the supporting corporations and foundations, including MEXT-JSPS. And finally, we sincerely hope SSDM 2011 enhances your research for upcoming years and provides you with an invaluable experience.

September 2011



Shigeaki Zaima
General Chair, SSDM 2011
Professor, Nagoya University

SUPPORTING COMPANIES, FOUNDATIONS, AND ORGANIZATIONS

Sponsoring Companies and Foundations:

Applied Materials Japan, Inc.
Association of Super-Advanced Electronics Technologies (ASET)
DENSO Corporation
ESCO, Ltd.
Foundation for Promotion of Material Science and Technology of Japan
FUJITSU LIMITED
Hitachi, Ltd.
Hitachi Kokusai Electric Inc.
KLA-Tencor Japan Ltd.
Mitsubishi Electric Corporation
NEC Corporation
Panasonic Corporation
Renesas Electronics Corporation
ROHM Co, Ltd.
Semiconductor Energy Laboratory Co., Ltd.
Sharp Corporation
Sony Corporation
Tokyo Electron Ltd.
Toshiba Corporation
ULVAC, Inc.
(in alphabetical order)

as of August 31, 2011

Subsidizing Foundations and Organizations:

Inoue Foundation for Science
Ministry of Education, Culture, Sports, Science and Technology
Nagoya Convention & Visitors Bureau
Nippon Sheet Glass Foundation for Materials Science and Engineering
Support Center for Advanced Telecommunications Technology Research, Foundation
The Murata Science Foundation
(in alphabetical order)

as of August 31, 2011

COMMITTEE MEMBERS

ORGANIZING COMMITTEE

Chair: S. Zaima (Nagoya Univ.)
Vice-chair: K. Kyuma (Mitsubishi Electric Corp.)
Member: Y. Aoyagi (Ritsumeikan Univ.)
Y. Arakawa (Univ. of Tokyo)
T. Asano (Kyushu Univ.)
S. Chung (National Chiao Tung Univ.)
Y. Horiike (NIMS)
Y. Inoue (Renesas Electronics Corp.)
H. Ishiwara (Tokyo Tech, Professor emeritus)
H. Ito (Tokyo Electron Ltd.)
A. Kamisawa (ROHM Co., Ltd.)
T. Kamiya (NICT)
T. Kanayama (AIST)
Y. Kawamura (ASET)
M. Koyanagi (Tohoku Univ.)
T. Makimoto (NTT Corp.)
K. Natori (Tokyo Tech)
T. Ohmi (Tohoku Univ.)
N. Saito (NHK)
H. Sakaki (Toyota Technological Inst.)
T. Shibata (Univ. of Tokyo)
Y. Shiraki (Tokyo City Univ.)
J. Sone (NIMS)
K. Tada (Kanazawa Inst. of Tech.)
S. Tahara (NEC Corp.)
A. Takahashi (Sharp Corp.)
K. Taniguchi (Nara Nat'l Col. of Tech.)
T. Tatsumi (Sony Corp.)
K. Torii (Hitachi, Ltd.)
Y. Tsunashima (Toshiba Corp.)
H. Uchida (Panasonic Corp.)
J. Ueda (SIRIJ)
H. Watanabe (EIDEC)
E. Yano (Fujitsu Labs. Ltd.)
Y. Yasuda (Tohoku Univ.)
N. Yokoyama (AIST)

STEERING COMMITTEE

Chair: M. Horii (Nagoya Univ.)
Vice-chair: T. Oomori (Mitsubishi Electric Corp.)
Secretary: H. Kondo (Nagoya Univ.)
O. Nakatsuka (Nagoya Univ.)
Member: H. Ikeda (Shizuoka Univ.)
M. Iwaya (Meijo Univ.)
M. Kato (Nagoya Inst. of Tech.)
T. Kawano (Toyohashi Univ. of Tech.)
S. Kumagai (Toyota Technological Inst.)
S. H. Lee (KAIST)
K. Makihara (Nagoya Univ.)
H. Miyake (Mie Univ.)
Y. Neo (Shizuoka Univ.)
K. Nishikawa (Mitsubishi Electric Corp.)
Y. Ohno (Nagoya Univ.)
M. Sakashita (Nagoya Univ.)
K. Takeda (Nagoya Univ.)
T. Takeuchi (Meijo Univ.)
W. Takeuchi (Nagoya Univ.)
S. Uno (Ritsumeikan Univ.)
J. Xu (National Lab. of Solid State Microstructures)
M. Yamaguchi (Nagoya Univ.)
W. Yeh (Shimane Univ.)
Y. C. Yeo (National Univ. of Singapore)
H. W. Zan (NCTU)

INTERNATIONAL ADVISORY COMMITTEE

C. Y. Chang (National Chiao Tung Univ.)
G. Declerck (IMEC)
L. Esaki (The Sci. and Tech. Promotion Foundation of Ibaraki)
J. S. Harris (Stanford Univ.)
K. v. Klitzing (Max Planck Inst.)
D. L. Kwong (IME)
M. Nakamura (Hitachi, Ltd.)
Y. Nishi (Stanford Univ.)
K. H. Ploog (Paul Drude Inst.)
T. Sugano (Univ. of Tokyo)
K. Takahashi (Tokyo Tech)
S. Tanaka (ISTEC)

PROGRAM COMMITTEE

Chair: T. Fukui (Hokkaido Univ.)
Vice-chair: S. Miyazaki (Nagoya Univ.)
Y. H. Jeong (POSTECH)
H. Yamaguchi (NTT Basic Res. Labs.)
Secretary: S. Hara (Hokkaido Univ.)
K. Uchida (Tokyo Tech)
S. Ohmi (Tokyo Tech)
S. Higashi (Hiroshima Univ.)

Subcommittee Members:

[1] Advanced LSI Processing & Materials Science

Chair: T. Nabatame (NIMS)
Vice-Chair: J. Yugami (Renesas Electronics Corp.)
B. H. Lee (GIST)
Member: T. Aoyama (Toshiba Corp.)
Y. Hayami (Fujitsu Semiconductor Ltd.)
K. Kita (Univ. of Tokyo)
S. Lee (National Univ. of Singapore)
S. Maitrejean (CEA LETI/MINATEC)
S. Migita (AIST)
O. Nakatsuka (Nagoya Univ.)
T. Nakayama (Chiba Univ.)
E. Nishimura (Tokyo Electron Ltd.)
H. Nohira (Tokyo City Univ.)
S. Tsujikawa (Sony Corp.)
P. Ye (Purdue Univ.)

[2] Advanced Interconnect / Materials Technology and Characterization

Chair: S. Ogawa (AIST)
Vice-Chair: M. Kodera (Toshiba Corp.)
G. Beyer (IMEC)
Member: T. Fukushima (Tohoku Univ.)
J. Gambino (IBM)
T. Hasegawa (Sony Corp.)
S. Hsu (National Tsing Hua Univ.)
A. Ikeda (Panasonic Corp.)
H. Ishii (Toyohashi Univ. of Tech.)
K. Ito (Kyoto Univ.)
P. Leduc (CEA-LETI/MINATEC)
N. Nakano (Keio Univ.)
Y. Otsuka (Toray Research Center Inc.)
M. Sato (AIST)
M. Ueki (Renesas Electronics Corp.)

[3] CMOS Devices / Device Physics

Chair: H. Wakabayashi (Sony Corp.)
Vice-Chair: D. Hisamoto (Hitachi, Ltd.)
 F. Boeuf (STMicroelectronics)
Member: B. Doris (IBM)
 H. Fujimoto (Panasonic Corp.)
 M. Hane (Renesas Electronics Corp.)
 T. Hiramoto (Univ. of Tokyo)
 N. Mori (Osaka Univ.)
 Y. Nishida (Renesas Electronics Corp.)
 K. Okano (Toshiba Corp.)
 O. Weber (CEA-LETI)
 F. L. Yang (National Nano Device Labs.)
 E. Yoshida (Fujitsu Semiconductor Ltd.)

[4] Advanced Memory Technology

Chair: M. Moniwa (Renesas Electronics Corp.)
Vice-Chair: T. Endoh (Tohoku Univ.)
 M. J. Tsai (ITRI)
Member: Y. C. Chen (Macronix International Co., Ltd.)
 T. Eshita (Fujitsu Semiconductor Ltd.)
 K. Hamada (Elpida Memory, Inc.)
 H. Hwang (GIST)
 K. Ishihara (Sharp Corp.)
 G. H. Koh (Samsung Electronics Co., Ltd.)
 S. Miura (NEC Corp.)
 Y. Sasago (Hitachi, Ltd.)
 S. Shuto (Toshiba Corp.)
 E. Yang (eMemory Technology Inc.)

[5] Advanced Circuits and Systems

Chair: S. Sugawa (Tohoku Univ.)
Vice-Chair: T. Koide (Hiroshima Univ.)
 H. Lin (National Chung Hsing Univ.)
Member: J. Akita (Kanazawa Univ.)
 J. C. Guo (National Chiao Tung Univ.)
 T. Hirose (Kobe Univ.)
 M. Horiguchi (Renesas Electronics Corp.)
 M. Ikebe (Hokkaido Univ.)
 K. Kagawa (Shizuoka Univ.)
 H. Morimura (NTT Microsystem Integration Labs.)
 T. Noll (RWTH Aachen Univ.)
 K. Okada (Tokyo Tech)
 H. Takao (Kagawa Univ.)
 H. Toshiyoshi (Univ. of Tokyo)

[6] Compound Semiconductor Electron Devices and Related Technologies

Chair: S. Tanaka (Shibaura Inst. of Tech.)
Vice-Chair: Y. Miyamoto (Tokyo Tech)
 E. Y. Chang (National Chiao Tung Univ.)
Member: K. J. Chen (Hong Kong Univ. of Sci. & Tech.)
 R. Hattori (Mitsubishi Electric Corp.)
 M. Kuzuhara (Univ. of Fukui)
 J. H. Lee (Kyungpook National Univ.)
 K. Maezawa (Univ. of Toyama)
 G. Meneghesso (Univ. of Padova)
 Y. Ohno (Univ. of Tokushima)
 S. Sasa (Osaka Inst. of Tech.)
 J. Suda (Kyoto Univ.)
 T. Suzuki (JAIST)
 T. Tanaka (Panasonic Corp.)

[7] Photonic Devices and Optoelectronic Integration

Chair: M. Tokushima (AIST)
Vice-Chair: Y. Ishikawa (Univ. of Tokyo)
 J. Michel (MIT)
Member: K. Akiyama (Mitsubishi Electric Corp.)
 Y. J. Chiu (National Sun Yat-sen Univ.)
 P. Fauchet (Univ. of Rochester)
 J. Fujikata (NEC Corp.)
 N. Iizuka (Toshiba Corp.)
 H. Isshiki (Univ. of Electro-Communications)
 S. Noda (Kyoto Univ.)
 S. Saito (Hitachi Ltd.)
 A. Wakahara (Toyohashi Univ. of Tech.)

[8] Advanced Material Synthesis and Crystal Growth Technology

Chair: H. Hibino (NTT Basic Res. Labs.)
Vice-Chair: K. Hara (Shizuoka Univ.)
 R. Notzel (Eindhoven Univ. of Tech.)
Member: T. Iwai (Fujitsu Labs. Ltd.)
 T. Kawae (Kanazawa Univ.)
 M. Kondow (Osaka Univ.)
 Y. Matsumoto (Tokyo Tech)
 T. Nagata (NIMS)
 T. Suemasu (Univ. of Tsukuba)
 M. Takahashi (JAEA)
 E. S. Tok (National Univ. of Singapore)
 K. Ueda (Nagoya Univ.)

[9] Physics and Application of Novel Functional Devices and Materials

Chair: K. Ono (RIKEN)
Vice-Chair: H. Gotoh (NTT Corp.)
 Y. Yeo (National Univ. of Singapore)
Member: D. Austing (Nat'l Res. Council of Canada)
 H. Inokawa (Shizuoka Univ.)
 A. Kanda (Univ. of Tsukuba)
 H. C. Kuo (National Chiao Tung Univ.)
 S. Kuroki (Tohoku Univ.)
 T. Machida (Univ. of Tokyo)
 T. Nakaoka (Sophia Univ.)
 T. Tanamoto (Toshiba Corp.)
 Y. Uraoka (NAIST)

[10] Organic Materials Science, Device Physics, and Applications

Chair: H. Usui (Tokyo Univ. of Agri. & Tech.)
Vice-Chair: T. Someya (Univ. of Tokyo)
 T. Lee (GIST)
Member: S. Ekgasit (Chulalongkorn Univ.)
 E. Itoh (Shinshu Univ.)
 K. Kato (Niigata Univ.)
 H. Lee (Sungkyunkwan Univ.)
 H. Maeda (Dai Nippon Printing Co. Ltd.)
 T. Manaka (Tokyo Tech)
 S. Naka (Univ. of Toyama)
 M. Sakai (Chiba Univ.)
 T. Shimada (Hokkaido Univ.)
 S. H. Su (I-Shou Univ.)
 K. Takimoto (Canon Inc.)
 M. Yoshida (AIST)

[11] Micro/Nano Electromechanical Systems and Bio/Medical Analyses

Chair: K. Sawada (Toyohashi Univ. of Tech.)
Vice-Chair: K. Ajito (NTT Corp.)
 Y. S. Yang (National Chiao Tung Univ.)
Member: H. Nishio (OMRON Corp.)
 J. Ohta (NAIST)
 T. Sakata (Univ. of Tokyo)
 M. Sasaki (Toyota Technological Inst.)
 J. K. Shin (Kyungpook National Univ.)
 H. Suzuki (Hiroshima Univ.)
 Y. Taguchi (Keio Univ.)
 T. Tanaka (Tohoku Univ.)

[12] Spintronics Materials and Devices

- Chair:** M. Yamamoto (Hokkaido Univ.)
- Vice-Chair:** H. Munakata (Tokyo Tech)
J. Zhao (Chinese Academy of Sciences)
- Member:** K. Ito (Hitachi, Ltd.)
S. Kuroda (Univ. of Tsukuba)
S. Nakamura (Toshiba Corp.)
Y. Ohno (Tohoku Univ.)
M. Oogane (Tohoku Univ.)
H. Saito (AIST)
S. Seo (Sejong Univ.)
M. Tanaka (Univ. of Tokyo)

[13] Application of Nanotubes, Nanowires, and Graphene

- Chair:** J. Motohisa (Hokkaido Univ.)
- Vice-Chair:** Y. Ohno (Nagoya Univ.)
Y. H. Lee (Sung Kyun Kwan Univ.)
- Member:** S. Akita (Osaka Prefecture Univ.)
K. Maehashi (Osaka Univ.)
K. Nagashio (Univ. of Tokyo)
K. Nishiguchi (NTT Basic Res. Labs.)
S. Sato (AIST)
K. Tateno (NTT Basic Res. Labs.)
S. Uno (Ritsumeikan Univ.)
L. E. Wernersson (Lund Univ.)

[14] Photovoltaics & Power Semiconductor Devices

- Co-Chair:** N. Usami (Tohoku Univ.)
M. Ishiko (Toyota Central R&D Labs.)
- Vice-Chair:** A. Masuda (AIST)
P. Mawby (Univ. of Warwick)
- Member:** T. Fuyuki (NAIST)
N. Ikeda (Advanced Power Device Res.)
H. Katagiri (NNCT)
N. Kojima (Toyota Technological Inst.)
Y. Kurokawa (Tokyo Tech)
H. S. Lee (Shinsung Holdings Co., Ltd)
K. Nishioka (Univ. of Miyazaki)
K. Ohdaira (JAIST)
I. Omura (Kyushu Inst. of Tech.)
H. Tsuchida (CRIEPI)
T. Ujihara (Nagoya Univ.)

GENERAL INFORMATION

DATE

Conference: **September 28-30, 2011 (Official language is English)**

Short Courses/Workshops: **September 27, 2011 (in English)**

CONFERENCE VENUE

Aichi Industry & Labor Center (WINC AICHI)

4-4-38 Meieki, Nakamura-ku, Nagoya, Aichi 450-0002, Japan

Phone: +81-52-571-6131 Fax: +81-52-571-6132

<http://www.winc-aichi.jp/>

SSDM 2011 will be held at WINC AICHI, the main Conference room of WINC AICHI. The access map to the Conference is available in the conference website and also on Page 61 in this booklet. The conference rooms are distributed over the venue. For details, see the map on the conference website and on Page 62-64 in this booklet.

Nagoya Marriott Associa Hotel

1-1-4 Meieki, Nakamura-ku Nagoya, Aichi 450-6002, Japan

Phone: + 81-52-584-1212 Fax: + 81-52-584-1213

<http://www.associa.com/english/>

Conference Banquet will be held on September 28, 19:00-21:00 at Tower Ball Room, 16F, in Nagoya Marriott Associa Hotel. The hotel is located in five minutes walk from the WINC AICHI. The access map from WINC AICHI to the hotel is available on the conference website and on Page 61 in this booklet. The Banquet fee is NOT included in the Registration fee. Participants who wish to attend the banquet are requested to order the banquet ticket beforehand. Drinks and appetizers will be served. During the Banquet, SSDM Young Researcher Award ceremony will be held.

TECHNICAL SESSIONS AND EVENTS

Oral and Poster Presentations:

The oral presentations will be held at halls located on 5th, 10th, 11th, and 12th floor in WINC AICHI. during the conference. The poster presentations will be held on September 29, 13:30-15:00, at Exhibition Hall, 6F, in WINC AICHI.

Plenary Sessions:

Plenary Sessions are scheduled on September 28, 9:40-12:15 at WINC HALL, 2F, in WINC AICHI. Non-Technical Plenary Talk-Sep.28, 2011, “Social Contribution and Next Giant Leap of Semiconductors” by Masao Fukuma (Semiconductor Industry Research Institute Japan, Japan) will be held from 9:40-10:25. Technical Plenary Talk-Sep.28, 2011, “A Car Guy’s Expectations for Electronics” by Moritaka Yoshida (Toyota Motor Corporation, Japan) will be held from 10:45-11:30 and “Electronics Proliferation through

Diversification” by Tsu-Jae King Liu (University of California at Berkeley, U.S.A) from 11:30-12:15.

Welcome Reception:

The welcome Reception will be held on September 27, 18:00-20:00 at Conference Room 1002, 10F, in WINC AICHI.

Rump Sessions:

SSDM 2011 is organizing Rump Session to be held on September 29, 19:00-21:00 at HALL 1&2, 5F, in WINC AICHI. Details can be found on Page 44.

Short Courses (in English):

On September 27, 10:00-17:30, two short course lectures will be held at “Toyoda Auditorium Nagoya University Symposion” and “Noyori Conference Hall”, in Nagoya University. Two courses are for beginners, young researchers and engineers, and students.

- 1) Material and Processing for Advanced CMOS – From Fundamental to State-of-the-Art –
- 2) Fundamentals and Applications of Carbon Nanotube and Graphene

*Registrants for short course are able to attend both courses freely.

Workshops (in English):

Workshop will be held on September 27, 13:00-17:45 at Hall 1 and Hall 2, 5F, in WINC AICHI.

- 1) Current Status and Future Prospective of Wide Gap Semiconductor Power Devices
- 2) Advancement in Printed Organic Electronics

*A resistant for one workshop is NOT ABLE to attend another workshop.

Award Ceremony:

Award Ceremony for SSDM Award and SSDM Paper Award will be held in Plenary Sessions, which will start at 9:30 AM on September 28 at WINC HALL,2F, in WINC AICHI.

Exhibition:

Exhibition will be held at the exhibition space, Conference Room 1001, 10F. It will start from 8:30-18:00 on September 28, from 8:30-19:00 on September 29, and from 8:30-14:00 on September 30. For details, see Page 48.

REGISTRATION

The Registration desk will be open September 27 to 30. Open hours are as follows:
September 27 16:00 – 19:00 at conference room (10F)
September 28 08:30 – 12:30 at WINC HALL Area (2F)
September 28 12:30 – 17:30 at conference room (10F)

September 29 08:30 – 17:30 at conference room (10F)

September 30 08:30 – 15:30 at conference room (10F)

SPECIAL ISSUE of JJAP

Authors of SSDM 2011 papers are encouraged to submit their original papers to the Special Issue of Japanese Journal of Applied Physics which will be published in February and April, 2012.

INSURANCE

The organizer cannot accept responsibility for accidents that may occur during a delegate's stay. Delegates are therefore encouraged to obtain travel insurances (medical, personal accident, and luggage) in their home countries prior to departure.

CLIMATE

Nagoya is warm and sometimes humid in September. The temperature range is 18-30°C.

ELECTRICAL APPLIANCES

Japan operates on 100 volts for electrical appliances. The frequency is 50 Hz in eastern Japan including Tokyo and 60 Hz in western Japan including Nagoya (conference site), Kyoto and Osaka.

INTERNET ACCESS

Complementary internet connection will be available on Speakers Room, 11F, where you can only use the SSDM PC installed in the room to use internet access freely or check your presentation.

PLENARY SESSION

September 28 (Wednesday) 9:40-12:15
2F WINC HALL, WINC AICHI

Non -Technical Plenary Talk

9:40-10:25

“Social Contribution and Next Giant Leap of Semiconductors”

Masao Fukuma

Semiconductor Industry Research Institute Japan, Japan

Technical Plenary Talk

10:45-11:30

“ A Car Guy’s Expectations for Electronics ”

Moritaka Yoshida

Toyota Motor Corporation, Japan

11:30-12:15

“ Electronics Proliferation through Diversification. ”

Tsu-Jae King Liu

University of California at Berkeley, USA

TECHNICAL PROGRAM

Opening & Plenary Sessions (WINC HALL)

Opening Session

Chair: M. Hori, Nagoya Univ.

9:30

Welcome Address

S. Zaima, Nagoya Univ.

Non-Technical Plenary Session

Chair: T. Fukui, Hokkaido Univ.

9:40 PL-1-1

Social Contribution and Next Giant Leap of Semiconductors M. Fukuma, Semiconductor Industry Research Institute Japan, Japan

SSDM Award / Paper Award Presentation

S. Zaima, Nagoya Univ.

Technical Plenary Sessions

Chair: T. Fukui, Hokkaido Univ.

10:45 PL-2-1

A Car Guy's Expectations for Electronics M. Yoshida, Toyota Motor Corporation, Japan

11:30 PL-2-2

Electronics Proliferation through Diversification.

Tsu-Jae King Liu, University of California at Berkeley, USA

12:15-13:30 Lunch

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>A-1: GaN FET Technologies (Area 6) (13:30-15:15) Chairs: T. Tanaka (Panasonic Corp.) S. Tanaka (Shibaura Institute of Tech.)</p>	<p>BL-1: Organic Photovoltaics (1) (Area 10&14) (13:30-15:15) Chairs: A. Masuda (AIST) E. Itoh (Shinshu Univ.)</p>	<p>B-1: OLEDs (Area 10) (13:30-15:15) Chairs: K. Takimoto (Canon Inc.) T. Lee (GIST)</p>	<p>C-1: Future Interconnect (Area 2) (13:30-15:15) Chairs: S. Ogawa (AIST) M. Sato (AIST)</p>	<p>D-1: Modeling and Circuits (Area 3) (13:30-15:10) Chairs: E. Yoshida (Fujitsu Semiconductor Ltd.) N. Mori (Osaka Univ.)</p>	<p>E-1: Ge-MOS (Area 1) (13:30-15:20) Chairs: T. Nabatame (NIMS) B. H. Lee (GIST)</p>	<p>F-1: STT-RAM (Area 4) (13:30-15:00) Chairs: G. H. Koh (Samsung Electronics Co., Ltd) S. Miura (NEC Corp.)</p>
<p>13:30 A-1-1 (Invited) InAlN/GaN HEMTs: Recent Progress and Challenges for the Future <i>J. Kuzmik^{1,2}, ¹Slovak Academy of Sciences and ²TU Vienna (Slovakia)</i></p>	<p>13:30 BL-1-1 Determination of Carrier Lifetime in Bulk-heterojunction Solar Cells by Continuous-wave Photoinduced Absorption Spectroscopy <i>Y. Terada¹, W. Shinke¹, T. Kobayashi¹, T. Nagase¹ and H. Naito^{1,2}, ¹Osaka Prefecture Univ. and ²CREST-JST (Japan)</i></p>	<p>13:30 B-1-1 Solution-processed small molecular phosphorescent organic light emitting devices with a mixed single layer <i>Z. Wang, S. Naka and H. Okada, Univ. of Toyama (Japan)</i></p>	<p>13:30 C-1-1 (Invited) TSV and Cu-Cu direct bonding: two key technologies for High Density 3D <i>N. Sillon, H. Ben Jamaa, P. Leduc, L. Di Cioccio, S. Cheramy and T. Signamarcheix, CEA-Leti, Minatec campus (France)</i></p>	<p>13:30 D-1-1 Simple and Efficient MASTAR Threshold Voltage and Subthreshold Slope Models for Double Gate Structures <i>J. Lacord^{1,2}, J. L. Huguenin^{1,2}, G. Ghibaudo¹, T. Skotnicki¹ and F. Boeuf¹, ¹STMicroelectronics and ²IMEP-LAHC (France)</i></p>	<p>13:30 E-1-1 (Invited) Investigation of the Electrical Properties of Ge/High-k Gate Stack: GeO₂ VS Si-cap <i>J. Mitard, F. Bellenger, L. Witters, B. De Jaeger, B. Vincent, L. Nyns, K. Martens, E. Vrancken, G. Wang, D. Lin, R. Loo, M. Caymax, K. De Meyer, M. Heyns and N. Horiguchi, IMEC (Belgium)</i></p>	<p>13:30 F-1-1 (Invited) Magnetoresistive Random Access Memory with Spin Transfer Torque Write (Spin RAM) -Present and Future- <i>H. Ohno, Tohoku Univ. (Japan)</i></p>
<p>14:00 A-1-2 High-Power and High-Gain S-band AlGaIn/GaN HEMTs with Source Field Plates on Si Substrate <i>S. Nakazawa, N. Tsurumi, M. Nishijima, Y. Ando, M. Ishida, T. Ueda and T. Tanaka, Panasonic Corp. (Japan)</i></p>	<p>13:45 BL-1-2 Analysis of anomalous discharging processes in pentacene/C₆₀ double-layer organic solar cell <i>X. Chen, D. Taguchi, K. Lee, T. Manaka and M. Iwamoto, Tokyo Tech (Japan)</i></p>	<p>13:45 B-1-2 Hole Injection Enhancement in Organic Light-emitting Diodes by Introducing an Au Nanoparticle Layer <i>D. Wang and K. Fujita, Kyushu Univ. (Japan)</i></p>	<p>14:00 C-1-2 Fabrication of Graphene Directly on SiO₂ without Transfer Processes by Annealing Sputtered Amorphous Carbon <i>M. Sato¹, M. Inukai², E. Ikenaga², T. Muro², S. Ogawa³, Y. Takakuwa⁴, H. Nakano¹, A. Kawabata¹, M. Nihei¹ and N. Yokoyama¹, ¹AIST/GNC, ²JASRI/Spring-8 and ³Tohoku Univ. (Japan)</i></p>	<p>13:50 D-1-2 Accurate and Ready-to-use Parasitic Capacitances Models for Advanced 2D/3D CMOS Device Structure Comparison <i>J. Lacord^{1,2}, D. Hoguet¹, D. Rideau¹, G. Ghibaudo¹ and F. Boeuf¹, ¹STMicroelectronics and ²IMEP-LAHC (France)</i></p>	<p>14:00 E-1-2 1.2 nm-EOT Al₂O₃/Ge Gate Stack with GeO₂-free Interface <i>T. Tabata^{1,2}, C. H. Lee^{1,2}, T. Nishimura^{1,2}, S. K. Wang^{1,2}, K. Kita^{1,2} and A. Toriumi^{1,2}, ¹Univ. of Tokyo and ²CREST-JST (Japan)</i></p>	<p>14:00 F-1-2 Studies on Static Noise Margin and Scalability for Low-Power and High-Density Nonvolatile SRAM using Spin-Transfer-Torque (STT) MTJs <i>T. Ohsawa, F. Iga, S. Ikeda, T. Hanyu, H. Ohno and T. Endoh, Tohoku Univ. (Japan)</i></p>
<p>14:15 A-1-3 RF power characteristics of high-thermal-efficiency AlGaIn/GaN HEMTs on diamond <i>K. Hiram, M. Kasu and Y. Taniyasu, NTT Basic Res. Labs. NTT Corp. (Japan)</i></p>	<p>14:00 BL-1-3 Probing electric field distribution of P3HT in ITO/PI/P3HT/Au by using EFISHG measurement <i>R. Miyazawa, D. Taguchi, T. Manaka and M. Iwamoto, Tokyo Tech (Japan)</i></p>	<p>14:00 B-1-3 Improvement on Electroluminescence of Red Organic Light Emitting Diode by Doping with Sensitizers <i>S. H. Yang, C. H. Chuang, S. C. Huang and P. J. Shih, National Kaohsiung Univ. of Applied Sciences (Taiwan)</i></p>	<p>14:20 C-1-3 Initial Growth Observation of Multilayer Graphene on SiO₂/Si substrates Using Raman Spectroscopy and XPS <i>Y. Ojiro¹, S. Ogawa¹, M. Inukai², M. Sato^{1,3}, E. Ikenaga², T. Muro², M. Nihei², Y. Takakuwa⁴ and N. Yokoyama¹, ¹Tohoku Univ., ²JASRI/Spring-8 and ³AIST/GNC (Japan)</i></p>	<p>14:10 D-1-3 An Accurate Prediction Model of Temperature Dependent Current Mismatch in All Inversion and Influence of Sub-threshold Hump on Mismatch Characteristics <i>K. Sakakibara and K. Arimoto, Renesas Electronics Corp. (Japan)</i></p>	<p>14:20 E-1-3 Effective Passivation of Interface Dipole in TiN-Gate Ge-MOS Capacitor with Ultrathin SiO₂/GeO₂ Bilayer by Nitrogen Incorporation <i>K. Sakamoto, Y. Iwamura, K. Yamamoto, H. Yang, D. Wang and H. Nakashima, Kyushu Univ. (Japan)</i></p>	<p>14:20 F-1-3 A Study for Adopting PMOS Memory Cell for 1T1R STT-RAM with Asymmetric Switching Current MTJ <i>H. Koike and T. Endoh, Tohoku Univ. (Japan)</i></p>

Opening & Plenary Sessions (WINC HALL)

Opening Session

Chair: M. Hori, Nagoya Univ.

9:30

Welcome Address

S. Zaima, Nagoya Univ.

Non-Technical Plenary Session

Chair: T. Fukui, Hokkaido Univ.

9:40 PL-1-1

Social Contribution and Next Giant Leap of Semiconductors M. Fukuma, Semiconductor Industry Research Institute Japan, Japan

SSDM Award / Paper Award Presentation

S. Zaima, Nagoya Univ.

Technical Plenary Sessions

Chair: T. Fukui, Hokkaido Univ.

10:45 PL-2-1

A Car Guy's Expectations for Electronics M. Yoshida, Toyota Motor Corporation, Japan

11:30 PL-2-2

Electronics Proliferation through Diversification.

Tsu-Jae King Liu, University of California at Berkeley, USA

12:15-13:30 Lunch

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>GH-1: Image Sensor and MEMS Technology (I) (Area 5&11) (13:30-15:10) Chairs: S. Sugawa (Tohoku Univ.) T. Tokuda (NAIST)</p>		<p>I-1: Optical Link and Related Devices (Area 7) (13:30-15:15) Chairs: Y. Ishikawa (Univ. of Tokyo) N. Iizuka (Toshiba Corp.)</p>		<p>K-1: CNT Property (Area 13) (13:30-15:15) Chairs: S. Akita (Osaka Prefecture Univ.) Y. Ohno (Nagoya Univ.)</p>	<p>L-1: Quantum Well& III-V Solar Cell (Area 14) (13:30-15:15) Chairs: F. Finger (FZ Julich) N. Kojima (Toyota Technological Inst.)</p>	<p>M-1: Nitrides (Area 8) (13:30-15:15) Chairs: T. Nagata (NIMS) K. Hara (Shizuoka Univ.)</p>	
<p>13:30 GH-1-1 (Invited) High Speed Vision for Gesture UI, Dynamic Image Control and Visual Feedback <i>M. Ishikawa, Univ. of Tokyo (Japan)</i></p>		<p>13:30 I-1-1 (Invited) Lens-integrated surface-emitting DFB laser arrays for short-reach optical links <i>K. Adachi^{1,2}, K. Shinoda^{1,2}, T. Kitatani^{1,2}, Y. Matsuoka¹, T. Sugawara¹ and S. Tsuji^{1,2}, ¹Hitachi,Ltd. and ²PETRA (Japan)</i></p>		<p>13:30 K-1-1 (Invited) Carbon Nanotube Clamped Metal Atomic Chain: Fabrication, Structure and Property <i>D. M. Tang, L. C. Yin, C. Liu and H. M. Cheng, Chinese Academy of Sciences (China)</i></p>	<p>13:30 L-1-1 (Invited) Quantum Well Solar Cells <i>(UK)</i></p>	<p>13:30 M-1-1 (Invited) Progress in Nonpolar and Semipolar GaN-base Materials and Devices <i>J.S. Speck, Univ. of California, Santa Barbara (USA)</i></p>	
<p>14:00 GH-1-2 A 2-D Optical Pulse Receiver/Imager with Two-Port Pixels for Simultaneously Producing Image and Communication Signals <i>S. Kawahito¹, S. Itoh¹, Y. Iwama¹, I. Takai¹, M. Andoh¹, K. Yasutomi¹ and K. Kagawa¹, ¹Shizuoka Univ. and ²Toyota Central R&D Labs, Inc. (Japan)</i></p>		<p>14:00 I-1-2 Performance of Low-Loss and Low-Cost Optoelectronic Module with Polynorbornene Waveguide for 10-Gbps Data Transmission. <i>Y. Ito¹, S. Terada¹, S. Arai¹, M. Fujiwara¹, T. Mori¹, K. Choki¹, T. Fukushima¹ and M. Koyanagi¹, ¹Sumitomo Bakelite Co., Ltd. and ²Tohoku Univ. (Japan)</i></p>		<p>14:00 K-1-2 Fabrication of Carbon Nanowalls on Carbon Fiber Paper <i>S. Mitsuguchi¹, M. Hiramatsu¹, H. Kondo², M. Hori² and H. Kano³, ¹Meijo Univ., ²Nagoya Univ. and ³NU Eco Eng. Co., LTD. (Japan)</i></p>	<p>14:00 L-1-2 Non-Radiative Carrier Recombination in the Strain-Balanced InGaAs/GaAsP Multiple Quantum Wells for Solar Cell Application <i>T. Aihara¹, Y. Nakano¹, A. Fukuyama¹, Y. Wang², M. Sugiyama², Y. Nakano² and T. Ikari¹, ¹Univ. of Miyazaki and ²Univ. of Tokyo (Japan)</i></p>	<p>14:00 M-1-2 Tilted domain and indium content of MOVPE-grown InGaN layer on <i>m</i>-plane GaN substrate <i>K. Shojiki¹, T. Hanada^{1,2}, T. Shimada¹, Y. Liu^{1,2}, R. Katayama^{1,2} and T. Matsuoka^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)</i></p>	
<p>14:20 GH-1-3 Improved Near-Infrared Sensitivity for a Side-Illuminated Photo Sensor <i>T. Ariyoshi, N. Uryu, A. Baba and Y. Arima, Kyushu Inst. of Tech. (Japan)</i></p>		<p>14:15 I-1-3 Low Voltage InGaAs/InAlAs Quantum Well Mach-Zehnder Modulator with Single Microring Resonator <i>H. Kaneshige, Y. Ueyama, H. Yamada, T. Arakawa and Y. Kokubun, Yokohama National Univ. (Japan)</i></p>		<p>14:15 K-1-3 Alignment of Carbon Nanotubes on Sapphire Surfaces with Strong Interactions <i>S. Jeong¹ and A. Oshiyama², ¹Chonbuk Nat. Univ. and ²Univ. of Tokyo (Korea)</i></p>	<p>14:15 L-1-3 Kinetics of strain relaxation in lattice-mismatched III-V heteroepitaxy <i>T. Sasaki¹, K. Shimomura¹, H. Suzuki², M. Takahashi¹, I. Kamiya¹, Y. Ohshita¹ and M. Yamaguchi¹, ¹Toyota Tech. Inst., ²Univ. of Miyazaki and ³JAEA (Japan)</i></p>	<p>14:15 M-1-3 Effect of Phase Purity on Dislocation Density of PR-MOVPE-Grown InN <i>T. Iwabuchi¹, Y. Liu^{1,2}, T. Kimura^{1,2}, Y. Zhang^{1,2}, K. Prasertsuk¹, R. Katayama^{1,2} and T. Matsuoka^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)</i></p>	

Wednesday, September 28

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
A-1: GaN FET Technologies (Area 6)	BL-1: Organic Photovoltaics (1) (Area 10&14)	B-1: OLEDs (Area 10)	C-1: Future Interconnect (Area 2)	D-1: Modeling and Circuits (Area 3)	E-1: Ge-MOS (Area 1)	F-1: STT-RAM (Area 4)
<p>14:30 A-1-4 Improvement of Current Collapse in Deeply Recessed Gate AlGaIn/GaN High Electron Mobility Transistors without Field Modulating Structure <i>A. Imai, K. Yamanaka, Y. Suzuki, T. Nanjo, M. Suita, K. Shiozawa, Y. Abe, E. Yagyu and A. Shima, Mitsubishi Electric Corp. (Japan)</i></p> <p>14:45 A-1-5 Temperature Dependence and Current Collapse of AlGaIn/GaN Super Hetero-junction Field Effect Transistor <i>S. Yagi¹, S. Hirata¹, Y. Sumida¹, A. Nakajima², H. Kawai¹ and E. M. Sankara Narayanan³, ¹POWDEC, K. K. and ²Univ. Sheffield (Japan)</i></p> <p>15:00 A-1-6 Sputtered amorphous AlN gate dielectric for AlGaIn/GaN metal-insulator-semiconductor heterojunction field-effect transistor <i>H. A. Shih, M. Kudo, M. Akabori and T. Suzuki, JAIST (Japan)</i></p>	<p>14:15 BL-1-4 Designing of Organic Solar Cell Module for Obtaining Maximum Performance <i>H. Ogo, T. Miyadera, T. Taima, A. Masuda and Y. Yoshida¹, AIST (Japan)</i></p> <p>14:30 BL-1-5 In situ monitoring of organic solar cells during thermal annealing <i>K. T. Hung, C. Y. Hsiao, H. T. Wu, S. W. Fu, H. J. Chen and C. F. Shih, National Cheng Kung Univ. (Taiwan)</i></p> <p>14:45 BL-1-6 RF-Sputtered High-Mobility Indium Molybdenum Thin Films for Organic Solar Cell Applications <i>H. J. Chang, W. F. Chen, S. S. Cheng, K. M. Huang, T. H. Huang, C. L. Ho and M. C. Wu, National Tsing Hua Univ. (Taiwan)</i></p> <p>15:00 BL-1-7 Comprehensive Studies of Solvent Annealing on Organic Photovoltaics <i>H. T. Wu, C. Y. Hsiao, K. T. Hung, H. J. Chen, S. W. Fu, S. H. Wu and C. F. Shih, National Cheng Kung Univ. (Taiwan)</i></p>	<p>14:15 B-1-4 White Organic Light-Emitting Diodes Combining Blue Organic Light-Emitting Diodes with a Sr₂SiO₄:Eu³⁺ Color Conversion Layer <i>S. H. Su, W. Y. Wang and M. Yokoyama, I-Shou Univ. (Taiwan)</i></p> <p>14:30 B-1-5 Pattern Formation of Phosphorescent Polymer Thin Films by Spin-Coated Photoreactive Monomer Films <i>D. Miyagawa, M. Muroyama, K. Tanaka and H. Usui, Tokyo Univ. of Agri. and Tech. (Japan)</i></p> <p>14:45 B-1-6 Device Parameters Determination by Novel Schottky Model Fitting for Organic Light-Emitting Diodes (OLEDs) <i>T. Hirai, K. Weber, M. Bown and K. Ueno, CSIRO (Australia)</i></p> <p>15:00 B-1-7 (Late News) Three Terminal Nano-Scale Electrode for Molecular Transistor Evaluation <i>K. Tsutsui, M. Morita, M. Tokuda, H. Takagi, Y. Ito and Y. Wada, Toyo Univ. (Japan)</i></p>	<p>14:40 C-1-4 STC: Single-Tube Characterization Methodology for Experimental and Analytical Evaluation of Carbon Nanotube Synthesis <i>H. Y. Chen, A. Lim, L. S. Liyanage, C. Beasley, N. Patil, H. Wei, S. Mitra and H. S. P. Wong, Stanford Univ. (USA)</i></p> <p>15:00 C-1-5 (Late News) Effect of H₂ gas addition on Si Oxidation Process with Ar and O₂ Mixture Surface Wave Plasma <i>K. Takeda and M. Hori, Nagoya Univ. (Japan)</i></p>	<p>14:30 D-1-4 A Stacked Inverter-based CMOS Power Amplifier in 65nm CMOS Process <i>H. Kiumarsi, Y. Mizuochi, H. Ito, N. Ishihara and K. Masu, Tokyo Tech (Japan)</i></p> <p>14:50 D-1-5 Design of Power-Efficient 130GHz Common-Source Amplifiers <i>K. Katayama¹, M. Motoyoshi², K. Takano² and M. Fujishima¹, ¹Hiroshima Univ. and ²Univ. of Tokyo (Japan)</i></p>	<p>14:40 E-1-4 Defect Control in Germanium Oxide Film Thermally Grown on Germanium Substrate <i>Y. Oniki and T. Ueno, Tokyo Univ. of Agri. and Tech. (Japan)</i></p> <p>15:00 E-1-5 High-Electron-Mobility Ge n-MOSFET with TiN Metal Gate <i>T. Yamanaka, K. Yamamoto, K. Sakamoto, H. Yang, D. Wang and H. Nakashima, Kyushu Univ. (Japan)</i></p>	<p>14:40 F-1-4 Novel 2step Writing Method for STT-RAM to Improve Switching Probability and Write Speed <i>F. Iga, Y. Suzuki, T. Ohsawa, S. Ikeda, T. Hanyu, H. Ohno and T. Endoh, Tohoku Univ. (Japan)</i></p>
Coffee Break						
A-2: III-V HBTs and FETs (Area 6) (15:40-16:55) Chairs: K. Maezawa (Univ. of Toyama) Y. Miyamoto (Tokyo Tech)	BL-2: Organic Photovoltaics (2) (Area 10&14) (15:40-17:25) Chairs: S. H. Su (I-Shou Univ.) N.Kojima (Toyota Technological Inst.)	B-2: Organic device fabrication process and interface control (Area 10) (15:40-17:25) Chairs: H. Usui (Tokyo Univ. of Agri. & Tech.) K. Takimoto (Canon Inc.)		D-2: Device & Characteristics (Area 3) (15:40-17:00) Chairs: K. Okano (Toshiba Corp.) F. Boeuf (STMicroelectronics)	E-2: Characterization in Gate Stacks (Area 1) (15:45-17:15) Chairs: S. Tsujikawa (Sony Corp.) H. Nohira (Tokyo City Univ.)	F-2: FeRAM/DRAM/SRAM (Area 4) (15:40-17:30) Chairs: K. Hamada (Elpida Memory, Inc.) T. Eshita (Fujitsu Semiconductor Ltd.)
<p>15:40 A-2-1 (Invited) Extending the Bandwidth and Functionality of High Performance InP HBT Technologies <i>M. Urteaga¹, R. Pierson¹, J. Bergman¹, D. H. Kim¹, P. Rowell¹, B. Brar¹ and M. Rodwell², ¹Teledyne Scientific Corp. and ²Univ. of California, Santa Barbara (USA)</i></p> <p>16:10 A-2-2 Low-turn-on voltage heterojunction bipolar transistors with a C-doped In_{0.5}Ga_{0.5}As_{0.5}Sb_{0.5} base grown by metalorganic chemical vapor deposition <i>T. Hoshi, H. Sugiyama, H. Yokoyama, K. Kurishima and M. Ida, NTT Corp. (Japan)</i></p>	<p>15:40 BL-2-1 Optimization of Carrier Collection Structure in Graded Organic Solar Cells <i>T. Horioka¹, Z. Wang¹, S. Naka¹ and H. Okada^{1,2}, ¹Univ. of Toyama and ²Center for Basic Res. and Development in Natural Sciences (Japan)</i></p> <p>15:55 BL-2-2 Solution Processable Thin Film Organic Photovoltaic Cells based on Far Red Sensitive Soluble Squaraine Dyes <i>S. S. Pandey, T. Mizuno, S. K. Das, Y. Ogomi and S. Hayase, Kyushu Inst. of Tech. (Japan)</i></p>	<p>15:40 B-2-1 (Invited) Nanotransfer Direct Printing Methods <i>M. M. Sung, Hanyang Univ. (Korea)</i></p> <p>16:10 B-2-2 Work Function controlled Zn:Cu electrode for all-printed polymer diode <i>M. Yoshida, S. Uemura, H. Tokuhisa, N. Takada and T. Kamata, AIST (Japan)</i></p>		<p>15:40 D-2-1 Current Drive Enhancement of Strained Ge nMISFET with SiGe Stressors by Uniaxial Tensile Stress <i>Y. Kamimuta, Y. Moriyama, K. Ikeda, M. Oda and T. Tezuka, MIRAI-Toshiba (Japan)</i></p> <p>16:00 D-2-2 Experimental Study of Si Monolayers for Future Extremely-Thin SOIs (ETSOLs): Phonon Confinement Effects and Strain due to Si Bending <i>T. Mizuno¹, K. Tobe¹, Y. Maruyama¹ and T. Sameshima², ¹Kanagawa Univ. and ²Tokyo Univ. of Agri. and Tech. (Japan)</i></p>	<p>15:45 E-2-1 (Invited) In depth characterization of electrical effects of dopants (Al, La, Mg, N) in high-k/metal gate stacks <i>G. Reimbold¹, M. Cassé¹, X. Garros¹, C. Leroux², M. Charbonnier¹, L. Brunet^{2,1}, S. Baudou^{1,1}, P. Caubert¹, C. Fenouillet-Béranger^{1,2}, F. Andrieu¹, O. Weber¹, P. Perreau^{1,2} and F. Martin¹, ¹CEA-LETI/MI-NATEC and ²STMicroelectronics (France)</i></p> <p>16:15 E-2-2 Role of Al atoms in (TaC)_{1-x}Al_x gate electrode on V_{th} for HfO₂ gate stack <i>M. Kimura¹, T. Nabatame², H. Yamada¹, A. Oh¹, T. Chikyow² and T. Ohishi¹, ¹Shibaura Inst. of Tech. and ²MANA Foundry and MANA Advanced Device Materials Group, National Inst. for Materials Sci. (Japan)</i></p>	<p>15:40 F-2-1 (Invited) An Overview of Embedded Ferroelectric Memory Technology <i>K. R. Udayakumar, T. S. Moise, S. R. Summerfelt, J. Rodriguez, M. Ball, L. Wang, H. McAdams and S. Madan, Texas Instruments Inc. (USA)</i></p> <p>16:10 F-2-2 Data Disturbance-free NAND-type Ferroelectric-gate Thin Film Transistor Array using Solution-processed ITO and Stacked (BLT/PPZT) Gate Insulator <i>B. N. Q. Trinh¹, T. Miyasako¹, T. Kaneda¹, B. V. Thanh¹, P. T. Tue², E. Tokumitsu^{1,3} and T. Shimoda^{1,2}, ¹JST, ²JAIST and ³Tokyo Tech (Japan)</i></p>

Wednesday, September 28

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>GH-1: Image Sensor and MEMS Technology (1) (Area 5&11)</p> <p>14:40 GH-1-4 (Invited) RF MEMS Switch Technology in OMRON <i>T. Seki, Y. Uno, K. Narise, T. Masuda, K. Inoue and F. Sato, OMRON Corp. (Japan)</i></p>		<p>I-1: Optical Link and Related Devices (Area 7)</p> <p>14:30 I-1-4 Magnetically Controllable Optical Intensity and Mode Redistribution in Semiconductor Active Optical Isolators <i>H. Shimizu, K. Uehara and K. Tazawa, Tokyo Univ. of Agri. & Tech. (Japan)</i></p> <p>14:45 I-1-5 An inverted InAlAs/InGaAs avalanche photodiode with low-high field profile <i>M. Nada, Y. Muramoto, H. Yokoyama, N. Shigekawa, T. Ishibashi and S. Kodama, NTT Photonics Labs. (Japan)</i></p> <p>15:00 I-1-6 Responsivity Characteristics of InP/InGaAs Heterojunction Phototransistors with Strained InAs/InGaAs Multiquantum Well Absorption Layers <i>H. Egusa¹, H. Fukano¹, S. Tane¹, T. Sato¹ and M. Mitsuhashi^{2,3},¹Osaka Univ. and ²NTT Photonics Labs. (Japan)</i></p>		<p>K-1: CNT Property (Area 13)</p> <p>14:30 K-1-4 Sensing Property of Horizontally Aligned Carbon Nanotube Field-Effect Transistor on Quartz Substrate <i>S. Okuda, S. Okamoto, Y. Ohno, K. Maehashi, K. Inoue and K. Matsu-moto, Osaka Univ. (Japan)</i></p> <p>14:45 K-1-5 Estimation of height of defect-induced barriers in metallic CNTs <i>Y. Okigawa, Y. Ohno, S. Kishimoto and T. Mizutani, Nagoya Univ. (Japan)</i></p> <p>15:00 K-1-6 Room Temperature Single Charge Memory by Carbon Nanotube Transistor With SiN_x/Al₂O₃ Wrapped Double Gate Insulator Layers <i>T. Kamimura^{1,2,3}, Y. Hayashi^{2,3} and K. Matsumoto^{1,2,3},¹Osaka Univ., ²CREST-JST and ³AIST (Japan)</i></p>	<p>L-1: Quantum Well& III-V Solar Cell (Area 14)</p> <p>14:30 L-1-4 InGaN/GaN solar cells grown on wet-etched patterned sapphire substrates <i>C. H. Yang, Y. C. Yao, C. M. Cheng, M. H. Lee and Y. J. Lee, National Taiwan Normal Univ. (Taiwan)</i></p> <p>14:45 L-1-5 Effect of Thermal Stress on a N-related Recombination Center in GaAsN Grown by Chemical Beam Epitaxy <i>B. Bouzazi, N. Kojima, Y. Ohshita and M. Yamaguchi, Toyota Tech. Inst. (Japan)</i></p> <p>15:00 L-1-6 2-dimensional mapping of power consumption due to series resistance evaluated by simulator for concentrator photovoltaic module <i>Y. Ota and K. Nishioka, Univ. of Miyazaki (Japan)</i></p>	<p>M-1: Nitrides (Area 8)</p> <p>14:30 M-1-4 Surface Supersaturation in Nucleus and Spiral Growth of GaN in MOVPE <i>T. Akasaka, Y. Kobayashi and M. Kasu, NTT Basic Res. Labs. (Japan)</i></p> <p>14:45 M-1-5 Growth of Nitrogen-Polar 2H-AlN on Step-Height-Controlled 6H-SiC (000-1) Substrate by Molecular-Beam Epitaxy <i>H. Okumura, T. Kimoto and J. Suda, Kyoto Univ. (Japan)</i></p> <p>15:00 M-1-6 A Novel Chemical Lift-Off Process based on Embedded Nano-rods Template <i>S. S. Yen, W. Y. Chen, J. R. Chang, S. P. Chang, P. M. Tu, Y. C. Hsu, Y. J. Li, Y. C. Chen, K. P. Sou and C. Y. Chang, National Chiao Tung Univ. (Taiwan)</i></p>	

Coffee Break

<p>GH-2: Image Sensor and MEMS Technology (2) (Area 5&11) (15:40-17:20) Chairs: K. Sawada (Toyo-hashi Univ. of Tech.) H. Morimura (NTT Microsystem Integration Labs.)</p> <p>15:40 GH-2-1 (Invited) WLAN(IEEE 802.11n)/m-WiMAX(IEEE 802.16e) 2x2 MIMO FRONT-END MODULE USING MEMS & LTCC TECHNOLOGY <i>K. Chun¹, S. Kang¹, Y. Jang¹, J. C. Kim², C. S. Kim³ and I. S. Song²,¹Soeul National Univ., ²Korea Electronics Tech. Inst. and ³Samsung Advanced Inst. of Tech. (Korea)</i></p> <p>16:10 GH-2-2 Manipulation of Dispersed Magnetic Beads for On-chip Immunoassay <i>T. Ishikawa^{1,2}, J. S. Lee¹ and R. Miyake^{1,2},¹Hiroshima Univ. and ²CREST-JST (Japan)</i></p>		<p>I-2: Photonic Crystals (Area 7) (15:40-17:10) Chairs: M. Tokushima (AIST) S. Saito (Hitachi Ltd.)</p> <p>15:40 I-2-1 (Invited) Photonic Crystal Devices Fabricated by CMOS-Compatible Process <i>T. Baba^{1,2},¹Yokohama National Univ. and ²CREST-JST (Japan)</i></p> <p>16:10 I-2-2 An Epitaxially Regrown GaAs Based Photonic Crystal Surface Emitting Laser <i>D. M. Williams¹, K. M. Groom¹, B. J. Stevens¹, Q. Jiang¹, D. T. D. Childs¹, R. J. Taylor¹, S. Khamas¹, R. A. Hogg¹, N. Ikeda² and Y. Sugimoto²,¹Univ. of Sheffield and ²NIMS (UK)</i></p>		<p>K-2: CNT Device (Area 13) (15:40-17:25) Chairs: K. Maehashi (Osaka Univ.) S. Saito (AIST)</p> <p>15:40 K-2-1 Resistance distribution of CNT network measured by conductive atomic force microscopy <i>K. Housayama, Y. Okigawa, S. Kishimoto, Y. Ohno and T. Mizutani, Nagoya Univ. (Japan)</i></p> <p>15:55 K-2-2 Theoretical Study of AC Response of Defective Carbon Nanotubes: Tube Diameter Dependence <i>D. Hirai¹, T. Yamamoto^{1,2} and S. Watanabe¹,¹Univ. of Tokyo and ²Tokyo Univ. of Sci. (Japan)</i></p>	<p>L-2: Thin-Film Silicon Solar Cells (Area 14) (15:40-17:25) Chairs: A. Masuda (AIST) K. Ohdaira (JAIST)</p> <p>15:40 L-2-1 (Invited) Materials for thin film silicon solar cells <i>F. Finger, R. Carius, T. Chen, A. Lambertz and V. Sminov, IEK5 - Photovoltaik, Forschungszentrum Jülich (Germany)</i></p> <p>16:10 L-2-6 Effect of Hydrogen Radical-Injection on Growth Property and Crystallinity of Microcrystalline Silicon Thin Film <i>Y. Abe, A. Fukushima, Y. Lu, K. Takekanda, H. Kondo, K. Ishikawa, M. Sekine and M. Hori, Nagoya Univ. (Japan)</i></p>	<p>M-2: Oxides (Area 8) (15:40-17:25) Chairs: K. Hara (Shizuoka Univ.) T. Nagata (NIMS)</p> <p>15:40 M-2-1 (Invited) Multi-dimensional Nanostructured Oxide Devices <i>H. Taknaka, A. Ono, T. Kusizaki, K. Fujiwara and A. Hattori, Osaka Univ. (Japan)</i></p> <p>16:10 M-2-2 Crystal growth and optical characterizations of nonpolar m-plane ZnO on the m-plane sapphire substrate by PLD <i>C. C. Kuo¹, B. H. Lin^{1,2}, W. R. Liu², C. H. Hsu^{1,2} and W. F. Hsieh¹,¹National Chiao Tung Univ. and ²National Synchrotron Radiation Research Center (Taiwan)</i></p>	
---	--	--	--	---	--	---	--

Wednesday, September 28

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>A-2: III-V HBTs and FETs (Area 6)</p>	<p>BL-2: Organic Photovoltaics (2) (Area 10&14)</p>	<p>B-2: Organic device fabrication process and interface control (Area 10)</p>		<p>D-2: Device & Characteristics (Area 3)</p>	<p>E-2: Characterization in Gate Stacks (Area 1)</p>	<p>F-2: FeRAM/DRAM/SRAM (Area 4)</p>
<p>16:25 A-2-3 Effects of Plasma-PH₃ passivation on Mobility Degradation Mechanisms and Current Conduction Mechanisms of In_{0.53}Ga_{0.47}As N-MOSFET A. B. S. Sumarlina^{1,2}, H. J. Oh¹, A. Du² and S. J. Lee¹, ¹National Univ. of Singapore and ²GLOBALFOUNDRIES Singapore Pte.Ltd. (Singapore)</p>	<p>16:10 BL-2-3 Highly Efficient Organic Solar Cell Employing a Solution Processed Hole Transporting Layer W. K. Lin, S. H. Su, Y. F. Lin, J. R. Wang, J. L. Huang and M. Yokoyama, I-shou Univ. (Taiwan)</p>	<p>16:25 B-2-3 Interface Control of ITO and Spin-Coated Polymer by Reactive Self-Assembled Monolayer S. H. Kim¹, H. Ohtsuka¹, M. C. Tria², R. C. Advincula¹ and H. Usui¹, ¹Tokyo Univ. of Agri. and Tech. and ²Univ. Houston (Japan)</p>		<p>16:20 D-2-3 Lateral Source Relaxed/Strained Layer Heterostructures for Ballistic CMOS: Physical Relaxation Mechanism for Strained Layers by O⁻ Ion Implantation T. Mizuno, J. Takehi and S. Tanabe, Kanagawa Univ. (Japan)</p>	<p>16:35 E-2-3 Impurity Profile Extraction of Semiconductor Devices from STM Tunneling Currents by Current Continuity Based Simulation K. Fukuda¹, M. Nishizawa¹, T. Tada¹, L. Bolotov², K. Suzuki³, S. Sato³, H. Arimoto¹ and T. Kanayama¹, ¹AIST, ²Univ. of Tsukuba and ³Fujitsu Semiconductor Ltd. (Japan)</p>	<p>16:30 F-2-3 Process Development of ALD-Rutile-TiO₂/Ru(O₂) for DRAM MIMcap Application and its Leakage Mechanism Analysis K. Tomida¹, M. Popovici¹, J. Swerts¹, W. C. Wang², B. Kaczer¹, M. A. Pawlak¹, S. Van Elshocht¹, M. S. Kim¹, I. Debusschere¹, V. V. Afanasiev², L. Altimime¹ and J. A. Kittl¹, ¹IMEC and ²Catholic Univ. of Leuven (Belgium)</p>
<p>16:40 A-2-4 In_{0.53}Ga_{0.47}As Channel N-MOSFETs with Shallow Metallic S/D Extension Z. Zhu, X. Gong, Ivana and Y. C. Yeo, National Univ. of Singapore (Singapore)</p>	<p>16:25 BL-2-4 Sodium Doping at CuPc/C60 Interface for Photovoltaic Application H. J. Chen, K. T. Hung, C. Y. Hsiao, S. W. Fu, H. T. Wu, S. H. Wu and C. F. Shih, National Cheng Kung Univ. (Taiwan)</p>	<p>16:40 B-2-4 Field induced selective growth of organic conductive wires and molecular break junction by Joule heating M. Sakai¹, Y. Urabe¹, H. Yamauchi¹, M. Nakamura² and K. Kudo¹, ¹Chiba Univ. and ²NAIST (Japan)</p>		<p>16:40 D-2-4 Recovery Characteristic of Anomalous Stress Induced Leakage Current of 5.6nm Oxide Films T. Inatsuka, Y. Kumagai, R. Kuroda, A. Teramoto, S. Sugawa and T. Ohmi, Tohoku Univ. (Japan)</p>	<p>16:55 E-2-4 Influence of channel area scaling on Weibull distribution of TDDB for poly-Si channel FET I. Hirano, M. Saito, T. Numata and Y. Mitani, Toshiba Corp. (Japan)</p>	<p>16:50 F-2-4 Optimization and Variation Studies of BJT-based Ultra Thin Body Capacitor-less DRAM Cell M. H. Cho, C. Shin and T. J. King Liu, UC, Berkeley (USA)</p>
	<p>16:40 BL-2-5 Charge trapping in organic solar cells with plasmonic silver nanoparticles M. Weis¹, K. Vegso¹, P. Siffalovic¹, M. Jergel¹, E. Majkova¹, K. Lee², X. Chen², L. Zhang², D. Taguchi², T. Manaka² and M. Iwamoto², ¹Slovak Academy of Sci. and ²Tohoku Tech (Slovakia)</p>	<p>16:55 B-2-5 Bulk crystal growth of organic semiconductors for thermoelectric applications Y. Ikuta, Y. Tsuchida, N. Muraya, T. Nagahama and T. Shimada, Hokkaido Univ. (Japan)</p>				<p>17:10 F-2-5 A Compact Half Select Disturb Free SRAM Cell with Stacked Vertical MOS-FET H. Na^{1,2} and T. Endoh^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)</p>
	<p>16:55 BL-2-6 Effects of the Film Thickness on the Photocurrent Generation from Polythiophene-fullerene Thin films Containing of Silver Nanoparticles J. You¹, Y. Takahashi¹, H. Yonemura¹, T. Akiyama² and S. Yamada¹, ¹Kyushu Univ. and ²Univ. of Shiga Prefecture (Japan)</p>	<p>17:10 B-2-6 Geometric characterization of superoleophobic film K. Tsuji and S. Shiratori, Keio Univ. (Japan)</p>				
	<p>17:10 BL-2-7 Improvement of Short-Circuit Current in Plasmonic Organic Solar Cells Based on Grating Structures A. Baba, D. Murashima, N. Aoki, K. Shinbo, K. Kato and F. Kaneko, Niigata Univ. (Japan)</p>					

Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)

Wednesday, September 28

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>GH-2: Image Sensor and MEMS Technology (2) (Area 5&11)</p> <p>16:30 GH-2-3 In-pixel type small-scale integrated C-V converter with chopper stabilized CMOS inverter <i>R. Kodama¹, H. Miyao¹, M. Ishida¹ and H. Takao^{1,2}, ¹Toyoashi Univ. of Tech. and ²Kagawa Univ. (Japan)</i></p> <p>16:50 GH-2-4 A Monolithically-Integrated, Batch Post-Processed 17.8 V Silicon Solar Cell for Remote MEMS Driving <i>I. Mori, S. Morishita, M. Kubota, K. Watanabe and Y. Mita, Univ. of Tokyo (Japan)</i></p> <p>17:05 GH-2-5 A novel CMOS image sensor with on-chip micro LED array for spatiotemporally controlled light stimulation and on-chip imaging of a neuronal tissue <i>A. Nakajima¹, T. Kobayashi^{1,2}, T. Noda^{1,2}, K. Sasagawa^{1,2}, T. Tokuda^{1,2}, Y. Ishikawa^{1,2}, S. Shiosaka^{1,2} and J. Ohita^{1,2}, ¹NAIST and ²CREST-JST (Japan)</i></p>		<p>I-2: Photonic Crystals (Area 7)</p> <p>16:25 I-2-3 Photonic Crystal Band-edge Laser on a Flexible Substrate <i>K. S. Hsu^{1,2}, T. T. Chiu^{1,2} and M. H. Shih^{1,2}, ¹RCAS and ²National Chiao Tung Univ. (Taiwan)</i></p> <p>16:40 I-2-4 Large Area of Ultraviolet GaN-based Photonic Quasicrystal Laser <i>C. C. Chen¹, M. Y. Kuo², C. H. Chiu¹, P. M. Tu¹, M. H. Shih², S. P. Chang¹, J. K. Huang¹, H. C. Kuo¹, H. W. Zan¹ and C. Y. Chang¹, ¹National Chiao Tung Univ. and ²RCAS (Taiwan)</i></p> <p>16:55 I-2-5 Optical Characteristics Improvement of High Q Microcavity Light Emitting Diodes with Buried AlN Current Blocking Apertures <i>Y. L. Wu, B. S. Cheng, T. C. Lu, C. H. Chiu, C. H. Chen, P. M. Tu, H. C. Kuo and S. C. Wang, National Chiao Tung Univ. (Taiwan)</i></p>		<p>K-2: CNT Device (Area 13)</p> <p>16:10 K-2-3 Argon Ion Bombardment to Improve Contacts in Solution-Processed Single-Walled Carbon Nanotube Thin Film Transistor <i>X. Yi, G. Nakagawa, H. Ozawa, T. Fujigaya, N. Nakashima and T. Asano, Kyushu Univ. (Japan)</i></p> <p>16:25 K-2-4 Optimization of Source/Drain Doping Concentration of Carbon Nanotube FETs to Suppress Off-state Leakage Current while Keeping Ideal On-state Current <i>B. P. Algul and K. Uchida, Tokyo Tech (Japan)</i></p> <p>16:40 K-2-5 Spin-Related Novel Optical Phenomena in Single-Walled Carbon Nanotubes <i>S. Konabe^{1,2} and S. Okada^{1,2}, ¹Univ. of Tsukuba and ²CREST-JST (Japan)</i></p> <p>16:55 K-2-6 Carbon Nanotube Photonics: Light emission in silicon and optical gain <i>N. Izard¹, E. Gaufres^{1,2}, A. Beck¹, A. Noury¹, X. L. Roux² and L. Vivien¹, ¹Univ. Paris-Sud and ²Univ. Montréal (France)</i></p>	<p>L-2: Thin-Film Silicon Solar Cells (Area 14)</p> <p>16:25 L-2-3 Development of the TCO Layer for Nanocrystalline Cubic Silicon Carbide / Silicon Heterojunction Solar Cells with Aluminum Oxide Passivation Layers <i>J. Irikawa, S. Miyajima, T. Watahiki and M. Konagai, Tokyo Tech (Japan)</i></p> <p>16:40 L-2-4 Embedded Biomimetic Nanostructures for Enhanced Optical Absorption in Thin-Film Solar Cells <i>H. W. Han¹, M. A. Tsai¹, Y. L. Tsai¹, P. C. Tesng¹, P. Yu¹, H. C. Kuo¹, C. H. Shen¹, J. M. Shieh^{1,2}, S. H. Lin¹ and C. C. Lin¹, ¹National Chiao Tung Univ. and ²National Nano Device Labs. (Taiwan)</i></p> <p>16:55 L-2-5 Photovoltaic Property of Wide-Gap Nanocrystalline Silicon Layers <i>R. Mentek, B. Gelloz and N. Koshida, Tokyo Univ. of Agri. and Tech. (Japan)</i></p> <p>17:10 L-2-2 Medium Range Order (MRO) in Hydrogenated Amorphous Si Detected by a Non-Vanishing Ligand Field Splitting, Δ LF, in Si L_{2,3} Core Level X-ray Spectra <i>G. Lucovsky¹, G.N. Parsons¹, D. Zeller¹, R. Lujan² and R.A. Stree², ¹North Carolina State Univ. and ²Palo Alto Research Center (USA)</i></p>	<p>M-2: Oxides (Area 8)</p> <p>16:25 M-2-3 Processing Induced Pre-Existing Vacated (Empty) O-atom Defect Sites in Remote Plasma Deposited GeO₂ and SiO₂ Gate Dielectrics <i>G. Lucovsky, J. Kim, K. Wu, D. Zeller, B. Papas and J. L. Whitten, North Carolina State Univ. (USA)</i></p> <p>16:40 M-2-4 Epitaxy of Spinel Zn₂TiO₄ (111) on GaN (001) for MOS Application <i>S. W. Fu, J. C. Wu, C. Y. Hsiao, K. T. Hung, S. H. Wu, H. J. Chen, H. T. Wu and C. F. Shih, National Cheng Kung Univ. (Taiwan)</i></p> <p>16:55 M-2-5 Functional Oxides Integrated Epitaxially onto Semiconductors <i>R. Droopad, G. Radhakrishnan, R. Contreras-Guerro, W. Priyantha and N. Theodoropoulou, Texas State Univ. (USA)</i></p>	

Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)

Thursday, September 29

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
		B-3: Novel structure and fabrication process for OTFT (Area 10) (9:00-10:15) Chairs: H. Maeda (Dai Nippon Printing Co. Ltd.) H. Usui (Tokyo Univ. of Agri. & Tech.)	C-3: Memory Application (Area 2) (9:00-10:00) Chairs: A. Ikeda (Panasonic Corp.) M. Ueki (Renesas Electronics Corp.)		E-3: Process Technology and Analysis (Area 1) (9:00-10:20) Chairs: H. Nohira (Tokyo City Univ.) S. Tsujikawa (Sony Corp.)	F-3: NAND (Area 4) (9:00-10:00) Chairs: E. Yang (eMemory Technology Inc.) M. Moniwa (Renesas Electronics Corp.)
		9:00 B-3-1 Room temperature fabrication of HFON gate insulator for low-voltage operating pentacene-based organic field-effect transistors <i>M. Liao¹, H. Ishiura^{1,2} and S. Ohmi¹, ¹Toyo Tech and ²Konkuk Univ. (Japan)</i>	9:00 C-3-1 Improvement of thermal stability in High Density Ta₂O₅ 3D capacitor by additional thin SiO₂ layer <i>M. Detalle, H. Dekkers, G. Potoms, A. Phommahaxay, D. S. Tezcan, P. Soussan and G. Beyer, IMEC (Belgium)</i>		9:00 E-3-1 Soft X-ray Photoelectron Spectroscopy on Chemical Bonding States of Boron Doped in Si Fin Structures <i>Y. Miyata¹, J. Kanehara¹, H. Nohira², Y. Izumi³, T. Muro³, T. Kinoshita³, P. Ahmet¹, K. Kakushima¹, K. Tsutsui¹, T. Hattori¹ and H. Iwai¹, ¹Tokyo Tech, ²Tokyo City Univ. and ³JASRI/SPring-8 (Japan)</i>	9:00 F-3-1 First 64kb Ferroelectric-NAND Flash Memory Array with 7.5 V Program, 10⁸ Endurance and Long Data Retention <i>X. Zhang¹, M. Takahashi¹, K. Takeuchi² and S. Sakai¹, ¹AIST and ²Univ. of Tokyo (Japan)</i>
		9:30 B-3-3 UV-Ozone Effect of the Organic Thin Film Transistor with PVP Gate Dielectric in Low Temperature <i>H. J. Yun¹, K. H. Baek², L. M. Do², S. Y. Lee¹, K. S. Jeong¹, Y. M. Kim¹, S. D. Yang¹, H. D. Lee¹ and G. W. Lee¹, ¹Chungnam National Univ. and ²ETRI (Korea)</i>	9:20 C-3-2 Pico-Ampere Switching ReRAM with Vertically Contacted 5 nm-diameter Carbon Nanotube Electrodes for BEOL-Based Memory <i>H. Nakano, M. Takahashi, T. Murakami, A. Kawabata, M. Sato, M. Nihei and N. Yokoyama, AIST (Japan)</i>		9:20 E-3-2 Concentration Depth Profiling of Heavily Doped Boron at and near SiO₂/Si Interface by Angle-resolved Soft X-ray Photoelectron Spectroscopy <i>K. Kakushima¹, J. Kanehara¹, Y. Izumi², T. Muro², T. Kinoshita², P. Ahmet¹, K. Tsutsui¹, T. Hattori¹ and H. Iwai¹, ¹Tokyo Tech and ²JASRI/SPring-8 (Japan)</i>	9:20 F-3-2 Assessment of Erase-Verify Function in NAND Arrays with Charge-Based Capacitance Measurement <i>L. H. Chong, Y. W. Chang, K. F. Chen, Y. J. Chen, S. H. Ku, N. K. Zous, I. J. Huang, T. Han, M. S. Chen, W. P. Lu, K. C. Chen and C. Y. Lu, Macronix Int. Co., Ltd. (Taiwan)</i>
		9:45 B-3-4 Spatial Control of the Threshold Voltage of Low-Voltage Organic Transistors by Microcontact Printing of Alkyl- and Fluoroalkyl-phosphonic Acids <i>I. Hirata¹, U. Zschieschang², F. Ante², T. Yokota¹, K. Kuribara¹, T. Yamamoto¹, K. Takimiya³, M. Ikeda⁴, H. Kuwabara¹, H. Klauk², T. Sekitani¹ and T. Someya¹, ¹Univ. of Tokyo, ²Max Planck Inst. for Solid State Res., ³Hiroshima Univ. and ⁴Nippon Kayaku Corp., Ltd. (Japan)</i>	9:40 C-3-3 Performance Evaluation of a Logic-IP Compatible (LIC) Embedded DRAM with Cylinder Capacitors in Low-k/Cu BEOL Layers <i>I. kume, N. inoue, K. Hijioka, J. Kawahra, K. Takeda, N. Furutake, H. Shirai, K. Kazama, S. Kuwabara, M. Watarai, T. Sakoh, T. Takahashi, T. Ogura, T. Taiji, K. Kasama, M. Sakamoto, M. Hane and Y. Hayashi, Renesas Electronics Corp. (Japan)</i>		9:40 E-3-3 On the Si Surface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology <i>R. Kuroda, A. Teramoto, X. Li, T. Suwa, S. Sugawa and T. Ohmi, Tohoku Univ. (Japan)</i>	9:40 F-3-3 Disturb-free 3D vertical FG NAND with Separated-Sidewall Control Gate <i>M. S. Seo^{1,2} and T. Endoh^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)</i>
		10:00 B-3-5 Air-Stable Polymer and Blade Coating Technique for High-Performance Vertical Polymer Transistors <i>H. W. Zan, Y. C. Chao, C. H. Chung, Y. H. Hsu and H. F. Meng, National Chiao Tung Univ. (Taiwan)</i>			10:00 E-3-4 High Quality and Low Thermal Budget Silicon Nitride Deposition Using PECVD for Gate Spacer, Silicide Block and Contact Etch Stopper <i>Y. Nakao, R. Kuroda, H. Tanaka, A. Teramoto, S. Sugawa and T. Ohmi, Tohoku Univ. (Japan)</i>	

Coffee Break

Short Presentation (10:45-12:00)

Short Presentation P-6 (10:45-12:00) Chairs: T. Suzuki (JAIST) S. Sasa (Osaka Inst. of Tech.)	Short Presentation P-10 (10:45-12:00) Chairs: T. Shimada (Hokkaido Univ.) S. Naka (Univ. of Toyama)	Short Presentation P-2 (10:45-12:00) Chairs: M. Ueki (Renesas Electronics Corp.) A. Ikeda (Panasonic Corp.)	Short Presentation P-3 (10:45-12:00) Chairs: H. Fujimoto (Panasonic Corp.) O. Weber (CEA-LETI/MINATEC)	Short Presentation P-1 (10:45-12:00) Chairs: K. Kita (Univ. of Tokyo) E. Nishimura (Tokyo Electron Ltd.)	Short Presentation P-4 (10:45-12:00) Chairs: T. Eshita (Fujitsu Semiconductor Ltd.) T. Endoh (Tohoku Univ.)
--	--	--	---	---	--

12:00-13:30 Lunch

Thursday, September 29

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
G-3: Variation and Reliability (Area 5) (9:00-10:15) Chairs: H. Takao (Kagawa Univ.) S. Sugawa (Tohoku Univ.)	H-3: Electric, Magnetic and Optical Biosensing (Area 11) (9:00-10:15) Chairs: Y. S. Yang (National Chiao Tung Univ.) H. Suzuki (Hiroshima Univ.)	I-3: Plasmonics and Nonlinear Devices (Area 7) (9:00-10:15) Chairs: H. Isshiki (The Univ. of Electro-Communications) J. Fujikata (NEC Corp.)	J-3: Graphene Quantum Transport (Area 9) (9:00-10:15) Chairs: T. Machida (Univ. of Tokyo) A. Kanda (Univ. of Tsukuba)	K-3: Nanowire/Nanotube FET (Area 13) (9:00-10:00) Chairs: J. Motohisa (Hokkaido Univ.) C. Liu (Chinese Academy of Sciences)	L-3: Compound Thin Film Solar Cells. (Area 14) (9:00-10:15) Chairs: N. J. Ekins-Daukes (Imperial College London) H. Katagiri (NNCT)	M-3: III-V Compounds (Area 8) (9:00-10:15) Chairs: M. Kondow (Osaka Univ.) T. Suemasu (Univ. of Tsukuba)	
9:00 G-3-1 Multi-core LSI Lifetime Extension by NBTI-Recovery-based Self-healing <i>T. Matsumoto¹, H. Makino¹, K. Kobayashi³ and H. Onodera^{1,2},¹Kyoto Univ.,²Kyoto Inst. of Tech. and³CREST-JST (Japan)</i>	9:00 H-3-1 (Invited) Bio-particles Detection based on Dielectrophoretic Microfluidic Chip Combined with Optical Method <i>H. C. Chang, C. C. Chung and I. F. Cheng, National Cheng Kung Univ. (Taiwan)</i>	9:00 I-3-1 (Invited) Plasmonic Nanophotonic Structures for Future Communications and Energy Applications <i>H. A. Atwater, California Inst. of Tech. (USA)</i>	9:00 J-3-1 (Invited) Electronic transport in graphene nanostructures <i>T. Ihn, S. Dröscher, J. Güttinger, A. Jacobsen, H. Knowles, F. Molitor, S. Schnez, P. Simonet, C. Stampfer and K. Ensslin, Solid State Physics Lab. (Switzerland)</i>	9:00 K-3-1 Electron mobility calculations of free-standing Si-nanowires with atomistic electron-phonon interactions <i>Y. Yamada, H. Tsuchiya and M. Ogawa, Kobe Univ. (Japan)</i>	9:00 L-3-1 (Invited) Hetero Junction Engineering for High Efficiency Cu(In,Ga)Se₂ Solar Cells <i>T. Minemoto, Ritsumeikan Univ. (Japan)</i>	9:00 M-3-1 (Invited) Morphological and compositional interface stability of metastable ternary and quaternary (Ga,In)(As,Sb) quantum wells <i>A. Trampert, Paul-Drude-Institute (Germany)</i>	
9:20 G-3-2 Experimental Comparison of Process Variation in 65nm and 180nm CMOS Using Ring Oscillators with Adjustable Delay <i>T. Ansari, W. Imafuku, M. Yasuda, S. Sasaki, H. J. Mattausch and T. Koide, Hiroshima Univ. (Japan)</i>	9:30 H-3-2 Study on Micro Optical Diffusion Sensor using Laser-induced Dielectrophoresis <i>Y. Ishii, Y. Taguchi and Y. Nagasaka, Keio Univ. (Japan)</i>	9:30 I-3-2 Femtosecond Two-photon Fluorescence Microscopy of Surface Plasmon Polariton <i>T. Hattori¹, A. Kubo¹, K. Oguri², H. Nakano² and H. T. Miyazaki¹,¹Univ. of Tsukuba,²NTT Basic Res. Labs. and³NIMS (Japan)</i>	9:30 J-3-2 Introducing Nonuniform Strain to Graphene: Toward Strain Engineering <i>H. Tomori^{1,2}, H. Goto^{1,2}, Y. Nukui^{1,2}, Y. Toyota^{1,2}, Y. Ootuka¹, K. Tsukagoshi^{2,3}, S. Moriyama¹, E. Watanabe¹, D. Tsuya¹ and A. Kanda^{1,2},¹Univ. of Tsukuba,²CREST-JST and³NIMS (Japan)</i>	9:15 K-3-2 Charge transfer by multiple donors in a Si nanowire <i>G. P. Lansbergen, Y. Ono and A. Fujiwara, NTT Basic Res. Labs. (Japan)</i>	9:30 L-3-2 Cu(In,Al)S₂ thin film solar cells prepared from sulfurization of Cu-In-Al precursors <i>Y. Oda, R. Hamazaki, S. Fukamizu, A. Yamamoto, T. Minemoto and H. Takakura, Ritsumeikan Univ. (Japan)</i>	9:30 M-3-2 High-speed three-dimensional reciprocal-space mapping during MBE growth of InGaAs <i>W. Hu¹, H. Suzuki², T. Sasaki¹, M. Kozu¹ and M. Takahashi^{1,4},¹JAEA,²Univ. of Miyazaki,³Toyota Technological Inst. and⁴Univ. of Hyogo (Japan)</i>	
9:40 G-3-3 Effect of Resin-Molded Package Structure on Silicon Chip Surface Stress Distribution <i>N. Ueda, E. Nishiyama and H. Watanabe, RICOH Co., Ltd. (Japan)</i>	9:45 H-3-3 Development and Evaluation of Local Illumination Device beyond Diffraction Limit using Polymeric Nanohole Array <i>T. Ono^{1,2}, R. Iizuka^{1,2}, T. Akagi^{1,2}, T. Funatsu^{1,2} and T. Ichiki^{1,2},¹Univ. of Tokyo and²CREST-JST (Japan)</i>	9:45 I-3-3 Modal phase matcing in ZnO channel waveguide for highly efficient second harmonic generation <i>Y. Taira, T. Kita, Y. Morales and H. Yamada, Tohoku Univ. (Japan)</i>	9:45 J-3-3 Device Performance of Graphene Nanoribbon MOSFET and Tunneling FET with Phonon Scattering: A Computation Study <i>K. T. Lam¹, S. K. Chin² and G. Liang^{1,2},¹National Univ. of Singapore and²Inst. of High Performance Computing (Singapore)</i>	9:30 K-3-3 High-performance Carbon Nanotube Thin-film Transistors with >600 cm²V⁻¹s⁻¹ Mobility and >10⁷ On/off Ratio <i>D. M. Sun¹, M. Y. Timmermans², Y. Tian², A. G. Nasibulin², S. Kishimoto¹, T. Mizutani¹ and E. I. Kauppinen²,¹Y. Ohno¹,¹Nagoya Univ. and²Aalto Univ. (Japan)</i>	9:45 L-3-3 Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n⁻BaSi₂/p⁻Si Tunnel Junction to Undoped BaSi₂ Overlayers <i>W. J. Du¹, T. Saito¹, M. A. Khan¹, K. Nakamura¹, M. Baba¹, K. Toh¹, K. Toko¹, N. Usami^{2,3} and T. Suemasu^{1,3},¹Univ. of Tsukuba,²Tohoku Univ. and³CREST-JST (Japan)</i>	9:45 M-3-3 Effect of Initial In Coverage for Preparation of InSb Bilayer on Electrical Properties of InSb Films Grown By Surface Reconstruction Controlled Epitaxy <i>M. Mori¹, Y. Yasui¹, K. Nakayama¹, K. Nakatani¹ and K. Maezawa¹, Univ. of Toyama (Japan)</i>	
10:00 G-3-4 (Late News) Investigation of Subthreshold Drain Current Mismatch Characteristics for Nanoscale MOSFETs <i>J. J. Y. Kuo and P. Su, National Chiao Tung Univ. (Taiwan)</i>	10:00 H-3-4 Point of care biosensing protocol based on magnetically induced self-assembly of functionalized particles dispersed in colloids <i>Y. Yang^{1,2}, T. Takamura¹ and A. Sandhu^{1,3},¹Tokyo Tech,²Tsinghua Univ. and³Toyoashi Univ. of Tech. (Japan)</i>	10:00 I-3-4 MgO:LiNbO₃ Waveguide Second-Harmonic Generation Devices with Domain-Inverted Gratings Formed by 2-Step Voltage Application under UV Light <i>M. Fujimura, E. Kitado, T. Inoue and T. Suhara, Osaka Univ. (Japan)</i>	10:00 J-3-4 Mobility Difference in Top and Bottom Surfaces of Multilayer Graphene Placed on Silicon Dioxide <i>Y. Nukui^{1,2}, H. Tomori^{1,2}, H. Goto^{1,2}, Y. Toyota^{1,2}, Y. Ootuka¹, K. Tsukagoshi^{2,3} and A. Kanda^{1,2},¹Univ. of Tsukuba,²CREST-JST and³NIMS (Japan)</i>	9:45 K-3-4 Ambipolar Conversion of Polymer-Coated All Single-Walled Carbon Nanotube Field-Effect Transistors <i>S. Aikawa^{1,2}, E. Einarsson¹, S. Chitashi¹, E. Nishikawa¹ and S. Maruyama¹,¹Univ. of Tokyo and²Tokyo Univ. of Sci. (Japan)</i>	10:00 L-3-4 Annealing of the BaSi₂ Epitaxial Films Implanted with BF₃ Ions <i>K. O. Hara^{1,4}, N. Usami^{1,4}, Y. Hoshi¹, Y. Shiraki¹, M. Suzuno¹, K. Toko^{1,4} and T. Suemasu^{1,4},¹Tohoku Univ.,²Tokyo City Univ.,³Univ. of Tsukuba and⁴CREST-JST (Japan)</i>	10:00 M-3-4 Characteristics of Nitrogen δ-doped AlGaAs/GaAs Quantum Wells grown by Molecular Beam Epitaxy <i>S. Furuse, K. Sumiya, M. Morifuji and F. Ishikawa, Osaka Univ. (Japan)</i>	

Coffee Break

Short Presentation (10:45-12:00)							
Short Presentation P-5 (10:45-12:00) Chairs: K. Kagawa (Shizuoka Univ.) T. Koide (Hiroshima Univ.)	Short Presentation P-11 (10:45-12:00) Chairs: K.Sawada (Toyoashi University of Tech.) T.Tanaka (Tohoku Univ.)	Short Presentation P-7 (10:45-12:00) Chairs: H. Isshiki (The Univ. of Electro-Communications) N. Iizuka (Toshiba Corp.)	Short Presentation P-9 (10:45-12:00) Chairs: K. Ono (RIKEN) H. Gotoh (NTT Basic Res. Labs.)	Short Presentation P-13 (10:45-12:00) Chairs: Y. Ohno (Nagoya Univ.) J. Motohisa (Hokkaido Univ.)	Short Presentation P-14 (10:45-12:00) Chairs: M. Ishiko (Toyota Central R&D Labs., Inc) Y. Kurokawa (Tokyo Tech)	Short Presentation P-8 (10:45-12:00) Chairs: H. Hibino (NTT Basic Res. Labs.) T. Iwai (Fujitsu Labs. Ltd.)	Short Presentation P-12 (10:45-12:00) Chairs: M. Yamamoto (Hokkaido Univ.) H. Munekata (Tokyo Tech.)

12:00-13:30 Lunch

Thursday, September 29

POSTER SESSION (13:30-15:00, 6F Exhibition Hall)

Area 1: Advanced LSI Processing & Materials Science

(20 Papers)

P-1-1
High Quality Germanium Dioxide Formation using Damage-Free and Low-Temperature Neutral Beam Oxidation Process
A. Wada¹, K. Endo², M. Masahara² and S. Samukawa¹, ¹Tohoku Univ. and ²AIST (Japan)

P-1-2
Passivation of Ge(100) and (111) Surfaces by Termination of Nonmetal Elements
D. H. Lee, K. Kubo, T. Kanashima and M. Okuyama, Osaka Univ. (Japan)

P-1-3
First-Principles Study on Interface Properties of GeO₂/Ge System
S. Saito and T. Ono, Osaka Univ. (Japan)

P-1-4
Evaluation of Thermally-Grown Ge Oxide on Ge(100) and Ge(111) Surfaces
S. K. Sahari¹, A. Ohta¹, M. Matsui¹, H. Murakami¹, S. Higashi¹ and S. Miyazaki², ¹Hiroshima Univ. and ²Nagoya Univ. (Japan)

P-1-5
Control of Defect Properties in Ge Heteroepitaxial Layers by Sn Incorporation and H₂-Annealing
M. Adachi, Y. Shimura, O. Nakatsuka and S. Zaima, Nagoya Univ. (Japan)

P-1-6
Formation of Ohmic Contacts with Shallow NiGe/n⁺ Ge Junction
M. Miura^{1,2}, M. Noguchi^{1,2}, J. Fujikata^{1,2}, T. Horikawa^{1,3}, M. Takahashi^{1,3}, Y. Noguchi^{1,3} and Y. Arakawa^{1,4}, ¹PECST, ²PETRA, ³AIST and ⁴Univ. of Tokyo (Japan)

P-1-7
Estimation of breakdown electric-field strength reflecting local structures of SiO₂ by using first-principles molecular orbital calculation technique
H. Seki¹, Y. Shibuya², D. Kobayashi³, H. Nohira⁴, K. Yasuoka¹ and K. Hirose³, ¹Keio Univ., ²Tokyo City Univ. and ³ISAS/JAXA (Japan)

P-1-8
Clear Difference between Chemical Structure of SiO₂/Si Interface Formed Using Oxygen Radicals and That Formed Using Oxygen Molecules
T. Siwa¹, Y. Kumagai¹, A. Teramoto¹, T. Muro², T. Kinoshita², S. Sugawa¹, T. Hattori¹ and T. Ohmi¹, ¹Tohoku Univ. and ²Japan Synchrotron Radiation Res. Inst. (Japan)

P-1-9
Thermal Stability of Single and Alloy Noble Metals as for PMOS Gate Electrode
C. Choi¹, J. Ahn¹ and R. Choi², ¹Hanyang Univ. and ²Inha Univ. (Korea)

P-1-10
Analysis of Raman Spectra from Offset Spacer Region of Si-MOSFET Structure using Simulated Stress Tensor and Absorbed Light Intensity by FDTD Simulation
A. Satoh¹, T. Tada¹, V. Poborchii¹, T. Kanayama¹, S. Satoh¹ and H. Arimoto¹, ¹AIST and ²Fujitsu Semiconductor Ltd. (Japan)

P-1-11
Chemical Bonding States of As in Si Shallow Junctions Detected by Soft X-ray Photoelectron Spectroscopy and their Profiles
J. Kanehara¹, Y. Miyata¹, H. Nohira², Y. Izumi³, T. Muro³, T. Kinoshita⁴, P. Ahmet¹, K. Kakushima¹, K. Tsutsui¹, T. Hattori¹ and H. Iwai¹, ¹Tokyo Tech, ²Tokyo City Univ. and ³JASRI/SPring-8 (Japan)

P-1-12
Comprehensive Understanding of Flatband Voltage Shift Based on Energy Band Alignment of the Whole Metal/high-k/SiO₂/Si Stack
X. Wang¹, W. Wang¹, K. Han¹, J. Zhang², X. Ma¹, J. Xiang¹, D. Chen¹ and T. Ye¹, ¹Chinese Academy of Sci. and ²North China Univ.of Tech. (China)

P-1-13
Lateral Large-Grained Low-Temperature Polycrystalline Silicon-Germanium Thin-Film Transistors on Glass Substrate
Y. Okabe¹, K. Kondo¹, J. Suzuki², K. Kitahara² and A. Hara¹, ¹Tohoku Gakuin Univ. and ²Shimane Univ. (Japan)

P-1-14
Enhanced Sidewall Growth (ESG) process: towards PEALD with conformality above 100%
S. Ueda, A. Fukazawa, H. Fukuda and N. Kobayashi, ASM Japan K.K. (Japan)

P-1-15
Mean time to failure distribution in thin oxide film: Observation at nano and devices scale and modelling using a filamentary growth model
P. Delcroix^{1,2}, S. Blonkowski¹, M. Kogelschatz² and M. Rafik¹, ¹STMicroelectronics and ²CNRS (France)

P-1-16
Electrical Characteristics of Back Gated FET on a Wrinkle Free Graphene Channel
C. H. Cho, S. K. Lim, C. G. Kang, Y. G. Lee, H. J. Hwang, E. Park and B. H. Lee, Gwangju Inst. of Sci. and Tech. (Korea)

P-1-17
Novel activation method of B by soft X-ray undulator
T. Fukuoka¹, A. Heya¹, N. Matsuo¹, K. Kanda¹ and T. Noguchi², ¹Univ. of Hyogo and ²Univ. of the Ryukyus (Japan)

P-1-18
Impact of Zirconia addition for ALD Hafina in HKMG Device Fabricated GF vs. GL
C. K. Chiang^{1,3}, C. H. Wu¹, H. Y. Huang¹, J. F. Lin¹, C. L. Yang³, J. Y. Wu¹ and S. J. Wang¹, ¹National Cheng Kung Univ., ²Chung Hua Univ. and ³United Microelectronics Corp. (Taiwan)

P-1-19 (Late News)
Fermi Level Depinning for Metal/Germanium Schottky Junction by CF₄ Plasma Treatment
J. R. Wu, C. Y. Hou, M. L. Wu, C. C. Lin and Y. H. Wu, National Tsing-Hua Univ. (Taiwan)

Area 2: Advanced Interconnect / Materials Technology and Characterization

(18 Papers)

P-2-1
Direct wafer bonding technology of 300mm wafer
S. Hongo, K. Tanida, N. Yamaguchi and K. Takahashi, Toshiba Corp. (Japan)

P-2-2
Thinning Process Induced Surface Defects in Ultra-Thin Si Wafer
M. Murugesan¹, H. Nohira², C. Miyazaki³, H. Shimamoto³, H. Kobayashi¹, T. Fukushima¹, T. Tanaka¹ and M. Koyanagi¹, ¹Tohoku Univ., ²Tokyo City Univ. and ³ASET (Japan)

P-2-3
Mn₂O₃ Slurry Reuse for SiO₂ Film CMP
S. Kishii^{1,3}, K. Nakamura¹, K. Hanawa², S. Watanabe¹, Y. Arimoto¹, S. Kurokawa³ and T. K. Doi³, ¹Fujitsu Labs. Ltd., ²Showa Denko K. K. and ³Kyushu Univ. (Japan)

P-2-4
Optimum Design of MEMS Resonator Array to Measure the Young's Modulus of Nano-Scale Thin Films for the Reliability of Semiconductor Devices
H. Yamagishi¹, S. Ito¹, T. Namazu^{1,2}, T. Takeuchi¹, K. Murakami¹, Y. Kawashimo³ and T. Takano⁴, ¹Univ. of Hyogo, ²PRESTO-JST, ³Shinko Seiki Co. Ltd. and ⁴The New Industry Research Organization (Japan)

P-2-5
A New Technique for in-Plane Poisson's Ratio Measurement of Thin Films - Cases of Single-Crystal Silicon and Aluminum Thin Films -
T. Fujii¹, T. Namazu^{1,2}, M. Takahashi¹, M. Tanaka¹, K. Yoshiki¹ and S. Inoue¹, ¹Univ. of Hyogo and ²PRESTO-JST (Japan)

P-2-6
Evolution of Wafer Shape and Localized Stress of Silicon Surrounded by Through Silicon Via Patterns along Various Process Integration Steps
C. H. Lee¹, S. H. Jie¹, S. H. Son¹, J. T. Kim¹, H. W. Yoo¹, I. K. Han¹ and W. S. Yoo², ¹Hynix Semiconductor Inc. and ²WaferMasters, Inc. (Korea)

P-2-7
Improvement of the BCB Adhesion on Cr/Au Metal Layer for RF Packaging Module
N. Jeon, Y. H. Oh, Y. Ryoo and K. S. Seo, Seoul National Univ. (Korea)

P-2-8
Testkey Design of Through Silicon Vias (TSVs) for Accurate De-embedding and RF Model Parameters Extraction
J. Y. Wang¹, T. K. Huang¹, Y. C. Wu¹, S. S. H. Hsu¹, Z. H. Lin², C. S. Lin², S. S. Sheu², T. K. Ku² and C. H. Lin², ¹National Tsing Hua Univ. and ²ITRI (Taiwan)

P-2-9
Study of Local Charging Phenomena during SiO₂ Contact Hole Etching
T. Yagisawa¹, T. Tatsumi² and T. Makabe¹, ¹Keio Univ. and ²Sony Corp. (Japan)

P-2-10
Thermal Cycling Reliability of ChipArray® Thin Core Ball Grid Array assemblies with Fast Cure and Reworkable Capillary Flow Underfill
H. Shi and T. Ueda, Waseda Univ. (Japan)

P-2-11
Selective Heating of Microbumps Using Microwave for Low Strain Heterogeneous Chip Stack Integration
L. Qiu and T. Asano, Kyushu Univ. (Japan)

P-2-12
Room temperature fabrication of silver nanowire transparent electrodes
T. Tokuno, M. Nogi, M. Karakawa, J. T. Jiu and K. Suganuma, Osaka Univ. (Japan)

P-2-13
Low-Energy Ion-Beam-Assisted Sputtering for Si Nanocrystals
C. Y. Hsiao, K. W. Su, K. T. Hung, H. T. Wu, H. J. Chen, S. W. Fu, S. H. Wu and C. F. Shih, National Cheng Kung Univ. (Taiwan)

P-2-14
Highly Accurate Lattice-Strain mapping near Interfaces of Hetero-Structures by Convergent-Beam and Nano-Beam Electron Diffraction
K. Saitoh, H. Nakahara, Y. Daikyo and N. Tanaka, Nagoya Univ. (Japan)

P-2-15
Multi-layer Graphene for High-Frequency Interconnect
H. J. Lee, E. Kim and J. W. Jung, Sejong Univ. (Korea)

P-2-16
Investigation of Electrical Properties of HfN/HfSiON Gate Stacks In-situ Formed on Si(100) and Si(110)
T. Sano and S. Ohmi, Tokyo Tech (Japan)

P-2-18 (Late News)
MIM Capacitors with High Capacitance Density and Low Quadratic Voltage Coefficient by Employing Crystalline-TiO₂/SiO₂ Stacked Dielectric
C. C. Lin, W. Y. Ou, J. R.Wu, M. L.Wu, L. L.Chen and Y. H. Wu, National Tsing Hua Univ. (Taiwan)

Area 3: CMOS Devices / Device Physics

(22 Papers)

P-3-1
Impact of Aspect Ratio on the Subthreshold RTN Amplitude of Multi-Gate MOSFETs
B. K. Lu, M. L. Fan and P. Su, National Chiao Tung Univ. (Taiwan)

P-3-2
Saturation Behavior in the Generation of Interface Traps by Hot-Carrier Stress in Nanoscale MOSFETs
M. Hu, T. Yamane and T. Tsuchiya, Shimane Univ. (Japan)

P-3-3
Investigation of Temperature Dependence on DC and Low-Frequency Noise Characteristics in Uniaxial Tensile Strained nMOSFETs
S. C. Tsai¹, S. L. Wu¹, J. F. Chen¹, S. J. Chang¹, C. Y. Chang¹, P. C. Huang¹, C. Y. Wu¹, M. S. Chen¹, Y. C. Cheng³ and O. Cheng³, ¹National Cheng Kung Univ., ²Cheng Shiu Univ. and ³United Microelectronics Corp. (Taiwan)

P-3-5
The Effect of La₂O₃ Capping Layer Thickness on Hot Carrier Degradation of n-MOSFETs with High-k/Metal Gate Stack
D. W. Kim¹, S. H. Lee¹, C. G. Kim¹, T. K. Oh² and B. K. Kang¹, ¹Pohang Univ. Sci. Tech. and ²Hynix Semiconductor Inc. (Korea)

Thursday, September 29

Area 4: Advanced Memory Technology

(16 Papers)

P-4-1

Pushing Scaling Limit Due to Short Channel Effects and Channel Boosting Leakage from 13nm to 8nm with SOI NAND Flash Memory Cells

K. Miyaji, C. Hung and K. Takeuchi, Univ. of Tokyo (Japan)

P-4-4

Electrical Property of DNA FET —Charge Retention Property—

S. Takagi¹, N. Matsuo¹, K. Yamana¹, A. Heya¹, T. Takada¹ and S. Yokoyama², ¹Univ. of Hyogo and ²Hiroshima Univ. (Japan)

P-4-5

Areal and Structural Effect on Oxide based RRAM cell for Improving Resistive Switching Characteristics

K. C. Ryoo^{1,2}, J. H. Oh^{1,2}, S.H. Jung¹, G. T. Jeong², H. S. Jeong² and B. G. Park¹, ¹Seoul National Univ. and ²Samsung Electronics. Co., Ltd. (Korea)

P-4-6

Investigation of Switching Behavior of 2-terminal Devices on VO₂

I. P. Radu^{1,2}, K. Martens¹, B. Govoreanu¹, S. Mertens¹, X. Shi¹, M. Cantoro¹, M. Schaeckers¹, M. Jurczak¹, S. De Gendt^{1,2}, A. Stesmans^{1,2}, M. Heyns^{1,2} and J. A. Kittl¹, ¹IMEC and ²Univ. of Leuven (Belgium)

P-4-7

Evaluation of the WO₃ Film Properties for ReRAM Application

Y. Y. Chen^{1,2}, W. C. Chien¹, M. H. Lee², Y. C. Chen², A. T. H. Chuang², T. J. Hong¹, S. J. Lin¹, T. B. Wu¹ and C. Y. Lu², ¹National Tsing Hua Univ. and ²Macronix International Corp., Ltd. (Taiwan)

P-4-8

Characterization and improved endurance for HfO₂ resistive memory with CMP treated TiN bottom electrode

P. S. Chen¹, Y. S. Chen^{2,3}, H. Y. Lee², T. Y. Wu², W. H. Liu², P. Y. Gu², F. Chen² and M. J. Tsai², ¹MingShin Univ. Sci. and Eng., ²Industrial Tech. Res. Inst. and ³National Tsing Hua Univ. (Taiwan)

P-4-9

Study of Bipolar Multilevel Memristive Mechanism and Characterizations in a Thin FeO_x Transition Layer Device

G. Y. Wu¹, Y. F. Chang¹, L. W. Feng¹, C. Y. Chang¹ and T. C. Chang², ¹National Chiao Tung Univ. and ²National Sun Yat-Sen Univ. (Taiwan)

P-4-10

Multi-Level Phase-Change Memory Cells with SiN or Ta₂O₅ Barrier Layers

A. Gyanathan and Y. C. Yeo, National Univ. of Singapore (Singapore)

P-4-11

Endurance enhancement of elevated-confined phase change random access memory

*H. X. Yang^{1,2}, L. P. Shi¹, H. K. Lee¹, R. Zhao¹ and T. C. Chong², ¹A*STAR, ²National Univ. of Singapore and ³Singapore Univ. of Tech. and Design (Singapore)*

P-4-12

Simulation of Retention Behavior for the Phase Change Memory

J. Chen, D. Song, G. Du, G. Lian, J. Kang and X. Liu, Peking Univ. (China)

P-4-13 (Late News)

Filament Formation by Cu and Ag Ions for Memory Applications Utilizaing Oxide Dielectrics With Pre-existing Vacated O-atom Sites

Z. Zhang¹, E. Katz¹, D. Zeller², G. Lucovsky² and L. F. Brillson¹, ¹Ohio State Univ. and ²North Carolina State Univ. (USA)

P-4-14 (Late News)

Effect of Oxidation Amount on Gradual Switching Behavior in Reset Transition of Al/TiO₂ based Resistive Switching Memory and its Mechanism for MLC Operation

J. H. Oh^{1,2}, K. C. Ryoo^{1,2}, S. Jung¹, Y. Park² and B. G. Park¹, ¹Seoul National Univ. and ²Samsung Electronics Co., Ltd. (Korea)

P-4-15 (Late News)

Design and Optimization of Program and Restore Operations in CMOS-Compatible Nonvolatile Latch

J. G. Lee and S. Masui, Tohoku Univ. (Japan)

P-3-6

Characterization of Oxide Traps in 28 nm pMOSFETs with Σ -Shaped SiGe-S/D by Utilizing Random Telegraph Noise (RTN)

B. C. Wang¹, S. L. Wu¹, S. J. Chang¹, C. T. Huang and O. Cheng, ¹National Cheng Kung Univ. and ²Univ. of Cheng Shiu (Taiwan)

P-3-7

Hot-Carrier Effects on High-frequency Characteristics of RF LDMOS Transistors

K. M. Chen¹, Z. W. Mou¹, H. C. Kuo², C. S. Chiu¹, B. Y. Chen¹, W. D. Liu¹, M. Y. Chen¹, Y. C. Yang³, K. L. Wang³ and G. W. Huang^{1,2}, ¹National Nano Device Labs., ²National Chiao Tung Univ. and ³United Microelectronics Corp. (Taiwan)

P-3-8

Impact of OFF-state Degradation under Dynamic Stress on Reliability of Nanoscale n-Channel Metal-Oxide-Semiconductor Field-Effect Transistors at Elevated Temperature

N. H. Lee¹, K. J. Kim¹, H. W. Kim² and B. K. Kang¹, ¹POSTECH and ²Samsung Electronics Corp. Ltd. (Korea)

P-3-9

Modeling Subthreshold Current and Threshold Voltage of Fully-Depleted Double-gate Junctionless(J-less) Transistors

Z. M. Lin¹, H. C. Lin^{1,2}, K. M. Liu³ and T. Y. Huang¹, ¹National Chiao Tung Univ., ²Labs of National Nano Device and ³National Dong Hwa Univ. (Taiwan)

P-3-10

Integration of InGaAs Nanowire Vertical Surrounding-Gate Transistors on Si

K. Tomioka^{1,2}, M. Yoshimura¹ and T. Fukui¹, ¹Hokkaido Univ. and ²PREST-JST (Japan)

P-3-11

Body Channel Type Vertical MOSFET to Suppress Gate Leakage Current

T. Sasaki^{1,2} and T. Endoh^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)

P-3-12

Investigation of Short-Channel Effects in Junctionless Nanowire Transistors

P. Razavi, N. Dehdashti-Akhavan, R. Yu, G. Fagas, I. Ferain and J.P. Colinge, Univ. College Cork (Ireland)

P-3-13

Stack Gate Technique for Feasible Bulk FinFETs

Y. B. Liao¹, M. H. Chiang², W. C. Hsu¹, Y. S. Lai³ and H. Li², ¹National Cheng Kung Univ., ²National Ilan Univ. and ³National Nano Device Lab. (Taiwan)

P-3-14

Strain Effects on Ballistic Currents of Silicon Nanowire pFETs with Different Orientations

J. Qin, X. Liu, H. Xu, J. Zhang and G. Du, Peking Univ. (China)

P-3-16

Evidence of the universality of the hole mobility in accumulation MOS transistors

P. Gaubert, A. Teramoto, S. Sugawa and T. Ohmi, Tohoku Univ. (Japan)

P-3-17

Simulation of Electron Transport in Source and Drain Electrodes of Ultrathin Body III-V Channel MOSFETs

Y. Maegawa¹, S. Koba¹, H. Tsuchiya^{1,2} and M. Ogawa¹, ¹Kobe Univ. and ²CREST-JST (Japan)

P-3-18

Evaluation of Drain Current Fluctuations of Si MOSFETs using BSIM3-like Current Model and TCAD

A. Satoh¹, T. Tada¹, T. Kanayama¹, S. Satoh² and H. Arimoto¹, ¹AIST and ²Fujitsu Semiconductor Ltd. (Japan)

P-3-20 (Late News)

Critical Parameters for Accurate Calculation of Si Nanowire MOSFET Current

K. Natori, Tokyo Tech (Japan)

P-3-21 (Late News)

Impact of Poly Depletion on Accurate Evaluation of Self-Heating Effects in SOI MOSFETs with Four-point Gate Resistance Measurement Method

N. Beppu, T. Takahashi, T. Ohashi and K. Uchida, Tokyo Tech (Japan)

P-3-22 (Late News)

Random Interface-Traps-Induced Characteristic Fluctuation in 16-nm High-k/Metal Gate CMOS Device and Digital Circuit

Y. Y. Chiu, Y. Li and H. W. Cheng, National Chiao Tung Univ. (Taiwan)

P-4-16 (Late News)

SET polarity dependent resistive switching memory characteristics using IrOx/GdOx/WOx/W structure

D. Jana¹, S. Maikap¹, T. C. Tien², H. Y. Lee², W. S. Chen², F. T. Chen², M. J. Kao² and M. J. Tsai², ¹Chang Gung Univ. and ²ITRI (Taiwan)

Area 5: Advanced Circuits and Systems

(17 Papers)

P-5-1

Wireless Charge Based Capacitance Measurement Circuits with On-chip Spiral Inductor for RFID Biosensor

B. Kim¹, S. Uno² and K. Nakazato¹, ¹Nagoya Univ. and ²Ritsumeikan Univ. (Japan)

P-5-2

SPICE MOSFET Analog Model Parameter Verification and Re-optimization Based on g_m/I_b Lookup Table Design Methodology

T. Konishi¹, B. Patrick¹, T. Kaho² and S. Masui¹, ¹Tohoku Univ. and ²NTT Network Innovation Labs. (Japan)

P-5-3

Write Speed Evaluation of Reconfigurable Spin Logic Block with SPRAM for 3D-Stacked Reconfigurable Spin Processor

R. Nakazawa¹, H. Kino¹, K. Kiyoyama^{1,2}, M. Koyanagi¹ and T. Tanaka¹, ¹Tohoku Univ. and ²Nagasaki Inst. of Applied Science (Japan)

P-5-4

Nonvolatile Low Power 16-bit/32-bit MTJ Based Binary Counter and its Scaling

S. Togashi, T. Ohsawa and T. Endoh, Tohoku Univ. (Japan)

P-5-5

Evaluation of Reconfigurable Processor Test Chip for Dependable 3D Stacked Multicore Processor

H. Hashimoto, T. Fukushima, K. W. Lee, T. Tanaka and M. Koyanagi, Tohoku Univ. (Japan)

P-5-6

A High-Voltage Tolerant Interface Circuit for Embedded CMOS Non-volatile Memories

C. Y. Huang and H. Lin, National Chung Hsing Univ. (Taiwan)

P-5-7

The Integrated a-Si Gate Driver Circuit using Voltage Controlled Capacitance Modeling for HDIV/XGA

S. K. Han¹, J. Y. Kim¹, H. Choi¹, K. H. M. Choi¹, Y. S. Choi¹, K. M. Park² and S. Y. Choi², ¹LG Display Co. Ltd. and ²Kyungpook National Univ. (Korea)

P-5-8

A Fully-Parallel Self-Learning Analog Support Vector Machine Employing Compact Gaussian-Generation Circuits

R. Zhang and T. Shibata, Univ. of Tokyo (Japan)

P-5-9

Current Compensation Circuit for Precise Nano-Ampere Current Reference

K. Isono, T. Hirose, Y. Osaki, N. Kuroki and M. Numa, Kobe Univ. (Japan)

P-5-10

A Wide-Range Tunable Level-Keeper using Vertical MOSFETs for Current-Reuse Systems

S. Tanoi^{1,2} and T. Endoh^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)

P-5-11

A Reduced-Ripple PMOS Charge Pump Circuit with Small Filtering Capacitors

B. Y. Jaw and H. Lin, National Chung Hsing Univ. (Taiwan)

P-5-12

CMOS Op-amp Offset Calibration Technique Using a Closed Loop Offset Amplifier and Compact Resistor String DAC

H. Morimoto¹, H. Goto¹, H. Fujiwara² and K. Nakamura¹, ¹Kyushu Inst. of Tech. and ²New Japan Radio Co. Ltd. (Japan)

P-5-13

A Twistedly-Cascaded Time Difference Amplifier for High Robustness Against Process Variation

N. Harigai, K. Niitsu, D. Oki, M. Sakurai, T. J. Yamaguchi and H. Kobayashi, Gunma Univ. (Japan)

Thursday, September 29

P-5-14

An Experimental Verification of the Design Margin Analysis Method for Even-Stage Ring Oscillators with CMOS Latch

Y. Hirakawa, N. Mimura, A. Motomura and K. Nakamura, Kyushu Inst. of Tech. (Japan)

P-5-15

Analysis of Cascode Structure for 60GHz Amplifier Design in 65nm CMOS

Q. Bu, N. Li, H. Asada, K. Okada and A. Matsuzawa, Tokyo Tech (Japan)

P-5-16

MOS Power Cells for Output Power Levels of 17 to 23 dBm

R. L. Wang¹, C. H. Liu², C. C. Chuang², C. H. Tu¹, Y. Z. Juang² and Y. K. Su², ¹National Kaohsiung Normal Univ., ²National Cheng Kung Univ. and ³National Chip Implementation Center (Taiwan)

P-5-17

Power Amplifier for E-band Wireless Link Using 0.1 μ m GaAs pHEMT

M. Kang, B. Kim, K. Kim and W. Byun, ETRI (Korea)

Area 6: Compound Semiconductor Electron Devices and Related Technologies (12 Papers)

P-6-1

Hot Carrier Effect on RF Characteristics of High-k/Metal Gate SiGe Channel pMOSFETs

E. Y. Jeong¹, H. C. Sagong¹, D. Y. Choi¹, C. W. Sohn¹, J. S. Lee¹, C. Y. Kang² and Y. H. Jeong¹, ¹POSTECH and ²SEMATECH (Korea)

P-6-2

Effect of Etch Damage on Device performance in Trench-gate and Mesa-gate GaN Vertical MOSFET

K. W. Kim¹, S. D. Jung¹, M. K. Kwon¹, R. H. Kim¹, D. S. Kim¹, K. S. Im¹, H. S. Kang¹, C. H. Won¹, K. I. Jang¹, J. H. Lee², K. S. Kim¹ and J. H. Lee¹, ¹Kyungpook National Univ. and ²Samsung LED (Korea)

P-6-3

Electrical and Photo-response Properties of Titanium Contacts on n-type N-face and Ga-face GaN Layer for Vertical Power Devices Prepared by ELOG and Laser Lift-off

D. K. Kim¹, C. J. Lee¹, Y. J. Kwon¹, J. Y. Yun¹, D. S. Kim¹, H. B. Lee², J. H. Lee² and S. H. Hahn¹, ¹Kyungbook National Univ. and ²Samsung LED (Korea)

P-6-4

Plasma-Induced Damage of GaN and Its Recovery by Atomic Hydrogens at a Room Temperature

Y. Lu¹, S. Chen¹, R. Kometani¹, K. Takeda¹, H. Kondo¹, T. Egawa², K. Ishikawa¹, H. Amano¹, M. Sekine¹ and M. Hori¹, ¹Nagoya Univ. and ²Nagoya Inst. of Tech. (Japan)

P-6-5

Temperature Dependent Characteristics of Fe/n-GaN Schottky Diodes

R. Adari¹, B. Sarkar¹, T. Patil¹, D. Banerjee^{1,2}, P. Suggiseti¹, S. Ganguly¹ and D. Saha¹, ¹Center of Excellence in Nanoelectronics and ²IITB-Monash Research Academy (India)

P-6-6

Air-Gap Capacitance-Voltage Analyses of InP Surfaces after Wet and Dry Processes

T. Yoshida, Shimane Univ. (Japan)

P-6-7

High-Voltage AlGaIn/GaN HEMTs on Si Substrate with Implant Isolation

C. J. Yu¹, C. F. Huang¹, P. J. Chu¹, K. Y. Chen¹, S. S. H. Hsu¹, H. C. Chiu¹ and F. Zhao¹, ¹National Tsing Hua Univ., ²Chang Gung Univ. and ³Univ. of South Carolina (Taiwan)

P-6-8

Investigation of Plasma-Induced Damages in GaN with Different Processing

C. Y. Lee, H. Sekiguchi, H. Okada and A. Wakahara, Toyohashi Univ. of Tech. (Japan)

P-6-10

2D Device Simulation of AlGaIn/GaN HFET Current Collapse Caused by Deep Levels in GaN Buffer Layer

Y. Ikawa, T. Hosokawa, Y. Kio, J. P. Ao and Y. Ohno, Univ. of Tokushima (Japan)

P-6-11

Deep levels in n-GaN Doped with Carbon Studied by Deep Level and Minority Carrier Transient Spectroscopies

U. Honda¹, Y. Yamada¹, Y. Tokuda¹ and K. Shiojima², ¹Aichi Inst. of Tech. and ²Univ. of Fukui (Japan)

P-6-12 (Late News)

An Al₂O₃/InSb/Si MOS Diode Having an Ultra-Thin InSb Layer

A. Kadoda¹, T. Iwasugi¹, K. Nakatani¹, K. Nakayama¹, M. Mori¹, K. Maezawa¹, E. Miyazaki² and T. Mizutani², ¹Univ. of Toyama and ²Nagoya Univ. (Japan)

Area 7: Photonic Devices and Optoelectronic Integration (30 Papers)

P-7-1

GaN-based LED with embedded air voids array structure

D. S. Kuo, S. J. Chang, T. K. Ko², W. Y. Yen² and S. J. Hon², National Cheng Kung Univ. (Taiwan)

P-7-2

Investigation of Efficiency Droop for UV-LED with N-type AlGaIn Layer

Y. C. Chen¹, C. C. Tu¹, J. R. Chang¹, P. M. Tu¹, S. P. Chang¹, S. S. Yen¹, Y. C. Chen¹, H. C. Kuo¹ and C. Y. Chang¹, ¹National Chiao Tung Univ. and ²Chung Yuan Christian Univ. (Taiwan)

P-7-3

Nanoscale epitaxial lateral overgrowth of GaN-based light-emitting diodes on a SiO₂ nanorod-array patterned sapphire template

C. H. Chiu¹, C. C. Lin¹, C. H. Wang¹, S. P. Chang^{1,2}, C. Y. Jang¹, Z. Y. Li¹, H. C. Yang², H. C. Kuo¹, T. C. Lu¹ and S. C. Wang¹, ¹National Chiao Tung Univ. and ²Epistar Co. Ltd. (Taiwan)

P-7-4

Enhanced Light Output of Vertical GaN-Based LEDs with Surface Roughening Using IZO Nano Roughened

P. R. Wang, S. J. Wang, D. M. Kuo, C. H. Kuo, H. R. Kuo, T. H. Lin and P. H. Wang, National Cheng Kung Univ. (Taiwan)

P-7-5

Elucidating the electrical characteristics of an inversion domain boundary in p-type GaN of light-emitting diodes

Y. S. Wang¹, M. C. Hsieh¹, J. F. Chen¹, J. B. Huang² and N. C. Chen¹, ¹National Chiao Tung Univ., ²National Taiwan Univ. of Sci. and Tech. and ³Chang Gung Univ. (Taiwan)

P-7-6

Deep UV Light Emitting Diodes on AlN Templates Grown by Commercialized MOCVD (<1200°C)

M. Kurouchi, T. Takeuchi and Y. Aoyagi, Ritsumeikan Univ. (Japan)

P-7-7

An n-ZnO/p-GaN Ultraviolet Light Emitting Diode Prepared Using Radio-Frequency Magnetron Cosputtering System

N. J. Wu¹, C. P. Hsu¹, Y. J. Tsai¹, B. T. Lai¹ and D. S. Liu¹, ¹National Formosa Univ. and ²ITRI (Taiwan)

P-7-8

Low efficiency droop of InGaIn/GaN blue LEDs with super-lattice active structure

S. P. Chang^{1,2}, J. R. Chang¹, B. M. Tu¹, Y. C. Chen¹, K. P. Sou¹, Y. C. Hsu¹, S. S. Yen¹, Y. J. Li¹, H. C. Yang¹, T. C. Hsu¹, H. C. Kuo¹ and C. Y. Chang¹, ¹National Chiao Tung Univ. and ²Epistar Corp. Ltd. (Taiwan)

P-7-9

Design of Optically Pumped PbS-Based Mid-Infrared Surface Emitting Lasers

Y. Sugiyama, K. Kodama, Y. Isaji, T. Yokoyama, S. Kobayashi, Y. Takano and A. Ishida, Shizuoka Univ. (Japan)

P-7-10

The Fabrication of a multiple Outputs Semiconductor Ring Laser Diode and its Output Characteristics

M. C. Shih, C. S. Chen and W. H. Lan, National Univ. of Kaohsiung (Taiwan)

P-7-12

Study on Structure Dependent Optical Characteristics of GaAs-related Photonic Crystal Cavities

K. Nakano, R. Nakao, H. Nagatomo, K. Kukita, K. Uwai, F. Ishikawa, M. Morifuji and M. Kondow, Osaka Univ. (Japan)

P-7-13

Enhanced localized surface plasmon resonance in a stacked structure

H. H. Chen, Y. T. Chang, C. W. Yu, S. Y. Huang, F. T. Chuang and S. C. Lee, National Taiwan Univ. (Taiwan)

P-7-14

Low-temperature Photoluminescence Characteristics of GaAs Quantum-well Waveguides

Y. Nagao, Y. Kuwamura, A. Nizamuddin, T. Nakahora, T. Hotani, N. Katsuki and T. Katsuyama, Univ. of Fukui (Japan)

P-7-15

Band-pass Optical Filter in Light-induced Self-written Waveguide

H. Watanabe¹, M. Tomiki¹, H. Sakata¹, T. Yamashita², A. Kawasaki² and M. Kagami², ¹Shizuoka Univ. and ²Toyota Central R&D Labs. (Japan)

P-7-16

Basic Study of Coupling on 3D Cross of Si Photonic Wire waveguide for Optical Interconnection on Inter/inner-chip

K. Furuya^{1,2}, T. Takei^{1,2}, T. Kamei^{1,2}, Y. Sakakibara^{1,2} and M. Mori^{1,2}, ¹AIST and ²PECST (Japan)

P-7-17

Fabrication and Characterization of InGaAs/InAlAs Multiple FACQW Structures with Larger Tolerance to Impurity in Intrinsic Layer

Y. Amma and T. Arakawa, Yokohama National Univ. (Japan)

P-7-18

Numerical Demonstration of InP 1xN Planar Optical Switch Based on Beam Deflection

S. Che, M. Zaitu, A.Higo, T. Tanemura and Y. Nakano, Univ. of Tokyo (Japan)

P-7-19

Effect of Plasma Processes on the Characteristics of GaAs Related Optical Device Structure

A. Watanabe, F. Ishikawa and M. Kondow, Osaka Univ. (Japan)

P-7-20

Characterization of the Oxide Film Obtained by Wet Oxidation of Al_{0.5}Ga_{0.5}As with x=0.55-0.99

Y. Hirai, T. Yamada, M. Kondow and F. Ishikawa, Osaka Univ. (Japan)

P-7-21

Structural and luminescence properties of highly crystalline ZnO nanoparticles prepared by sol-gel method

W. Bousslama¹, H. Elhouichet^{1,2}, B. Geltoz³, B. Sieber¹, M. Moreau¹, M. Fèrid¹ and N. Koshida³, ¹Centre National de Recherches en Sciences des Matériaux, ²Faculté des Sciences de Tunis, ³Tokyo Univ. of Agri. and Tech. and ⁴Université Lille 1 (Tunisia)

P-7-22

Reduction of Hydrogen Annealing Temperature for Shape Transformation of Si Surface by Very Short Water Rinse

M. Fukuyama, Y. Amemiya and S. Yokoyama, Hiroshima Univ. (Japan)

P-7-23

Optical fiber sensor with multimode interference structure

Y. Matsumoto, S. Tawe, K. Tsuruta and H. Fukano, Okayama Univ. (Japan)

P-7-24

Periodic Arrangement of Au Nanoparticles on SOI Photodiode for Absorption Enhancement

A. Ono, H. Satoh, R. Kawai and H. Inokawa, Shizuoka Univ. (Japan)

P-7-25

Enhanced Light Sensitivity of Thin SOI Photodiode by Metal Line-and-Space Grating of Various Materials

H. Satoh, H. Inokawa and A. Ono, Shizuoka Univ. (Japan)

P-7-26

Wavelength Sensitive PIN Photodetector Using Guided Mode Resonance

K. W. Lai, S. D. Lin, Y. J. Fu and Y. S. Li, National Chiao Tung Univ. (Taiwan)

P-7-27

Active Layer Thickness Dependence of the Bandwidth of Amorphous Silicon Photoconductors

T. Maruyama, H. Otsuka and K. Iiyama, Kanazawa Univ. (Japan)

P-7-28

A Visible Light Blinded Photo-detector With an ITO/ZST/Si MIS Device Structure

K. E. Chiu, Y. Y. Lin, Y. C. Sun, M. C. Shih and W. H. Lan, National Univ. of Kaohsiung (Taiwan)

P-7-29

GaN-based MIS Ultra-violet Photodetectors with the CsF current suppressing Layer

C. H. Chen, C. M. Tsai, C. F. Cheng, S. F. Yen and P. Y. Su¹, Cheng Shiu Univ. (Taiwan)

Thursday, September 29

P-7-30

Performance Improvement of 850nm Si Photodiodes by Symmetric Layout in Standard 0.18 μ m CMOS Technology
F. P. Chou¹, G. Y. Chen¹, C. W. Wang¹, Z. Y. Li¹, Y. C. Liu², W. K. Huang³ and Y. M. Hsin¹, ¹National Central Univ., ²HTC Corp. and ³Novatek Microelectronics Corp. (Taiwan)

Area 8: Advanced Material Synthesis and Crystal Growth Technology (24 Papers)

P-8-1

Selective-area growth of 4-color InAs-QD ensembles for broadband light source

K. Takeuchi¹, N. Ozaki¹, S. Ohkouchi², N. Ikeda³, Y. Sugimoto³, K. Asakawa⁴ and R. A. Hogg⁵, ¹Wakayama Univ., ²NEC Corp., ³NIMS, ⁴Univ. of Tsukuba and ⁵Univ. of Sheffield (Japan)

P-8-2

Characterization of highly stacked InGaAs quantum dots structures grown with ultrahigh-rate MBE growth technique

F. Tanoue^{1,2}, H. Sugawara¹, K. Akahane² and N. Yamamoto², ¹Tokyo Metropolitan Univ. and ²NICT (Japan)

P-8-3

Field Emission Properties of 10-nm Pillars of Organics Fabricated by Pt particles and Plasma Etching

T. Suzuki¹, K. Takeda^{1,4}, H. Kondo¹, K. Ishikawa¹, Y. Setsuhara^{2,4}, M. Shiratani^{3,4}, M. Sekine^{1,4} and M. Hori^{1,4}, ¹Nagoya Univ., ²Osaka Univ., ³Kyushu Univ. and ⁴CREST-JST (Japan)

P-8-4

Self-induced InAs nanowires grown on natural-oxide-covered Si(111) by molecular-beam epitaxy
S. Wang, X. Yu, H. Wang and J. Zhao, Chinese Academy of Sci. (China)

P-8-5

Epitaxial graphene produced by thermal decomposition of TiC

W. Norimatsu^{1,2}, K. Kimura¹ and M. Kusunoki^{1,2}, ¹Nagoya Univ. and ²JFCC (Japan)

P-8-6

Forms of CVD-grown graphene layers on polycrystalline nickel

K. Kanazaki, H. Hibino and T. Makimoto, NTT Basic Res. Labs. (Japan)

P-8-7

Influence of Annealing Atmosphere on the Epitaxial Graphene Growth on 3C-SiC (111)/Si (111)
H. R. Aryal, K. Fujita and T. Egawa, Nagoya Inst. of Tech. (Japan)

P-8-8

Graphene Synthesis on Cu-Ni alloy by Chemical Vapor Deposition

E. Kim¹, Y. S. Kim¹, S. H. Chun¹, W. G. Lee² and J. Jung¹, ¹Sejong Univ. and ²National Nano Fab Center (Korea)

P-8-9

Quantum Chemical Molecular Dynamics Simulation on Si Thin-film Crystal Growth for Solar Cells

T. Kuvahara, Y. Higuchi, N. Ozawa, T. Shimazaki and M. Kubo, Tohoku Univ. (Japan)

P-8-10

Growing high crystallinity Ge NCs on patterned Si substrate by post thermal annealing

C. W. Chiu, T. W. Liao and C. H. Kuan, National Taiwan Univ. (Taiwan)

P-8-11

Polytype transformation path on 4H-SiC during top-seeded solution growth

S. Harada, Alexander, K. Seki, Y. Yamamoto and T. Ujihara, Nagoya Univ. (Japan)

P-8-12

Alignment of In-plane Crystallographic Grain Orientations in Polycrystalline Si Films by Normal and Oblique-Angle Ion-Implantations

A. Nakajima¹, S. Kuroki², S. Fujii² and T. Ito¹, ¹Hiroshima Univ. and ²Tohoku Univ. (Japan)

P-8-13

Novel Direct Patterning Technique of Vapor-Deposited Si Thin Films by Laser-Induced Si/Ag Layer Exchange

M. Kiyooka and H. Ikenoue, Kochi National College of Tech. (Japan)

P-8-14

Excimer laser crystallization of a-Ge nanowires on Si substrate

T. W. Liao, Y. K. Wu, C. W. Chiu, H. M. Chen and C. H. Kuan, National Taiwan Univ. (Taiwan)

P-8-15

Characterization of GaGdN/AlGaN/GaGdN Triple-layer Structures with High Gd Concentration for Tunneling Magnetoresistance Devices

K. Higashi, D. Abe, Y. Mitsuno, S. Komori, S. Sano, S. Hasegawa and H. Asahi, Osaka Univ. (Japan)

P-8-16

Molecular Beam Epitaxy of AlGaPN alloys for Optical Confinement structure of Monolithic Optoelectronic Integrated Circuits on Si Substrate.

K. Kumagai, T. Kawai, K. Yamane, H. Sekiguchi, H. Okada and A. Wakahara, Toyohashi Univ. of Tech. (Japan)

P-8-17

Improving Si Doping Efficiency in GaAsN Epilayers by Using (211)B and (311)B GaAs Substrates

X. Han, M. Inagaki, N. Kojima, Y. Ohshita and M. Yamaguchi, Toyota Technological Inst. (Japan)

P-8-18

Quality improvement of GaN grown on Si (111) using metal-organic vapor-phase epitaxy

C. W. Hsu, J. H. Lin, Y. F. Chen and Y. K. Su, National Cheng Kung Univ. (Taiwan)

P-8-19

Controlling the Immobilized process of Au NPs onto TiO₂(110) through Electrostatic Interaction of Ionic Liquids

S. Suzuki¹, Y. Ohta¹, T. Kurimoto¹, S. Kuvabata^{2,3} and T. Torimoto^{1,3}, ¹Nagoya Univ., ²Osaka Univ. and ³CREST-JST (Japan)

P-8-22

The bias-crystallization mechanism on structural characteristics and electrical properties of Zn-In-Sn-O film

K. J. Chen, F. Y. Hung, S. J. Chang, T. S. Lui, S. P. Chang, Z. S. Hu, T. P. Chen and T. Y. Liao, National Cheng Kung Univ. (Taiwan)

P-8-23

Growth of ZnMgTe/ZnTe Waveguide Structures and Analysis of the Light Polarization with the Electric Field

Y. Kumagai and M. Kobayashi, Waseda Univ. (Japan)

P-8-24

Optical Properties of Ordered arrays of Silica-Metal Core-Shell Nanoparticles

K. Sugawa¹, T. Sakai¹, D. Tanaka¹, J. Otsuki¹ and T. Akiyama², ¹Nihon Univ. and ²Univ. of Shiga Prefecture (Japan)

P-8-25

Photoluminescence and conduction type of Mg,Zn_{1-x}O:(N,Cu) films

S. K. Mohanta, A. Nakamura and J. Temmyo, Shizuoka Univ. (Japan)

Area 9: Physics and Application of Novel Functional Devices and Materials

(19 Papers)

P-9-1

Photo-rechargeable Battery Based on Photo-induced Copper Intercalation into Quasi-One-Dimensional Compound KFeS₂

S. Takenoshita, R. Yatabe, M. Kozaki, H. Kuriyaki and K. Toko, Kyushu Univ. (Japan)

P-9-2

Gap Plasmon Enhancement on a Silver Nanowire with AFM Metal Tip

Y. C. Wang^{1,2}, C. T. Yuan¹, M. Y. Kuo¹, M. C. Wu², J. Tang¹ and M. H. Shih¹, ¹National Tsing Hua Univ. and ²Academia Sinica (Taiwan)

P-9-3

Observation of cavity polaritons in one-dimensional photonic crystal with organic dye J-aggregates

K. Ishii, M. Yamashima, Y. Kondo, S. Nakanishi and N. Tsurumachi, Kagawa Univ. (Japan)

P-9-4

Phonon-Assisted Band-to-Band Luminescence and Carrier Recombination Processes in SrTiO₃
Y. Yamada and Y. Kanemitsu, Kyoto Univ. (Japan)

P-9-5

Effects of Interface Grading on Electronic States in Columnar Type-II Quantum Dots

T. Kawazu, NIMS (Japan)

P-9-6

Dynamic Nuclear Polarization Induced by Breakdown of Even-integer Quantum Hall Effect

S. Umezawa¹, R. Moriya¹, T. Yamashita¹, M. Kawamura^{2,3}, S. Masubuchi^{1,3}, Y. Hashimoto¹, S. Katsumoto⁴ and T. Machida¹, ¹Univ. of Tokyo, ²RIKEN and ³PRESTO-JST (Japan)

P-9-7

A Multi-purpose Electrostatically Defined Silicon Quantum Dot Structure

M. A. Sulthoni, T. Kodera, Y. Kawano and S. Oda, Tokyo Tech (Japan)

P-9-8

Time-resolved observation of carrier and coherent phonon in 4H-SiC under off-resonant excitation

K. Kato, K. Oguri, A. Ishizawa, H. Nakano and T. Sogawa, NTT Basic Res. Labs. (Japan)

P-9-9

First-Principles Study of Electronic Structures of AlN/GaN Superlattices

K. Kamiya¹, M. Kasu¹ and K. Shiraishi¹, ¹Univ. of Tsukuba and ²NTT Basic Res. Labs. (Japan)

P-9-11

Effect of Capping Layer Growth on Bound Exciton Luminescence in Nitrogen δ -Doped GaAs

Y. Harada, T. Kubo, T. Inoue, O. Kojima and T. Kita, Kobe Univ. (Japan)

P-9-12

Electron emission properties of GaAsN/GaAs quantum well containing N-related localized states: the influence of illumination

M. C. Hsieh, J. F. Wang, K. H. Tseng, C. H. Chao, Y. C. Chi, R. C. C. Chen, C. H. Yang, Y. S. Wang, C. H. Chiang and J. F. Chen, National Chiao Tung Univ. (Taiwan)

P-9-13

Electrical Characteristics and TDDB Reliability of ZrO₂/Al₂O₃/ZrO₂ Stack High- κ Gate Dielectric

C. L. Lin¹, S. C. Wu¹, C. C. Tang¹ and M. Y. Li², ¹Feng Chia Univ. and ²ProMOS Tech. Inc. (Taiwan)

P-9-14

Retention characteristics of resistance switching memory using Si/CaF₂/CdF₂ quantum-well structures

M. Watanabe and K. Uryu, Tokyo Tech (Japan)

P-9-15

Two Terminal Switching Device for Spin Transfer Torque (STT) MRAM

G. H. Kil, H. J. Yang, S. H. Lee and Y. H. Song, Hanyang Univ. (Korea)

P-9-16

P-type Tunneling Transistors with Poly-Si by Sequential Lateral Solidification (SLS) Growth Technique

M. H. Lee, T. H. Wu and S. C. Weng, National Taiwan Normal Univ. (Taiwan)

P-9-17

In-situ TEM Observation for Formation of Au Nanowires and Nanogaps caused by Electromigration

Y. Murakami, M. Arita, K. Hamada and Y. Takahashi, Hokkaido Univ. (Japan)

P-9-18

Optical selection rules for graphene nanoribbons

K. Sasaki, K. Kato, Y. Tokura and T. Sogawa, NTT Basic Res. Labs. (Japan)

P-9-19

Tunnel Spin Injection into Graphene Using Al₂O₃/PTCA Barrier Grown by Atomic Layer Deposition

T. Yamaguchi¹, S. Masubuchi¹, K. Iguchi¹, R. Moriya¹ and T. Machida^{1,2}, ¹Univ. of Tokyo and ²PRESTO-JST (Japan)

P-9-20 (Late News)

Si-Nanowire-Based Memristors Constructed Using Top-Down Methods for Flexible Electronic Systems

T. Moon¹, J. Kang¹, Y. Han¹, C. Kim², Y. Jeon¹, H. Kim¹ and S. Kim¹, ¹Korea Univ. and ²Lawrence Berkeley National Laboratory (Korea)

Thursday, September 29

Area 10: Organic Materials Science, Device Physics, and Applications (20 Papers)

P-10-1

Formation of Organic Nanodots Using Diamine Derivative and Self-Assembled Monolayer
T. Morimoto¹, S. G. Park¹, T. Inden¹, T. Nishikawa¹ and T. Mori¹, ¹Nagoya Univ. and ²Iwate Univ. (Japan)

P-10-2

Thermal Annealing Effects on Aligned π -Conjugated Polymer Films Fabricated by Capillary Action
T. Higashi, N. Yamasaki, H. Utsumi, H. Yoshida, A. Fujii and M. Ozaki, Osaka Univ. (Japan)

P-10-3

Fabrication and Characterization of Uniaxially Oriented Vinylidene Fluoride Oligomer Thin Films
Y. Kuroda, Y. Koshiba, M. Misaki, S. Horie, K. Ishida and Y. Ueda, Kobe Univ. (Japan)

P-10-4

Enhancing the performance of pentacene-based organic thin film transistors by inserting alternately stacked NPB and Alq₃ buffer layers
C. M. Wu, S. H. Su, W. C. Weng, H. L. Tsai and M. Yokoyama, I-Shou Univ. (Taiwan)

P-10-5

Charge transport through film surface and substrate interface in solution-processed polymer field-effect transistors
K. Takagi¹, T. Nagase^{1,2}, T. Kobayashi^{1,2}, T. Kushida³ and H. Naito^{1,2}, ¹Osaka Prefecture Univ. and ²Teijin Ltd. (Japan)

P-10-6

Light-Emitting Field-Effect Transistors Having Metal Electrodes Modified with an Organic Thin Film
A. Okada, Y. Fukaya, S. Hotta and T. Yamao, Kyoto Inst. of Tech. (Japan)

P-10-7

High Transparent Conductive Film by Self-Assembled Silver Nanoparticles Network Electrode with Anti-Reflective Coating
K. Fujimoto¹, S. Shiratori¹, K. Yamane², K. Nakata² and K. Tamari², ¹Keio Univ. and ²Toda Kogyo Corp. (Japan)

P-10-8

Crystalline quality variations in epitaxial-grown C₆₀ thin films by magnesium atoms doping.
C. Morales, N. Kojima, S. Nishi, N. Ogata and M. Yamaguchi, Toyota Technological Inst. (Japan)

P-10-9

Metal patterning for organic electronics based on metal undeposition effect on soft polymer surfaces
K. Tsuchi and T. Tsuchioka, Osaka Kyoiku Univ. (Japan)

P-10-10

Change in Capacitance of Organic Light-Emitting Diodes
T. Inden¹, T. Sato², S. G. Park¹, T. Morimoto¹, T. Nishikawa¹ and T. Mori¹, ¹Nagoya Univ., ²Toyota Central Research & Development Labs. and ³Iwate Univ. (Japan)

P-10-11

Dependence of additive-solvent on bulk-heterojunction organic photovoltaic cell fabricated by electrospray deposition method
K. Takagi^{1,2}, T. Asano^{1,2}, T. Fukuda¹, Z. Honda¹, N. Kamata¹, H. Shirai¹, J. Ju¹, Y. Yamagata² and Y. Tajima², ¹Saitama Univ and ²RIKEN (Japan)

P-10-12

Fabrication of the inverted bulk heterojunction organic solar cell on titanium oxide nanosheet
Y. Maruyama and E. Itoh, Shinshu Univ. (Japan)

P-10-13

Relationship between the work function of the hole collection electrode and the temperature dependence of open-circuit voltage in multi layered organic solar cells
T. Shiratori and E. Itoh, Shinshu Univ. (Japan)

P-10-14

Improvement of hole injection characteristics in multilayered organic photovoltaic devices by the insertion of organic interfacial layer
S. Nakagoshi and E. Itoh, Shinshu Univ. (Japan)

P-10-15

Doping Effects of Liquid Crystalline Phthalocyanine in Bulk Heterojunction Polymer Solar Cells
T. Masuda¹, T. Hori¹, N. Fukuoka¹, Y. Miyake^{1,2}, D. Q. Duy¹, T. Hayashi¹, T. Kamikado¹, H. Yoshida¹, A. Fujii¹, Y. Shimizu¹ and M. Ozaki¹, ¹Osaka Univ. and ²AIST (Japan)

P-10-16

Fundamental Study on Organic Solar Cells based on Soluble ZnPc
I. Yamada^{1,2}, M. Umeda¹, Y. Hayashi¹, T. Soga¹ and N. Shibata¹, ¹Nagoya Inst. of Tech. and ²Suzuka National College of Tech. (Japan)

P-10-17

The examination of the most appropriate size of ZnO nanorods in organic-inorganic hybrid solar cells
T. Ichikawa and S. Shiratori, Keio Univ. (Japan)

P-10-18

Fabrication and Evaluation of Organic Photoelectric Conversion Devices using Electrodeposited Polyaniline Films as a Hole Transporting Layer
K. Inoue, A. Suzuki, T. Oku and T. Akiyama, Univ. of Shiga Prefecture (Japan)

P-10-19 (Late News)

Fullerene Memory Transistors with a Chargeable Polymer
D. T. Toan, H. Sakai, T. Matsushima and H. Murata, JAIST (Japan)

P-10-20 (Late News)

Printed OTFT-backplane for Electrophoretic Display Characterized by High Uniformity of Performance over a Large Area
J. W. Hwang, G. S. Ryu, J. S. Kim and C. K. Song, Dong-A Univ. (Korea)

Area 11: Micro/Nano Electromechanical Systems and Bio/Medical Analyses

(14 Papers)

P-11-1

Quantitative characterization of guided motion of dynein-microtubule system
N. Ashikari^{1,2}, Y. Shitaka², H. Sakaue¹, T. Takahagi¹, H. Kojima², K. Oiwa² and H. Suzuki¹, ¹Hiroshima Univ. and ²NICT (Japan)

P-11-2

Label-free detection of creatinine using a disposable poly-N-isopropylacrylamide as an encapsulating enzyme material based on high- κ Eu,Ti,O₂ EIS devices
T. M. Pan¹, P. Y. Liao¹, K. Y. Chang¹, C. W. Lin¹ and L. Chi², ¹Chang Gung University and ²Westfälische Wilhelms-Universität Münster (Taiwan)

P-11-3

Development of Implantable Si Neural Probe with Stimulus and Recording Electrodes for Deep Brain Stimulation
Y. Yukita, S. Lee, S. Kanno, K. Lee, T. Fukushima, M. Koyanagi, N. Katayama, H. Mushiaki and T. Tanaka, Tohoku Univ. (Japan)

P-11-4

Band-to-Band Tunneling Transistor for Application to Bio Sensor
T. Tabei, K. Shibahara and S. Yokoyama, Hiroshima Univ. (Japan)

P-11-5

Scaling of the Pull-In Voltage in a Novel CMOS-compatible NEMS Switch
D. J. Baek, S. J. Choi, D. I. Moon and Y. K. Choi, KAIST (Korea)

P-11-6

Photoresist Spray Coating Using Aperture toward Trench-type 3D Microdevices
N. Fukuda, S. Kumagai and M. Sasaki, Toyota Technological Inst. (Japan)

P-11-7

Analysis of Sharp Dip Structures on THz Transmission Spectra of Metallic Meshes
T. Hasebe and H. Tabata, Univ. of Tokyo (Japan)

P-11-8

Realization of ion-sensitive field-effect transistor on SOI substrate with engineered sensing membrane for high stability
H. J. Jang and W. J. Cho, Kwangwoon Univ. (Korea)

P-11-9

Acceleration Sensor Based on CMOS Inverter Having Force Balanced Movable Gate Electrode
M. Suzuki¹, J. Kogure¹, K. Kitamura¹, T. Takahashi¹, S. Yokoyama², H. Tokunaga³ and S. Aoyagi¹, ¹Kansai Univ., ²Hiroshima Univ. and ³M. T. C. Corp. (Japan)

P-11-10

Carbon Nanotube Network Conjugated by Nanoparticles with Defined Nanometer-Scaled Gaps
M. Kobayashi^{1,2,3}, S. Kumagai^{3,4}, K. Shiba^{1,3}, Y. Uraoka^{2,3} and I. Yamashita^{2,3}, ¹Japanese Foundation for Cancer Res., ²NAIST, ³CREST-JST and ⁴Toyota Technological Inst. (Japan)

P-11-11

Plasma Induced Damage Affecting Mechanical Properties of Silicon Microcantilevers and Effects of Thermal Annealing on Their Recovery
A. Wada¹, Y. Yanagisawa¹, M. Tomura¹, C.-H. Huang¹, S. Yamasaki², T. Ono¹ and S. Samukawa¹, ¹Tohoku Univ. and ²AIST (Japan)

P-11-12

Engineering Biocompatibility and Assembly in Carbon Nanotube Electrodes Using the Physicochemical Properties of Chitosan
L. Bugnicourt, S. Trigueros and S. A. Contera, Univ. of Oxford and Ecole Central de Lyon (UK)

P-11-13

Nanoparticle-Induced Crystallization of Amorphous Ge Film Using Ferritin
M. Uenuma^{1,2}, B. Zheng^{1,2}, T. Imazawa^{1,2}, N. Okamoto¹, M. Horita^{1,2}, T. Nishida^{1,2}, Y. Ishikawa^{1,2}, H. Watanabe^{2,3}, I. Yamashita^{1,2} and Y. Uraoka^{1,2}, ¹NAIST, ²CREST-JST and ³Osaka Univ. (Japan)

P-11-14

Extending Rotation Range of Spatial Light Modulator by Metal-Induced Lateral Crystallization of Amorphous Si Using Ni Ferritin Molecules
S. Kumagai^{1,3}, S. Miyachi¹, H. Murase¹, I. Yamashita^{2,3}, Y. Uraoka^{2,3} and M. Sasaki^{1,3}, ¹Toyota Technological Institute, ²NAIST and ³CREST-JST (Japan)

Area 12: Spintronics Materials and Devices

(16 Papers)

P-12-1

Investigation of Regular Arrangements of Ferromagnetic MnAs Nanoclusters for New Planar Magneto-electronic Devices
M. T. Elm¹, M. Fischer³, P. J. Klar³ and S. Hara^{1,2}, ¹Hokkaido Univ., ²PRESTO-JST and ³Justus-Liebig Univ. (Japan)

P-12-2

Structure and Magnetic Properties of Diluted Magnetic Semiconductor Superlattice GaGdAs/GaAs Grown by MBE
Y. Uda, H. Miyagawa, S. Koshiba, N. Tsurumachi, S. Nakanishi, Y. Tanaka, H. Itoh and N. Takahashi, Kagawa Univ. (Japan)

P-12-3

Magnetic behaviors of (Ga,Mn)As/Co₂FeAl Bilayers grown by molecular-beam epitaxy
S. H. Nie^{1,2}, L. Chen¹, K. K. Meng¹, X. Z. Yu¹, L. J. Zhu¹, W. S. Yan¹, Y. G. Zhao² and J. H. Zhao¹, ¹Chinese Academy of Sci., ²Tsinghua Univ and ³Univ. of Sci. & Tech. of China (China)

P-12-4

Magnetoresistance effects in La_xSr_{1-x}MnO₃/Nb-SrTiO₃/Co junctions
K. Tozawa, K. Kobayashi, T. Miyawaki, K. Ueda and H. Asano, Nagoya Univ. (Japan)

P-12-5

Anisotropic magnetoresistance in half-metallic Co₂MnSi epitaxial films
F. J. Yang, Y. Sakuraba and K. Takanashi, Tohoku Univ. (Japan)

P-12-6

Fabrication of MgAl₂O₄ thin films on ferromagnetic Heusler alloy Fe₂CrSi by reactive magnetron sputtering
N. Fukatani, K. Inagaki, K. Mari, H. Fujita, T. Miyawaki, K. Ueda and H. Asano, Nagoya Univ. (Japan)

P-12-7

Spectroscopic Detection of Double Exchange Magnetism Signatures in Mn L_{2,3} and O-vacancy Spectra in La_{1-x}Sr_xMnO₃ Alloys with x = 0.2
G. Lucovsky¹, C. Adamo² and D. G. Schlom², ¹North Carolina State Univ. and ²Cornell Univ. (USA)

Thursday, September 29

P-12-8

Formation of Nitrogen Vacancy Adjoining to Gd Ion Doped in GaN

D. Abe, K. Higashi, S. Emura, Y. K. Zhou, S. Hasegawa and H. Asahi, Osaka Univ. (Japan)

P-12-9

Effect of GaAs Surface Structure on Tunneling Anisotropic Magnetoresistance in Epitaxial Co_{0.9}Fe_{0.1}/n-GaAs Junctions

T. Uemura, T. Akiho, M. Harada, K. Matsuda and M. Yamamoto, Hokkaido Univ. (Japan)

P-12-10

Different magnetic properties of L1₀-FePt grown on sputtered and EB deposited MgO / GaAs structures

R. Ohsugi¹, M. Kohda^{1,2}, T. Seki³, M. Mizuguchi³, K. Takanashi³ and J. Nitta¹, ¹Tohoku Univ. and ²PRESTO-JST (Japan)

P-12-11

Tight-binding calculation of conductance and magnetoresistance in disordered FM/graphene/FM junctions

S. Honda¹, R. Sato², A. Yamamura², T. Hiraïwa², H. Itoh¹ and J. Inoue², ¹Kansai Univ. and ²Nagoya Univ. (Japan)

P-12-12

High-Speed-Search Nonvolatile TCAM Using MTJ Devices

S. Matsunaga, A. Katsumata, M. Natsui, T. Endoh, H. Ohno and T. Hanyu, Tohoku Univ. (Japan)

P-12-13

Fast Switching in Magnetic Tunnel Junctions with Double Barrier Layer

A. Makarov, V. Sverdlov, D. Osintsev and S. Selberherr, TU Wien (Austria)

P-12-14

Stochastic State Transition of a Spin Torque Nano Oscillator

K. Nakada¹, S. Yakata^{1,2} and T. Kimura^{1,2}, ¹Kyushu Univ. and ²CREST-JST (Japan)

P-12-15

Spin-Photon Memory and Spin Transistor with Floating Gate

V. Zayets, H. Saito, S. Yuasa and K. Ando, AIST (Japan)

P-12-16 (Late News)

Temperature Dependence of Spin Relaxation Time in InAs Columnar Quantum Dots at 10 to 50 K

S. Nakanishi¹, K. Sasayama¹, Y. Oyanagi¹, R. Yamaguchi¹, S. Lu², L. H. Li³, A. Fiore⁴ and A. Tackeuchi¹, ¹Waseda Univ., ²Chinese Academy of Sci., ³Ecole Polytechnique Federale de Lausanne and ⁴Eindhoven Univ. of Tech. (Japan)

Area 13: Application of Nanotubes, Nanowires, and Graphene

(28 Papers)

P-13-1

Fabrication and Characterization of InP Nanowire Light Emitting Diodes

S. Maeda¹, K. Tomioka^{1,2}, S. Hara¹ and J. Motohisa¹, ¹Hokkaido Univ. and ²PRESTO-JST (Japan)

P-13-2

Analysis of Bottom Channel Effect in Silicon Nanowire FET based on Bulk-Silicon: Reduction of Parasitic Capacitance caused by SiGe layer

M. D. Ko¹, S. H. Lee¹, R. H. Baek¹, C. H. Park¹, C. W. Sohn¹, C. K. Baek^{1,2}, J. S. Lee¹ and Y. H. Jeong¹, ¹POSTECH and ²NCNT (Korea)

P-13-3

A Multi Switching Current Study of Single-Electron Transistors Using Side Gate Bias Effect

J. E. Lee¹, J. W. Kim¹, J. H. Lee¹, K. C. Kang¹, J. H. Lee¹, H. C. Shin¹, K. J. Yoh² and B. G. Park¹, ¹Seoul National Univ. and ²Hokkaido Univ. (Korea)

P-13-4

Growth of GaAs Nanowires on Poly-Si by Selective-Area MOVPE

K. Ikejiri¹, K. Tomioka¹, S. Imai² and T. Fukui¹, ¹Hokkaido Univ. and ²Sharp Corp. (Japan)

P-13-5

Formation of ohmic contact of InP nanowires without annealing processes

G. Zhang, S. Saito, K. Tateno, H. Gotoh and T. Sogawa, NTT Basic Res. Labs. (Japan)

P-13-6

Suppression of surface nanocrystal nucleation in growth of GaAs nanowire on Si(111) by molecular beam epitaxy

J. K. Kwoen, N. Kumagai, K. Watanabe, S. Ohkouchi, S. Iwamoto and Y. Arakawa, Univ. of Tokyo (Japan)

P-13-7

Thermoelectric power of catalyst-free GaAs nanowires grown by MBE-VLS method

J. H. Paek, M. Yamaguchi and H. Amano, Nagoya Univ. (Japan)

P-13-8

Effect of the Drain Configuration on the Current-Voltage Characteristics of Vertical Nanowire Field Effect Transistors

S. Karmalkar, V. K. Gurugubelli and K. R. K. Maheswaran, Indian Inst. of Tech. (India)

P-13-9

Graphene Gated SiO₂ Core-shell Silicon Nanowire Transistors

J. E. Jin¹, J. H. Lee^{1,2}, D. H. Hwang¹, D. W. Kim¹, M. J. Kim^{1,2}, K. S. Son^{1,2}, D. Whang^{1,2} and S. W. Hwang¹, ¹Korea Univ. and ²Sungkyunkwan Univ. (Korea)

P-13-10

Tunable Magnetic Properties of Rhombohedral Graphite Thin Films

N. T. Cuong^{1,3}, M. Otani^{1,3} and S. Okada^{2,3}, ¹AIST, ²Univ. of Tsukuba and ³CREST-JST (Japan)

P-13-11

Precise control of layer number in graphene grown on Ni(111)

S. Entani, Y. Matsumoto, M. Ohtomo, P.V. Avramov, H. Naramoto and S. Sakai, JAEA (Japan)

P-13-12

Selective-area-grown graphene transistors by thermal chemical vapor deposition method

M. Oka¹, K. Tokumoto², T. Kyotani², M. Tokuda³, K. Tsutsui³ and Y. Wada³, ¹Hitachi Ltd., ²Tohoku Univ. and ³Toyo Univ. (Japan)

P-13-13

Electronic Structure and Energetics of Corrugated Graphene Sheet

S. Okada^{1,2} and T. Kawai^{1,2}, ¹Univ. of Tsukuba and ²NEC Corp. (Japan)

P-13-14

Ultrafast Synthesis of Nanographene Employing an Ultrahigh-density In-liquid Al-cohol Plasma

T. Hagino, H. Kondo, H. Kano, K. Ishikawa, M. Sekine and M. Hori, Nagoya Univ. (Japan)

P-13-15

RF Transmission Line Characteristics of Graphenes

H. J. Lee, E. Kim and J. Jung, Sejong Univ. (Korea)

P-13-16

Ballistic Current Model for Graphene Nanoribbon Field-Effect Transistors

Y. Li, Y. Zhang, F. Liu, Y. Yang, Y. Wang and X. Liu, Peking Univ. (China)

P-13-17

Formation of quantum dots in monolayer graphene with an energy gap

G. Giavaras¹ and F. Nori^{1,2}, ¹RIKEN and ²Univ. of Michigan (Japan)

P-13-18

Optical and electrical properties of graphene layers directly-grown by Alcohol-CVD

A. Nakamura and J. Temmyo, Shizuoka Univ. (Japan)

P-13-19

Crystallographic and Electrical Properties of Semiconducting Graphene Nanoribbon Grown Employing CH₄/H₂ plasma

H. J. Cho, K. Takeda, H. Kondo, K. Ishikawa, M. Sekine and M. Hori, Nagoya Univ. (Japan)

P-13-20

Effect of Plasma Treatment on CVD-grown Graphene/Metal Contact

T. Kwon, H. An and J. Jung, Sejong. Univ. (Korea)

P-13-21

Development of Two-Dimensional Strain-Distribution Sensor Using Carbon Nanotube-Dispersed Resin

K. Suzuki, Y. Suzuki, Y. Ohashi, M. Ohnishi and H. Miura, Tohoku Univ. (Japan)

P-13-22

Improvement of transfer characteristics for PZT-CNT-FET by ionic liquid

S. Kataoka¹, T. Arie^{1,2} and S. Akita^{1,2}, ¹Osaka Prefecture Univ. and ²CREST-JST (Japan)

P-13-23

Strain Dependence of the Electronic Conductivity of Carbon Nanotubes and Graphene Sheets

M. Ohnishi, K. Suzuki and H. Miura, Tohoku Univ. (Japan)

P-13-24

Analysis of FET Operation Mechanism in SWNT Networks Using Scanning Gate Microscopy

X. Wei¹, K. Maeda¹, T. Yahagi¹, S. Shimozono¹, M. Matsunaga¹, N. Aoki¹, J. P. Bird² and Y. Ochiai¹, ¹Chiba Univ. and ²Univ. at Buffalo (Japan)

P-13-27

Interfaces of High-k Gate Insulator in Carbon Nanotube FETs

K. Suzuki, Y. Ohno, S. Kishimoto and T. Mizutani, Nagoya Univ. (Japan)

P-13-28

Observation of n-type conduction in CNTFETs with Au contacts in vacuum

H. Imaeda, S. Ishii, S. Kishimoto, Y. Ohno and T. Mizutani, Nagoya Univ. (Japan)

Area 14: Photovoltaics & Power Semiconductor Devices

(21 Papers)

P-14-1

Atomic Layer Deposited Aluminum Oxide Passivation Layers for Crystalline Silicon: Effects of Deposition Temperature on Film and Interface Structures

H. Lee^{1,5}, N. Sawamoto^{1,5}, T. Tachibana^{1,5}, N. Ikeno^{1,5}, K. Arafune^{2,5}, H. Yoshida^{2,5}, S. Sato^{1,2,5}, K. Matsumoto³, K. Takahashi³, T. Chikyo⁴ and A. Ogura^{1,5}, ¹Meiji Univ., ²Univ. of Hyogo, ³Tokyo Electron Ltd., ⁴NIMS and ⁵CREST-JST (Japan)

P-14-2

Surface Recombination of Crystalline Silicon Substrates Passivated by Atomic Layer Deposited AlO₂

K. Arafune^{1,5}, S. Miki^{1,5}, R. Matsutani^{1,5}, J. Hamano^{1,5}, H. Yoshida^{1,5}, T. Tachibana^{2,5}, A. Ogura^{2,5}, K. Matsumoto³, K. Takahashi³, Y. Ohshita^{4,5} and S. Sato^{1,5}, ¹Univ. of Hyogo, ²Meiji Univ., ³Tokyo Electron Ltd., ⁴Toyota Technological Inst. and ⁵CREST-JST (Japan)

P-14-3

Optimization of a-Si/c-Si heterojunction solar cells by BF₃ ion implantation

T. H. Tasi, Y. C. Wu and C. H. Chen, National Tsing Hua Univ. (Taiwan)

P-14-4

Amorphous Silicon Thin Film Solar Cell Utilizing ITO Patterned Electrode

H. W. Liu, T. G. Chen, C. H. Chang and P. Yu, National Chiao Tung Univ. (Taiwan)

P-14-5

Patterned Glass Substrates for Enhanced Solar Energy Harvesting in Thin Film Solar Cells

T. G. Chen, Y. L. Tsai, M. A. Tsai, P. Yu, J. M. Shieh and H. C. Kuo, National Chiao Tung Univ. (Taiwan)

P-14-6

Electrode-Contact Enhancement in Silicon Nanowire-Array-Textured Solar Cells

C. Chen¹, R. Jia¹, H. Li¹, Y. Meng¹, S. Kasai² and H. Tamotsu², ¹Chinese Academy of Sci. and ²Hokkaido Univ. (China)

P-14-7

Theoretical Study on the Effect of Size and Interface of Si Quantum Dots on Carrier Multiplication

S. Hirose, R. Nagumo, R. Miura, A. Suzuki, H. Tsuboi, N. Hatakeyama, H. Takaba and A. Miyamoto, Tohoku Univ. (Japan)

P-14-8

Enhanced Conversion Efficiency of a Crystalline Silicon Solar Cell with Frustum Nanorod Arrays

Y. L. Tsai, M. A. Tsai, P. C. Tseng, H. C. Chen, H. C. Kuo and P. C. Yu, National Chiao Tung Univ. (Taiwan)

P-14-9

Transfer of CuInS₂ Layer by Lift-Off Process and Its Superstrate-Type Solar Cell Applications

Y. Abe, S. Osada, S. Fukamizu, Y. Oda, T. Minemoto, K. Nakanishi, T. Ohta and H. Takakura, Ritsumeikan Univ. (Japan)

P-14-10

First principles study on Cd and Zn doping in CuInSe₂ and related compounds

T. Maeda and T. Wada, Ryukoku Univ. (Japan)

P-14-11

N-H structure in GaAsN and interaction between N-H local vibration mode and lower frequency phonon

K. Ikeda, M. Inagaki, S. Wada, N. Kojima, Y. Ohshita and M. Yamaguchi, Toyota Technological Inst. (Japan)

P-14-12

Thermally Activated Electron Transport in GaAsN

M. Inagaki, K. Ikeda, N. Kojima, Y. Ohshita and M. Yamaguchi, Toyota Technological Inst. (Japan)

P-14-13

Laser Annealing to Form High-Temperature Phase of FeS₂ (pyrite)

M. Umehara, Y. Takeda, H. Azuma and T. Motohiro, Toyota Central R&D Labs. Inc. (Japan)

P-14-14

Photoelectric Conversion Devices based on InP Porous Structures

R. Jinbo, T. Kudo and T. Sato, Hokkaido Univ. (Japan)

P-14-15

Hydrothermal Synthesis of TiO₂ Porous Hollow Nanospheres for Coating on the Photoelectrode of DSSCs

V. M. Mohan and K. Murakami, Shizuoka Univ. (Japan)

P-14-17

Investigation of Hot Carrier Degradation in STI-based High-Voltage LDMOSFETs by a Novel DCIV technique

Y. He and G. Zhang, Peking Univ. (China)

P-14-18

High accurate TCAD calibration methodology realizing smart-design of integrated power devices consisting of lateral-IGBT & Diode in SOI micro-inverters

H. Kato¹, S. Harada¹, C. S. Yun², V. Menailenko², Y. Ashida¹, S. Takahashi¹ and N. Tokura¹, ¹DENSO Corp. and ²Synopsys Inc. (Japan)

P-14-19

Current Transport Characteristics of Quasi-Al_{1-x}Ga_xN/SiC Heterojunction Bipolar Transistors with Various Band Discontinuities

T. Okuda, H. Miyake, T. Kimoto and J. Suda, Kyoto Univ. (Japan)

P-14-20

Estimation of the Surface Recombination Velocity from Thickness dependence of the carrier Lifetime in n-type 4H-SiC Epilayers

M. Kato, A. Yoshida and M. Ichimura, Nagoya Inst. of Tech. (Japan)

P-14-21 (Late News)

Semi-Quantitative Determination of Radiative Recombination Centers in Silicon Power Devices by Cross-Sectional Cathodoluminescence

R. Sugie, K. Inoue and M. Yoshikawa, Toray Research Center Inc. (Japan)

Thursday, September 29

Thursday, September 29

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>A-4: Novel III-V Devices and Applications (Area 6) (15:25-16:25) Chairs: S. Tanaka (Shibaura Inst. of Tech.) J. H. Lee (Kyungpook National Univ.)</p>	<p>KM-4: Nanowire Growth and Characterization (Area 8&13) (15:25-16:40) Chairs: T. Iwai (Fujitsu Labs. Ltd.) K. Tateno (NTT & Basic Res. Labs.)</p>	<p>B-4: Organic memory and photonic devices (I) (Area 10) (15:25-16:40) Chairs: K. Kato (Niigata Univ.) T. Shimada (Hokkaido Univ.)</p>	<p>C-4: Characterization (I) (Area 2) (15:25-16:35) Chairs: K. Ito (Kyoto Univ.) M. Kodera (Toshiba Corp.)</p>	<p>D-4: Tunnel-FET (Area 3) (15:25-16:45) Chairs: Y. Nishida (Renesas Electronics Corp.) F. L. Yang (National Nano Device Labs.)</p>	<p>E-4: Junction Technology and Physics (Area 1) (15:25-16:55) Chairs: S. Migita (AIST) T. Aoyama (Toshiba Corp.)</p>	<p>F-4: e-Flash (Area 4) (15:25-16:25) Chairs: T. Endoh (Tohoku Univ.) E. Yang (eMemory Technology Inc.)</p>
<p>15:25 A-4-1 GaAsSb/InGaAs Vertical Tunnel FET with a 25 nm-wide Channel Mesa Structure M. Fujimatsu, H. Saito and Y. Miyamoto, Tokyo Tech (Japan)</p>	<p>15:25 KM-4-1 (Invited) Analysis of Nanowire Dopant Incorporation and Distribution with Atom Probe Tomography and Nano Probe Scanning Auger Microscopy J. Connell¹, U. Givan^{1,2}, J. S. Hammond³, D. F. Paul³, Y. Rosenwaks² and L. J. Lauhon¹, ¹Northwestern Univ., ²Tel Aviv Univ. and ³Physical Electronics Inc. (USA)</p>	<p>15:25 B-4-1 (Invited) Organic resistive memory device composed of hyperbranched polystyrene and gold nanoparticles K. Fujita¹, K. Yasui², M. Ozawa², K. Odoi² and H. Ichikawa¹, ¹Kyushu Univ. and ²Nissan Chemical Industries, Ltd. (Japan)</p>	<p>15:25 C-4-1 (Invited) 1X nm Copper and Low-k reliability A. Tökei and K. Croes, IMEC (Belgium)</p>	<p>15:25 D-4-1 Device characteristics of planar-type In_{0.53}Ga_{0.47}As channel band-to-band tunneling MOSFETs R. Iida, S. H. Kim, M. Yokoyama, N. Taoka, S. H. Lee, M. Takenaka and S. Takagi, Univ. of Tokyo (Japan)</p>	<p>15:25 E-4-1 (Invited) Challenges to Strained Source/Drain and Advanced Silicide for High Performance Transistors T. Yamaguchi, Renesas Electronics Corp. (Japan)</p>	<p>15:25 F-4-1 A Zero Additional Process to Standard CMOS, 8F², Scalable Embedded Flash Memory with Drain-side Assisted Erase Scheme Y. Shinozuka, K. Miyaji and K. Takeuchi, Univ. of Tokyo (Japan)</p>
<p>15:40 A-4-2 Pnp AlGaIn/InGaIn Heterojunction Bipolar Light-Emitting Transistors with a Quantum Well in the Base K. Kumakura, T. Makimoto and H. Yamamoto, NTT Basic Res. Labs. (Japan)</p>	<p>15:55 KM-4-2 Heteroepitaxy of Vertical InAs Nanowires on Thin Graphitic Films Y. J. Hong and T. Fukui, Hokkaido Univ. (Japan)</p>	<p>15:55 B-4-2 Organic Ferroelectric FET Memory using Flat P(VDF-TeFE) thin film T. Kanashima, K. Yabe and M. Okuyama, Osaka Univ. (Japan)</p>	<p>15:55 C-4-2 Characterization of Patterned SiOC film by STEM-VEELS at Lower (80kV) Acceleration Energy Y. Otsuka¹, Y. Shimizu¹, T. Najjou¹ and S. Ogawa², ¹Toray Research Center Inc. and ²AIST (Japan)</p>	<p>15:45 D-4-2 Design of Thin-Body Double-Gated Vertical-Channel Tunneling Field-Effect Transistors for Ultra-Low Power Logic Circuits M. C. Sun^{1,2}, S. W. Kim¹, H. W. Kim¹, G. Kim¹, H. Kim¹, J. H. Lee¹, H. Shin¹ and B. G. Park¹, ¹Seoul National Univ. and ²Samsung Electronics Co., Ltd. (Korea)</p>	<p>15:55 E-4-2 Reduction of NiGe/nGe Schottky Barrier Height by S and P Co-introduction for Metal Source/Drain in Ge nMOSFETs M. Koike, Y. Kamimuta and T. Tezuka, MIRAI-Toshiba (Japan)</p>	<p>15:45 F-4-2 Practical Consideration of Endurance and Performance for sub-90 nm Embedded 2T-1F1N Flash Memory beyond Smart Card IC Y. K. Lee, B. Seo, J. Park, C. Jeon, Y. Jeong, S. B. Ryu, H. Yoo, Y. Kim, J. U. Han and E. Jung, Samsung Electronics Co. (Korea)</p>
<p>15:55 A-4-3 Fluidic Self-Assembly for Heterogeneous Integration of High Performance Resonant Tunneling Diodes Using Low-Melting Point Alloy Bumps J. Nakano, T. Shibata, T. Okatsu, M. Mori and K. Maezawa, Univ. of Toyama (Japan)</p>			<p>16:15 C-4-3 Nano-scale Boron Mapping in Silicon Devices Using C₁-corrected STEM-EELS N. Nakanishi, H. Arie, Y. Kunimune, T. Ide, Y. Hirose, N. Hattori and T. Koyama, Renesas Electronics Corp. (Japan)</p>	<p>16:05 D-4-3 Tunnel Field-Effect Transistor using InAs Nanowire/Si Heterojunction K. Tomioka^{1,2} and T. Fukui¹, ¹Hokkaido Univ. and ²PRESTO-JST (Japan)</p>	<p>16:15 E-4-3 Improvement of Phosphorus Activation in In-Situ Phosphorus Doped Silicon Epitaxial Film by Cryogenic Silicon Ion-Implantation and Recrystallization Annealing H. Itokawa¹, S. Teehan², J. Li², P. W. De-Haven², N. C. Berliner², J. J. Demarest², N. R. Klymko³, P. Ronsheim³ and V. Paruchuri², ¹Toshiba America Electronic Components, Inc., ²IBM Research at Albany Nanotech Center and ³IBM Semiconductor Research and Development Center (USA)</p>	<p>16:05 F-4-3 Direct Comparison of Electrical Characteristics for Double-Gate and Tri-Gate Flash Memories Y. X. Liu¹, T. Kamei², T. Matsukawa¹, K. Endo¹, S. Ouchi¹, J. Tsukada¹, H. Yamauchi¹, Y. Ishikawa¹, T. Hayashida², K. Sakamoto¹, A. Ogura² and M. Masahara^{1,2}, ¹AIST and ²Meiji Univ. (Japan)</p>
<p>16:10 A-4-4 Operating Principle and Integration of In-Plane Gate Logic Devices Y. Komatsuzaki¹, K. Saba¹, K. Onomitsu², H. Yamaguchi² and Y. Horikoshi¹, ¹Waseda Univ. and ²NTT Basic Res. Labs. (Japan)</p>	<p>16:25 KM-4-4 Low voltage operable field emission triodes with high transconductance based on laterally grown ZnO nanowires T. H. Lin, F. S. Tsai, Y. C. Tu, R. M. Ko and S. J. Wang, National Cheng Kung Univ. (Taiwan)</p>	<p>16:25 B-4-4 ADE-FDTD Analysis of Lasing Dynamics in Cholesteric Liquid Crystal as a Chiral Photonic Media T. Matsui and M. Kitaguchi, Mie Univ. (Japan)</p>		<p>16:25 D-4-4 Tunnel Field-Effect Transistor with L-shaped Germanium Source: Device Physics and Design K. L. Low¹, C. Zhan¹, G. Han¹, Y. Yang¹, K. H. Goh¹, P. Guo¹, E. H. Toh² and Y. C. Yeo¹, ¹National Univ. of Singapore and ²GLOBALFOUNDRIES Singapore Pte. Ltd. (Singapore)</p>	<p>16:35 E-4-4 A Study of Fermi-level Pinning in Ge Schottky and MIS Tunnel Junctions T. Nishimura^{1,2}, K. Nagashio^{1,2}, K. Kita^{1,2} and A. Toriumi^{1,2}, ¹Univ. of Tokyo and ²CREST-JST (Japan)</p>	

Coffee Break

Thursday, September 29

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>G-4: Circuits for 3D Structure (Area 5) (15:25-16:35) Chairs: H. C. Lin (National Chung Hsing Univ.) T. Koide (Hiroshima Univ.)</p>	<p>H-4: Neural Interface Technology (Area 11) (15:25-16:40) Chairs: T. Tanaka (Tohoku Univ.) Y. Taguchi (Keio Univ.)</p>	<p>I-4: Novel Optical Devices (Area 7) (15:25-16:25) Chairs: J. Fujikata (NEC Corp.) Y. Ishikawa (Univ. of Tokyo)</p>	<p>J-4: Advanced MOSFETs and Transport (Area 9) (15:25-16:40) Chairs: Y. Uraoka (NAIST) S. Kuroki (Tohoku Univ.)</p>				
<p>15:25 G-4-1 (Invited) Challenges and Trends of Resistive Memory (Memristor) Based Circuits for 3D-IC Applications <i>M. F. Chang^{1,2}, P. F. Chiu², C. H. Chuang¹, C. W. Wu¹, M. S. Ho³, P. C. Chen⁴, S. S. Sheu², M. J. Tsai² and T. K. Ku², ¹National Tsing Hua Univ., ²ITRI, ³National Chung Hsing Univ. and ⁴I-Shou Univ. (Taiwan)</i></p>	<p>15:25 H-4-1 (Invited) CMOS LSI for excitation and measurement of neural activity with microelectrode array <i>A. Shimada¹, T. Iwata², N. Nakano² and K. Torimitsu¹, ¹NTT Basic Res. Labs. and ²Keio Univ. (Japan)</i></p>	<p>15:25 I-4-1 Silicon Mach-Zehnder optical phase shifter <i>M. Saito, T. Kita and H. Yamada, Tohoku Univ. (Japan)</i></p>	<p>15:25 J-4-1 Multi Electron Wave Packet Dynamics in Applied Electric Fields <i>Y. Takada¹, Y. T. Yoon¹, T. Shiokawa¹, S. Konabe^{1,3}, M. Arikawa², M. Muraguchi^{2,3}, T. Endoh^{2,3}, Y. Hatsugai^{1,2,3} and K. Shiraishi^{1,3}, ¹Univ. of Tsukuba, ²Tohoku Univ. and ³CREST-JST (Japan)</i></p>				
<p>15:55 G-4-2 A Block-Parallel SAR ADC for CMOS Image Sensor with 3-D Stacked Structure <i>K. Kiyoyama^{1,2}, K. W. Lee², T. Fukushima², H. Naganuma², H. Kobayashi¹, T. Tanaka² and M. Koyanagi², ¹Nagasaki Institute of Applied Science, ²Tohoku Univ. and ³Association of Super-Advanced Electronics Technologies (Japan)</i></p>	<p>15:55 H-4-2 Development of Pillar-Shaped Stimulus Electrode Array for High Efficient Stimulation of Fully Implantable Retinal Prosthesis <i>Y. Watanabe, C. Kigure, K. Lee, T. Fukushima, M. Koyanagi and T. Tanaka, Tohoku Univ. (Japan)</i></p>	<p>15:40 I-4-2 Terahertz radiation from a (113)B GaAs/AlAs coupled multilayer cavity by ultrashort laser pulse excitation <i>S. Katoh¹, T. Takimoto¹, Y. Nakagawa^{1,2}, K. Morita¹, T. Kitada¹ and T. Isu¹, ¹Univ. of Tokushima and ²NICHIA Corp. (Japan)</i></p>					
<p>16:15 G-4-3 Adaptive Through-Silicon-Via Control with Clustering for 3D Solid-State-Drive Boost Converter System <i>K. Johguchi, T. Hatanaka and K. Takeuchi, Univ. of Tokyo (Japan)</i></p>	<p>16:10 H-4-3 CMOS image sensor for fluorescent beads counting <i>K. Sasagawa^{1,3}, K. Ando¹, T. Kobayashi^{1,3}, T. Noda^{1,3}, T. Tokuda^{1,3}, R. Iino^{2,3}, H. Noji^{2,3} and J. Ohta^{1,3}, ¹NAIST, ²Univ. of Tokyo and ³CREST-JST (Japan)</i></p>	<p>15:55 I-4-3 (Late News) A High-Sensitivity Gate/Body-Tied PMOSFET-Type Photodetector with an Overlapping Control Gate <i>J. Jung¹, S. H. Seo², S. H. Jo¹, M. Bae¹ and J. K. Shin¹, ¹Kyungpook National Univ. and ²Samsung Mobile Display (Korea)</i></p>	<p>15:55 J-4-3 Impact of Quantum Confinement on Backgate-Bias Modulated Threshold-Voltage Characteristics for Ultra-Thin-Body Germanium-On-Insulator MOSFETs <i>C. H. Yu, Y. S. Wu, V. P. H. Hu and P. Su, National Chiao Tung Univ. (Taiwan)</i></p>				
	<p>16:25 H-4-4 Brain interface device with permeable hydrogel membrane for <i>in vivo</i> analysis of neural cells <i>H. Takehara, A. Nagaoka, J. Noguchi, T. Akagi, H. Kasai and T. Ichiki, Univ. of Tokyo (Japan)</i></p>						
			<p>16:10 J-4-4 Fabrication of spin-MOSFETs using CoFe/Mg/AIO₂/Si Tunnel Junctions for the source and drain <i>T. Okishio, Y. Takamura and S. Sugahara, Tokyo Tech (Japan)</i></p>				
			<p>16:25 J-4-5 Strain Effects on Avalanche Multiplication in a Silicon Nanodot Array <i>N. Mori^{1,2}, H. Minari^{1,2}, S. Uno^{3,4}, H. Mizuta^{4,5} and N. Koshida⁶, ¹Osaka Univ., ²CREST-JST, ³Ritsumeikan Univ., ⁴Univ. of Southampton, ⁵JAIST and ⁶Tokyo Univ. of Agri. and Tech. (Japan)</i></p>				

Coffee Break

Thursday, September 29

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>A-5: Oxide Devices (Area 6) (17:05-18:20) Chairs: S. Sasa (Osaka Inst. of Tech.) T. Suzuki (JAIST)</p>	<p>KM-5: Nanowire and Quantum Structures (Area 8&13) (17:05-18:20) Chairs: T. Suemasu (Univ. of Tsukuba) L. Lauhon (Northwestern University)</p>	<p>B-5: Organic memory and photonic devices (2) (Area 10) (17:05-18:20) Chairs: T. Someya (Univ. of Tokyo) H. Usui (Tokyo Univ. of Agri. & Tech.)</p>	<p>C-5: 3D Interconnect (1) (Area 2) (17:05-18:25) Chairs: T. Fukushima (Tohoku Univ.) N. Nakano (Keio Univ.)</p>	<p>D-5: Noise and Fluctuation (Area 3) (17:05-18:25) Chairs: F. L. Yang (National Nano Device Labs.) F. Boeuf (STMicroelectronics)</p>	<p>E-5: Ge Metallization (Area 1) (17:20-18:20) Chairs: B. H. Lee (GIST) S. Migita (AIST)</p>	<p>F-5: CT-Flash (Area 4) (17:05-18:05) Chairs: S. Shuto (Toshiba Corp.) Y. Sasago (Hitachi, Ltd.)</p>
<p>17:05 A-5-1 Zinc Oxide Thin-Film Transistors on Flexible Plastic Substrates and Glass Substrates Fabricated at Room Temperature T. Higaki, Y. Kimura, T. Maemoto, S. Sasa and M. Inoue, Osaka Inst. of Tech. (Japan)</p>	<p>17:05 KM-5-1 (Invited) Epitaxial metal nanocrystal-semiconductor quantum dot plasmonic nanostructures A. Urbanczyk¹, F. W.M. van Otten¹ and R. Nötzel², ¹Eindhoven Univ. of Tech. and ²Technical Univ. of Madorid (Netherlands)</p>	<p>17:05 B-5-1 Evaluation of Polyvinylalcohol:Rhodamine Film Deposition Using Optical Waveguide and Surface Plasmon Resonance Spectroscopies S. Yokoyama, K. Shinbo, Y. Ohdaira, A. Baba, K. Kato and F. Kaneko, Niigata Univ. (Japan)</p>	<p>17:05 C-5-1 Through Silicon Via (TSV) Fabrication with Low-k Dielectric Liner and Its Implications on Parasitic Capacitance and Leakage Current L. Zhang^{1,2}, H. Y. Li¹, S. Gao¹ and C. S. Tan¹, ¹A*STAR and ²Nanyang Technological Univ. (Singapore)</p>	<p>17:05 D-5-1 Impact of Random Telegraph Noise Reduction with Buried Channel MOSFET H. Suzuki, R. Kuroda, A. Teramoto, A. Yonezawa, S. Sugawa and T. Ohmi, Tohoku Univ. (Japan)</p>	<p>17:20 E-5-1 Formation and Properties of Epitaxial NiGe/Ge(110) Contacts J. Yokoi, O. Nakatsuka and S. Zaima, Nagoya Univ. (Japan)</p>	<p>17:05 F-5-1 A Novel Operating Scheme for 2-bit/Cell Split Gate SONOS Flash Memory C. H. Chou¹, S. S. Chung¹, C. H. Lee², T. M. Hsieh², J. C. Liou², C. H. Chen², P. ZP. Chen³ and H. H. Chen¹, ¹National Chiao Tung Univ., ²Solid State System and ³UMC (Taiwan)</p>
<p>17:20 A-5-2 Low Temperature Processed Zinc Oxide Thin Film Transistors by Plasma Assisted Atomic Layer Deposition Y. Kawamura¹, M. Tani¹, N. Hattori², N. Miyatake², M. Horita¹, Y. Ishikawa¹ and Y. Uraoka^{1,3}, ¹NAIST, ²Mitsui Eng. and Shipbuilding Co., Ltd. and ³CREST-JST (Japan)</p>	<p>17:35 KM-5-2 Growth and Characterization of MnAs Nanoclusters Embedded in GaAs Nanowires by Metal-Organic Vapor Phase Epitaxy M. Yatago¹, S. Sakita¹ and S. Hara^{1,2}, ¹Hokkaido Univ. and ²PRESTO-JST (Japan)</p>	<p>17:20 B-5-2 Two-stage polarization reversal process in a pentacene/poly(vinylidene fluoride-trifluoroethylene) double-layer capacitor J. Li, D. Taguchi, T. Manaka and M. Iwamoto, Tokyo Tech (Japan)</p>	<p>17:25 C-5-2 Impacts of Microbump-Induced Local Bending Stress in 3D-LSI H. Kino¹, M. Murugesan¹, K. W. Lee¹, J. C. Bea¹, C. Miyazaki², H. Kobayashi¹, H. Shimamoto², T. Fukushima¹, T. Tanaka¹ and M. Koyanagi¹, ¹Tohoku Univ. and ²ASET (Japan)</p>	<p>17:25 D-5-2 Random Trap Fluctuation (RTF) Induced Vth Variability and the Impact on the Reliability of Strained-Silicon CMOS Devices E. R. Hsieh¹, C. Y. Cheng¹, S. S. Chung¹, C. H. Tsai², R. M. Huang², C. T. Tsa² and C. W. Liang², ¹National Chiao Tung Univ. and ²UMC (Taiwan)</p>	<p>17:40 E-5-2 Improvement of Thermal stability of Ni-Germanide with Ni/Co/Ni/TiN Structure for High Performance Ge MOSFETs H. S. Shin¹, S. K. Oh¹, M. H. Kang^{1,2}, H. M. Kwon¹, J. W. Oh¹, P. Majhi³, R. Jammy³, G. W. Lee¹ and H. D. Lee¹, ¹Chungnam National Univ., ²National NanoFab Center and ³SEMATECH (Korea)</p>	<p>17:25 F-5-2 Re-examination of Performance and Reliability Degradation in MONOS Memory with Ultra-thin (~ 2nm) SiN Charge Trap Layers H. Kusai, M. Morota, M. Oda, S. Fujii, K. Sakuma and M. Koyama, Toshiba Corp. (Japan)</p>
<p>17:35 A-5-3 Effects of Excimer Laser annealing of Oxide Semiconductor Films M. Fujii¹, R. Ishihara², T. Chen², J. der Cingel², M. R. T. Mofrad², M. Kasami³, K. Yano³, M. Horita^{1,4}, Y. Ishikawa^{1,4} and Y. Uraoka^{1,4}, ¹NAIST, ²Delft Univ. of Tech., ³Idemitsu Kosan Co., Ltd. and ⁴CREST-JST (Japan)</p>	<p>17:50 KM-5-3 Study of the Indium Content Distribution of Core-shell InGaN/GaN Multi-Quantum Wells (MQWs) on GaN Nanorods Y. J. Li, S. P. Chang, J. R. Chang, Y. C. Chen, K. P. Sou, Y. C. Hsu, H. C. Kuo and C. Y. Chang, National Chiao Tung Univ. (Taiwan)</p>	<p>17:35 B-5-3 In situ Electrochemical and Transmission Surface Plasmon Resonance for Studies of Electropolymerized Poly(3-Aminobenzoic acid) Thin Film S. Sriwichai¹, A. Baba², S. Phanichphant¹, K. Shinbo², K. Kato² and F. Kaneko², ¹Chiang Mai Univ. and ²Niigata Univ. (Thailand)</p>	<p>17:45 C-5-3 Room-Temperature Bonding of LSI Chips on PEN Film Using Mechanical Caulking of Au Cone Bump T. Shuto, N. Watanabe, A. Ikeda and T. Asano, Kyushu Univ. (Japan)</p>	<p>17:45 D-5-3 Uniaxial Strain Effect on Flicker Noise and Random Telegraph Noise of SiC Strained nMOSFETs in 40nm Technology K. L. Yeh, C. S. Chang and J. C. Guo, National Chiao Tung Univ. (Taiwan)</p>	<p>18:00 E-5-3 Marked Suppression of the Fermi-level Pinning at Atomically Matched Fe₃Si/p-Ge(111) Contacts K. Kasahara¹, S. Yamada¹, M. Miyao¹ and K. Hamaya^{1,2}, ¹Kyushu Univ. and ²PRESTO-JST (Japan)</p>	<p>17:45 F-5-3 Robust Data Retention and Superior Endurance SONOS Nonvolatile Memory with NH₃ Plasma Treated and Pd NCS Embedded Charge Storage Layer S. H. Liu¹, W. L. Yang¹, S. T. Chen¹, M. R. Ye¹ and T. S. Chao², ¹Feng Chia Univ. and ²National Chiao Tung Univ. (Taiwan)</p>
<p>17:50 A-5-4 High Mobility Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistor with a Strong Reduction Capping Layer H. W. Zan¹, C. C. Yeh¹, C. C. Tsa¹, H. F. Meng¹ and C. C. Yeh¹, ¹National Chiao Tung Univ. and ²E Ink Holdings Inc. (Taiwan)</p>	<p>18:05 KM-5-4 Study on the growth of In-rich InGaAs nanowires by selective-area metal-organic vapor phase epitaxy Y. Kohashi, S. Hara and J. Motohisa, Hokkaido Univ. (Japan)</p>	<p>17:50 B-5-4 Transient Absorption Decay and Photoconductive Characteristics of NPh₂-Silole Doped Fluorene Blend Film T. Fukuda¹, S. Kimura¹, Z. Honda¹, N. Kamata¹, K. Mori¹, K. Hatano¹ and A. Furube², ¹Saitama Univ. and ²AIST (Japan)</p>	<p>18:05 C-5-4 3D Chip Stacking of RF Devices with Cu TSV, Cu/Sn Bumps and Sealing Ring W. Zhang¹, B. Majeed¹, X. Sun¹, G. Posada¹, C. Diekmann², C. Eggs², E. Schmidhammer² and W. De Raedt¹, ¹IMEC and ²EPCOS AG (Belgium)</p>	<p>18:05 D-5-4 Characteristics of hot hole injection, trapping, and detrapping in gate oxide of poly-Si TFTs Y. Kamakura^{1,2}, T. Himukashi¹, H. Tsuji¹ and K. Taniguchi¹, ¹Osaka Univ. and ²CREST-JST (Japan)</p>		
<p>18:05 A-5-5 The Influence of a SnInGaZnO Electron Barrier Layer on the performance of Low-Driving Voltage InGaZnO Thin-Film Transistors H. Y. Huang¹, S. J. Wang¹, C. H. Wu², C. K. Chiang¹, Y. C. Huang¹ and J. Y. Su¹, ¹National Cheng Kung Univ. and ²Chung Hua Univ. (Taiwan)</p>		<p>18:05 B-5-5 (Late News) Antireflective Protective Coating by Ion-Assisted Vapor Deposition Polymerization of Fluoropolymer Thin Films K. Senda^{1,2}, T. Matsuda¹, K. Tanaka¹ and H. Usui², ¹Sumitomo Precision Products Co., Ltd. and ²Tokyo Univ. Agri. & Tech. (Japan)</p>				

Rump Sessions : 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”

Thursday, September 29

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>G-5: RF Circuits (1) (Area 5) (17:05-18:20) Chairs: M. Horiguchi (Renesas Electronics Corp.) H. Morimura (NTT Microsystem Integration Labs.)</p>		<p>I-5: Er-Doped Devices (Area 7) (17:05-18:05) Chairs: A. Wakahara (Toyohashi Univ. of Tech.) H. Isshiki (The Univ. of Electro-Communications)</p>	<p>J-5: MEMS & Thin-Film Devices (Area 9) (17:05-18:20) Chairs: Y. Uraoka (NAIST) H. Inokawa (Shizuoka Univ.)</p>				
<p>17:05 G-5-1 An Injection-Locked LC Frequency Divider to Achieve Wide Locking Range and Low Power Consumption <i>H. M. Hsu and G. L. Fu, National Chung Hsin Univ. (Taiwan)</i></p>		<p>17:05 I-5-1 A GaAs/AlAs multilayer cavity with Er-doped InAs quantum dots embedded in strain-relaxed InGaAs barriers for ultrafast all-optical switches <i>H. Ueyama¹, T. Takahashi¹, Y. Nakagawa^{1,2}, K. Morita¹, T. Kitada¹ and T. Isu¹, ¹Univ. of Tokushima and ²NICHLA Corp. (Japan)</i></p>	<p>17:05 J-5-1 Micromechanical Characterization of Optical Absorption in a GaAs/AlGaAs Heterostructure <i>T. Watanabe^{1,2}, H. Okamoto¹, K. Onomitsu¹, H. Gotoh¹, T. Sogawa¹ and H. Yamaguchi^{1,2}, ¹NTT Basic Res. Labs. and ²Tohoku Univ. (Japan)</i></p>				
<p>17:25 G-5-2 A 0.1-V 13-GHz Transformer-Based Quadrature VCO with a Capacitor Coupling Technique in 90nm CMOS <i>T. Kamimura, S. Lee, S. Tanoi, H. Ito, N. Ishihara and K. Masu, Tokyo Tech (Japan)</i></p>		<p>17:20 I-5-2 Strong suppression of scattering loss in Er_{0.4}Y_{1.6}SiO₅ crystalline waveguides <i>T. Nakajima¹, T. Shinagawa¹, T. Sugawara², Y. Jiang², T. Kimura¹ and H. Isshiki¹, ¹Univ. of Electro-Communications and ²Shincron Co., Ltd. (Japan)</i></p>	<p>17:20 J-5-2 Mechanical idler generation <i>I. Mahboob, Q. Wilmart, K. Nishiguchi, A. Fujiwara and H. Yamaguchi, NTT Basic Res. Labs. (Japan)</i></p>				
<p>17:45 G-5-3 1.2-17.6 GHz Ring-VCO-Based PLL with Injection Locking in 65 nm CMOS <i>S. Lee, H. Ito, S. Amakawa, S. Tanoi, N. Ishihara and K. Masu, Tokyo Tech (Japan)</i></p>		<p>17:35 I-5-3 Er₂Y_{2-x}SiO₅ compact waveguide slotted into Si photonic crystal <i>T. Sato, T. Nakajima, T. Kimura and H. Isshiki, Univ. of Electro-Communications (Japan)</i></p>	<p>17:35 J-5-3 Theory of Resonant Tunneling through a Donor State <i>N. Mori¹, A. Patané² and L. Eaves², ¹Osaka Univ. and ²Univ. of Nottingham (Japan)</i></p>				
<p>18:05 G-5-4 (Late News) A novel approach of Cap-sharing to reduce the big loop filter capacitance in semi-digital PLL <i>P. Sareen, M. Dietl and K. Dewan, Texas Instruments (Germany)</i></p>		<p>17:50 I-5-4 Energy levels and interaction between Er³⁺-ions located at the two crystallographic sites of Er₂O₃ grown on Si(111) <i>H. Omi and T. Tawara, NTT Basic Res. Labs. (Japan)</i></p>	<p>17:50 J-5-4 Tri-Gate Poly-Si TFTs Fabricated by CW Laser Lateral Crystallization for Improvement of Electron Transport Properties <i>S. Fujii, Y. Kawasaki, S. Kuroki and K. Kotani, Tohoku Univ. (Japan)</i></p>				
			<p>18:05 J-5-5 Bottom Electrode Modification of ZrO₂-Based RRAM Device with Au Nanodots <i>D. Y. Lee, I. C. Yao and T. Y. Tseng, National Chiao Tung Univ. (Taiwan)</i></p>				

Rump Sessions : 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”

Friday, September 30

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>AL-6: SiC&GaN Power Switching Devices (1) (Area 6&14) (9:00-10:45) Chairs: R. Hattori (Mitsubishi Electric Corp.) M. Ishiko (Toyota Central R&D Labs., Inc)</p>	<p>KM-6: Graphene Synthesis (Area 8&13) (9:00-10:45) Chairs: H. Hibino (NTT Basic Res. Labs.) S. Tanaka (Kyushu Univ.)</p>	<p>B-6: Device physics and characterization of OTFT (1) (Area 10) (9:00-10:45) Chairs: M. Yoshida (AIST) M. Sakai (Chiba Univ.)</p>		<p>D-6: Advanced CMOS Devices (Area 3) (9:00-10:30) Chairs: T. Hiramoto (Univ. of Tokyo) B. Doris (IBM)</p>	<p>E-6: Ge Process Technology (1) (Area 1) (9:00-10:20) Chairs: K. Kita (Univ. of Tokyo) J. Yugami (Renesas Electronics Corp.)</p>	<p>F-6: PRAM/ReRAM (1) (Area 4) (9:00-10:50) Chairs: Y. Sasago (Hitachi, Ltd.) Y. C. Chen (Macronix International Co., Ltd.)</p>
<p>9:00 AL-6-1 (Invited) High-Voltage SiC Power Devices for Energy Electronics <i>T. Kimoto and J. Suda, Kyoto Univ. (Japan)</i></p>	<p>9:00 KM-6-1 (Invited) Formation of graphene nanostructures on vicinal SiC surfaces <i>S. Tanaka, T. Kajiwara, Y. Kurisu and K. Morita, Kyushu Univ. (Japan)</i></p>	<p>9:00 B-6-1 (Invited) Device Physics of Organic Transistors <i>T. Hasegawa, AIST (Japan)</i></p>		<p>9:00 D-6-1 (Invited) Advanced Foundry CMOS: From Planar into the Multi-Gate Era <i>A. Wei, GLOBALFOUNDRIES (USA)</i></p>	<p>9:00 E-6-1 Hybrid-Formation of (100), (110), and (111) Ge-on-Insulator Structures on (100) Si Platform <i>M. Kurosawa^{1,2}, T. Sadoh¹ and M. Miyao¹, ¹Kyushu Univ. and ²JSPS (Japan)</i></p>	<p>9:00 F-6-1 (Invited) Entropy-controlled Phase-change Memory <i>J. Tominaga, P. Fons, A. Kolobov, R. Simpson and X. Wang, AIST (Japan)</i></p>
<p>9:30 AL-6-2 Thermodynamic Control of Interface Layer Formation in High-k Gate Stacks on 4H-SiC <i>S. Nakatsubo, T. Nishimura, K. Kita, K. Nagashio and A. Toriumi, Univ. of Tokyo (Japan)</i></p>	<p>9:30 KM-6-2 Tuning of Structural and Electronic properties of Epitaxial Graphene by Substrate Microfabrication <i>H. Fukidome¹, H. Handa¹, M. Kotsugi^{2,3}, Th. Seyller⁴, Y. Kawai¹, T. Ohkouchi², K. Horri², R. Takahashi¹, K. Imaizumi¹, Y. Enta⁶, M. Suemitsu¹ and T. Kinoshita^{2,3,1}, ¹Tohoku Univ., ²JASRI/Spring-8, ³CREST-JST, ⁴Friedrich-Alexander-Universität Erlangen-Nürnberg, ⁵Fritz-Harber-Institut and ⁶Hirosaki Univ. (Japan)</i></p>	<p>9:30 B-6-2 Direct Observation of Charge Carrier Concentrations in Operating Field-Effect Transistors of Pentacene by Electron Spin Resonance <i>H. Tanaka¹, M. Hirate¹, S. Watanabe¹, H. Ito¹, K. Marumoto^{2,3}, T. Takenobu^{4,4}, Y. Iwasa¹ and S. Kuroda¹, ¹Nagoya Univ., ²Univ. of Tsukuba, ³PRESTO-JST, ⁴Waseda Univ. and ⁵Univ. of Tokyo (Japan)</i></p>		<p>9:30 D-6-2 Observation of Hole Velocity Enhancement in Ge-rich Strained SiGe-on-insulator Tri-gate MOSFETs <i>K. Ikeda, M. Oda, T. Irisawa, Y. Kamimuta, Y. Moriyama and T. Tezuka, MIRAI-Toshiba (Japan)</i></p>	<p>9:20 E-6-2 Dual-Gated Germanium Junctionless p-MOSFETs <i>D. D. Zhao^{1,2,3}, C. H. Lee^{1,2}, T. Nishimura^{1,2}, K. Nagashio^{1,2} and A. Toriumi^{1,2,1}, ¹Univ. of Tokyo, ²CREST-JST and ³Beijing Normal Univ. (Japan)</i></p>	<p>9:30 F-6-2 Effect of Resistance Drift on the Activation Energy for Crystallization in Phase Change Memory <i>C. Ahn¹, B. Lee¹, R. G. D. Jayasingh¹, M. Asheghi¹, G. Hurkx², K.E. Goodson¹ and H. S. P. Wong¹, ¹Stanford Univ. and ²NXP-TSMC Research Center (USA)</i></p>
<p>9:45 AL-6-3 Characteristics of 4H-SiC p-Channel MOSFETs with Ion-Implanted Buried Channel <i>M. Okamoto, M. Iijima, T. Nagano, K. Fukuda and H. Okumura, AIST (Japan)</i></p>	<p>9:45 KM-6-3 Theory on Initial Stage of Epitaxial Graphene Growth on SiC(0001) <i>H. Kageshima¹, H. Hibino¹, H. Yamaguchi¹ and M. Nagase¹, ¹NTT Basic Res. Labs. and ²Univ. of Tokushima (Japan)</i></p>	<p>9:45 B-6-3 Probing ambipolar carrier injection into pentacene field effect transistors using charge modulation spectroscopy and displacement current measurement <i>T. Manaka, S. Kawashima, Y. Tanaka and M. Iwamoto, Tokyo Tech (Japan)</i></p>		<p>9:50 D-6-3 Extremely Small Within-Device Variability in Intrinsic Channel Tri-Gate Silicon Nanowire MOSFETs <i>K. Mao, T. Mizutani, A. Kumar, T. Saraya and T. Hiramoto, Univ. of Tokyo (Japan)</i></p>	<p>9:40 E-6-3 Control of Surface Roughness on Ge by Wet Chemical Treatments and Its Effects on Electron Mobility in n-FETs <i>C. H. Lee^{1,2}, T. Nishimura^{1,2}, T. Tabata^{1,2}, M. Yoshida¹, K. Nagashio^{1,2}, K. Kita^{1,2} and A. Toriumi^{1,2,1}, ¹Univ. of Tokyo and ²CREST-JST (Japan)</i></p>	<p>9:50 F-6-3 Effect of Interfacial oxide layer on Switching Uniformity of Ge₂Sb₂Te₅ Based Resistive Switching Memory Device <i>J. Y. Woo, S. J. Jung, S. M. Sadaf, E. J. Cha and H. S. Hwang, Gwangju Inst. of Sci. and Tech. (Korea)</i></p>
<p>10:00 AL-6-4 A Simple Thermal Impedance Measurement of SiC JFETs with Constant Current Operation <i>T. Kim and T. Funaki, Osaka Univ. (Japan)</i></p>	<p>10:00 KM-6-4 Formation of Graphene on Diamond C(111) Surfaces by Vacuum Annealing <i>S. Ogawa¹, T. Yamada¹, S. Ishidzuka¹, A. Yoshigoe¹, T. Kaga¹, H. Hozumi¹, M. Hasegawa¹, Y. Teraoka¹ and Y. Takakuwa¹, ¹Tohoku Univ., ²AIST, ³Akita Nat. Col. Tech. and ⁴JAEA (Japan)</i></p>	<p>10:00 B-6-4 Four-Probe Measurements on Field-Effect Transistors of High-Mobility Conjugated Polymers <i>H. Ito, T. Nozaki, H. Tanaka and S. Kuroda, Nagoya Univ. (Japan)</i></p>		<p>10:10 D-6-4 Enhanced Performance of Tri-Gate Transistors with Gnox Using Optimized Novel SOI Realization Technology <i>S. H. Kim^{1,2}, H. J. Bae¹, C. W. Oh¹, D. W. Kim¹, S. Yamada¹, G. Y. Jin¹ and Y. H. Roh¹, ¹Samsung Electronics Co. and ²Sungkyunkwan Univ. (Korea)</i></p>	<p>10:00 E-6-4 Strain and Dislocation Structures of Ge_{1-x}Sn_x Heteroepitaxial Layers Grown on Ge(110) Substrates <i>T. Asano¹, Y. Shimura^{1,2}, O. Nakatsuka¹ and S. Zaima¹, ¹Nagoya Univ. and ²JSPS (Japan)</i></p>	<p>10:10 F-6-4 Improvement in resistive switching parameters by selecting the SET polarity in IrO₂/TaO₂/WO₃/W structure <i>A. Prakash¹, S. Maikap¹, C. S. Lat¹, H. Y. Lee¹, W. S. Chen¹, F. T. Chen¹, M. J. Kao² and M. J. Tsai¹, ¹Chang Gung Univ. and ²ITRI (Taiwan)</i></p>
<p>10:15 AL-6-5 Effects of Substrate Defects on the Gate Leakage Current of AlGaIn/GaN Heterojunction FETs Fabricated on Na Flux Bulk GaN <i>R. Hasegawa¹, N. Yafune², H. Tokuda¹, Y. Mori¹, H. Amano¹ and M. Kuzuhara¹, ¹Univ. of Fukui, ²Sharp Corp., ³Osaka Univ. and ⁴Nagoya Univ. (Japan)</i></p>		<p>10:15 B-6-5 Analyzing diffusion-like interfacial carrier transport process in pentacene organic field-effect transistors by time-resolved second harmonic generation and impedance spectroscopy <i>L. Zhang, D. Taguchi, H. Msada, T. Manaka and M. Iwamoto, Tokyo Tech (Japan)</i></p>				<p>10:30 F-6-5 Reset Current Reduction with Excellent Filament Controllability by using Area Minimized and Field Enhanced Unipolar RRAM structure <i>K. C. Ryoo^{1,2}, S. H. Park¹, J. H. Oh^{1,2}, S. H. Jung¹, H. S. Jeong² and B. G. Park¹, ¹Seoul National Univ. and ²Samsung Electronics Co., Ltd. (Korea)</i></p>
<p>10:30 AL-6-6 Fabrication of GaN MOSFET using Selectively Re-grown n-GaN Layer on Etched Source and Drain Regions <i>D. S. Kim, H. S. Kang, C. H. Won, C. H. Bu, K. I. Jang, C. M. Yang, K. S. Im, K. W. Kim, S. D. Jung, R. H. Kim, M. K. Kwon and J. H. Lee, Kyungpook National Univ. (Korea)</i></p>	<p>10:30 KM-6-6 Large Area CVD Graphene Film as Transparent Electrode for Organic Electronics <i>G. Kalita, K. Wakita and M. Umeno, Chubu Univ. (Japan)</i></p>	<p>10:30 B-6-6 Electric and structural characterizations on annealed dinaphthothienothiophene thin-film transistors. <i>K. Kuribara¹, H. Wang², N. Uchiyama¹, K. Fukuda¹, T. Yokota¹, T. Sekitani¹, U. Zschieschang³, C. Jaye⁴, D. Fischer⁴, H. Klauk⁵, T. Yamamoto³, K. Takimiya¹, M. Ikeda⁶, H. Kuwabara⁶, Y. L. Loo⁷ and T. Someya¹, ¹Univ. of Tokyo, ²Princeton Univ., ³Max Planck Inst. for Solid State Res., ⁴National Inst. of Standards and Tech., ⁵Hiroshima Univ. and ⁶Nippon Kayaku Corp., Ltd. (Japan)</i></p>				

Coffee Break

Friday, September 30

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>G-6: Analog and Digital Circuits (Area 5) (9:00-10:50) Chairs: M. Ikebe (Hokkaido Univ.) T. Hirose (Kobe Univ.)</p>	<p>H-6: Micro Fabrication and Micro fluidic Devices (Area 11) (9:00-10:45) Chairs: M. Sasaki (Toyota Technological Inst.) T. Sakata (Univ. of Tokyo)</p>	<p>CI-6: Optical Interconnect (I) (Area 2&7) (9:00-10:45) Chairs: M. Tokushima (AIST) Y. Ishikawa (Univ. of Tokyo)</p>	<p>J-6: Photon & Spin in Nanostructures (Area 9) (9:00-10:45) Chairs: H. Gotoh (NTT Basic Res. Labs.) K. Oto (Chiba Univ.)</p>				<p>N-6: Spintronics materials and devices (Area 12) (9:00-10:45) Chairs: S. Kuroda (Univ. of Tsukuba) H. Saito (AIST)</p>
<p>9:00 G-6-1 A 220nA 32-kHz Crystal Oscillator with wide Voltage Range (1.0 - 5.5 V) for Battery-Operated MCUs <i>O. Ozawa, M. Horiguchi, Y. Okuda, A. Anzai, T. Ito, H. Shibata and M. Hiraki, Renesas Electronics Corp. (Japan)</i></p>	<p>9:00 H-6-1 (Invited) Wet Process Innovation based on Micro/Nano Science: Controllable Anisotropy in Silicon Etching for MEMS 3D Structuring <i>K. Sato, Nagoya Univ. (Japan)</i></p>	<p>9:00 CI-6-1 (Invited) Silicon Photonics in Next Generation Computers <i>M. R. Watts, MIT (USA)</i></p>	<p>9:00 J-6-1 (Invited) Acoustic transport and manipulation of carriers and spins in GaAs <i>P. V. Santos, K. Biermann, A. Hernández-Minguez, S. Lazic and R. Hey, Paul Drude Institute for Solid-State Electronics (Germany)</i></p>				<p>9:00 N-6-1 (Invited) Spin-torque induced magnetization switching and oscillation in half-metallic Co₂MnSi-based CPP-GMR devices <i>Y. Sakuraba, R. Okura, K. Izumi, T. Seki, S. Bosu, M. Mizuguchi, K. Saito and K. Takahashi, Tohoku Univ. (Japan)</i></p>
<p>9:20 G-6-2 A 12b Low Power Multi-Slope ADC with Time to Digital Converter <i>K. Kim, M. Ikebe, A. Kondou, J. Motohisa, Y. Amemiya and E. Sano, Hokkaido Univ. (Japan)</i></p>	<p>9:30 H-6-2 Oxygen sensor microarray sheet for <i>in situ</i> sensing of oxygen consumption of cultivated cell <i>M. Kojima¹, H. Takehara¹, T. Akagi¹, H. Shiono¹ and T. Ichiki¹, ¹Univ. of Tokyo and ²Nikon Instruments Inc. (Japan)</i></p>	<p>9:30 CI-6-2 (Invited) High Speed Optoelectronic Devices in Silicon <i>L. Vivien¹, D. Marris-Morini¹, G. Rasigade¹, M. Ziebell¹, P. Chaysakul¹, X. Le Roux¹, E. Cassan¹ and J. M. Fedéli², ¹Univ. Paris Sud and ²CEA-LETI/MINATEC (France)</i></p>	<p>9:30 J-6-2 (Invited) Imaging of Spin Polarized Quantum Hall Current in GaAs Quantum Well by Scanning Kerr Microscope <i>K. Oto¹, T. Matsuda¹, Y. Gunji¹, D. Fukuoka¹, K. Muro¹, N. Kumada² and Y. Hirayama^{3,4}, ¹Chiba Univ., ²NTT Basic Res. Labs., ³Tohoku Univ. and ⁴ERATO (Japan)</i></p>				<p>9:30 N-6-2 Magnetoresistance Effect in Current-Perpendicular-to-Plane Magnetoresistive Devices using Co₂Fe₂Mn_{1-x}Si Heusler Alloy <i>M. Oogane, J. Sato, H. Naganuma and Y. Ando, Tohoku Univ. (Japan)</i></p>
<p>9:40 G-6-3 Compact Multi-Bit Encoder for High Speed Frequency-Mapping Associative Memory <i>S. Sasaki, M. Yasuda, A. Kawabata, T. Koide and H. J. Mattausch, Hiroshima Univ. (Japan)</i></p>	<p>9:45 H-6-3 Silicon based Lab-On-a-Chip system for Single-Nucleotide-Polymorphism: Fabrication and characterization <i>B. Majeed¹, B. Jones¹, D. S. Tezcan¹, N. Tutun¹, L. Haspeslagh¹, S. Peeters², P. Fiorini¹, M. O. de Beek¹, C. van Hoof¹, M. Hiraoka³, H. Tanaka² and I. Yamashita⁴, ¹Imec and ²Panasonic corp. (Belgium)</i></p>	<p>10:00 CI-6-3 Si Waveguide-Integrated MSM Ge Photodiode <i>J. Fujikata^{1,2}, M. Noguchi^{1,2}, M. Miura^{1,2}, D. Okamoto^{1,2}, T. Horikawa¹ and Y. Arakawa^{1,3}, ¹PECST, ²PETRA, ³AIST and ⁴Univ. of Tokyo (Japan)</i></p>	<p>10:00 J-6-3 Inherently fast spin relaxation of exciton in photo-excited self-assembled quantum dots <i>Y. H. Liao¹, J. I. Clemente² and S. J. Cheng¹, ¹National Chiao-Tung Univ. and ²Universitat Jaume I, Castello (Taiwan)</i></p>				<p>9:45 N-6-3 Fabrication of Fully Epitaxial Magnetic Tunnel Junctions with CoFe Electrodes and a MgO Barrier on Ge(001) Substrates via a MgO Interlayer <i>G. F. Li, T. Taira, H. X. Liu, K. Matsuda, T. Uemura and M. Yamamoto, Hokkaido Univ. (Japan)</i></p>
<p>10:00 G-6-4 An Efficient Image-Vector-Generation Processor for Edge-Based Complementary Feature Representations <i>N. Yamashita and T. Shibata, Univ. of Tokyo (Japan)</i></p>	<p>10:00 H-6-4 Sub-micro-liter Electrochemical Single-Nucleotide-Polymorphism Detector for Lab-On-Chip System <i>H. Tanaka¹, P. Fiorini², S. Peeters², B. Majeed², T. Sierken², M. O. de Beek² and I. Yamashita¹, ¹Panasonic Corp. and ²Imec (Japan)</i></p>	<p>10:15 CI-6-4 Adjacent Channel Crosstalk in 0.18-μm Si CMOS Photodiode Arrays with Body Contact <i>G. Y. Chen, F. P. Chou, C. W. Wang and Y. M. Hsin, National Central Univ. (Taiwan)</i></p>	<p>10:15 J-6-4 Wavelength tunable single-photon source with a side gate <i>T. Nakaoka^{1,2,3}, Y. Tamura¹, T. Miyazawa¹, K. Watanabe¹, Y. Ota¹, S. Iwamoto¹ and Y. Arakawa¹, ¹Univ. of Tokyo, ²PRESTO-JST and ³Sophia Univ. (Japan)</i></p>				<p>10:00 N-6-4 Quasiparticle Tunneling Spectroscopy in Fe₂N/MgO/NbN Junctions <i>K. Sakuma¹, T. Hohjo¹, T. Miyavaki¹, K. Ueda¹, H. Asano¹, Y. Komazaki² and M. Tsunoda³, ¹Nagoya Univ. and ²Tohoku Univ. (Japan)</i></p>
<p>10:20 G-6-5 (Late News) Asynchronous Pulse Transmitter for Power Reduction in ThruChip Interface <i>M. Saito, N. Miura and T. Kuroda, Keio Univ. (Japan)</i></p>	<p>10:15 H-6-5 Recovery based nanowire field-effect transistor detection of pathogenic avian influenza DNA <i>C. H. Lin¹, K. N. Teng¹, C. J. Chu^{2,3}, C. D. Chen², L. C. Tsai³ and Y. S. Yang¹, ¹National Chiao Tung Univ., ²Academia Sinica and ³National Taipei Univ. of Tech. (Taiwan)</i></p>	<p>10:30 CI-6-5 Low-operation Voltage and High-speed Silicon Ring Optical Modulator with p/n Junctions along Waveguide <i>Y. Amemiya, R. Furutani, M. Fukuyama and S. Yokoyama, Hiroshima Univ. (Japan)</i></p>	<p>10:30 J-6-5 Donor-location-dependent RTS Observed by Trapping and Detrapping of a Photoexcited Electron by a Single Donor <i>A. Udhiarto, D. Moraru, T. Mizuno and M. Tabe, Shizuoka Univ. (Japan)</i></p>				<p>10:15 N-6-5 (Invited) Ultrafast Magneto-Optics Study on Magnetic Semiconductor (Ga,Mn)As <i>X. H. Zhang, Y. G. Zhu, L. F. Han, H. Yue, L. Chen and J. H. Zhao, Chinese Academy of Sci. (China)</i></p>
<p>10:35 G-6-6 (Late News) Post-Fabrication Independent L and Q Adjustment of On-Chip Inductors by Above-CMOS Processing for Rapid Prototyping of RF SoCs <i>Y. Sasaki and K. Kotani, Tohoku Univ. (Japan)</i></p>	<p>10:30 H-6-6 Ultralarge-scale DNA microreactor array enabling one-step synthesis of mutant protein library on chip <i>S. Sato^{1,2}, M. Biyani^{1,3}, T. Akagi^{1,3} and T. Ichiki^{1,3}, ¹Univ. of Tokyo, ²CMSI and ³CREST-JST (Japan)</i></p>						

Coffee Break

Friday, September 30

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
<p>AL-7: SiC&GaN Power Switching Devices (2) (Area 6&14) (11:15-12:30) Chairs: N. Ikeda (Advanced Power Device Res. Assoc.) M. Kuzuhara (Univ. of Fukui)</p>	<p>KM-7: Graphene Application (Area 8&13) (11:15-12:30) Chairs: K. Maehashi (Osaka Univ.) H. Kageshima (NTT Basic Res. Labs.)</p>	<p>B-7: Device physics and characterization of OTFT (2) (Area 10) (11:15-12:30) Chairs: E. Itoh (Shinshu Univ.) T. Manaka (Tokyo Tech)</p>		<p>D-7: ET-SOI and Nanowire Devices (Area 3) (11:15-12:25) Chairs: M. Hane (Renesas Electronics Corp.) O. Weber (CEA-LETI/MINATEC)</p>	<p>E-7: Ge Process Technology (2) (Area 1) (10:45-12:05) Chairs: T. Aoyama (Toshiba Corp.) T. Nabatame (NIMS)</p>	<p>F-7: ReRAM (2) (Area 4) (11:15-12:40) Chairs: M. J. Tsai (ITRI) K. Ishihara (Sharp Corp.)</p>
<p>11:15 AL-7-1 InAlN/AlN/GaN Schottky Source/Drain MIS-HEMT with High Breakdown Voltage Q. Zhou¹, H. Chen², C. Zhou², Z. H. Feng¹, S. J. Cai² and K. J. Chen¹, ¹Hong Kong Univ. of Sci. and Tech. and ²Hebei Semiconductor Res. Inst. (China)</p>	<p>11:15 KM-7-1 (Invited) Epitaxial CVD Growth of Graphene and Oriented Dipole Monolayer on Transport Property H. Ago¹, C. M. Orofeo¹, Y. Ogawa¹, B. Hu¹, Y. Ito¹, K. Kawahara¹, M. Tsuji¹, K. Ikeda¹, S. Mizuno¹ and H. Hibino², ¹Kyushu Univ. and ²NTT Basic Res. Labs. (Japan)</p>	<p>11:15 B-7-1 Upward and Downward Orientation of an Interface Dipole Monolayer on Pentacene Organic Field-Effect Transistors: A Comparison Study O. Y. Wei¹, M. Weis², T. Manaka¹ and M. Iwamoto¹, ¹Tokyo Tech and ²Slovak Academy of Sci (Japan)</p>		<p>11:15 D-7-1 (Invited) Extremely Thin SOI (ETSOI) - a Planar CMOS Technology for System-on-chip Applications K. Cheng¹, A. Khakifirooz¹, P. Kulkarni¹, S. Ponoth¹, B. Haran¹, A. Kumar¹, T. Adam¹, A. Reznicek¹, N. Loubet¹, H. He¹, J. Kuss¹, M. Wang¹, T. M. Levin¹, F. Monsieur¹, Q. Liu², R. Sreenivasan¹, J. Cai¹, A. Kimball¹, S. Mehta¹, S. Luming¹, Y. Zhu¹, Z. Zhu¹, T. Yamamoto¹, A. Bryant¹, C. H. Lin¹, S. Naczas¹, H. Jagannathan¹, L. F. Edge¹, S. Allegret-Maref¹, A. Dube¹, S. Kanakasabapathy¹, S. Schmitz¹, A. Inada¹, S. Seo¹, M. Raymond¹, Z. Zhang¹, A. Yagishita¹, J. Demarest¹, J. Li¹, M. Hopstaken¹, N. Berliner¹, A. Upham¹, R. Johnson¹, S. Holmes¹, T. Standaert¹, M. Smalley¹, N. Zamdmer¹, Z. Ren¹, T. Nagumo¹, T. Wu¹, H. Bu¹, V. Paruchuri¹, D. Sadana¹, V. Narayanan¹, W. Haensch¹, J. O'Neill¹, T. Hook¹, M. Khare¹, G. Shahidi¹ and B. Doris¹, ¹IBM, ²STMicroelectronics, ³GLOBALFOUNDRIES, ⁴Renesas and ⁵Toshiba (USA)</p>	<p>10:45 E-7-1 Strained Ge Layers on SiGe(Sn) Buffer Layers Formed by Solid-phase Mixing Method T. Yamaha¹, K. Mochizuki¹, Y. Shimura^{1,2}, O. Nakatsuka¹ and S. Zaima¹, ¹Nagoya Univ. and ²JSPS (Japan)</p>	<p>11:15 F-7-1 (Invited) Current Status and Future Challenges of Resistive Switching Memories W. C. Chien, F. M. Lee, Y. Y. Lin, Y. C. Chen, M. H. Lee, H. L. Lung, K. Y. Hsieh and C. Y. Lu, <i>Macronix International Co., Ltd. (Taiwan)</i></p>
<p>11:30 AL-7-2 Selective Electrochemical Formation of Recessed-Oxide-Gate Structures for Al-GaN/GaN HEMTs N. Azumaishi¹, N. Harada¹ and T. Hashizume^{1,2}, ¹Hokkaido Univ. and ²CREST-JST (Japan)</p>	<p>11:45 KM-7-2 Touch Pressure Sensor using Metal/PVDF-TrFE/Graphene Device E. J. Paek, H. J. Hwang, S. K. Lee, C. G. Kang, C. H. Cho, Y. G. Lee, S. K. Lim and B. H. Lee, <i>GIST (Korea)</i></p>	<p>11:30 B-7-2 Mobility Improvement in Top-Gate Benzothienobenzothiophene Organic Transistors Processed by Spin Coating F. Mochizuki¹, T. Endo¹, T. Nagase¹, T. Kobayashi¹, K. Takimiya², M. Ikeda^{3,4} and H. Naito¹, ¹Osaka Prefecture Univ., ²Hiroshima Univ., ³Nippon Kayaku Corp., Ltd. and ⁴Kyushu Univ. (Japan)</p>		<p>11:45 D-7-2 Carrier Transport Mechanisms in Schottky Barrier Source/Drain Nanowire FETs with Lateral Silicidation Process T. Ishikawa, M. Saitoh, K. Ota, C. Tanaka and T. Numata, <i>Toshiba Corp. (Japan)</i></p>	<p>11:05 E-7-2 Evaluation of Anisotropic Strain Relaxation in SSOI Nanostructure by Oil-Immersion Raman Spectroscopy D. Kosemura¹, M. Tomita¹, K. Usuda² and A. Ogura¹, ¹Meiji Univ. and ²AIST (Japan)</p>	<p>11:45 F-7-2 Investigation of Forming and Its Controllability in Novel HfO₂-Based 1T1R 40nm-Crossbar RRAM Cells B. Govoreanu¹, S. Kubicek¹, G. Kar¹, Y. Y. Chen^{1,2}, V. Paraschiv¹, M. Rakowski^{1,2}, R. Degraeve¹, L. Goux¹, S. Clima¹, N. Jos-sart¹, C. Adelman¹, O. Richard¹, T. Raes¹, D. Vangoidenhoven¹, T. Vandeweyer¹, H. Tielens¹, K. Kellens¹, K. Devriendt¹, N. Heylen¹, S. Brus¹, B. Verbrugge¹, L. Pantisano¹, H. Bender¹, G. Pourtois¹, J.A. Kittl¹, D.J. Wouters^{1,2}, L. Altimime¹ and M. Jurczak¹, ¹Imec and ²Katholieke Univ. Leuven (Belgium)</p>
<p>11:45 AL-7-3 AlGaIn/GaN HFET grown on 6-inch diameter Si(111) substrates by MOCVD S. M. Cho, E. J. Hwang, J. Park, K. C. Kim and T. Jang, <i>LG Electronics Inst. of Tech. (Korea)</i></p>	<p>12:00 KM-7-3 Valinomycin-Modified Graphene Field-Effect Transistors for Potassium Ion Sensors Y. Sofue, Y. Ohno, K. Maehashi, K. Inoue and K. Matsumoto, <i>Osaka Univ. (Japan)</i></p>	<p>11:45 B-7-3 TIPS-Pentacene Organic Field-Effect Transistors Utilizing Poly(p-silsesquioxane) Insulating Layers With Different Phenol Groups Y. Nakanishi¹, H. Kajii¹, K. Tamura² and Y. Ohmori¹, ¹Osaka Univ. and ²Tokyo Ohka Kogyo Corp. Ltd. (Japan)</p>		<p>12:05 D-7-3 Advantages of Silicon Nanowire MOS-FETs over Planar Ones Investigated from the Viewpoints of Static and Noise Properties W. Feng^{1,2}, R. Hettiarachchi^{1,2}, S. Sato³, K. Kakushima³, M. Niwa^{1,2}, H. Iwai¹, K. Yamada^{1,2} and K. Ohmori^{1,2}, ¹Univ. of Tsukuba, ²CREST-JST and ³Tokyo Tech (Japan)</p>	<p>11:25 E-7-3 Channel strain measurements in 32nm-node CMOSFETs M. Takei¹, H. Hashiguchi¹, T. Yamaguchi¹, D. Kosemura¹, K. Nagata^{1,2} and A. Ogura¹, ¹Meiji Univ. and ²JSPS (Japan)</p>	<p>12:05 F-7-3 CMOS Compatible Hf-based RRAM with Ultra-low Switching Currents/Power F. Zhang¹, X. Li², B. Gao¹, B. Chen¹, P. Huang¹, Y. Fu¹, Y. Chen¹, L. Liu¹, J. Kang¹, N. Singh³, G. Q. Lo² and D. L. Kwong², ¹Peking Univ. and ²A*STAR (China)</p>
<p>12:00 AL-7-4 AlGaIn/GaN HEMTs on Silicon with Hybrid Schottky-Ohmic Drain for Improved DC Characteristics Y. S. Lin, Y. W. Lian, H. C. Lu, Y. C. Huang and S. S. H. Hsu, <i>National Tsing Hua Univ. (Taiwan)</i></p>	<p>12:15 KM-7-4 Effect of ionic liquid on transfer characteristic of graphene channel on PZT J. Suzuki¹, S. Kataoka¹, T. Arie^{1,2} and S. Akita^{1,2}, ¹Osaka prefecture Univ. and ²CREST-JST (Japan)</p>	<p>12:00 B-7-4 Effects of Film Morphology on Bipolar Transport of Solution-Processed Top-gate-Type Organic Field-Effect Transistors Utilizing Blended Fluorene Derivatives H. Kajii, K. Koivai and Y. Ohmori, <i>Osaka Univ. (Japan)</i></p>		<p>11:45 E-7-4 Characterization of strain and crystallinity in patterned embedded Silicon Germanium structures S. Mochizuki¹, A. Madan², A. Pofelski³, A. G. Domenicucci², P. L. Flaitz², J. Li², Y. Y. Wang², T. Pinto³, C. W. Lai³, J. R. Holst³, E. C. T. Harley², M. W. Stoker², A. Reznicek², D. Schepis² and V. Paruchuri², ¹Renesas Electronics, ²IBM, ³STMicroelectronics and ⁴GLOBALFOUNDRIES Singapore (USA)</p>	<p>11:25 F-7-4 (Late News) Alloy and Strain Induced Multivalency in Magneli Phase Ti₃O_{2n+3} and TiO₂-HfO₂ Alloys: Singlet Negative Ion States and Non-Linear Metallic Conduction G. Lucovsky and J. W. Kim, <i>NC State Univ. (USA)</i></p>	

Friday, September 30

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
<p>G-7: RF Circuits (2) (Area 5) (11:15-12:35) Chairs: J. C. Guo (National Chiao Tung Univ.) M. Ikebe (Hokkaido Univ.)</p>	<p>H-7: Nano fabrication and Application (Area 11) (11:15-12:15) Chairs: K. Ajito (NTT Corp.) H. Nishio (OMRON Corp.)</p>	<p>CI-7: Optical Interconnect (2) (Area 2&7) (11:15-12:25) Chairs: S. Ogawa (AIST) H. Ishii (Toyohashi Univ. of Tech.)</p>	<p>J-7: Quantum Transport in Nanostructures (Area 9) (11:15-12:30) Chairs: T. Machida (Univ. of Tokyo) T. Nakaoka (Sophia Univ.)</p>				<p>N-7: Spin transport in semiconductors (Area 12) (11:15-12:30) Chairs: M. Yamamoto (Hokkaido Univ.) Y. Ohno (Tohoku Univ.)</p>
<p>11:15 G-7-1 A 60-GHz Band Low Power Differential CMOS LNA with Current-Reuse Topology Y. Subouchi, S. Kawai, T. Mitomo, S. Saigusa and O. Watanabe, Toshiba Corp. (Japan)</p>	<p>11:15 H-7-1 Electrostatic Control Mechanism of Lipid Bilayer Self-Spreading Using Nanogap as Molecule Gate Y. Kashimura, K. Furukawa and K. Torimitsu, NTT Basic Res. Labs. (Japan)</p>	<p>11:15 CI-7-1 (Invited) Optical Interconnection based on Silicon photonics S. Itabashi, K. Yamada, R. Kou, T. Watanabe, H. Shinjima, H. Nishi and T. Tsuchizawa, NTT Microsystem Integration Labs. (Japan)</p>					<p>11:15 N-7-1 (Invited) Spin Injection and Transport in a Si Channel at Room Temperature T. Suzuki¹, T. Sasaki², T. Oikawa², M. Shiraishi³, Y. Suzuki³ and K. Noguchi², ¹AIT, ²TDK Corp. and ³Osaka Univ. (Japan)</p>
<p>11:35 G-7-2 Low Voltage and Low power UWB CMOS LNA using Forward Body Biasing Technique J. R. Huang and J. C. Guo, National Chiao Tung Univ. (Taiwan)</p>	<p>11:30 H-7-2 Fabrication of a micro-lens array for Reflective Electron Beam Lithography B. Vereecke¹, L. Haspeslagh¹, F. Lazarino¹, R. A. Miller¹, K. Kellens¹, H. Dekkers¹, R. Freed² and L. Grella², ¹Imec and ²KLA-Tencor Corp. (Belgium)</p>	<p>11:45 CI-7-2 High Efficient Unidirectional Optical Coupler for Through Silicon Photonic Via in Optoelectronic 3D-LSI A. Noriki, K. W. Lee, J. Bea, T. Fukushima, T. Tanaka and M. Koyanagi, Tohoku Univ. (Japan)</p>	<p>11:30 J-7-2 Coulomb diamonds and Two-electron Spin Blockade in Cotunneling Regime of Serial Vertical Triple Quantum Dot Device S. Amaha^{1,2}, W. Izumida³, T. Hatano^{3,4}, S. Teraoka^{2,5}, K. Ono^{1,2}, K. Kono¹, S. Taucha^{2,5}, J. Gupta⁶ and D. G. Austing⁸, ¹RIKEN, ²ICORP-JST, ³Tohoku Univ., ⁴ERATO-JST, ⁵Univ. of Tokyo and ⁶NRC-Canada (Japan)</p>				<p>11:45 N-7-2 Electrical Creation of Spin Accumulation in p-type Ge H. Saito¹, S. Watanabe^{1,2}, Y. Mineno^{1,3}, S. Sharma¹, R. Jansen¹, S. Yuasa¹ and K. Ando¹, ¹AIST and ²Univ. of Tsukuba (Japan)</p>
<p>11:55 G-7-3 An Inverter-based Wideband Low Noise Amplifier in 40nm CMOS Process D. N. Saimi Dharmiza, M. Otoru, S. Tanoi, H. Ito, N. Ishihara and K. Masu, Tokyo Tech (Japan)</p>	<p>11:45 H-7-3 Fabricating a 2D Array of Φ6-nm, High Density ($1.2 \times 10^{12} \text{ cm}^{-2}$), and Periodic Silicon-Nanodisk Structures and Its Optical Characteristics for Solar Cells M. F. Budiman^{1,4}, M. Igarashi^{1,4}, K. M. Itoh^{2,4}, I. Yamashita^{3,4}, W. Hu^{1,4} and S. Samukawa^{1,4}, ¹Tohoku Univ., ²Keio Univ., ³NAIST and ⁴CREST-JST (Japan)</p>	<p>12:05 CI-7-3 Investigation of grating coupler type optical I/O interface at the 1.55 μm wavelength range T. Osaka, T. Kita and H. Yamada, Tohoku Univ. (Japan)</p>	<p>11:45 J-7-3 Electrostatic tuning of plasmonic cavities for edge magnetoplasmons M. Hashisaka¹, N. Kumada², H. Kamata^{1,2}, K. Washio¹, K. Muraki² and T. Fujisawa¹, ¹Tokyo Tech and ²NTT Basic Res. Labs. (Japan)</p>				<p>12:00 N-7-3 Radius dependence of Aharonov-Casher spin interference in InGaAs ring arrays F. Nagasawa¹, J. Takagi¹, Y. Kunihashi¹, M. Kohda^{1,2} and J. Nitta¹, ¹Tohoku Univ. and ²PRESTO-JST (Japan)</p>
<p>12:15 G-7-4 A High Efficiency Linear CMOS Power Amplifier for 5.8 GHz Dedicated Short Range Wireless Communication Systems Y. Suh¹, S. He¹, Q. Liu¹, K. Horie² and T. Yoshimasu¹, ¹Waseda Univ. and ²Toshiba Corp. (Japan)</p>			<p>12:00 J-7-4 Effect of Free Carriers on Dopant-induced Surface Potential in SOI-FETs M. Anwar¹, R. Nowak^{1,2}, D. Moraru¹, R. Jablonski², T. Mizuno¹ and M. Taber¹, ¹Shizuoka Univ. and ²Warsaw Univ. of Tech. (Japan)</p>				<p>12:15 N-7-4 Effect of MgO Barrier Insertion on Spin-dependent Transport Properties of CoFe/n-GaAs T. Akiho, T. Uemura, M. Harada, K. Matsuda and M. Yamamoto, Hokkaido Univ. (Japan)</p>

Friday, September 30

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
AL-7: SiC&GaN Power Switching Devices (2) (Area 6&14) 12:15 AL-7-5 Step-stress Reliability Studies on AlGaIn/GaN HEMTs on Silicon with Buffer Thickness Dependence <i>A. F. Wilson, A. Wakejima, S. L. Selvaraj and T. Egawa, Nagoya Inst. of Tech. (Japan)</i>	KM-7: Graphene Application (Area 8&13)	B-7: Device physics and characterization of OTFT (2) (Area 10) 12:15 B-7-5 Effects of Silver Nanoparticles Organic Envelope on Pentacene Organic Field-effect Transistors <i>K. Lee, M. Weis, X. Chen, D. Taguchi, T. Manaka and M. Iwamoto, Tokyo Tech (Japan)</i>		D-7: ET-SOI and Nanowire Devices (Area 3)	E-7: Ge Process Technology (2) (Area 1)	F-7: ReRAM (2) (Area 4)
12:30-14:00 Lunch						
A-8: Processing and Characterization Technologies (Area 6) (14:00-15:30) Chairs: Y. Miyamoto (Tokyo Tech) Y. Ohno (Univ. of Tokushima)		B-8: OTFT application (1) (Area 10) (14:00-15:45) Chairs: M. Sakai (Chiba Univ.) M. Yoshida (AIST)	C-8: 3D Interconnect (2) and Characterization (2) (Area 2) (14:00-15:50) Chairs: P. Leduc (CEA-LETI/MINATEC) T. Hasegawa (Sony Corp.)	D-8: Device Reliability (Area 3) (14:00-15:30) Chairs: D. Hisamoto (Hitachi, Ltd.) B. Doris (IBM)	E-8: III-V CMOS Technology (Area 1) (13:35-15:55) Chairs: E. Nishimura (Tokyo Electron Ltd.) T. Nakayama (Chiba Univ.)	F-8: ReRAM (3) (Area 4) (14:00-15:40) Chairs: K. Ishihara (Sharp Corp.) M. Moniwa (Renesas Electronics Corp.)
14:00 A-8-1 High Integrity SiO₂ Gate Insulator Formed by Microwave-Excited PECVD for AlGaIn/GaN Hybrid MOS-HFET on Si Substrate <i>H. Kamabayashi^{1,3}, T. Nomura¹, S. Kato¹, H. Ueda², A. Teramoto³, S. Sugawa³ and T. Ohmi³, ¹Advanced Power Device Res. Association, ²Tokyo Electron Tech. Development Inst. Inc. and ³Tohoku Univ. (Japan)</i>		14:00 B-8-1 (Invited) Organic Thin-Film Transistor-Based Non-Volatile Memory Devices <i>J. S. Lee, Kookmin Univ. (Korea)</i>	14:00 C-8-1 (Invited) Low temperature curable nano-inks for printed wiring and transparent films <i>K. Sugauma, M. Nogi, T. Tokuno and J. Jiu, Osaka Univ. (Japan)</i>	14:00 D-8-1 (Invited) A Consistent Modeling Framework to Explain Negative Bias Temperature Instability (NBTI) DC Stress, Recovery and AC Experiments <i>S. Mahapatra¹, A. E. Islam², S. Deora¹, V. D. Maheta¹ and M. A. Alam², ¹IIT Bombay and ²Purdue Univ. (India)</i>	13:35 E-8-1 (Invited) Challenges for High-k/III-V CMOS: Interfacial Chemistry, Defects, and Fermi Level Pinning <i>R. M. Wallace, Univ. of Texas (USA)</i>	14:00 F-8-1 50nm HfO₂ ReRAM with 50-Times Endurance Enhancement by Set/Reset Turnback Pulse & Verify Scheme <i>K. Higuchi, K. Miyaji, K. Johguchi and K. Takeuchi, Univ. of Tokyo (Japan)</i>
14:15 A-8-2 Low-Leakage Current n-GaN/AlGaIn/GaN HEMT with TaO_xN_y Gate Dielectric <i>T. Sato, J. Okayasu, T. Yamanouchi, T. Yashiro, J. Suzuki and M. Takikawa, Advantest Labs. Ltd. (Japan)</i>			14:30 C-8-2 Stress from Tungsten-Filled TSVs Measured by Raman Spectroscopy on Cross-Sectional Samples <i>J. Gambino¹, D. Vanslette¹, B. Webb¹, C. Luce¹, G. Chrisman¹, T. Ueda², T. Ishigaki², K. Kang² and W.S. Yoo², ¹IBM and ²Wafer-Masters, Inc. (USA)</i>	14:30 D-8-2 HCI and NBTI Induced statistical Variability in CMOS Transistors <i>A. Cathignol¹, F. Cacho², X. Federspiel² and D. Roy², ¹IBM and ²STMicroelectronics (France)</i>	14:05 E-8-2 Guiding Principles for Bonding and Passivation at III-V – oxide Interfaces <i>J. Robertson and L. Lin, Cambridge Univ. (UK)</i>	14:20 F-8-2 Hetero-device complementary resistive switches with high switch speed and reliability for cross point array applications <i>D. Lee, J. Park, S. Jung, G. Choi, J. M. Lee, M. Siddik, J. Shin, S. Kim, J. Woo and H. Hwang, Gwangju Inst. of Sci. and Tech. (Korea)</i>
14:30 A-8-3 Impacts of Dry Etching of GaN and Al-GaN Surfaces on Interface Properties of GaN-based MOS Structures <i>S. Kim¹, Y. Hori¹, N. Azumaishi¹ and T. Hashizume^{1,2}, ¹Hokkaido Univ. and ²CREST-JST (Japan)</i>		14:45 B-8-3 High performance of pentacene field effect transistors using graphene electrodes and substrate treatments <i>S. Lee¹, G. Jo¹, S. J. Kang¹, G. Wang¹, M. Choi¹, W. Park¹, J. Yoon¹, T. Kwon¹, D. Y. Kim¹, Y. H. Kahng¹ and T. Lee^{1,2}, ¹Gwangju Inst. of Sci. and Tech. and ²Seoul National Univ. (Korea)</i>	14:50 C-8-3 Evaluation of Thermo-Mechanical Stress Induced by W-TSVs in 3D-LSI with W/Cu Hybrid TSVs <i>H. Hashiguchi¹, M. Murugesan¹, J. C. Bea¹, K. W. Lee¹, T. Fukushima¹, H. Kobayashi², T. Tanaka¹ and M. Koyanagi¹, ¹Tohoku Univ. and ²Association of Super-Advanced Electronics Tech. (Japan)</i>	14:50 D-8-3 Compact Reaction-Diffusion Model for Accurate NBTI Prediction <i>C. Ma^{1,2}, M. Miyake¹, H. J. Mattausch¹, K. Matsuzawa², T. Itzuka², T. Hozhida², A. Kinoshita², T. Arakawa², J. He² and M. Miura-Mattausch¹, ¹Hiroshima Univ., ²STARC and ³Peking Univ. (Japan)</i>	14:25 E-8-3 Effect of sulfur treatment on HfO₂/InGaAs MOS interfaces properties <i>R. Suzuki¹, S. Lee¹, S. H. Kim¹, T. Hoshii¹, M. Yokoyama¹, N. Taoka¹, T. Yasuda¹, W. Jevasuwan², T. Maeda², O. Ichikawa¹, N. Fukuhara³, M. Hata³, M. Takenaka¹ and S. Takagi¹, ¹Univ. of Tokyo, ²AIST and ³Sumitomo Chemical Co., Ltd. (Japan)</i>	14:40 F-8-3 Flexible One Diode-One Resistor Cross-bar Resistive-Switching Memory <i>C. W. Hsu¹, J. J. Huang¹, Y. M. Tseng¹, T. H. Hou¹, W. H. Chang², W. Y. Jiang² and C. H. Lin², ¹National Chiao Tung Univ. and ²Winbond Electronics Corp. (Taiwan)</i>
14:45 A-8-4 Damage-free GaN Etching by Chlorine Neutral Beam <i>Y. Tamura^{1,3}, X. Y. Wang^{1,3}, C. H. Huang^{1,3}, T. Kubota¹, J. Ohta¹, H. Fujioka^{2,3} and S. Samukawa^{1,3}, ¹Tohoku Univ., ²Univ. of Tokyo and ³CREST-JST (Japan)</i>		15:00 B-8-4 Variation of Active Layer Thickness of Polymer Thin Film Transistors and its Effect on Digital Circuits Performance <i>L. Reséndiz¹, M. Estrada², A. Cerdeira² and V. Cabrera¹, ¹Inst. UPIITA - IPN and ²Res. CINVESTAV (Mexico)</i>	15:10 C-8-4 Size and Deformation Mode Dependencies on the Strength of Dry-Etched Single Crystal Silicon Micro-Beams <i>T. Namazu^{1,2}, H. Yamagiwa¹, T. Fujii¹, M. Saito¹, K. Yamada¹ and T. Miyatake³, ¹Univ. of Hyogo, ²PRESTO-JST and ³Panasonic Electric Works Co., Ltd. (Japan)</i>	15:10 D-8-4 Enhanced Degradation by NBT stress in Si Nanowire Transistor <i>K. Ota¹, M. Saitoh¹, C. Tanaka¹, Y. Nakabayashi¹, K. Uchida² and T. Numata¹, ¹Toshiba Corp. and ²Tokyo Tech (Japan)</i>	14:55 E-8-4 Effects of Nitrided-InGaAs Interfacial Layers formed by ECR nitrogen plasma on Al₂O₃/InGaAs MOS Properties <i>T. Hoshii¹, S. Lee¹, R. Suzuki¹, N. Taoka¹, M. Yokoyama¹, H. Yamada², W. Jevasuwan³, M. Hata², T. Yasuda³, M. Takenaka¹ and S. Takagi¹, ¹Univ. of Tokyo, ²AIST and ³Sumitomo Chemical Co., Ltd. and ³AIST (Japan)</i>	15:00 F-8-4 Formation free low power resistive switching memory using IrO_x/AlO_x/W cross-point with excellent uniformity and multi level operation <i>W. Banerjee, S. Z. Rahaman and S. Maikap, Chang Gung Univ. (Taiwan)</i>

Friday, September 30

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
G-7: RF Circuits (2) (Area 5)	H-7: Nano fabrication and Application (Area 11)	CI-7: Optical Interconnect (2) (Area 2&7)	J-7: Quantum Transport in Nanostructures (Area 9)				N-7: Spin transport in semiconductors (Area 12)
			12:15 J-7-5 Nanoparticle Single-Electron Transistor with Metal Bridged Top-Gate Electrodes <i>Y. Azuma^{1,2}, S. Suzuki^{1,2}, K. Maeda^{1,2}, N. Okabayashi^{1,2}, D. Tanaka^{2,3}, T. Teranishi^{2,3}, M. R. Buitelaar⁴, C. G. Smith⁴ and Y. Majima^{1,2,3}, ¹Tokyo Tech, ²CREST-JST, ³Tsukuba Univ., ⁴Univ. of Cambridge and ⁵Sunchon National Univ. (Japan)</i>				

12:30-14:00 Lunch

		I-8: SiGe-Based Optical Devices (Area 7) (14:00-15:30) Chairs: S. Saito (Hitachi Ltd.) N. Iizuka (Toshiba Corp.)	J-8: Qubit and Novel Functional Devices (Area 9) (14:00-15:45) Chairs: K. Ono (RIKEN) T. Tanamoto (Toshiba Corp.)	K-8: Graphene Property (Area 13) (14:00-15:45) Chairs: J. H. Ahn (Sungkyunkwan Univ.) S. Sato (AIST)	L-8: Power Devices & ICs (Area 14) (14:00-15:45) Chairs: M. Ishiko (Toyota Central R&D Labs., Inc) N. Ikeda (Advanced Power Device Res. Assoc.)	M-8: Growth techniques of Si and Ge (Area 8) (14:00-15:45) Chairs: H. Hibino (NTT Basic Res. Labs.) K. Hara (Shizuoka Univ.)	N-8: Circuit application of spintronics devices (Area 12) (14:00-15:30) Chairs: K. Ito (Hitachi, Ltd.) M. Oogane (Tohoku Univ.)
		14:00 I-8-1 Electroluminescence from One-dimensionally Self-Aligned Si-based Quantum Dots with High Areal Dot Density <i>K. Makihara¹, H. Deki², M. Ikeda³ and S. Miyazaki¹, ¹Nagoya Univ., ²Hiroshima Kokusai Gakuin Univ. and ³Hiroshima Univ. (Japan)</i>	14:00 J-8-1 (Invited) Atomic physics and quantum optics using circuits behaving as tunable artificial atoms <i>F. Nori^{1,2}, ¹RIKEN and ²Univ. of Michigan (Japan)</i>	14:00 K-8-1 (Invited) Trends and Future of Ultrafast Transistors and Terahertz Light Amplification by Stimulated Emission of Radiation Using Graphene <i>T. Otsuji^{1,2}, ¹Tohoku Univ. and ²CREST-JST (Japan)</i>	14:00 L-8-1 (Invited) Key Power Device Technologies Catering to Sustainable Growth of Power Electronics <i>G. Majumdar, Mitsubishi Electric Corp. (Japan)</i>	14:00 M-8-1 Impact on TFT Characteristics of Rapid Crystallization of Si using Nickel-Metal Induced Lateral Crystallization <i>S. Nagata, G. Nakagawa and T. Asano, Kyushu Univ. (Japan)</i>	14:00 N-8-1 Anisotropic phase coherent length affected by coexistence of a spin orbit interaction and an in-plane magnetic field in InGaAs narrow wire structures <i>S. Nonaka¹, Y. Kunihashi¹, M. Kohda^{1,2} and J. Nitta¹, ¹Tohoku Univ. and ²PRESTO-JST (Japan)</i>
		14:15 I-8-2 Demonstration of Silicon Nanocavity LED with Enhanced Luminescence <i>S. Nakayama, S. Iwamoto, S. Kako, S. Ishida and Y. Arakawa, Univ. of Tokyo (Japan)</i>	14:30 J-8-2 Steady-state solution for dark states using a three-level system in coupled quantum dots <i>T. Tanamoto¹, K. Ono² and F. Nori^{2,3}, ¹Toshiba Corp., ²RIKEN and ³Univ. of Michigan (Japan)</i>	14:30 K-8-2 Effects of Randomly Distributed Local Dirac Points in Graphene Channel on Its FET Transfer Characteristics <i>R. Ifuku, K. Nagashio, T. Nishimura and A. Toriumi, Univ. of Tokyo (Japan)</i>	14:30 L-8-2 Extraction enhanced lateral IGBT (E² LIGBT) : A super high speed LIGBT superior to LDMOS <i>S. Ashida¹, S. Takahashi¹, S. Shiraki¹, N. Tokura¹ and A. Nakagawa², ¹DENSO Corp. and ²Nakagawa Consulting Office (Japan)</i>	14:15 M-8-2 High Speed Lateral Crystallization of Amorphous Silicon Films on Glass Substrates by Micro-Thermal-Plasma-Jet Irradiation and Its Application to Thin Film Transistor Fabrication <i>Y. Fujita, S. Hayashi, H. Murakami and S. Higashi, Hiroshima Univ. (Japan)</i>	14:15 N-8-2 A Compact Nonvolatile Logic Element Using an MTJ/MOS-Hybrid Structure <i>D. Suzuki, M. Natsui, T. Endoh, H. Ohno and T. Hanyu, Tohoku Univ. (Japan)</i>
		14:30 I-8-3 Si/SiO₂ Bilayer Beam Structure for Photoelastic Control of Si Photonic Devices <i>M. Hirase, Y. Ishikawa and K. Wada, Univ. of Tokyo (Japan)</i>	14:45 J-8-3 Ultra-Low-Power Superconducting Logic Devices using Adiabatic Quantum Flux Parametron <i>N. Yoshikawa, D. Ozawa and Y. Yamamashi, Yokohama National Univ. (Japan)</i>	14:45 K-8-3 Graphene Growth on Sidewall of Catalyst by CVD and Its Application to Graphene Transistors <i>H. An¹, W. G. Lee² and J. W. Jung¹, ¹Sejong Univ. and ²National Nano Fab Center (Korea)</i>	14:45 L-8-3 High Voltage and high reliability SOI power IC technologies and their application to 750V 4.5A micro-inverter IC <i>S. Shiraki, S. Takahashi, A. Yamada, M. Yamamoto, K. Senda, Y. Ashida, A. Hiruma and N. Tokura, DENSO Corp. (Japan)</i>	14:30 M-8-3 Investigation of Ni Metal Induced Lateral Crystallization with a-Si Film Thickness at Very Thin Extent <i>G. Nakagawa, T. Nakamae and T. Asano, Kyushu Univ. (Japan)</i>	14:30 N-8-3 Physics-based SPICE Model of Spin Torque Oscillators <i>H. Lim, S. Ahn, S. Lee and H. Shin, Ewha Womans Univ. (Korea)</i>
		14:45 I-8-4 Light Detection and Emission in Germanium-On-Insulator Diodes <i>K. Tani^{1,2,3}, S. Saito^{1,2,3}, Y. Lee¹, K. Oda^{1,2,3}, T. Mine³, T. Sugawara^{1,2,3} and T. Ido^{1,2,3}, ¹PECST, ²PETRA and ³Hitech, Ltd. (Japan)</i>	15:00 J-8-4 Atto-Joule Operation of High-Speed Shift Register Based on Ultra Low-Power Rapid Single Flux Quantum Circuit Technology <i>A. Fujimaki¹, M. Tanaka^{1,2}, A. Kitayama¹, T. Kouketsu¹ and M. Ito¹, ¹Nagoya Univ. and ²UC, Berkeley (Japan)</i>	15:00 K-8-4 Electrical Conductance in Graphene Contacting with Metal <i>T. Moriyama, K. Nagashio, T. Nishimura and A. Toriumi, Univ. of Tokyo (Japan)</i>	15:00 L-8-4 A Novel FEM-LDMOS of Improved Off-state Breakdown Voltage Without Additional Mask <i>H. B. Chen¹, C. J. Chang², J. J. Wu¹, W. C. Chen³, C. C. Tsai² and C. Y. Chang¹, ¹National Chiao Tung Univ., ²Himax Technologies and ³Yanguard International Semiconductor Corp. (Taiwan)</i>	14:45 M-8-4 Orientation Control of Al-Induced Crystallized Silicon by Diffusion Barrier Layers <i>A. Okada¹, K. Toko¹, K. Hara², N. Usami^{2,3} and T. Suemasu^{1,3}, ¹Univ. of Tsukuba, ²Tohoku Univ. and ³CREST-JST (Japan)</i>	14:45 N-8-4 Time-Resolved Switching Characteristic in Magnetic Tunnel Junction with Spin Transfer Torque Write Scheme <i>F. Iga, Y. Yoshida, S. Ikeda, T. Hanyu, H. Ohno and T. Endoh, Tohoku Univ. (Japan)</i>

Friday, September 30

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
A-8: Processing and Characterization Technologies (Area 6)		B-8: OTFT application (1) (Area 10)	C-8: 3D Interconnect (2) and Characterization (2) (Area 2)	D-8: Device Reliability (Area 3)	E-8: III-V CMOS Technology (Area 1)	F-8: ReRAM (3) (Area 4)
<p>15:00 A-8-5 Germanium/Ni-InGaAs Solid-State Reaction for Contact Resistance Reduction on n⁺-In_{0.53}Ga_{0.47}As <i>H. X. Guo, E. Y. J. Kong, X. Zhang and Y. C. Yeo, National Univ. of Singapore (Singapore)</i></p> <p>15:15 A-8-6 Fabrication and analysis of AlN/GaAs(001) metal-insulator-semiconductor structure <i>M. Kudo, H. A. Shih, M. Akabori and T. Suzuki, JAIST (Japan)</i></p>		<p>15:15 B-8-5 Control of switching voltage of low voltage organic complementary inverter using floating gate structure <i>T. Yokota¹, T. Sekitani¹, T. Nakagawa¹, Y. Noguchi¹, K. Takeuchi¹, U. Zschieschang², H. Klauk² and T. Someya¹, ¹Univ. of Tokyo, and ²Max Planck Inst. for Solid State Res. (Japan)</i></p> <p>15:30 B-8-6 3V-Operation Organic Transistors on Shape-Memory Film with Polyimide Planarization Layer <i>Y. Kato¹, T. Sekitani¹, T. Yokota¹, K. Kuribara¹, U. Zschieschang², H. Klauk², T. Yamamoto³, K. Takimiya⁴, M. Ikeda⁴, H. Kuwabara⁴ and T. Someya¹, ¹Univ. of Tokyo, ²Max Planck Inst. for Solid State Res., ³Hiroshima Univ. and ⁴Nippon Kayaku Corp. Ltd. (Japan)</i></p>	<p>15:30 C-8-5 Local Interface Strength Evaluation for LSI Interconnect with Micron Resolution <i>N. Shishido^{1,3}, C. Chen¹, H. Sato^{1,5}, S. Kamiya^{1,5}, M. Nishida^{1,5}, M. Omiya^{2,5}, T. Nokuo^{3,5}, T. Nagasawa^{3,5}, T. Suzuki¹ and T. Nakamura⁴, ¹Nagoya Inst. of Tech., ²Keio Univ., ³JEOL Ltd., ⁴Fujitsu Labs. Ltd. and ⁵CREST-JST (Japan)</i></p>		<p>15:15 E-8-5 Controlling anion composition at MIS interfaces on III-V Channels by Plasma Processing <i>W. Jevasiwan¹, Y. Urabe¹, T. Maeda¹, N. Miyata¹, T. Yasuda¹, A. Ohtake², H. Yamada³, M. Hata³, S. Lee¹, T. Hoshii⁴, M. Takenaka⁴ and S. Takagi¹, ¹AIST, ²NIMS, ³Sumitomo Chemical. Co., Ltd. and ⁴Univ. of Tokyo (Japan)</i></p> <p>15:35 E-8-6 Formation of Ultra-thin and Uniform Ni-InGaAs Alloyed Contact for Scaled Metal S/D InGaAs MOSFETs <i>T. Irisawa, M. Oda and T. Tezuka, AIST (Japan)</i></p>	<p>15:20 F-8-5 Highly Uniform and Reliable Switching Properties in NbO₂ Based RRAM Devices <i>S. M. Sadaf, X. Liu, S. H. Choudhury, J. Shin, J. Woo, M. Siddik and H. Hwang, Gwangju Inst. of Sci. and Tech. (Korea)</i></p>

Coffee Break

		B-9: OTFT application (2) (Area 10) (16:10-17:25) Chairs: T. Manaka (Tokyo Tech) K. Kato (Niigata Univ.)	C-9: Characterization (3) (Area 2) (16:10-17:30) Chairs: J. Gambino (IBM Microelectronics) Y. Otsuka (Toray Research Center Inc.)		E-9: Advanced Si Technology (Area 1) (16:10-17:25) Chairs: J. Yugami (Renesas Electronics Corp.) T. Nakayama (Chiba Univ.)	F-9: ReRAM (4) (Area 4) (16:10-17:10) Chairs: Y. C. Chen (Macronix International Co., Ltd.) T. Endoh (Tohoku Univ.)
		<p>16:10 B-9-1 Bending test of organic TFTs with a soluble polycrystalline semiconductor <i>T. Tokuhara, T. Sekitani, T. Yokota and T. Someya, Univ. of Tokyo (Japan)</i></p> <p>16:25 B-9-2 Solution-processed C₆₀ field-effect transistors with high mobility <i>W. Kang¹, M. Kitamura^{1,2}, M. Kamura^{1,3}, S. Amori^{1,4} and Y. Arakawa¹, ¹Univ. of Tokyo, ²Kobe Univ. and ³Sharp Corp. (Japan)</i></p>	<p>16:10 C-9-1 In Situ Analysis of Plasma-Induced Modification on Porous SiOCH Films <i>H. Yamamoto, K. Asano, K. Ishikawa, K. Takeda, H. Kondo, M. Sekine and M. Hori, Nagoya Univ. (Japan)</i></p> <p>16:30 C-9-2 Potential Characterization of Interconnect Corrosion by Kelvin Probe Force Microscopy <i>M. Kodera, Y. Yoshimizu and K. Uchida, Toshiba Corp. (Japan)</i></p>		<p>16:10 E-9-1 Silicon-On-Insulator Fabrication Using Si/HfO₂/Si Epitaxial Structure <i>S. Migita and H. Ota, AIST (Japan)</i></p> <p>16:30 E-9-2 Enabling epitaxy on ultrathin implanted SOI <i>L. Grenouillet¹, N. Posseme¹, S. Ponoht², N. Loubet³, V. Destefanis¹, Y. Le Tiec¹, S. Mehta², A. Kumar², Q. Liu³, B. Haran², K. Cheng², N. Berliner², J. Fullam², J. Kuss², G. Shahidi², O. Faynot², B. Doris² and M. Vinet¹, ¹CEA-LETI, ²IBM and ³ST Microelectronics (USA)</i></p>	<p>16:10 F-9-1 Record resistance ratio and bipolar/unipolar resistive switching scenario using novel Cu/GeO₂/W memory device <i>S. Z. Rahaman¹, S. Maikap¹, S. K. Ray^{1,2}, H. Y. Lee³, W. S. Chen³, F. T. Chen³, M. J. Kao³ and M. J. Tsai³, ¹Chang Gung Univ., ²Indian Inst. of Tech. and ³ITRI (Taiwan)</i></p> <p>16:30 F-9-2 Effects of Ti interfacial layer on resistive switching memory performance using Cu filament in high-κ Ta₂O₅ solid-electrolyte <i>A. K. Sahoo¹, S. Z. Rahaman¹, S. Maikap¹, H. Y. Lee², W. S. Chen², F. T. Chen², M. J. Kao² and M. J. Tsai², ¹Chang Gung Univ. and ²ITRI (Taiwan)</i></p>

Friday, September 30

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
		<p>I-8: SiGe-Based Optical Devices (Area 7)</p> <p>15:00 I-8-5 Improving Optical Properties of Ge Layers Fabricated by Epitaxial Growth Combined with Ge Condensation K. Oda^{1,2,3}, K. Tani^{1,2,3}, S. Saito^{1,2,3}, T. Okumura¹ and T. Ido^{1,2,3} ¹PETRA, ²PECST and ³Hitachi Ltd. (Japan)</p> <p>15:15 I-8-6 Photoluminescence from n⁺-Ge microdisk on Si-on-Insulator Structure K. Takinai¹, A. Yoshida¹, Y. Ishikawa¹, K. Wada¹, T. Tsuchizawa², T. Watanabe², K. Yamada² and S. Itabashi², ¹Univ. of Tokyo and ²NTT Microsystem Integration Labs. (Japan)</p>	<p>J-8: Qubit and Novel Functional Devices (Area 9)</p> <p>15:15 J-8-5 Induced Dielectric Polarization and Piezoelectric Effects on Valence Band alignment in Multi-Quantum Well Composed of Wurtzite Semiconductors S. Emura, M. Morifuji, M. Kondow and H. Asahi, Osaka Univ. (Japan)</p> <p>15:30 J-8-6 (Late News) Correlation measurement of I/f noise in semiconductor point contacts with a common lead M. Yamagishi¹, M. Hashisaka¹, K. Muraki² and T. Fujisawa¹, ¹Tokyo Tech and ²NTT Basic Res. Labs. (Japan)</p>	<p>K-8: Graphene Property (Area 13)</p> <p>15:15 K-8-5 Electronic Structure Modulation of Graphene Adsorbed by Metal Pillars Y. Takagi^{1,2} and S. Okada^{1,2}, ¹Univ. of Tsukuba and ²CREST-JST (Japan)</p> <p>15:30 K-8-6 (Late News) Field-Effect Transistor with Graphene by Direct Alcohol CVD M. Ishii, A. Nakamura, H. Inokawa and J. Temmyo, Shizuoka Univ. (Japan)</p>	<p>L-8: Power Devices & ICs (Area 14)</p> <p>15:15 L-8-5 Reduction of Power Loss of Zero Current Switching Converter by Optimizing Power Devices S. Machida¹, N. Kikuchi¹, T. Segawa², Y. Shimo² and M. Kobayashi², ¹Toyota Central R&D Labs. Inc. and ²Toyota Motor Corp. (Japan)</p> <p>15:30 L-8-6 Dynamic-Carrier-Distribution-Based Compact Modeling of P-i-N Diode Reverse Recovery Effect J. Nakashima, M. Miyake and M. Miura-Mattausch, Hiroshima Univ. (Japan)</p>	<p>M-8: Growth techniques of Si and Ge (Area 8)</p> <p>15:00 M-8-5 Phosphorus Mediated Growth of Ge Layer on Si(001) Substrate H. Hanafusa¹, N. Hirose², A. Kasamatsu², T. Mimura², T. Matsui² and Y. Suda¹, ¹Tokyo Univ. of Agri. and Tech. and ²NICT (Japan)</p> <p>15:15 M-8-6 Precise thickness and strain control during epitaxial growth of strained Ge/SiGe multilayers by industrial class CVD M. Myronov, X. C. Liu, A. Dobbie and D. R. Leadley, Univ. of Warwick (UK)</p> <p>15:30 M-8-7 Boron and Carbon co-doping in high percentage Silicon-Germanium Alloys - Effects of Dopant Incorporation, Strain Compensation and Microstructure - A. Reznicek, T. N. Adam, Z. Zhu, J. Li, R. Murphy, S. W. Badell, V. Paruchuri and D.K. Sadana, IBM (USA)</p>	<p>N-8: Circuit application of spintronics devices (Area 12)</p> <p>15:00 N-8-5 Mixing Effect in Magnetic Tunnel Junctions G. Shiomi¹, Y. Masugata¹, S. Ishibashi¹, H. Tomita¹, D. Maehara², T. Nozaki², S. Miwa¹, H. Kubota², A. Fukushima², S. Yuasa² and Y. Suzuki¹, ¹Osaka Univ. and ²AIST (Japan)</p> <p>15:15 N-8-6 Role of Synthetic Ferrimagnets in MTJs from Wave Packet Dynamics M. Arikawa¹, M. Muraguchi^{1,2}, Y. Hatsugai^{1,3}, K. Shiraiishi³ and T. Endoh¹, ¹Tohoku Univ., ²CREST-JST and ³Univ. of Tsukuba (Japan)</p>

Coffee Break

		<p>I-9: Quantum-Dot Devices (Area 7) (16:10-17:25) Chairs: A. Wakahara (Toyohashi Univ. of Tech.) M. Tokushima (AIST)</p>		<p>K-9: Graphene Device (Area 13) (16:10-17:25) Chairs: T. Otsuji (Tohoku Univ.) H. Tsuchiya (Kobe Univ.)</p>	<p>L-9: Novel Concepts (Area 14) (16:10-17:25) Chairs: N. Usami (Tohoku Univ.) Y. Kurokawa (Tokyo Tech)</p>	<p>M-9: Characterization of group IV related materials (Area 8) (16:10-17:10) Chairs: K. Hara (Shizuoka Univ.) H. Hibino (NTT Basic Res. Labs.)</p>	<p>N-9: Physics of spintronics devices (Area 12) (16:10-17:25) Chairs: J. H. Zhao (Chinese Academy of Sciences) K. Ito (Hitachi, Ltd.)</p>
		<p>16:10 I-9-1 Effect of Reduced Stacking Periods on Modulation Bandwidth of Self-Assembled Quantum-Dot Lasers: Theoretical Study M. Ishida¹, Y. Tanaka^{2,3,4,5}, T. Yamamoto^{2,3,4,5}, M. Sugawara² and Y. Arakawa¹, ¹Univ. of Tokyo, ²Fujitsu Labs. Ltd., ³Fujitsu Ltd., ⁴PETRA and ⁵QD Laser, Inc. (Japan)</p> <p>16:25 I-9-2 Characterization of wavelength tunable quantum dot external cavity laser (QD-ECL) for 1.3-μm waveband narrow line-width coherent light source N. Yamamoto¹, K. Akahane¹, T. Kawanishi¹, Y. Yoshioka¹ and H. Takai², ¹NICT and ²Tokyo Denki Univ. (Japan)</p>		<p>16:10 K-9-1 Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001) S. Tanabe, Y. Sekine, H. Kageshima and H. Hibino, NTT Basic Res. Labs. (Japan)</p> <p>16:25 K-9-2 Electric-field-induced band gap of bilayer graphene in ionic liquid Y. Yamashiro, Y. Ohno, K. Maehashi, K. Inoue and K. Matsumoto, Osaka Univ. (Japan)</p>	<p>16:10 L-9-1 CO₂ conversion with light and water by GaN photo-electrode S. Yotsuhashi¹, M. Deguchi¹, Y. Zenitani¹, R. Hinogami¹, H. Hashiba¹, Y. Yamada¹ and K. Ohkawa¹, ¹Panasonic Corp. and ²Tokyo Univ. of Sci. (Japan)</p> <p>16:25 L-9-2 Local Characterization of Multicrystalline Silicon Solar Cells through Photothermal and Potential Measurements by Scanning Probe Microscopy K. Hara and T. Takahashi, Univ. of Tokyo (Japan)</p>	<p>16:10 M-9-1 Probing Transverse-Optical Phonons in Strained Si Nanowire: Strain Profiles and Nanomechanical properties A. Tarun¹, N. Hayazawa¹, O. Moutanabbir² and S. Kawata¹, ¹RIKEN and ²Max Planck Inst. (MPI) (Japan)</p> <p>16:25 M-9-2 Leakage Current Control of Fluoride Ultra-thin Films Grown on Ge Substrates K. Takahashi, Y. Hayashi, R. Kayanuma and K. Tsutsui, Tokyo Tech (Japan)</p>	<p>16:10 N-9-1 Giant Zeeman splitting in the magneto-reflectance spectra of a dilated magnetic semiconductor (Zn,Cr)Te N. Matsumoto, K. Kanazawa and S. Kuroda, Univ. of Tsukuba (Japan)</p> <p>16:25 N-9-2 Observation of magnetic domain wall motion induced by adiabatic spin transfer torque in Co/Ni nanowires T. Koyama¹, K. Ueda¹, D. Chiba^{1,2}, S. Fukami¹, H. Tanigawa³, T. Suzuki¹, N. Ohshima², N. Ishiwata³, Y. Nakatani¹ and T. Ono¹, ¹Kyoto Univ., ²PRESTO-JST, ³NEC Corp. and ⁴Univ. of Electro-communications (Japan)</p>

Friday, September 30

5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
		<p>B-9: OTFT application (2) (Area 10)</p> <p>16:40 B-9-3 Inkjet printing of small-molecule semiconductor thin films for high-performance organic transistors <i>H. Minemawari¹, T. Yamada¹, M. Matsui¹, J. Tsutsumi¹, S. Haas¹, R. Kumai^{1,2} and T. Hasegawa¹, ¹AIST and ²KEK (Japan)</i></p> <p>16:55 B-9-4 High performance top-contact organic thin-film-transistors using screen printed source and drain electrodes <i>Y. Zhao¹, M. Kaltenbrunner², T. Sekitani¹, S. Bauer² and T. Someya¹, ¹Univ. of Tokyo and ²Johannes Kepler Univ. Linz (Japan)</i></p> <p>17:10 B-9-5 Hotpress Method for Thin Crystalline Organic Field-Effect Transistors <i>A. Inoue¹, T. Okamoto¹, Y. Joho¹, M. Sakai¹, H. Yamauchi¹, M. Nakamura^{1,2} and K. Kudo¹, ¹Chiba Univ. and ²NAIST (Japan)</i></p>	<p>C-9: Characterization (3) (Area 2)</p> <p>16:50 C-9-3 Oxidation Resistance of Ti Oxide Self-Formed Barrier in Cu Interconnects <i>K. Ito¹, K. Kohama¹, K. Hamasaka¹, Y. Shirai¹ and M. Murakami², ¹Kyoto Univ. and ²The Ritsumeikan Trust (Japan)</i></p> <p>17:10 C-9-4 Effects of Cu Film Texture and Barrier Structure on Cu Grain Growth <i>K. Kohama¹, T. Matsumoto¹, K. Ito¹, Y. Shirai¹ and M. Murakami², ¹Kyoto Univ. and ²The Ritsumeikan Trust (Japan)</i></p>		<p>E-9: Advanced Si Technology (Area 1)</p> <p>16:50 E-9-3 Performance and Variability Comparisons between ALD- and PVD-TiN Gate FinFET <i>T. Hayashida^{1,2}, K. Endo³, Y. X. Liu³, S. Ouchi³, T. Matsukawa³, W. Mizubayashi³, S. Migita³, Y. Morita³, H. Ota³, H. Hashiguchi¹, D. Kosemura¹, T. Kamei¹, J. Tsukada³, Y. Ishikawa³, H. Yamauchi³, A. Ogura¹ and M. Masahara^{1,3}, ¹Meiji Univ., ²JSPS and ³AIST (Japan)</i></p> <p>17:10 E-9-4 (Late News) Extremely scaled (~0.2 nm) equivalent oxide thickness of higher-k ALD-HfO₂ gate stacks <i>Y. Morita, S. Migita, W. Mizubayashi and H. Ota, AIST (Japan)</i></p>	<p>F-9: ReRAM (4) (Area 4)</p> <p>16:50 F-9-3 Improving switching characteristics of Cu/Si₃N₄/Pt device with low voltage stress to perform forming <i>Q. Liu, H. B. Lv, S. B. Long, W. Wang, Y. T. Li, Y. Wang, M. Wang, K. W. Zhang, H. W. Xie and M. Liu, Chinese Academy of Sci. (China)</i></p>

Friday, September 30

11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
		<p>I-9: Quantum-Dot Devices (Area 7)</p> <p>16:40 I-9-3 Integrated Amplifier for Gain Spectra Measurement of Bilayer Quantum Dot Laser Material <i>H. Shahid¹, D. T. D. Childs¹, M. A. Majid¹, K. Kennedy¹, R. Airey¹, R. A. Hogg¹, E. Clarke², P. Spencer² and R. Murray², ¹Univ. of Sheffield and ²Imperial College (UK)</i></p> <p>16:55 I-9-4 Optimization of quantum dot molecular beam epitaxy diode for broadband applications <i>M. A. Majid, M. Hugues, D. T. D. Childs and R. A. Hogg, Univ. of Sheffield (UK)</i></p> <p>17:10 I-9-5 Photoresponse improvement of InAs/GaAs quantum dot infrared photodetectors using GaAs_xSb_x overgrown layer <i>C. T. Huang, Y. C. Chen and S. C. Lee, National Taiwan Univ. (Taiwan)</i></p>		<p>K-9: Graphene Device (Area 13)</p> <p>16:40 K-9-3 Electron tunneling in bilayer graphene <i>p-n</i> junction controlled by gate electric field <i>H. Miyazaki^{1,2}, M. Lee¹, S. L. Li¹, A. Kanda^{2,3} and K. Tsukagoshi^{1,2}, ¹MANA, NIMS, ²CREST-JST and ³Univ. of Tsukuba (Japan)</i></p> <p>16:55 K-9-4 Gating Operation of Transport Current in Graphene Nanoribbon Fabricated by Helium Ion Microscope <i>S. Nakahara¹, T. Iijima², S. Ogawa², H. Miyazaki¹, S. Li³, K. Tsukagoshi¹, S. Sato¹ and N. Yokoyama¹, ¹AIST-GNC, ²AIST-ICAN and ³NIMS-MANA (Japan)</i></p> <p>17:10 K-9-5 RF Performance of Graphene Nano-Ribbon MOSFET vs. TFET <i>V. P. Sreenivas, K. T. Lam and G. Liang, National Univ. of Singapore (Singapore)</i></p>	<p>L-9: Novel Concepts (Area 14)</p> <p>16:40 L-9-3 Impact of light element impurities on crystalline defect generation in silicon substrate <i>T. Tachibana¹, T. Sameshima¹, T. Kojima¹, K. Arafune¹, K. Kakimoto¹, Y. Miyamura¹, H. Harada¹, T. Sekiguchi², Y. Ohshita² and A. Ogura¹, ¹Meiji Univ., ²Toyota Tech. Inst., ³Univ. of Hyogo, ⁴Kyusyu Univ. and ⁵NIMS (Japan)</i></p> <p>16:55 L-9-4 Flash-Lamp-Induced Explosive Crystallization of Amorphous Films Leaving Behind Periodic Microstructures <i>K. Ohdaira^{1,2} and H. Matsumura¹, ¹JAIST and ²PRESTO-JST (Japan)</i></p> <p>17:10 L-9-5 Preparation of a Diameter-controlled Silicon Nanowire Array by Metal Assisted Chemical Etching using Silica Nanoparticles (MAC-ES) <i>S. Kato¹, Y. Watanabe¹, Y. Kurokawa¹, A. Yamada¹, Y. Ohta², Y. Niwa² and M. Hirota², ¹Tokyo Tech and ²Nissan Res. Center (Japan)</i></p>	<p>M-9: Characterization of group IV related materials (Area 8)</p> <p>16:40 M-9-3 Analysis of Atomic Arrangement at 3C-SiC/Si(001) Interface by Aberration-Corrected Transmission Electron Microscopy <i>J. Yamasaki, S. Inamoto, H. Tamaki and N. Tanaka, Nagoya Univ. (Japan)</i></p> <p>16:55 M-9-4 (Late News) Germanium layer Transfer with Epitaxial Lift-off Technique <i>T. Maeda¹, H. Ishii¹, T. Itatani¹, T. Takada², M. Hata² and T. Yasuda¹, ¹AIST and ²Sumitomo Chemical Co., Ltd. (Japan)</i></p>	<p>N-9: Physics of spintronics devices (Area 12)</p> <p>16:40 N-9-3 Magnetic States and Minor loop analysis in Co/Cu/Co trilayer ring structures <i>A.S. Demiray¹, T. Miyawaki¹, Y. Watanabe¹, M. Kohda^{1,2} and J. Nitta¹, ¹Tohoku Univ. and ²PRESTO-JST (Japan)</i></p> <p>16:55 N-9-4 (Invited) Spin Current Generation and Utilization in Metals and Insulators <i>Eiji Saitoh, ¹Tohoku Univ., ²CREST-JST and ³ASRC-JAEA (Japan)</i></p>

RUMP SESSIONS

–September 29 (Thursday) 19:00-21:00

Session A (5F Hall 1)

“Opportunities and Challenges of Heterogeneous Integration on CMOS” -Photonics, MEMS, Sensors, etc -

Si CMOS miniaturization has brought great impacts on information and communication technologies for a long time. Miniaturization, so called More Moore, is going to down to less than 10nm, although there may be various technological difficulties and economical obstacles. Heterogeneous integration and/or integration with diverse functionalities such as photonics, MEMS (Micro Electro Mechanical Systems), sensing, etc., so called More Than Moore, is expected to open the new paradigm. In this rump session, experts of photonics, MEMS, sensing, and CMOS will discuss what is expected to be brought by heterogeneous integration, and how we should collaborate for their convergence system.

Organizer: S. Miyazaki (Nagoya Univ.)

Moderators: K. Masu (Tokyo Tech)
J. Fujikata (NEC Corp.)

Panelists: Y. Arakawa (Univ. of Tokyo)
N. Nishiyama (Tokyo Tech)
T. Seki (Omron Corp.)
T. Ohguro (Toshiba Corp.)
K. Maenaka (Univ. of Hyogo)

Session B (5F Hall 2)

“Future Roadmap for Graphene Science and Technology”

Graphene is a new class of two-dimensional materials and has a wide range of potential applications. In this rump session, panelists will propose optimistic scenarios for future graphene science and technology in several categories; quantum electronics, nanostructure, production, process, transistors, photonics, transparent electrodes, and so on. Some of the most difficult hurdles for the future will be picked up for each category, and the current challenges will be explained. By predicting how and when the hurdles are overcome in an optimistic manner, the future roadmap for graphene science and technology will be built.

Organizer: H. Yamaguchi (NTT Corp.)

Moderators: T. Otsuji (Tohoku Univ.)
H. Hibino (NTT Corp.)

Panelists: T. Ihn (ETH Zurich)
K. Nagashio (Univ. of Tokyo)
S. Sato (AIST)
S. Tanaka (Kyushu Univ.)
K. Uchida (Tokyo Tech)

SHORT COURSES

September 27, 2011, Nagoya University

=Short Course (1)=

Materials and Processing for Advanced CMOS – From Fundamentals to State-of-the-Art –

Organizer : Seiichi Miyazaki (Nagoya University)

This short course is aimed at graduated students and young researchers from both industry and academia, and world's leading experts in the field of silicon technology will lecture on the fundamental aspect and knowledge about material processing and device technologies for Si CMOS devices including the overview of technological issues and challenges in the past, today and the future. All lectures will be done in English, and all participants at SSDM 2011 are welcome.

10:00 - 11:30 **Plenary Lecture**

“3D Integration Technology and New Application”

Mitsumasa Koyanagi, New Industry Creation Hatchery Center, Tohoku University

(11:30 - 12:30 Lunch)

12:30 - 13:15 “Review on Advanced Gate Stack Technology”

Byoung Hun Lee, Gwangju Institute of Science and Technology

13:15 - 14:00 “Channel Engineering for Advanced CMOS Devices”

Shinichi Takagi, The University of Tokyo

14:00 - 14:45 “Control of Plasma-Surface Reactions for Next Generation Semiconductor Devices”

Tetsuya Tatsumi, Sony Corporation, Keio University

(14:45 - 15:00 Break)

15:00 - 15:45 “Advanced Lithography”

Shinji Okazaki, EUVA/GIGAPHOTON INC.

15:45 - 16:30 “Random Variability in Scaled MOS Transistors”

Toshiro Hiramoto, The University of Tokyo

16:30 - 17:30 Lab Tours

=Short Course (2)=

Fundamentals and Applications of Carbon Nanotube and Graphene

Organizers : Yutaka Ohno (Nagoya University)

Shintaro Sato (AIST)

This short course is intended for students and young researchers who are interested in electronics applications of carbon nanotubes and graphene. The world's leading experts in this field will lecture on their fundamental electronic structure and transport phenomena, growth and characterization techniques, device and conductor applications, together with recent progresses and future aspects. All lectures will be done in English, and all SSDM participants from overseas as well as Japan are welcome.

10:00 - 11:30 **Plenary Lecture**

“3D Integration Technology and New Application”

Mitsumasa Koyanagi, New Industry Creation Hatchery Center, Tohoku University

(11:30 - 12:30 Lunch)

12:30 - 13:15 “Electron and Phonon of Graphene Related Materials”

Riichiro Saito, Tohoku University

13:15 - 14:00 “Graphene Transport Modulated by Gate Electric field”

Kazuhiko Tsukagoshi, Hisao Miyazaki, Song-Lin Li, NIMS-MANA, CREST-JST

14:00 - 14:45 “Recent Advances in Growth and Characterization of Graphene and Nanotubes”

Hiroki Ago, Kyushu University

(14:45 - 15:00 Break)

15:00 - 15:45 “Carbon Nanotubes for VLSI: Interconnect and Transistor Applications”

Yuji Awano, Keio University

15:45 - 16:30 “Graphene Films for Electronic Applications”

Jong-Hyun Ahn, Sungkyunkwan University

16:30 - 17:30 Lab Tours

WORKSHOPS

September 27, 2011, WINC AICHI

=Workshop (1)=

Current Status and Future Prospective of Wide Gap Semiconductor Power Devices

Organizers : Hideto Miyake (Mie University)
Tatsuo Oomori (Mitsubishi Electric Corporation)

The power devices with wide bandgap semiconductors such as SiC and GaN are essentially superior to the Si device in the high breakdown electric field and the high-temperature operation. This year will be the first year when the power devices and HEMTs using SiC and GaN would come into practical applications, and the future trends are focused on. This workshop covered a broad range of areas from the crystal growth of SiC and GaN to their device applications.

13:00 - 13:45 “Seeking New Application Fields Using Group III Nitrides”
Hiroshi Amano, Nagoya University

13:45 - 14:30 “Automotive Applications of GaN Power Devices”
Tetsu Kachi and Tsutomu Uesugi, Toyota Central R&D Labs., Inc.

14:30 - 15:15 “Recent Progress of GaN HEMT for High Frequency and High Power Applications”
Masahito Kanamura, Toshihide Kikkawa, Fujitsu Labs. Ltd.

(15:15 - 15:30 Break)

15:30 - 16:15 “Progress and Future Challenges of SiC Power Devices”
Tsunenobu Kimoto, Kyoto University

16:15 - 17:00 “Development of SiC Single Crystals Growth”
Jun Kojima, Kazukuni Hara, Shoichi Yamauchi, Shoichi Onda,
R&D Partnership for Future Power Electronics Technology Research
Laboratories, DENSO CORPORATION

17:00 - 17:45 “Recent Progress of SiC Power Devices and Remaining Issues”
Tatsuo Oomori, Masayuki Imaizumi, Mitsubishi Electric Corporation

=Workshop (2)=

Recent Advancement in Printed Organic Electronics

Organizers : H. Usui (Tokyo University of Agriculture and Technology)
T. Someya (The University of Tokyo)

Rapid progress in organic electronics has been achieved in recent years, leading to promising results in the field of organic light emitting diodes (OLEDs) and organic field effect transistors (OFETs). Instead of replacing the conventional inorganic semiconductors, the final goal of organic electronics is considered to realize printed electronics, which can bring about innovative breakthrough in cost effectiveness, large scale, as well as flexibility. Although the roll-to-roll printed organic electronics have some ways to come into the market, there has been the steady progress in this area in recent years. This workshop reviews the current status and perspective of printed organic electronics especially in viewpoint of processing and application technologies.

13:00 - 13:45 “Introductory Talk and Overview of Printed Organic Electronics”
Takao Someya, The University of Tokyo

13:45 - 14:30 “Low-Temperature / High Resolution Printing Techniques for Flexible TFT Devices”
Toshihide Kamata,
National Institute of Advanced Industrial Science and Technology

14:30 - 15:15 “Flexible TFT Array by Printing Method”
Manabu Ito, Display Research Laboratory,
Technical Research Institute, Toppan Printing Co., Ltd.

(15:15 - 15:30 Break)

15:30 - 16:15 “A Rollable OLED Display Driven by OTFT”
Mao Katsuhara, Makoto Noda, Norihito Kobayashi, Akira Yumoto,
Ryouichi Yasuda, Shinichi Ushikura, Gen Yukawa, Nobukazu Hirai,
Iwao Yagi, and Kazumasa Nomoto,
Display Device Development Division, Sony Corporation

16:15 - 17:00 “Printed Electronics for Large Area Flexible Device”
Hiroki Maeda, Research & Development Center, Dai Nippon Printing Co., Ltd.

17:00 - 17:45 “Roll-to-Roll Gravure Printing Process for Penny RFID Tags”
Minhun Jung^{1,2}, Jinsoo Noh^{1,2}, Joonseok Kim^{1,2}, Kyunghwan Jung^{1,2},
Hwiwon Kang^{1,2}, ChaeminLim^{1,2}, Soyeon Kim², Kwangyong Lee¹,
Daae Kim², Dongsun Yeom², Yongsu Park¹, Minjin Lee¹,
Donghwan Kim^{1,2}, Yong-Gil Lee², Kwangyong Park² and Gyujin Cho¹,

¹Sunchon National University, ²Printed Electronics Research Institute, Paru Co., Ltd.

INSTRUCTION FOR SPEAKERS

Oral Presentation: Time Schedule

	Total session time	Presentation time	Discussion time
Plenary	45 min.	40 min.	5 min.
Invited	30 min.	25 min.	5 min.
Regular-1	20 min.	15 min.	5 min.
Regular-2	15 min.	10 min.	5 min.

BELL: First: Warning, Second: End of speech, Third: End of discussion.

Audio-Visual Equipment

The following equipments are ready at each conference meeting room during SSDM 2011:

- * LCD projector
- * PC (laptop computer), Windows XP, PowerPoint 2003-2010 and PDF
The use of personal PCs for presentations is prohibited.
- * Microphone
- * Projection laser pointer

Uploading Your Presentation

The single most important action of authors is to upload your presentation file to the PC in each session room using your own USB thumb drive. It is the presenter's responsibility to **upload the slide file as soon as possible in each session room at any break** well in advance to the session of presentation. At a short break, the PC may be too crowded to upload the file. If the chairman cannot find your presentation file at the beginning of the session, your presentation will be withdrawn.

In the presentation PC, each presenter's file should be positioned in the folder that corresponds to the session of presentation. The file must be compatible with Microsoft PowerPoint 2010 or Adobe Acrobat 9 on Microsoft Windows. Compatibility can be checked at the Speakers Room, Conference Room 1106 on 11th floor where the same PCs as in each session room are installed. Details will be informed on SSDM website at <http://www.ssdm.jp>.

Poster Presentation:

Presenting Poster

Poster sessions are scheduled for Thursday, September 29 from 13:30 to 15:00 at Exhibition Hall on 6th floor. Poster boards will be available with identifying labels. Authors are requested to prepare their posters between 10:00 and 15:00 on September 29 and remove them by 15:30 on September 29. Please note that after 16:00 all the remaining poster will be destroyed. Usable space on each poster board will be approximately 900 mm wide and 2,100 mm high. Pushpins will be available.

Each presentation will be assigned a board, labeled with the abstract number. Please display the paper title, author names and affiliations on the poster. Authors are requested to stay near by their posters during the poster session for discussions.

Short Oral Presentation for Poster Presenters

All poster presenters are required to make 2 minutes short oral presentation on September 29. The presentation time should be kept strictly to 2 minutes per poster presentation, including the time needed to move on to the next speaker. To ensure the session progresses smoothly, it is essential that these short presentations should be held in a quick, successive sequence. While one speaker is giving his/her presentation, next speakers should wait nearby in line for their turn in order to move on to the next presentation.

Please note that any absent speakers will be skipped and each presentation will be automatically stopped after 2 minutes have elapsed. Only a PC projector will be made available.

Short oral presentations will be held as follows:

- Area 1 11F 1102
- Area 2 10F 1003
- Area 3 11F 1101
- Area 4 11F 1103
- Area 5 11F 1104
- Area 6 5F Hall 1
- Area 7 12F 1201
- Area 8 12F 1207
- Area 9 12F 1202
- Area 10 10F 1002
- Area 11 11F 1107
- Area 12 12F 1208
- Area 13 12F 1203
- Area 14 12F 1204

Confidentiality:

We will delete all electronic files from the SSDM computers after presentations are completed. SSDM will not publish or distribute the presentation material.

Agreement not to pre-publication abstracts:

By submitting an abstract to the committee for review, the author(s) agrees that the work will not be published prior to the presentation at the conference. Papers found to be in breach of this agreement will be withdrawn by the conference committee.

EXHIBITION

On the days of the conference SSDM 2011 Exhibition will be held at Conference Room 1001, 10F of WINC AICHI. The show will feature the displays of the latest products of the following exhibitors. Complementary coffee service will be available at the Room 1001 during the intermissions of the technical sessions.

Exhibitors:

ELIONIX INC

HiSOL, Inc.

JEOL Ltd.

NTT Microsystem Integration Laboratories

R-DEC Co., Ltd.

SILVACO, Inc.

TNS Systems LLC

Tokai Region Nanotechnology Manufacturing Cluster

Show dates and hours:

September 28 : 8:30 - 18:00

September 29 : 8:30 - 19:00

September 30 : 8:30 - 14:00

AUTHOR INDEX

- A**
- Abe, D. ----- P-8-15, P-12-8
Abe, Y. ----- A-1-4
Abe, Y. ----- L-2-6
Abe, Y. ----- P-14-9
Adachi, K. ----- I-1-1
Adachi, M. ----- P-1-5
Adam, T. ----- D-7-1, M-8-7
Adamo, C. ----- P-12-7
Adari, R. ----- P-6-5
Adelmann, C. ----- F-7-2
Advincula, R. C. ----- B-2-3
Afanasiev, V. V. ----- F-2-3
Agarwal, S. ----- P-8-20
Ago, H. ----- KM-6-5
Ahmet, P. ----- E-3-1, E-3-2, P-1-11
Ahn, C. ----- F-6-2
Ahn, J. H. ----- KM-7-1
Ahn, J. H. ----- P-1-9
Ahn, S. ----- N-8-3
Aihara, T. ----- L-1-2
Aikawa, S. ----- K-3-4
Airey, R. ----- I-9-3, L-1-1
Ajmal Khan, M. ----- L-3-3
Akabori, M. ----- A-1-6, A-8-6
Akagi, T. ----- H-3-3, H-4-4, H-6-2, H-6-6
Akahane, K. ----- I-9-2, P-8-2
Akasaka, T. ----- M-1-4
Akiho, T. ----- N-7-4, P-12-9
Akita, S. ----- KM-7-4, P-13-22
Akiyama, T. ----- BL-2-6, P-8-24, P-10-18
Alam, M. A. ----- D-8-1
Alexander ----- P-8-11
Algul, B. P. ----- K-2-4
Allegret-Maret, S. ----- D-7-1
Altimime, L. ----- F-2-3, F-7-2
Amaha, S. ----- J-7-2
Amakawa, S. ----- G-5-3
Amano, H. ----- AL-6-5, P-6-4, P-13-7
Amemiya, Y. ----- G-6-2
Amemiya, Y. ----- CI-6-5, P-7-22
Amm, Y. ----- P-7-17
An, H. ----- B-3-2, K-8-3, P-13-20
An, H. M. ----- P-4-2
Anda, Y. ----- A-1-2
Ando, K. ----- H-4-3
Ando, K. ----- N-7-2, P-12-15
Ando, Y. ----- N-6-2
Andoh, M. ----- GH-1-2
Andrieu, F. ----- E-2-1
Ansari, T. ----- G-3-2
Ante, F. ----- B-3-4
Anwar, M. ----- J-7-4
Anzai, A. ----- G-6-1
Ao, J. P. ----- P-6-10
Aoki, N. ----- P-13-24
Aoki, N. ----- BL-2-7
- Aomori, S.** ----- B-9-2
Aoyagi, S. ----- P-11-9
Aoyagi, Y. ----- P-7-6
Arafune, K. ----- L-9-3, P-14-1, P-14-2
Arai, S. ----- I-1-2
Arakawa, T. ----- D-8-3
Arakawa, T. ----- I-1-3, P-7-17
Arakawa, Y. ----- B-9-2, CI-6-3, I-8-2, I-9-1, J-6-4, J-7-1, P-1-6, P-13-6
- Arie, H.** ----- C-4-3
Arie, T. ----- KM-7-4, P-13-22
Arikawa, M. ----- J-4-1, N-8-6
Arima, Y. ----- GH-1-3
Arimoto, H. ----- E-2-3, P-1-10, P-3-18
Arimoto, K. ----- D-1-3
Arimoto, Y. ----- P-2-3
Arita, M. ----- P-9-17
Ariyoshi, T. ----- GH-1-3
Arricca, B. ----- H-7-4L
Aryal, H. R. ----- P-8-7
Asada, H. ----- P-5-15
Asahi, H. ----- J-8-5, P-8-15, P-12-8
Asakawa, K. ----- P-8-1
Asano, H. ----- N-6-4, P-12-4, P-12-6
Asano, K. ----- C-9-1
Asano, T. ----- C-5-3, K-2-3, M-8-1, M-8-3, P-2-11
Asano, T. ----- E-6-4
Asano, T. ----- P-10-11
Asheghi, M. ----- F-6-2
Ashida, Y. ----- L-8-2, L-8-3, P-14-18
Ashikari, N. ----- P-11-1
Atwater, H. A. ----- I-3-1
Austing, D. G. ----- J-7-2
Avramov, P. V. ----- P-13-11
Azuma, H. ----- P-14-13
Azuma, Y. ----- J-7-5
Azumaishi, N. ----- A-8-3, AL-7-2
- B**
- Baba, A.** ----- B-5-1, B-5-3, BL-2-7
Baba, A. ----- GH-1-3
Baba, M. ----- L-3-3
Baba, T. ----- I-2-1
Badrutdinov, A. O. ----- J-7-1
Bae, H. J. ----- D-6-4
Bae, M. ----- I-4-3L
Baek, C. K. ----- P-13-2
Baek, D. J. ----- P-11-5
Baek, K. H. ----- B-3-3
Baek, R. H. ----- P-13-2
Bakar, S. A. ----- M-2-6
Ball, M. ----- F-2-1
Banerjee, D. ----- P-6-5
Banerjee, W. ----- F-8-4
Bang, K. H. ----- I-4-4L
Barnham, K. ----- L-1-1
Baudot, S. ----- E-2-1
- Bauer, S.** ----- B-9-4
Bea, J. C. ----- C-5-2, C-8-3, CI-7-2
Beasley, C. ----- C-1-4
Beck, A. ----- K-2-6
Bedell, S. W. ----- M-8-7
Bellenger, F. ----- E-1-1
Ben Jamaa, H. ----- C-1-1
Bender, H. ----- F-7-2
Beppu, N. ----- P-3-21L
Berg, M. ----- KM-4-3L
Bergman, J. ----- A-2-1
Berliner, N. ----- E-4-3, E-9-2, D-7-1
Beyer, G. ----- C-3-1
Biermann, K. ----- J-6-1
Bird, J. P. ----- P-13-24
Biyani, M. ----- H-6-6
Blonkowski, S. ----- P-1-15
Boeuf, F. ----- D-1-1, D-1-2
Bolotov, L. ----- E-2-3
Borg, M. ----- KM-4-3L
Bosu, S. ----- N-6-1
Bousslama, W. ----- P-7-21
Bouzazi, B. ----- L-1-5
Bown, M. ----- B-1-6
Brar, B. ----- A-2-1
Brillson, L. F. ----- P-4-13L
Brunet, L. ----- E-2-1
Brus, S. ----- F-7-2
Bryant, A. ----- D-7-1
Bu, C. H. ----- AL-6-6
Bu, Q. ----- P-5-15
Budiman, M. F. ----- H-7-3
Bugnicourt, L. ----- P-11-12
Buitelaar, M. R. ----- J-7-5
Byun, W. ----- P-5-17
- C**
- Cabrera, V.** ----- B-8-4
Cacho, F. ----- D-8-2
Cai, J. ----- D-7-1
Cai, S. J. ----- AL-7-1
Cantoro, M. ----- P-4-6
Carius, R. ----- L-2-1
Cassan, E. ----- CI-6-2
Cassé, M. ----- E-2-1
Cathignol, A. ----- D-8-2
Caubet, P. ----- E-2-1
Caymax, M. ----- E-1-1
Carreira, A. ----- B-8-4
Ceric, H. ----- P-3-4
Cha, E. ----- F-6-3
Chan, A. ----- L-1-1
Chang, C. H. ----- P-14-4
Chang, C. J. ----- L-8-4
Chang, C. S. ----- D-5-3
Chang, C. Y. ----- I-2-4, KM-5-3, L-8-4, M-1-6, P-4-9, P-7-2, P-7-8
Chang, C. Y. ----- P-3-3
Chang, E. Y. ----- P-6-9
Chang, H. C. ----- H-3-1
Chang, H. J. ----- BL-1-6
Chang, J. R. ----- KM-5-3, M-1-6, P-7-2, P-7-8
Chang, K. Y. ----- P-11-2
Chang, M. F. ----- G-4-1
Chang, S. J. ----- P-3-3, P-3-6, P-7-1, P-8-22
Chang, S. P. ----- I-2-4, M-1-6, KM-5-3, P-7-2, P-7-3, P-7-8
Chang, S. P. ----- P-8-22
Chang, T. C. ----- P-4-9
Chang, W. H. ----- F-8-3
Chang, Y. ----- I-4-4L
Chang, Y. F. ----- P-4-9
Chang, Y. T. ----- P-7-13
Chang, Y. W. ----- F-3-2
Chao, C. H. ----- P-9-12
Chao, T. S. ----- F-5-3
Chao, Y. C. ----- B-3-5
Charbonnier, M. ----- E-2-1
Chaysakul, P. ----- CI-6-2
Che, S. ----- P-7-18
Chen, B. ----- F-7-3
Chen, B. Y. ----- P-3-7
Chen, C. ----- C-8-5
Chen, C. ----- P-14-6
Chen, C. C. ----- I-2-4
Chen, C. D. ----- H-6-5
Chen, C. H. ----- F-5-1
Chen, C. H. ----- I-2-5
Chen, C. H. ----- P-1-20L
Chen, C. H. ----- P-7-29
Chen, C. H. ----- P-14-3
Chen, C. S. ----- P-7-10
Chen, D. ----- P-1-12
Chen, F. ----- P-4-8
Chen, F. T. ----- F-6-4, F-9-1, F-9-2, P-4-16L
Chen, G. Y. ----- CI-6-4, P-7-30
Chen, H. ----- AL-7-1
Chen, H. B. ----- L-8-4
Chen, H. C. ----- P-14-8
Chen, H. H. ----- F-5-1
Chen, H. H. ----- P-7-13
Chen, H. J. ----- BL-1-5, BL-1-7, BL-2-4, M-2-4, P-2-13
Chen, H. M. ----- P-8-14
Chen, H. Y. ----- C-1-4
Chen, J. ----- P-4-12
Chen, J. F. ----- P-3-3
Chen, J. F. ----- P-7-5, P-9-12
Chen, K. C. ----- F-3-2
Chen, K. F. ----- F-3-2
Chen, K. J. ----- AL-7-1
Chen, K. J. ----- P-8-22
Chen, K. M. ----- P-3-7
Chen, K. Y. ----- P-6-7
- Chen, L.** ----- N-6-5, P-12-3
Chen, L. L. ----- P-1-19L, P-2-18L
Chen, M. S. ----- F-3-2
Chen, M. S. ----- P-3-3
Chen, M. Y. ----- P-3-7
Chen, N. C. ----- P-7-5
Chen, P. ----- P-14-16
Chen, P. C. ----- G-4-1
Chen, P. S. ----- P-4-8
Chen, P. ZP. ----- F-5-1
Chen, R. C. C. ----- P-9-12
Chen, S. ----- P-6-4
Chen, S. L. ----- H-7-4L
Chen, S. T. ----- F-5-3
Chen, T. ----- A-5-3, L-2-1
Chen, T. G. ----- P-14-4, P-14-5
Chen, T. M. ----- P-14-16
Chen, T. P. ----- P-8-22
Chen, W. C. ----- L-8-4
Chen, W. F. ----- BL-1-6
Chen, W. S. ----- F-6-4, F-9-1, F-9-2, P-4-16L
Chen, W. Y. ----- M-1-6
Chen, X. ----- B-7-5, BL-1-2, BL-2-5
Chen, Y. ----- F-7-3
Chen, Y. C. ----- B-4-3
Chen, Y. C. ----- F-7-1, P-4-7
Chen, Y. C. ----- I-9-5
Chen, Y. C. ----- KM-5-3, M-1-6, P-7-2, P-7-8
Chen, Y. C. ----- P-7-2
Chen, Y. F. ----- P-8-18
Chen, Y. J. ----- F-3-2
Chen, Y. S. ----- P-4-8
Chen, Y. Y. ----- F-7-2
Chen, Y. Y. ----- P-4-7
Cheng, B. S. ----- I-2-5
Cheng, C. F. ----- P-7-29
Cheng, C. M. ----- L-1-4
Cheng, C. Y. ----- D-5-2
Cheng, H. C. ----- P-8-20
Cheng, H. M. ----- K-1-1
Cheng, H. W. ----- P-3-22L
Cheng, I. F. ----- H-3-1
Cheng, K. ----- D-7-1, E-9-2
Cheng, O. ----- P-3-3, P-3-6
Cheng, S. J. ----- J-6-3
Cheng, S. S. ----- BL-1-6
Cheng, Y. C. ----- P-3-3
Cheramy, S. ----- C-1-1
Chi, L. ----- P-11-2
Chi, Y. C. ----- P-9-12
Chiang, C. H. ----- P-9-12
Chiang, C. K. ----- A-5-5, P-1-18
Chiang, M. H. ----- P-3-13
Chiashi, S. ----- K-3-4
Chiba, D. ----- N-9-2
Chien, W. C. ----- F-7-1, P-4-7
Chikyow, T. ----- E-2-2, P-14-1

Childs, D. T. D. ----- I-2-2, I-9-3, I-9-4
Chin, A. F. D. ----- P-3-15
Chin, S. K. ----- J-3-3
Chiu, C. H. ----- I-2-4, I-2-5, P-7-3
Chiu, C. S. ----- P-3-7
Chiu, C. W. ----- P-8-10, P-8-14
Chiu, H. C. ----- P-6-7
Chiu, K. E. ----- P-7-28
Chiu, P. F. ----- G-4-1
Chiu, T. T. ----- I-2-3
Chiu, Y. Y. ----- P-3-22L
Cho, C. H. ----- KM-7-2, P-1-16
Cho, H. J. ----- P-13-19
Cho, J. H. ----- KM-7-1
Cho, M. H. ----- F-2-4
Cho, S. M. ----- AL-7-3
Cho, W. J. ----- P-4-2, P-4-3, P-11-8
Choi, C. H. ----- P-1-9
Choi, D. Y. ----- P-6-1
Choi, G. ----- F-8-2
Choi, H. ----- P-5-7
Choi, J. B. ----- J-4-2
Choi, J. W. ----- B-3-2
Choi, K. H. M. ----- P-5-7
Choi, M. ----- B-8-3
Choi, R. ----- P-1-9
Choi, S. J. ----- P-11-5
Choi, S. Y. ----- B-3-3
Choi, Y. H. ----- I-4-4L
Choi, Y. K. ----- P-11-5
Choi, Y. S. ----- P-5-7
Choki, K. ----- I-1-2
Chong, T. C. ----- P-4-11
Chong, L. H. ----- F-3-2
Chou, C. H. ----- F-5-1
Chou, F. P. ----- CI-6-4, P-7-30
Choudhury, S. H. ----- F-8-5
Chrisman, G. ----- C-8-2
Chu, C. J. ----- H-6-5
Chu, P. J. ----- P-6-7
Chuang, A. T. H. ----- P-4-7
Chuang, C. C. ----- P-5-16
Chuang, C. H. ----- B-1-3
Chuang, C. H. ----- G-4-1
Chuang, F. T. ----- P-7-13
Chun, K. ----- GH-2-1
Chun, S. H. ----- P-8-8
Chung, C. C. ----- H-3-1
Chung, C. H. ----- B-3-5
Chung, S. S. ----- D-5-2, F-5-1
Clarke, E. ----- I-9-3
Clima, S. ----- F-7-2
Climente, J. I. ----- J-6-3
Colinge, J. P. ----- P-3-12
Connell, J. ----- KM-4-1
Contera, S. A. ----- P-11-12
Contreras-Guererro, R. ----- M-2-5
Croes, K. ----- C-4-1
Cuong, N. T. ----- P-13-10

D

Daikyo, Y. ----- P-2-14
Das, S. K. ----- BL-2-2
De Gendt, S. ----- P-4-6
De Jaeger, B. ----- E-1-1
De Meyer, K. ----- E-1-1
De Raedt, W. ----- C-5-4
DeHaven, P. W. ----- E-4-3
Debusschere, I. ----- F-2-3
Degraeve, R. ----- F-7-2
Deguchi, M. ----- L-9-1
Dehdashti Akhavan, N. ----- P-3-12
Deki, H. ----- I-8-1
Dekkers, H. ----- C-3-1, H-7-2
Delcroix, P. ----- P-1-15
Demarest, J. ----- D-7-1
Demarest, J. J. ----- E-4-3
Demiray, A. S. ----- N-9-3
Deora, S. ----- D-8-1
Destefanis, V. ----- E-9-2
Detalle, M. ----- C-3-1
Devriendt, K. ----- F-7-2
Dewan, K. ----- G-5-4L
Di Cioccio, L. ----- C-1-1
Diekmann, C. ----- C-5-4
Dietl, M. ----- G-5-4L
Do, L. M. ----- B-3-3
Dobbie, A. ----- M-8-6
Doi, T. K. ----- P-2-3
Domenicucci, A. G. ----- E-7-4
Doris, B. ----- D-7-1, E-9-2
Dröschner, S. ----- J-3-1
Droopad, R. ----- M-2-5
Du, A. ----- A-2-3
Du, G. ----- P-3-14, P-3-19, P-4-12
Du, W. ----- L-3-3
Dube, A. ----- D-7-1
Duy, D. Q. ----- P-10-15

E

Eaves, L. ----- J-5-3
Edge, L. F. ----- D-7-1
Egard, M. ----- KM-4-3L
Egawa, T. ----- AL-7-5, P-6-4, P-8-7
Eggs, C. ----- C-5-4
Egusa, H. ----- I-1-6
Einarsson, E. ----- K-3-4
Ekins-Daukes, N. ----- L-1-1
Elhouichet, H. ----- P-7-21
Elm, M. T. ----- P-12-1
Emura, S. ----- J-8-5, P-12-8
Endo, K. ----- E-9-3, F-4-3, P-1-1
Endo, T. ----- B-7-2
Endoh, T. ----- F-1-2, F-1-3, F-1-4, F-2-5, F-3-3, J-4-1, N-8-2, N-8-4, N-8-6, P-3-11, P-5-4, P-5-10, P-12-12
Ensslin, K. ----- J-3-1
Enta, Y. ----- KM-6-2

Entani, S. ----- P-13-11
Estrada, M. ----- B-8-4

F

Fagas, G. ----- P-3-12
Fan, M. L. ----- P-3-1
Farrell, D. ----- L-1-1
Faynot, O. ----- E-9-2
Fédéli, J. M. ----- CI-6-2
Federspiel, X. ----- D-8-2
Feng, L. W. ----- P-4-9
Feng, W. ----- D-7-3
Feng, Z. H. ----- AL-7-1
Fenouillet-Béranger, C. ----- E-2-1
Ferain, I. ----- P-3-12
Ferid, M. ----- P-7-21
Finger, F. ----- L-2-1
Fiore, A. ----- P-12-16L
Fiorini, P. ----- H-6-3, H-6-4
Fischer, S. ----- B-6-6
Fischer, M. ----- P-12-1
Flaitz, P. L. ----- E-7-4
Fons, P. ----- F-6-1
Freed, R. ----- H-7-2
Fu, G. L. ----- G-5-1
Fu, S. W. ----- BL-1-5, BL-1-7, BL-2-4, M-2-4, P-2-13
Fu, Y. ----- F-7-3
Fu, Y. J. ----- P-7-26
Führer, M. ----- L-1-1
Fujigaya, T. ----- K-2-3
Fujii, A. ----- P-10-2, P-10-15
Fujii, M. ----- A-5-3
Fujii, S. ----- F-5-2
Fujii, S. ----- J-5-4, P-8-12
Fujii, T. ----- C-8-4, P-2-5
Fujikata, J. ----- CI-6-3, P-1-6
Fujimaki, A. ----- J-8-4
Fujimatsu, M. ----- A-4-1
Fujimoto, K. ----- P-10-7
Fujimura, M. ----- I-3-4
Fujioka, H. ----- A-8-4
Fujisawa, T. ----- J-7-3, J-8-6L
Fujishima, M. ----- D-1-5
Fujita, H. ----- P-12-6
Fujita, K. ----- B-1-2, B-4-1
Fujita, K. ----- P-8-7
Fujita, Y. ----- M-8-2
Fujiwara, A. ----- J-5-2, K-3-2
Fujiwara, H. ----- P-5-12
Fujiwara, K. ----- M-2-1
Fujiwara, M. ----- I-1-2
Fukami, S. ----- N-9-2
Fukamizu, S. ----- L-3-2, P-14-9
Fukano, H. ----- I-1-6, P-7-23
Fukatani, N. ----- P-12-6
Fukaya, Y. ----- P-10-6
Fukazawa, A. ----- P-1-14
Fukidome, H. ----- KM-6-2

Fukuda, H. ----- P-1-14
Fukuda, K. ----- B-6-6
Fukuda, K. ----- E-2-3
Fukuda, K. ----- AL-6-3
Fukuda, N. ----- P-11-6
Fukuda, T. ----- B-5-4, P-10-11
Fukuhara, N. ----- E-8-3
Fukui, T. ----- D-4-3, KM-4-2, P-3-10, P-13-4
Fukuma, M. ----- PL-1-1
Fukuoka, D. ----- J-6-2
Fukuoka, N. ----- P-10-15
Fukuoka, T. ----- P-1-17
Fukushima, A. ----- L-2-6
Fukushima, A. ----- N-8-5
Fukushima, T. ----- C-5-2, C-8-3, CI-7-2, G-4-2, H-4-2, I-1-2, P-2-2, P-5-5, P-11-3
Fukuyama, A. ----- L-1-2
Fukuyama, M. ----- CI-6-5, P-7-22
Fullam, J. ----- E-9-2
Furnak, T. ----- AL-6-4
Funatsu, T. ----- H-3-3
Furube, A. ----- B-5-4
Furukawa, K. ----- H-7-1
Furuse, S. ----- M-3-4
Furutake, N. ----- C-3-3
Furutani, R. ----- CI-6-5
Furuya, K. ----- P-7-16

G

Gambino, J. ----- C-8-2
Ganguly, S. ----- P-6-5
Gao, B. ----- F-7-3
Gao, S. ----- C-5-1
Garros, X. ----- E-2-1
Gaubert, P. ----- P-3-16
Gaufres, E. ----- K-2-6
Gelloz, B. ----- L-2-5, P-7-21
Ghalamestani, S. G. ----- KM-4-3L
Ghibaudo, G. ----- D-1-1, D-1-2
Ghosh, P. ----- P-13-26
Giavaras, G. ----- P-13-17
Givan, U. ----- KM-4-1
Goh, K. H. ----- D-4-4
Gong, X. ----- A-2-4
Goodson, K. E. ----- F-6-2
Goto, H. ----- J-3-2, J-3-4
Goto, H. ----- P-5-12
Gotoh, H. ----- J-5-1, P-13-5
Goux, L. ----- F-7-2
Govoreanu, B. ----- F-7-2, P-4-6
Grella, L. ----- H-7-2
Grenouillet, L. ----- E-9-2
Groom, K. M. ----- I-2-2
Gu, P. Y. ----- P-4-8
Gunji, Y. ----- J-6-2
Guo, H. X. ----- A-8-5
Guo, J. C. ----- D-5-3, G-7-2
Guo, P. ----- D-4-4
Gupta, J. ----- J-7-2

Gurugubelli, V. K. ----- P-13-8
Güttinger, J. ----- J-3-1
Gyanathan, A. ----- P-4-10

H

Haas, S. ----- B-9-3
Hagino, T. ----- P-13-14
Hahm, S. H. ----- P-6-3
Hamada, K. ----- P-9-17
Hamano, J. ----- P-14-2
Hamasaka, K. ----- C-9-3
Hamaya, K. ----- E-5-3
Hamazaki, R. ----- L-3-2
Hammond, J. S. ----- KM-4-1
Han, G. ----- D-4-4
Han, H. W. ----- L-2-4
Han, I. K. ----- P-2-6
Han, J. U. ----- F-4-2
Han, K. ----- P-1-12
Han, L. F. ----- N-6-5
Han, S. K. ----- P-5-7
Han, T. T. ----- F-3-2
Han, X. ----- P-8-17
Han, Y. ----- P-9-20L
Hanada, T. ----- M-1-2
Hanafusa, H. ----- M-8-5
Hanawa, K. ----- P-2-3
Handa, H. ----- KM-6-2
Hane, M. ----- C-3-3
Hanyu, T. ----- F-1-2, F-1-4, N-8-2, N-8-4, P-12-12
Hara, A. ----- P-1-13
Hara, K. ----- F-7-3
Hara, K. ----- C-5-1
Hara, K. O. ----- L-3-4
Hara, S. ----- KM-5-2, KM-5-4, P-12-1, P-13-1
Harada, H. ----- L-9-3
Harada, M. ----- N-7-4, P-12-9
Harada, N. ----- AL-7-2
Harada, S. ----- P-8-11
Harada, S. ----- P-14-18
Harada, Y. ----- P-9-11
Haran, B. ----- D-7-1, E-9-2
Harigai, N. ----- P-5-13
Harley, E. C. T. ----- E-7-4
Hasebe, T. ----- P-11-7
Hasegawa, M. ----- KM-6-4
Hasegawa, R. ----- AL-6-5
Hasegawa, S. ----- P-8-15, P-12-8
Hasegawa, T. ----- B-6-1, B-9-3
Hashiba, H. ----- L-9-1
Hashiguchi, H. ----- C-8-3
Hashiguchi, H. ----- E-7-3, E-9-3
Hashimoto, H. ----- P-5-5
Hashimoto, Y. ----- P-9-6
Hashisaka, M. ----- J-7-3, J-8-6L
Hashizume, T. ----- A-8-3, AL-7-2
Hasko, D. G. ----- J-4-2
Haspelslagh, L. ----- H-6-3, H-7-2
Hata, M. ----- E-8-3, E-8-4, E-8-5, M-9-4L

Hatakeyama, N.	P-14-7	Hirose, S.	P-14-7	Hsu, W. C.	P-3-13	I		Inoue, S.	P-2-5
Hatanaka, T.	G-4-3	Hirose, T.	P-5-9	Hsu, Y. C.	KM-5-3, M-1-6, P-7-8	Ichikawa, H.	B-4-1	Inoue, T.	I-3-4
Hatano, K.	B-5-4	Hirose, Y.	C-4-3	Hsu, Y. H.	B-3-5	Ichikawa, O.	E-8-3	Inoue, T.	P-9-11
Hatano, T.	J-7-2	Hirota, M.	L-9-5	Hsu, B.	KM-6-5	Ichikawa, T.	P-10-17	Inukai, M.	C-1-2, C-1-3
Hatsugai, Y.	J-4-1, N-8-6	Hiruma, A.	L-8-3	Hu, M.	P-3-2	Ichiki, T.	H-3-3, H-4-4, H-6-2, H-6-6	Irikawa, J.	L-2-3
Hattori, A.	M-2-1	Ho, C. L.	BL-1-6	Hu, V. P. H.	J-4-3	Ichimura, M.	P-14-20	Irisawa, T.	D-6-2, E-8-6
Hattori, N.	A-5-2	Ho, M. S.	G-4-1	Hu, W.	H-7-3	Ida, M.	A-2-2	Isaji, Y.	P-7-9
Hattori, N.	C-4-3	Hogg, R. A.	I-2-2, I-9-3, I-9-4, P-8-1	Hu, W.	M-3-7	Ide, T.	C-4-3	Ishibashi, S.	N-8-5
Hattori, T.	E-3-1, E-3-2, P-1-11	Hoguet, D.	D-1-2	Hu, Z. S.	P-8-22	Ido, T.	I-8-4, I-8-5	Ishibashi, T.	I-1-5
Hattori, T.	I-3-2	Hohjo, T.	N-6-4	Hua, M. Y.	H-7-4L	Ifuku, R.	K-8-2	Ishida, A.	P-7-9
Hattori, T.	P-1-8	Holt, J. R.	E-7-4	Huang, C. F.	P-6-7	Iga, F.	F-1-2, F-1-4, N-8-4	Ishida, K.	P-10-3
Hayase, S.	BL-2-2	Hon, S. J.	P-7-1	Huang, C. H.	A-8-4	Igarashi, M.	H-7-3	Ishida, M.	A-1-2
Hayashi, S.	M-8-2	Honda, S.	P-12-11	Huang, C. H.	H-7-4L	Iguchi, K.	P-9-19	Ishida, M.	I-9-1
Hayashi, T.	P-10-15	Honda, U.	P-6-11	Huang, C. H.	P-11-11	Ihn, T.	J-3-1	Ishida, M.	GH-2-3
Hayashi, Y.	C-3-3	Honda, Z.	B-5-4, P-10-11	Huang, C. T.	I-9-5	Iida, R.	D-4-1	Ishida, S.	I-8-2
Hayashi, Y.	K-1-6	Hong, T. J.	P-4-7	Huang, C. T.	P-3-6	Iijima, M.	AL-6-3	Ishidzuka, S.	KM-6-4
Hayashi, Y.	M-9-2	Hong, Y. J.	KM-4-2	Huang, C. Y.	B-4-3	Iijima, T.	K-9-4	Ishigaki, T.	C-8-2
Hayashi, Y.	P-10-16, P-13-26	Hongo, S.	P-2-1	Huang, C. Y.	P-5-6	Iino, R.	H-4-3	Ishihara, N.	D-1-4, G-5-2, G-5-3, G-7-3
Hayashida, T.	E-9-3, F-4-3	Hori, M.	C-1-5L, C-9-1, K-1-2, L-2-6, P-6-4, P-8-3, P-13-14, P-13-19	Huang, G. W.	P-3-7	Iiyama, K.	P-7-27	Ishihara, R.	A-5-3
Hayazawa, N.	M-9-1	Hori, T.	P-10-15	Huang, H. Y.	A-5-5, P-1-18	Iizuka, R.	H-3-3	Ishii, H.	M-9-4L
He, H.	D-7-1	Hori, Y.	A-8-3	Huang, I. J.	F-3-2	Iizuka, T.	D-8-3	Ishii, K.	P-9-3
He, J.	D-8-3	Horie, K.	G-7-4	Huang, J. B.	P-7-5	Ikari, T.	L-1-2	Ishii, M.	K-8-6L
He, S.	G-7-4	Horie, S.	P-10-3	Huang, J. J.	F-8-3	Ikawa, Y.	P-6-10	Ishii, S.	P-13-28
He, Y.	P-14-17	Horiguchi, M.	G-6-1	Huang, J. K.	I-2-4	Ikebe, M.	G-6-2	Ishii, Y.	H-3-2
Hernández-Mínguez, A.	J-6-1	Horiguchi, N.	E-1-1	Huang, J. L.	BL-2-3	Ikeda, A.	C-5-3	Ishikawa, F.	M-3-4, P-7-12, P-7-19, P-7-20
Hettiarachchi, R.	D-7-3	Horiguchi, N.	E-1-1	Huang, J. R.	G-7-2	Ikeda, K.	D-2-1, D-6-2	Ishikawa, K.	L-2-6, P-6-4, P-8-3, P-13-14, P-13-19, C-9-1
Hey, R.	J-6-1	Horikawa, T.	CI-6-3, P-1-6	Huang, K. M.	BL-1-6	Ikeda, K.	P-14-11, P-14-12	Ishikawa, M.	GH-1-1
Heya, A.	P-1-17, P-4-4	Horikoshi, Y.	A-4-4	Huang, P.	F-7-3	Ikeda, K.	KM-6-5	Ishikawa, T.	D-7-2
Heylen, N.	F-7-2	Horioka, T.	BL-2-1	Huang, P. C.	P-3-3	Ikeda, M.	B-3-4, B-6-6, B-7-2, B-8-6	Ishikawa, T.	GH-2-2
Heyns, M.	E-1-1, P-4-6	Horita, M.	A-5-2, A-5-3, P-11-13	Huang, P. W.	P-1-20L	Ikeda, M.	I-8-1	Ishikawa, T.	A-5-2, A-5-3, P-11-13
Hibino, H.	K-9-1, KM-6-3, KM-6-5, P-8-6	Horn, K.	KM-6-2	Huang, R. M.	D-5-2	Ikeda, N.	I-2-2, P-8-1	Ishikawa, Y.	E-9-3, F-4-3
Higaki, T.	A-5-1	Hoshi, T.	A-2-2	Huang, S. C.	B-1-3	Ikeda, S.	F-1-2, F-1-4, N-8-4	Ishikawa, Y.	I-8-3, I-8-6
Higashi, K.	P-8-15, P-12-8	Hoshi, Y.	L-3-4	Huang, S. M.	J-7-1	Ikejiri, K.	P-13-4	Ishikawa, Y.	GH-2-5
Higashi, S.	M-8-2, P-1-4	Hoshii, T.	E-8-3, E-8-4, E-8-5	Huang, S. Y.	P-7-13	Ikenaga, E.	C-1-2, C-1-3	Ishikawa, Y.	B-3-1
Higashi, T.	P-10-2	Hosokawa, T.	P-6-10	Huang, T. H.	BL-1-6	Ikeno, N.	P-14-1	Ishiwara, H.	N-9-2
Higo, A.	P-7-18	Hotani, T.	P-7-14	Huang, T. K.	P-2-8	Ikenoue, H.	P-8-13	Ishiwata, N.	P-9-8
Higuchi, K.	F-8-1	Hotta, S.	P-10-6	Huang, T. Y.	P-3-9	Ikuta, Y.	B-2-5	Islam, A. E.	D-8-1
Higuchi, Y.	P-8-9	Hou, C. Y.	P-1-19L	Huang, W. K.	P-7-30	Im, K. S.	AL-6-6, P-6-2	Isono, K.	P-5-9
Hijioka, K.	C-3-3	Hou, T. H.	F-8-3	Huang, Y. C.	A-5-5	Imaeda, H.	P-13-28	Isshiki, H.	I-5-2, I-5-3
Himukashi, T.	D-5-4	Housayama, K.	K-2-1	Huang, Y. C.	AL-7-4	Imafuku, W.	G-3-2	Isu, T.	I-4-2, I-5-1
Hinogami, R.	L-9-1	Hozhida, T.	D-8-3	Huang, Y. C.	P-8-20	Imai, A.	A-1-4	Itabashi, S.	CI-7-1, I-8-6
Hirai, D.	K-2-2	Hozumi, H.	KM-6-4	Huguenin, J. L.	D-1-1	Imai, S.	P-13-4	Itatani, T.	M-9-4L
Hirai, T.	B-1-6	Hsiao, C. Y.	BL-1-5, BL-1-7, BL-2-4, M-2-4, P-2-13	Hugues, M.	I-9-4	Imaizumi, K.	KM-6-2	Ito, H.	B-6-2, B-6-4
Hirai, Y.	P-7-20	Hsieh, E. R.	D-5-2	Hung, C.	P-4-1	Imazawa, T.	P-11-13	Ito, H.	D-1-4, G-5-2, G-5-3, G-7-3
Hiraiwa, T.	P-12-11	Hsieh, K. Y.	F-7-1	Hung, C. T.	P-7-11	Inada, A.	D-7-1	Ito, K.	C-9-3, C-9-4
Hirakawa, Y.	P-5-14	Hsieh, M. C.	P-7-5, P-9-12	Hung, F. Y.	P-8-22	Inagaki, K.	P-12-6	Ito, M.	J-8-4
Hiraki, M.	G-6-1	Hsieh, T. M.	F-5-1	Hung, K. T.	BL-1-5, BL-1-7, BL-2-4, M-2-4, P-2-13	Inagaki, M.	P-8-17, P-14-11, P-14-12	Ito, S.	P-2-4
Hirama, K.	A-1-3	Hsieh, W. F.	M-2-2	Hurkx, G. A. M.	F-6-2	Inamoto, S.	M-9-3	Ito, T.	G-6-1
Hiramatsu, M.	K-1-2	Hsin, Y. M.	CI-6-4, P-7-30	Hwang, D. H.	P-13-9	Inden, T.	P-10-1, P-10-10	Ito, T.	P-8-12
Hiramoto, T.	D-6-3	Hsu, C. H.	M-2-2	Hwang, E. J.	AL-7-3	Inokawa, H.	K-8-6L, P-7-24, P-7-25	Ito, Y.	B-1-7L
Hirano, I.	E-2-4	Hsu, C. P.	P-7-7	Hwang, H.	F-6-3, F-8-2, F-8-5	Inoue, A.	B-9-5	Ito, Y.	I-1-2
Hiraoka, M.	H-6-3	Hsu, C. W.	F-8-3	Hwang, H. J.	KM-7-2, P-1-16	Inoue, J.	P-12-11	Ito, Y.	KM-6-5
Hirase, M.	I-8-3	Hsu, C. W.	P-8-18	Hwang, J. W.	P-10-20L	Inoue, K.	K-1-4, KM-7-3, K-9-2	Itoh, E.	P-10-12, P-10-13, P-10-14
Hirata, I.	B-3-4	Hsu, C. Y.	P-6-9	Hwang, S. M.	I-4-4L	Inoue, K.	P-10-18	Itoh, H.	P-12-2
Hirata, S.	A-1-5	Hsu, H. M.	G-5-1	Hwang, S. W.	P-13-9	Inoue, K.	P-14-21L	Itoh, H.	P-12-11
Hirate, M.	B-6-2	Hsu, K. S.	I-2-3	Hylton, N.	L-1-1	Inoue, K.	GH-1-4	Itoh, K. M.	H-7-3
Hirayama, Y.	J-6-2	Hsu, S. S. H.	AL-7-4, P-2-8, P-6-7			Inoue, M.	A-5-1	Itoh, S.	GH-1-2
Hirose, K.	P-1-7	Hsu, T. C.	P-7-8			Inoue, N.	C-3-3	Itokawa, H.	E-4-3
Hirose, N.	M-8-5								

Ivana	A-2-4	Jones, B.	H-6-3	Kang, H. J.	J-4-2	Kawasaki, A.	P-7-15	Kim, T. G.	P-4-2
Iwabuchi, T.	M-1-3	Jossart, N.	F-7-2	Kang, H. S.	AL-6-6, P-6-2	Kawasaki, Y.	J-5-4	Kim, Y.	F-4-2
Iwai, H.	E-3-1, E-3-2, P-1-11, D-7-3	Ju, J.	P-10-11	Kang, J.	F-7-3, P-4-12	Kawashima, S.	B-6-3	Kim, Y. M.	B-3-3
Iwama, Y.	GH-1-2	Juang, Y. Z.	P-5-16	Kang, J.	P-9-20L	Kawashimo, Y.	P-2-4	Kim, Y. S.	P-8-8
Iwamoto, M.	B-5-2, B-6-3, B-6-5, B-7-1, B-7-5, BL-1-2, BL-1-3, BL-2-5	Jung, E.	F-4-2	Kang, K. C.	P-13-3	Kawata, S.	M-9-1	Kimball, A.	D-7-1
Iwamoto, S.	P-13-6, J-6-4, I-8-2	Jung, J.	B-3-2, K-8-3, P-2-15, P-8-8, P-13-15, P-13-20	Kang, K.	C-8-2	Kawazu, T.	P-9-5	Kimoto, T.	AL-6-1, M-1-5, P-14-19
Iwamura, Y.	E-1-3	Jung, J.	I-4-3L	Kang, M.	P-5-17	Kayanuma, R.	M-9-2	Kimura, K.	P-8-5
Iwasa, Y.	B-6-2	Jung, S.	I-4-4L	Kang, M. H.	E-5-2	Kazama, K.	C-3-3	Kimura, M.	E-2-2
Iwasugi, T.	P-6-12L	Jung, S.	I-4-4L	Kang, S.	GH-2-1	Kellens, K.	F-7-2, H-7-2	Kimura, S.	B-5-4
Iwata, T.	H-4-1	Jung, S.	F-6-5, P-4-5, P-4-14L	Kang, S. J.	B-8-3	Kennedy, K.	I-9-3	Kimura, T.	I-5-2, I-5-3
Izard, N.	K-2-6	Jung, S.	F-6-3, F-8-2	Kang, W.	B-9-2	Khakifirooz, A.	D-7-1	Kimura, T.	M-1-3
Izumi, K.	N-6-1	Jung, S. D.	P-6-2, AL-6-6	Kanno, S.	P-11-3	Khamas, S.	I-2-2	Kimura, T.	P-12-14
Izumi, Y.	E-3-1, E-3-2, P-1-11	Jurczak, M.	F-7-2, P-4-6	Kano, H.	K-1-2, P-13-14	Kigure, C.	H-4-2	Kimura, Y.	A-5-1
Izumida, W.	J-7-2			Kanzaki, K.	P-8-6	Kikuchi, N.	L-8-5	King Liu, T. J.	PL-2-2
		K		Kao, M. J.	F-6-4, F-9-1, F-9-2, P-4-16L	Kil, G. H.	P-9-15	Kino, H.	C-5-2, P-5-3
				Kar, G.	F-7-2	Kim, B.	P-5-1	Kinoshita, A.	D-8-3
				Karakawa, M.	P-2-12	Kim, B.	P-5-17	Kinoshita, T.	E-3-1, E-3-2, P-1-8, P-1-11, KM-6-2
Jablonski, R.	J-7-4	Kaczer, B.	F-2-3	Karmalkar, S.	P-13-8	Kim, B. J.	KM-7-1	Kio, Y.	P-6-10
Jacobsen, A.	J-3-1	Kadoda, A.	P-6-12L	Kasahara, K.	E-5-3	Kim, C.	P-9-20L	Kishii, S.	P-2-3
Jagannathan, H.	D-7-1	Kaga, T.	KM-6-4	Kasahara, K.	E-5-3	Kim, C. G.	P-3-5	Kishimoto, S.	K-1-5, K-2-1, K-3-3, P-13-27, P-13-28
Jammy, R.	E-5-2	Kagami, M.	P-7-15	Kasai, H.	H-4-4	Kim, C. S.	GH-2-1	Kisu, K.	G-6-2
Jana, D.	P-4-16L	Kageshima, H.	K-9-1, KM-6-3	Kasai, S.	P-14-6	Kim, D. H.	A-2-1	Kita, K.	AL-6-2, E-1-2, E-4-4, E-6-3
Jang, C. Y.	P-7-3	Kahng, Y. H.	B-8-3	Kasama, Y.	C-3-3	Kim, D. K.	P-6-3	Kita, T.	CI-7-3, I-3-3, I-4-1
Jang, H.	KM-7-1	Kaho, T.	P-5-2	Kasamatsu, A.	M-8-5	Kim, D. S.	AL-6-6, P-6-2, P-6-3	Kita, T.	P-9-11
Jang, H. J.	P-11-8	Kajii, H.	B-7-3, B-7-4	Kashimura, Y.	A-5-3	Kim, D. W.	P-3-5	Kitada, T.	I-4-2, I-5-1
Jang, K. I.	AL-6-6, P-6-2	Kajiwara, T.	KM-6-1	Kashimura, Y.	H-7-1	Kim, D. W.	D-6-4	Kitado, E.	I-3-4
Jang, T.	AL-7-3	Kakimoto, K.	L-9-3	Kashimura, Y.	H-7-1	Kim, D. W.	P-13-9	Kitaguchi, M.	B-4-4
Jang, W. Y.	F-8-3	Kako, S.	I-8-2	Kashimura, Y.	H-7-1	Kim, D. Y.	P-2-15, P-8-8, P-13-15	Kitahara, K.	P-1-13
Jang, Y.	GH-2-1	Kakushima, K.	D-7-3, E-3-1, E-3-2, P-1-11	Kasami, M.	A-5-3	Kim, E.	P-2-15, P-8-8, P-13-15	Kitamura, K.	P-11-9
Jansen, R.	N-7-2	Kalita, G.	KM-6-6	Kashimura, Y.	H-7-1	Kim, G.	D-4-2	Kitamura, M.	B-9-2
Jaouen, H.	P-2-17	Kaltenbrunner, M.	B-9-4	Kashimura, Y.	H-7-1	Kim, H.	D-4-2	Kitatani, T.	I-1-1
Jaw, B. Y.	P-5-11	Kamakura, Y.	D-5-4	Kashimura, Y.	H-7-1	Kim, H.	D-4-2	Kitayama, A.	J-8-4
Jaye, C.	B-6-6	Kato, H.	P-14-18	Kashimura, Y.	H-7-1	Kim, H. W.	D-4-2	Kitl, J. A.	F-2-3, F-7-2, P-4-6
Jeon, C.	F-4-2	Kato, H.	P-14-18	Kashimura, Y.	H-7-1	Kim, H. W.	D-4-2	Kiumarsi, H.	D-1-4
Jeon, N.	P-2-7	Kato, K.	B-5-1, B-5-3, BL-2-7	Kashimura, Y.	H-7-1	Kim, J.	M-2-3	Kiyooka, M.	P-8-13
Jeon, Y.	P-9-20L	Kato, K.	P-9-8, P-9-18	Kashimura, Y.	H-7-1	Kim, J. C.	GH-2-1	Kiyoyama, K.	G-4-2, P-5-3
Jeong, E. Y.	P-6-1	Kato, M.	P-14-20	Kashimura, Y.	H-7-1	Kim, J. S.	P-10-20L	Klar, P. J.	P-12-1
Jeong, G. T.	P-4-5	Kato, S.	A-8-1	Kashimura, Y.	H-7-1	Kim, J. T.	P-2-6	Klauk, H.	B-3-4, B-6-6, B-8-5, B-8-6
Jeong, H.	F-6-5, P-4-5	Kato, S.	L-9-5	Kashimura, Y.	H-7-1	Kim, J. W.	F-7-4L	Klymko, N. R.	E-4-3
Jeong, K. S.	B-3-3	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, J. Y.	P-5-7	Knowles, H.	J-3-1
Jeong, S.	K-1-3	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K.	P-5-17	Ko, M. D.	P-13-2
Jeong, Y.	F-4-2	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K. C.	AL-7-3	Ko, R. M.	KM-4-4
Jeong, Y. H.	P-6-1, P-13-2	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K. J.	P-3-8	Ko, T. K.	P-7-1
Jergel, M.	BL-2-5	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K. S.	P-6-2	Koba, S.	P-3-17
Jevasuwan, W.	E-8-3, E-8-4, E-8-5	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K. W.	P-6-2, AL-6-6	Kobayashi, D.	P-1-7
Jeyasingh, R. G. D.	F-6-2	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, K. W.	P-6-2, AL-6-6	Kobayashi, H.	C-5-2, C-8-3, G-4-2, P-2-2
Jia, R.	P-14-6	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, M. J.	P-13-9	Kobayashi, H.	P-5-13
Jiang, Q.	I-2-2	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, M. S.	F-2-3	Kobayashi, K.	G-3-1
Jiang, Y.	I-5-2	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, R. H.	AL-6-6, P-6-2	Kobayashi, K.	P-12-4
Jie, S. H.	P-2-6	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S.	A-8-3	Kobayashi, M.	L-8-5
Jin, G. Y.	D-6-4	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S.	F-8-2	Kobayashi, M.	P-8-23
Jin, J. E.	P-13-9	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S.	P-9-20L	Kobayashi, M.	P-11-10
Jinbo, R.	P-14-14	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S. H.	B-2-3	Kobayashi, N.	P-1-14
Jiu, J.	C-8-1, P-2-12	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S. H.	D-4-1, E-8-3	Kobayashi, S.	P-7-9
Jo, G.	B-8-3	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S. H.	D-4-1, E-8-3	Kobayashi, T.	B-7-2, P-10-5, BL-1-1
Jo, S. H.	I-4-3L	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, S. W.	D-4-2	Kobayashi, T.	H-4-3, GH-2-5
Johansson, S.	KM-4-3L	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1	Kim, T.	AL-6-4	Kobayashi, Y.	M-1-4
Johguchi, K.	F-8-1, G-4-3	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1				
Joho, Y.	B-9-5	Kato, Y.	B-8-6	Kashimura, Y.	H-7-1				

Kodama, K.	P-7-9	Kubo, K.	P-1-2	Kuwahara, T.	P-8-9	Lee, J. H.	P-13-9	Lian, Y. W.	AL-7-4
Kodama, R.	GH-2-3	Kubo, M.	P-8-9	Kuwamura, Y.	P-7-14	Lee, J. J.	J-4-2	Liang, C. W.	D-5-2
Kodama, S.	I-1-5	Kubo, T.	P-9-11	Kuzmik, J.	A-1-1	Lee, J. M.	F-8-2	Liang, G.	J-3-3, K-9-5
Kodera, M.	C-9-2	Kubota, H.	N-8-5	Kuzuhara, M.	AL-6-5	Lee, J. S.	B-8-1	Liao, M.	B-3-1
Kodera, T.	J-7-1	Kubota, M.	GH-2-4	Kwoen, J.	P-13-6	Lee, J. S.	P-6-1, P-13-2	Liao, P. Y.	P-11-2
Kodera, T.	P-9-7	Kubota, T.	A-8-4	Kwon, H. M.	E-5-2	Lee, K.	B-7-5, BL-1-2, BL-2-5	Liao, T. W.	P-8-10
Kogelschatz, M.	P-1-15	Kudo, K.	B-2-4, B-9-5	Kwon, M. K.	P-6-2, AL-6-6	Lee, K.	H-4-2, P-11-3	Liao, T. W.	P-8-14
Kogure, J.	P-11-9	Kudo, M.	A-1-6, A-8-6	Kwon, T.	B-8-3	Lee, K. H.	L-1-1	Liao, T. Y.	P-8-22
Kohama, K.	C-9-3, C-9-4	Kudo, T.	P-14-14	Kwon, T.	P-13-20	Lee, K. W.	C-8-3, C-5-2, G-4-2, P-5-5, CI-7-2	Liao, Y. B.	P-3-13
Kohashi, Y.	KM-5-4	Kukita, K.	P-7-12	Kwon, Y. J.	P-6-3	Lee, M.	K-9-3	Liao, Y. H.	J-6-3
Kohda, M.	N-7-3, N-8-1, N-9-3, P-12-10	Kulkarni, P.	D-7-1	Kwong, D. L.	F-7-3	Lee, M. H.	F-7-1, P-4-7	Lim, H.	N-8-3
Koide, T.	G-3-2, G-6-3	Kumada, N.	J-6-2, J-7-3	Kumagai, N.	P-13-12	Lee, M. H.	L-1-4, P-9-16	Lim, S. K.	P-1-16, KM-7-2
Koike, H.	F-1-3	Kumagai, K.	P-8-16	Kumagai, K.	P-8-16	Lee, N. H.	P-3-8	Lin, A.	C-1-4
Koike, M.	E-4-2	Kumagai, N.	J-7-1, P-13-6	Kumagai, N.	J-7-1, P-13-6	Lee, S.	B-8-3	Lin, B. H.	M-2-2
Koiwai, K.	B-7-4	Kumagai, S.	P-11-6, P-11-10, P-11-14	Kumagai, S.	P-11-6, P-11-10, P-11-14	Lee, S.	E-8-3, E-8-4, E-8-5	Lin, C. C.	L-2-4
Kojima, H.	P-11-1	Kumagai, Y.	D-2-4, P-1-8	Kumagai, Y.	D-2-4, P-1-8	Lee, S.	G-5-2, G-5-3	Lin, C. C.	P-1-19L, P-2-18L
Kojima, M.	H-6-2	Kumagai, Y.	P-8-23	Kumagai, Y.	P-8-23	Lee, S.	N-8-3	Lin, C. C.	P-7-3
Kojima, N.	L-1-5, P-8-17, P-10-8, P-14-11, P-14-12	Kumai, R.	B-9-3	Kumai, R.	B-9-3	Lee, S.	P-11-3	Lin, C. H.	P-2-8
Kojima, O.	P-9-11	Kumakura, K.	A-4-2	Kumakura, K.	A-4-2	Lee, S. C.	I-9-5, P-7-13	Lin, C. H.	D-7-1
Kojima, T.	L-9-3	Kumar, A.	D-6-3	Kumar, A.	D-6-3	Lee, S. H.	D-4-1	Lin, C. H.	F-8-3
Kokubun, Y.	I-1-3	Kumar, A.	D-7-1, E-9-2	Kumar, A.	D-7-1, E-9-2	Lee, S. H.	P-3-5	Lin, C. H.	H-6-5
Kolobov, A.	F-6-1	Kume, I.	C-3-3	Kume, I.	C-3-3	Lee, S. H.	P-9-15	Lin, C. L.	P-9-13
Komasaki, Y.	N-6-4	Kunihashi, Y.	N-7-3, N-8-1	Kunihashi, Y.	N-7-3, N-8-1	Lee, S. H.	P-13-2	Lin, C. S.	P-2-8
Komatsuzaki, Y.	A-4-4	Kunimune, Y.	C-4-3	Kunimune, Y.	C-4-3	Lee, S. J.	A-2-3	Lin, C. T.	P-1-20L
Kometani, R.	P-6-4	Kuo, C. C.	M-2-2	Kuo, C. C.	M-2-2	Lee, S. K.	KM-7-2	Lin, C. W.	P-11-2
Komori, S.	P-8-15	Kuo, C. H.	P-7-4	Kuo, C. H.	P-7-4	Lee, S. K.	KM-7-1	Lin, D.	E-1-1
Konabe, S.	J-4-1, K-2-5	Kuo, C. I.	P-6-9	Kuo, C. I.	P-6-9	Lee, S. Y.	B-3-3	Lin, H.	P-5-6, P-5-11
Konagai, M.	L-2-3	Kuo, D. M.	P-7-4	Kuo, D. M.	P-7-4	Lee, T.	B-8-3	Lin, H. C.	P-3-9
Kondo, H.	C-9-1, K-1-2, L-2-6, P-6-4, P-8-3, P-13-14, P-13-19	Kuo, D. S.	P-7-1	Kuo, D. S.	P-7-1	Lee, W. G.	K-8-3, P-8-8	Lin, J. C.	P-8-20
Kondo, K.	P-1-13	Kuo, H. C.	I-2-4, I-2-5, L-2-4, P-3-7, P-7-2, P-7-3, P-7-8, P-14-5, P-14-8, KM-5-3	Kuo, H. C.	I-2-4, I-2-5, L-2-4, P-3-7, P-7-2, P-7-3, P-7-8, P-14-5, P-14-8, KM-5-3	Lee, W. H.	B-8-2	Lin, J. F.	P-1-18
Kondo, Y.	P-9-3	Kuo, H. R.	P-7-4	Kuo, H. R.	P-7-4	Lee, Y.	I-8-4	Lin, J. H.	P-8-18
Kondou, A.	G-6-2	Kuo, J. J. Y.	G-3-4L	Kuo, J. J. Y.	G-3-4L	Lee, Y. G.	P-1-16, KM-7-2	Lin, L.	E-8-2
Kondow, M.	J-8-5, P-7-12, P-7-19, P-7-20	Kuo, M. Y.	I-2-4, P-9-2	Kuo, M. Y.	I-2-4, P-9-2	Lee, Y. J.	L-1-4	Lin, S. D.	P-7-26
Kong, E. Y. J.	A-8-5	Kuribara, K.	B-3-4, B-6-6, B-8-6	Kuribara, K.	B-3-4, B-6-6, B-8-6	Lee, Y. K.	F-4-2	Lin, S. H.	L-2-4
Konishi, T.	P-5-2	Kurimoto, T.	P-8-19	Kurimoto, T.	P-8-19	Leroux, C.	E-2-1	Lin, S. J.	P-4-7
Kono, K.	J-7-1, J-7-2	Kurishima, K.	A-2-2	Kurishima, K.	A-2-2	Levin, T. M.	D-7-1	Lin, T. H.	P-7-4, KM-4-4
Kosemura, D.	E-7-2, E-7-3, E-9-3	Kurusu, Y.	KM-6-1	Kurusu, Y.	KM-6-1	Li, G. F.	N-6-3	Lin, W. K.	BL-2-3
Koshiba, S.	P-12-2	Kuriyaki, H.	P-9-1	Kuriyaki, H.	P-9-1	Li, H.	P-3-13	Lin, Y. F.	BL-2-3
Koshiba, Y.	P-10-3	Kuroda, R.	D-2-4, D-5-1, E-3-3, E-3-4	Kuroda, R.	D-2-4, D-5-1, E-3-3, E-3-4	Li, H.	P-14-6	Lin, Y. S.	AL-7-4
Koshida, N.	J-4-5, L-2-5, P-7-21	Kuroda, S.	B-6-2, B-6-4	Kuroda, S.	B-6-2, B-6-4	Li, H. H.	P-8-20	Lin, Y. Y.	P-7-28
Kotani, K.	G-6-6L, J-5-4	Kuroda, S.	N-9-1	Kuroda, S.	N-9-1	Li, J.	B-5-2	Lin, Z. H.	P-2-8
Kotsugi, M.	KM-6-2	Kuroda, T.	G-6-5L	Kuroda, T.	G-6-5L	Li, J.	D-7-1	Lin, Z. M.	P-3-9
Kou, R.	CI-7-1	Kuroda, Y.	P-10-3	Kuroda, Y.	P-10-3	Li, J.	E-4-3	Lind, E.	KM-4-3L
Kouketsu, T.	J-8-4	Kurokawa, S.	P-2-3	Kurokawa, S.	P-2-3	Li, J.	E-7-4, M-8-7	Liou, J. C.	P-5-1
Koyama, M.	F-5-2	Kurokawa, Y.	L-9-5	Kurokawa, Y.	L-9-5	Li, L. H.	P-12-16L	Liu, C.	K-1-1
Koyama, T.	C-4-3	Kuroki, N.	P-5-9	Kuroki, N.	P-5-9	Li, M. Y.	P-9-13	Liu, C. H.	P-5-16
Koyama, T.	N-9-2	Kuroki, S.	J-5-4, P-8-12	Kuroki, S.	J-5-4, P-8-12	Li, N.	P-5-15	Liu, C. T.	B-8-2
Koyanagi, M.	C-5-2, C-8-3, G-4-2, H-4-2, I-1-2, P-2-2, P-5-3, P-5-5, P-11-3, CI-7-2	Kurosawa, M.	E-6-1	Kurosawa, M.	E-6-1	Li, S. L.	K-9-3, K-9-4	Liu, D. S.	P-7-7
Kozaki, M.	P-9-1	Kurouchi, M.	P-7-6	Kurouchi, M.	P-7-6	Li, X.	E-3-3	Liu, F.	P-13-16
Kozu, M.	M-3-2	Kusai, H.	F-5-2	Kusai, H.	F-5-2	Li, X.	F-7-3	Liu, H. W.	P-14-4
Ku, S. H.	F-3-2	Kushida, T.	P-10-5	Kushida, T.	P-10-5	Li, Y.	P-3-22L	Liu, H. X.	N-6-3
Ku, T. K.	G-4-1, P-2-8	Kusizaki, T.	M-2-1	Kusizaki, T.	M-2-1	Li, Y.	P-13-16	Liu, K. M.	P-3-9
Kuan, C. H.	P-8-10, P-8-14	Kuss, J.	D-7-1, E-9-2	Kuss, J.	D-7-1, E-9-2	Li, Y. J.	M-1-6, P-7-8, KM-5-3	Liu, L.	F-7-3
Kubicek, S.	F-7-2	Kusunoki, M.	P-8-5	Kusunoki, M.	P-8-5	Li, Y. S.	P-7-26	Liu, M.	F-9-3
Kubo, A.	I-3-2	Kuwabara, H.	B-3-4, B-6-6, B-8-6	Kuwabara, H.	B-3-4, B-6-6, B-8-6	Li, Y. T.	F-9-3	Liu, Q.	D-7-1, E-9-2
		Kuwabara, S.	C-3-3	Kuwabara, S.	C-3-3	Li, Z. Y.	P-7-3	Liu, Q.	F-9-3
		Kuwabata, S.	P-8-19	Kuwabata, S.	P-8-19	Li, Z. Y.	P-7-30	Liu, Q.	G-7-4
						Lian, G.	P-4-12	Liu, S. H.	F-5-3

Liu, T. J. K.	F-2-4	F-9-2, P-4-16L	Matsuzawa, K.	D-8-3	Miyazaki, C.	P-2-2	Motohisa, J.	G-6-2, KM-5-4, P-13-1	
Liu, W. D.	P-3-7	Majeed, B.	C-5-4, H-6-3, H-6-4	Mattausch, H. J.	D-8-3, G-3-2, G-6-3	Miyazaki, E.	P-6-12L	Motomura, A.	P-5-14
Liu, W. H.	P-4-8	Majhi, P.	E-5-2	McAdams, H.	F-2-1	Miyazaki, H.	K-9-3	Motoyoshi, M.	D-1-5
Liu, W. R.	M-2-2	Majid, M. A.	I-9-3, I-9-4	Mehta, S.	D-7-1, E-9-2	Miyazaki, H. T.	K-9-4	Mou, Z. W.	P-3-7
Liu, X.	F-8-5	Majima, Y.	J-7-5	Meng, H. F.	A-5-4, B-3-5	Miyazaki, S.	I-3-2	Moutanabbir, O.	M-9-1
Liu, X. C.	P-3-14, P-4-12, P-13-16	Majkova, E.	BL-2-5	Meng, K. K.	P-12-3	Miyazaki, S.	I-8-1, P-1-4	Muhanad, S.	M-2-6
Liu, X. C.	M-8-6	Majumdar, G.	L-8-1	Meng, Y.	P-14-6	Miyazawa, R.	BL-1-3	Muraguchi, M.	J-4-1, N-8-6
Liu, X. Y.	P-3-19	Makabe, T.	P-2-9	Meniailenko, V.	P-14-18	Miyazawa, T.	J-6-4	Murakami, H.	M-8-2, P-1-4
Liu, Y.	M-1-2, M-1-3	Makarov, A.	P-12-13	Mentek, R.	L-2-5	Mizubayashi, W.	E-9-3	Murakami, K.	P-2-4
Liu, Y. C.	P-7-30	Makihara, K.	I-8-1	Mertens, S.	P-4-6	Mizubayashi, W.	E-9-4L	Murakami, K.	P-14-15
Liu, Y. X.	E-9-3, F-4-3	Makimoto, T.	A-4-2, P-8-6	Migita, S.	E-9-1, E-9-3, E-9-4L	Mizuguchi, M.	N-6-1, P-12-10	Murakami, M.	C-9-3, C-9-4
Liyanage, L. S.	C-1-4	Makino, H.	G-3-1	Miki, S.	P-14-2	Mizuno, S.	KM-6-5	Murakami, T.	C-3-2
Lo, G. Q.	F-7-3	Mamat, M. H.	M-2-6	Miller, R. A.	H-7-2	Mizuno, T.	D-2-2, D-2-3	Murakami, Y.	P-9-17
Long, S. B.	F-9-3	Manaka, T.	B-5-2, B-6-3, B-6-5, B-7-1, B-7-5, BL-1-2, BL-1-3, BL-2-5	Mimura, N.	P-5-14	Mizuno, T.	J-6-5, J-7-4	Muraki, K.	J-7-3, J-8-6L
Loo, R.	E-1-1	Mao, K.	D-6-3	Mimura, T.	M-8-5	Mizuno, T.	BL-2-2	Muramoto, Y.	I-1-5
Loo, Y. L.	B-6-6	Mao, S.	P-13-25	Minari, H.	J-4-5	Mizuochi, Y.	D-1-4	Murase, H.	P-11-14
Loubet, N.	D-7-1, E-9-2	Mari, K.	P-12-6	Mine, T.	I-8-4	Mizuta, H.	J-4-5	Murashima, D.	BL-2-7
Low, K. L.	D-4-4	Marris-Morini, D.	CI-6-2	Minemawari, H.	B-9-3	Mizutani, T.	D-6-3	Murata, H.	P-10-19L
Lu, B. K.	P-3-1	Martens, K.	E-1-1, P-4-6	Minemoto, T.	L-3-1, L-3-2, P-14-9	Mizutani, T.	K-1-5, K-2-1, K-3-3, P-6-12L, P-13-27, P-13-28	Muraya, N.	B-2-5
Lu, C. Y.	F-3-2, F-7-1	Martin, F.	E-2-1	Mineno, Y.	N-7-2	Mochizuki, F.	B-7-2	Muro, K.	J-6-2
Lu, C. Y.	P-4-7	Marumoto, K.	B-6-2	Misaki, M.	P-10-3	Mochizuki, K.	E-7-1	Muro, T.	C-1-2, C-1-3, E-3-1, E-3-2, P-1-8, P-1-11
Lu, H. C.	AL-7-4	Maruyama, S.	K-3-4	Mita, Y.	GH-2-4	Mochizuki, S.	E-7-4	Muroyama, M.	B-1-5
Lu, S.	P-12-16L	Maruyama, T.	P-7-27	Mitani, Y.	E-2-4	Mofrad, M. R. T.	A-5-3	Murphy, R.	M-8-7
Lu, T. C.	I-2-5, P-7-3, P-7-11	Maruyama, Y.	D-2-2	Mitard, J.	E-1-1	Mohan, V. M.	P-14-15	Murray, R.	I-9-3
Lu, W. P.	F-3-2	Maruyama, Y.	P-10-12	Mitomo, T.	G-7-1	Mohanta, S. K.	P-8-25	Murugesan, M.	C-5-2, C-8-3, P-2-2
Lu, Y.	L-2-6	Masada, H.	B-6-5	Mitra, S.	C-1-4	Moise, T. S.	F-2-1	Mushiake, H.	P-11-3
Lu, Y.	P-6-4	Masahara, M.	E-9-3, F-4-3, P-1-1	Mitsuguchi, S.	K-1-2	Molitor, F.	J-3-1	Myronov, M.	M-8-6
Luce, C.	C-8-2	Masuhara, M.	E-9-3, F-4-3, P-1-1	Mitsuhara, M.	I-1-6	Monsieur, F.	D-7-1		
Lucovsky, G.	F-7-4L, L-2-2, M-2-3, P-4-13L, P-12-7	Masu, K.	D-1-4, G-5-2, G-5-3, G-7-3	Mitsuno, Y.	P-8-15	Moon, D. I.	P-11-5		
		Masubuchi, S.	P-9-6, P-9-19	Miura, H.	P-13-21, P-13-23	Moon, T.	P-9-20L		
Lue, C. E.	H-7-4L	Masuda, A.	BL-1-4	Miura, M.	P-1-6, CI-6-3	Morales, C.	P-10-8		
Lui, T. S.	P-8-22	Masuda, T.	P-10-15	Miura, N.	G-6-5L	Morales, Y.	I-3-3		
Lujan, R.	L-2-2	Masuda, T.	GH-1-4	Miura, R.	P-14-7	Morarar, D.	J-6-5, J-7-4		
Lung, H. L.	F-7-1	Masugata, Y.	N-8-5	Miura-Mattausch, M.	D-8-3, L-8-6	Moreau, M.	P-7-21		
Luning, S.	D-7-1	Masui, S.	P-4-15L, P-5-2	Miwa, S.	N-8-5	Mori, I.	GH-2-4		
Lv, H. B.	F-9-3	Matsuda, K.	N-6-3, N-7-4, P-12-9	Miyachi, S.	P-11-14	Mori, K.	B-5-4		
		Matsuda, T.	B-5-5L	Miyadera, T.	BL-1-4	Mori, M.	A-4-3, M-3-3, P-6-12L		
		Matsuda, T.	J-6-2	Miyagawa, D.	B-1-5	Mori, M.	P-7-16		
		Matsui, H.	B-9-3	Miyagawa, H.	P-12-2	Mori, N.	J-4-5		
		Matsui, M.	P-1-4	Miyaji, K.	F-4-1, F-8-1, P-4-1	Mori, N.	J-5-3		
		Machida, S.	L-8-5	Miyajima, S.	L-2-3	Mori, T.	I-1-2		
		Machida, T.	P-9-6, P-9-19	Miyake, H.	P-14-19	Mori, T.	P-10-1, P-10-10		
		Madan, A.	E-7-4	Miyake, M.	D-8-3, L-8-6	Mori, T.	AL-6-5		
		Madan, S.	F-2-1	Miyake, R.	GH-2-2	Mori, Y.	P-7-12		
		Maeda, K.	J-7-5	Miyake, Y.	P-10-15	Morifuji, M.	J-8-5, M-3-4, P-7-12		
		Maeda, K.	P-13-24	Miyamoto, A.	P-14-7	Morimoto, H.	P-5-12		
		Maeda, S.	P-13-1	Miyamoto, Y.	A-4-1	Morimoto, T.	P-10-1, P-10-10		
		Maeda, T.	E-8-3, E-8-5, M-9-4L	Miyamura, Y.	L-9-3	Morishita, S.	GH-2-4		
		Maeda, T.	P-14-10	Miyamoto, Y.	GH-2-3	Morita, K.	I-4-2, I-5-1		
		Maegawa, Y.	P-3-17	Miyao, M.	E-5-3	Morita, K.	KM-6-1		
		Maehara, D.	N-8-5	Miyao, M.	E-6-1	Morita, M.	B-1-7L		
		Maehashi, K.	K-1-4, K-9-2, KM-7-3	Miyasako, T.	F-2-2	Morita, Y.	E-9-3		
		Maemoto, T.	A-5-1	Miyata, N.	E-8-5	Morita, Y.	E-9-4L		
		Maetzawa, K.	A-4-3, M-3-3, P-6-12L	Miyata, Y.	E-3-1, P-1-11	Moriya, R.	P-9-6, P-9-19		
		Mahapatra, S.	D-8-1	Miyatake, N.	A-5-2	Moriyama, S.	J-3-2		
		Mahboob, I.	J-5-2	Miyatake, T.	C-8-4	Moriyama, T.	K-8-4		
		Maheswaran, K. R. K.	P-13-8	Miyawaki, T.	N-6-4, P-12-4, P-12-6	Morokawa, Y.	D-2-1, D-6-2		
		Maheta, V. D.	D-8-1	Miyawaki, T.	N-9-3	Morota, M.	F-5-2		
		Maikap, S.	F-6-4, F-8-4, F-9-1,	Miyazaki, C.	C-5-2	Motohiro, T.	P-14-13		

M

N

Nakagawa, T.	B-8-5	Nishiguchi, K.	J-5-2	Ogura, T.	C-3-3	Okamoto, M.	AL-6-3	Ozawa, N.	P-8-9
Nakagawa, Y.	I-4-2, I-5-1	Nishijima, M.	A-1-2	Oguri, K.	I-3-2, P-9-8	Okamoto, N.	P-11-13	Ozawa, O.	G-6-1
Nakagoshi, S.	P-10-14	Nishikawa, E.	K-3-4	Oh, C. W.	D-6-4	Okamoto, S.	K-1-4		
Nakahara, H.	P-2-14	Nishikawa, T.	P-10-1, P-10-10	Oh, H. J.	A-2-3	Okamoto, T.	B-9-5	P	
Nakaharai, S.	K-9-4	Nishimura, T.	E-1-2, E-4-4, E-6-2, E-6-3, K-8-2	Oh, J.	E-5-2	Okatsu, T.	A-4-3	Paek, E. J.	KM-7-2
Nakahora, T.	P-7-14	Nishimura, T.	K-8-4, AL-6-2	Oh, J. H.	F-6-5, P-4-5, P-4-14L	Okayasu, J.	A-8-2	Paek, J. H.	P-13-7
Nakajima, A.	A-1-5	Nishioka, K.	L-1-6	Oh, S. K.	E-5-2	Oki, D.	P-5-13	Pan, T. M.	P-11-2
Nakajima, A.	P-8-12	Nishiyama, E.	G-3-3	Oh, T. K.	P-3-5	Okigawa, Y.	K-1-5, K-2-1	Pandey, S. S.	BL-2-2
Nakajima, A.	GH-2-5	Nishizawa, M.	E-2-3	Oh, Y. H.	P-2-7	Okishio, T.	J-4-4	Pantisano, L.	F-7-2
Nakajima, T.	I-5-2, I-5-3	Nitta, J.	N-7-3, N-8-1, N-9-3, P-12-10	Ohashi, T.	P-3-21L	Oku, T.	P-10-18	Papas, B.	M-2-3
Nakamae, T.	M-8-3	Niwa, M.	D-7-3	Ohashi, Y.	P-13-21	Okuda, S.	K-1-4	Paraschiv, V.	F-7-2
Nakamura, A.	K-8-6L, P-8-25, P-13-18	Niwa, M.	D-7-3	Ohdaira, Y.	B-5-1	Okuda, T.	P-14-19	Park, B. G.	D-4-2
Nakamura, K.	L-3-3	Niwa, Y.	L-9-5	Ohdaira, K.	L-9-4	Okuda, Y.	G-6-1	Park, B. G.	F-6-5, P-4-5, P-4-14L, P-13-3
Nakamura, K.	P-2-3	Nizamuddin, A.	P-7-14	Ohi, A.	E-2-2	Okumura, H.	M-1-5	Park, C. H.	P-13-2
Nakamura, K.	P-5-12, P-5-14	Noda, T.	H-4-3, GH-2-5	Ohishi, T.	E-2-2	Okumura, H.	AL-6-3	Park, E.	P-1-16
Nakamura, M.	B-2-4, B-9-5	Nogi, M.	C-8-1, P-2-12	Ohkawa, K.	L-9-1	Okumura, T.	I-8-5	Park, J.	Okumura, T.
Nakamura, T.	C-8-5	Noguchi, J.	H-4-4	Ohkouchi, S.	P-8-1	Okura, R.	N-6-1	Park, J.	F-8-2
Nakanishi, K.	P-14-9	Noguchi, K.	N-7-1	Ohkouchi, S.	P-13-6	Okuyama, M.	B-4-2, P-1-2	Park, J.	F-4-2
Nakanishi, N.	C-4-3	Noguchi, M.	P-1-6, CI-6-3	Ohkouchi, T.	KM-6-2	Omi, H.	I-5-4	Park, K. M.	P-5-7
Nakanishi, S.	P-9-3, P-12-2	Noguchi, S.	P-1-17	Ohmi, S.	B-3-1, P-2-16	Omiya, M.	C-8-5	Park, S. G.	P-10-1, P-10-10
Nakanishi, S.	P-12-16L	Noguchi, Y.	B-8-5	Ohmi, T.	A-8-1, D-2-4, D-5-1, E-3-3, E-3-4, P-1-8, P-3-16	Oniki, Y.	E-1-4	Park, S. H.	F-6-5
Nakanishi, Y.	B-7-3	Noguchi, Y.	P-1-6	Ohmori, K.	D-7-3	Ono, A.	M-2-1	Park, W.	B-8-3
Nakano, H.	C-1-2, C-3-2	Nohira, H.	E-3-1, P-1-7, P-1-11, P-2-2	Ohmori, Y.	B-7-3, B-7-4	Ono, A.	P-7-24, P-7-25	Park, Y.	P-4-14L
Nakano, H.	I-3-2, P-9-8	Noji, H.	H-4-3	Ohnishi, M.	P-13-21, P-13-23,	Ono, K.	J-7-1, J-7-2, J-8-2	Parsons, G. N.	L-2-2
Nakano, J.	A-4-3	Nokuo, T.	C-8-5	Ohno, H.	F-1-1, F-1-2, F-1-4, N-8-2, N-8-4, P-12-12	Ono, T.	H-3-3	Paruchuri, V.	E-4-3, E-7-4, D-7-1, M-8-7
Nakano, K.	P-7-12	Nomura, T.	A-8-1	Ohno, Y.	K-1-4, K-9-2, KM-7-3	Ono, T.	N-9-2	Patané, A.	J-5-3
Nakano, N.	H-4-1	Nonaka, S.	N-8-1	Ohno, Y.	K-1-5, K-2-1, K-3-3, P-13-27, P-13-28	Ono, T.	P-1-3	Patil, N.	C-1-4
Nakano, Y.	L-1-2, P-7-18	Nori, F.	J-8-1, J-8-2, P-13-17	Ohno, Y.	P-6-10	Ono, T.	P-11-11	Patil, T.	P-6-5
Nakao, R.	P-7-12	Noriki, A.	CI-7-2	Ohno, Y.	F-1-2, F-1-4, P-5-4	Ono, Y.	K-3-2	Patrick, B.	P-5-2
Nakao, Y.	E-3-4	Norimatsu, W.	P-8-5	Ohno, Y.	N-9-2	Onodera, H.	G-3-1	Paul, D. F.	KM-4-1
Nakaoka, T.	J-6-4, J-7-1	Noury, A.	K-2-6	Ohno, Y.	N-8-5	Onomitsu, K.	A-4-4, J-5-1	Pawlak, M. A.	F-2-3
Nakashima, H.	E-1-3, E-1-5	Nowak, R.	J-7-4	Ohno, Y.	P-12-10	Oogane, M.	N-6-2	Peeters, S.	H-6-3, H-6-4
Nakashima, J.	L-8-6	Nozaki, T.	B-6-4	Ohno, Y.	P-1-4	Ootuka, Y.	J-3-2, J-3-4	Perreau, P.	E-2-1
Nakashima, N.	K-2-3	Nozaki, T.	N-8-5	Ohshita, Y.	L-1-3, L-1-5, L-9-3, P-8-17, P-14-2, P-14-11, P-14-12	Op de Beeck, M.	H-6-3, H-6-4	Phanichphant, S.	B-5-3
Nakata, K.	P-10-7	Nukui, Y.	J-3-2, J-3-4	Ohsugi, R.	P-12-10	Orofeo, C. M.	KM-6-5	Phommahaxay, A.	C-3-1
Nakatani, K.	M-3-3, P-6-12L	Numa, M.	P-5-9	Ohta, A.	P-1-4	Osada, S.	P-14-9	Pierson, R.	A-2-1
Nakatani, Y.	N-9-2	Numata, T.	D-7-2, D-8-4, E-2-4	Ohta, J.	A-8-4	Osaka, T.	CI-7-3	Pinto, T.	E-7-4
Nakatsubo, S.	AL-6-2	Nyns, L.	E-1-1	Ohta, J.	H-4-3, GH-2-5	Osaki, Y.	P-5-9	Poborchii, V.	P-1-10
Nakatsuka, O.	E-5-1, E-6-4, E-7-1, P-1-5	Nötzel, R.	KM-5-1	Ohta, J.	P-14-9	Oshiyama, A.	K-1-3	Pofelski, A.	E-7-4
Nakayama, K.	M-3-3, P-6-12L			Ohta, T.	L-9-5	Osintsev, D.	P-12-13	Ponoth, S.	D-7-1, E-9-2
Nakayama, S.	I-8-2			Ohta, Y.	P-8-19	Ota, H.	E-9-1, E-9-3, E-9-4L	Popovici, M.	F-2-3
Nakazato, K.	P-5-1	O		Ohta, Y.	E-8-5	Ota, K.	D-7-2, D-8-4	Posada, G.	C-5-4
Nakazawa, R.	P-5-3	O'Neill, J.	D-7-1	Ohtake, A.	E-8-5	Ota, Y.	J-6-4	Possémé, N.	E-9-2
Nakazawa, S.	A-1-2	Ochiai, Y.	P-13-24	Ohtake, A.	E-8-5	Ota, Y.	L-1-6	Potoms, G.	C-3-1
Namazu, T.	C-8-4, P-2-4, P-2-5	Oda, K.	I-8-4, I-8-5	Ohtomo, M.	P-13-11	Otani, M.	P-13-10	Pourtois, G.	F-7-2
Nanjo, T.	A-1-4	Oda, M.	D-2-1, D-6-2	Ohtsuka, H.	B-2-3	Oto, K.	J-6-2	Prakash, A.	F-6-4
Naramoto, H.	P-13-11	Oda, M.	E-8-6	Oikawa, T.	N-7-1	Otosaka, H.	P-7-27	Prasertsuk, K.	M-1-3
Narayanan, V.	D-7-1	Oda, M.	F-5-2	Oiwa, K.	P-11-1	Otsuji, T.	K-8-1	Priyantha, W.	M-2-5
Narise, K.	GH-1-4	Oda, S.	P-9-7	Ojiro, Y.	C-1-3	Otsuka, Y.	C-4-2		
Nasibulin, A. G.	K-3-3	Oda, Y.	L-3-2, P-14-9	Okabayashi, N.	J-7-5	Otsuki, J.	P-8-24		
Natori, K.	P-3-20L	Ôdoi, K.	B-4-1	Okabe, Y.	P-1-13	Oturu, M.	G-7-3	Q	
Natsui, M.	N-8-2, P-12-12	Ogata, N.	P-10-8	Okada, A.	M-8-4	Ou, W. Y.	P-2-18L	Qin, J.	P-3-14
Nie, S. H.	P-12-3	Ogata, N.	K-3-1, P-3-17	Okada, A.	P-10-6	O'uchi, S.	E-9-3, F-4-3	Qiu, L.	P-2-11
Nihei, M.	C-1-2, C-1-3, C-3-2	Ogawa, M.	C-1-2, C-1-3, KM-6-4	Okada, H.	B-1-1, BL-2-1	Oyanagi, Y.	P-12-16L		
Niitsu, K.	P-5-13	Ogawa, S.	C-4-2, K-9-4	Okada, H.	P-6-8, P-8-16	Ozaki, M.	P-10-2, P-10-15	R	
Nishi, H.	CI-7-1	Ogawa, Y.	KM-6-5	Okada, K.	P-5-15	Ozaki, N.	P-8-1	Radhakrishnan, G.	M-2-5
Nishi, S.	P-10-8	Ogo, H.	BL-1-4	Okada, S.	K-2-5, K-8-5, P-13-10, P-13-13	Ozawa, D.	J-8-3	Radu, I. P.	P-4-6
Nishida, M.	C-8-5	Ogomi, Y.	BL-2-2	Okai, M.	P-13-12	Ozawa, H.	K-2-3	Raes, T.	F-7-2
Nishida, T.	P-11-13	Ogura, A.	E-7-2, E-7-3, E-9-3, F-4-3, L-9-3, P-14-1, P-14-2	Okamoto, D.	CI-6-3	Ozawa, H.	B-4-1	Rafic, M.	P-1-15
				Okamoto, H.	J-5-1			Rahaman, S. Z.	F-8-4, F-9-1, F-9-2

Rakowski, M.	F-7-2	Sakamoto, K.	F-4-3	Schnez, S.	J-3-1	Shimomura, K.	L-1-3	Song, I. S.	GH-2-1
Rasigade, G.	CI-6-2	Sakamoto, M.	C-3-3	Segawa, T.	L-8-5	Shimozono, S.	P-13-24	Song, Y. H.	P-9-15
Ray, S. K.	F-9-1	Sakata, H.	P-7-15	Seki, H.	P-1-7	Shimura, Y.	E-6-4, E-7-1, P-1-5	Sou, K. P.	M-1-6, P-7-8, KM-5-3
Raymond, M.	D-7-1	Sakaue, H.	P-11-1	Shin, C.	P-8-11	Shin, C.	F-2-4	Soussan, P.	C-3-1
Razavi, P.	P-3-12	Sakita, S.	KM-5-2	Shin, H.	N-6-1, P-12-10	Shin, H.	D-4-2, P-13-3	Speck, J. S.	M-1-1
Reimbold, G.	E-2-1	Sakoh, T.	C-3-3	Shin, H.	GH-1-4	Shin, H.	N-8-3	Spencer, P.	I-9-3
Ren, Z.	D-7-1	Sakuma, K.	F-5-2	Shin, H.	P-6-8, P-8-16	Shin, H.	P-13-3	Sreenivasan, R.	D-7-1
Reséndiz, L.	B-8-4	Sakuma, K.	N-6-4	Sekiguchi, T.	L-9-3	Shin, H. S.	E-5-2	Sriwichai, S.	B-5-3
Reznicek, A.	D-7-1, E-7-4, M-8-7	Sakuraba, Y.	N-6-1, P-12-5	Sekine, M.	C-9-1, L-2-6, P-6-4, P-8-3, P-13-14, P-13-19	Shin, J.	F-8-2, F-8-5	Stampfer, C.	J-3-1
Richard, O.	F-7-2	Sakurai, M.	P-5-13	Sekine, Y.	K-9-1	Shin, J. K.	I-4-3L	Starkov, I.	P-3-4
Rideau, D.	D-1-2, P-2-17	Salmi Dharmiza, D. N.	G-7-3	Sekitani, T.	B-3-4, B-6-6, B-8-5, B-8-6, B-9-1, B-9-4	Shin, S. J.	J-4-2	Sterken, T.	H-6-4
Robertson, J.	E-8-2	Sameshima, T.	D-2-2	Selberherr, S.	P-12-13	Shinagawa, T.	I-5-2	Stesmans, A.	P-4-6
Roberts, J. S.	L-1-1	Sameshima, T.	L-9-3	Selvaraj, S. L.	AL-7-5	Shinbo, K.	B-5-1, B-5-3, BL-2-7	Stevens, B. J.	I-2-2
Rodriguez, J.	F-2-1	Samukawa, S.	A-8-4, H-7-3, P-1-1, P-11-11	Senda, K.	L-8-3	Shinke, W.	BL-1-1	Stoker, M. W.	E-7-4
Rodwell, M.	A-2-1	Sandhu, A.	H-3-4	Selva, K.	B-5-5L	Shinoda, K.	I-1-1	Street, R. A.	L-2-2
Roh, Y.	D-6-4	Sankara Narayanan, E. M.	A-1-5	Sendo, K.	L-8-3	Shinoda, H.	CI-7-1	Su, J. Y.	A-5-5
Ronsheim, P.	E-4-3	Sano, E.	G-6-2	Seo, B.	F-4-2	Shinozuka, Y.	F-4-1	Su, K. W.	P-2-13
Rosenwaks, Y.	KM-4-1	Sano, S.	P-8-15	Seo, K. S.	P-2-7	Shiojima, K.	P-6-11	Su, P.	G-3-4L
Roux, X. L.	CI-6-2, K-2-6	Sano, T.	P-2-16	Seo, M. S.	F-3-3	Shiokawa, T.	J-4-1	Su, P.	J-4-3, P-3-1
Rowell, P.	A-2-1	Santos, P. V.	J-6-1	Seo, S. H.	I-4-3L	Shiomi, G.	N-8-5	Su, P. Y.	P-7-29
Roy, D.	D-8-2	Saraya, T.	D-6-3	Serra, L.	J-7-1	Shiono, H.	H-6-2	Su, S. H.	B-1-4, P-10-4, BL-2-3
Rusop, M.	M-2-6	Sareen, P.	G-5-4L	Setsuhara, Y.	P-8-3	Shiosaka, S.	GH-2-5	Su, Y. H.	P-6-9
Ryoo, K. C.	F-6-5, P-4-5, P-4-14L	Sarkar, B.	P-6-5	Seyller, T.	KM-6-2	Shiozawa, K.	A-1-4	Su, Y. K.	B-4-3, P-5-16, P-8-18
Ryoo, Y.	P-2-7	Sasa, S.	A-5-1	Shahid, H.	I-9-3	Shirai, H.	C-3-3	Suda, J.	M-1-5, P-14-19, AL-6-1
Ryu, G. S.	P-10-20L	Sasagawa, K.	H-4-3, GH-2-5	Shahidi, G.	E-9-2, N-7-2	Shirai, H.	P-10-11	Suda, Y.	M-8-5
Ryu, SB.	F-4-2	Sasaki, K.	P-9-18	Sharma, S.	N-7-2	Shirai, Y.	C-9-3, C-9-4	Suemasu, T.	L-3-3, L-3-4, M-8-4
		Sasaki, M.	P-11-6, P-11-14	Shen, C. H.	L-2-4	Shiraishi, K.	J-4-1, N-8-6, P-9-9	Suemitsu, M.	KM-6-2
		Sasaki, S.	G-3-2, G-6-3	Shen, C. H.	L-2-4	Shiraishi, M.	N-7-1	Sugahara, S.	J-4-4
		Sasaki, T.	L-1-3, M-3-2	Sheu, S. S.	G-4-1, P-2-8	Shiraki, S.	L-8-2, L-8-3	Suganuma, K.	C-8-1, P-2-12
		Sasaki, T.	N-7-1	Shi, L. P.	P-4-11	Shiraki, Y.	L-3-4	Sugawa, K.	P-8-24
		Sasaki, T.	P-3-11	Shi, H.	P-2-10	Shiratani, M.	P-8-3	Sugawa, S.	A-8-1, D-2-4, D-5-1, E-3-3, E-3-4, P-1-8, P-3-16
		Sasaki, Y.	G-6-6L	Shi, X.	P-4-6	Shiratori, S.	B-2-6, P-10-7, P-10-17	Sugawara, H.	P-8-2
		Sasong, H. C.	P-13-26	Shiba, K.	P-11-10	Shirotori, T.	P-10-13	Sugawara, M.	I-9-1
		Saha, D.	P-6-5	Shibahara, K.	P-11-4	Shishido, N.	C-8-5	Sugawara, T.	I-1-1, I-8-4
		Saha, D.	P-6-5	Shibata, H.	G-6-1	Shitaka, Y.	P-11-1	Sugawara, T.	I-5-2
		Sahari, S. K.	P-1-4	Shibata, N.	P-10-16	Shoji, K.	M-1-2	Sugawara, T.	I-5-2
		Sahoo, A. K.	F-9-2	Shibata, T.	A-4-3	Shuto, T.	C-5-3	Suggiseti, P.	P-6-5
		Sahoo, S.	G-7-1	Shibata, T.	G-6-4, P-5-8	Siddik, M.	F-8-2, F-8-5	Sugie, R.	P-14-21L
		Saigusa, S.	F-7-1	Shibuya, Y.	P-1-7	Sieber, B.	P-7-21	Sugimoto, Y.	I-2-2, P-8-1
		Saito, H.	A-4-1	Shieh, J. M.	L-2-4, P-14-5	Siffalovic, P.	BL-2-5	Sugiyama, H.	A-2-2
		Saito, H.	N-7-2, P-12-15	Shigekawa, N.	I-1-5	Signamarcheix, T.	C-1-1	Sugiyama, M.	L-1-2
		Saito, K.	N-6-1	Shih, C. F.	M-2-4, P-2-13, BL-1-5, BL-1-7, BL-2-4	Sillon, N.	C-1-1	Sugiyama, Y.	P-7-9
		Saito, M.	C-8-4	Shih, H. A.	A-1-6, A-8-6	Simonet, P.	J-3-1	Suh, Y.	G-7-4
		Saito, M.	E-2-4	Shih, M. C.	P-7-10, P-7-28	Simpson, R.	F-6-1	Suhara, T.	I-3-4
		Saito, M.	G-6-5L	Shih, M. H.	I-2-3, I-2-4, P-9-2	Singh, N.	F-7-3	Suita, M.	A-1-4
		Saito, M.	I-4-1	Shih, P. J.	B-1-3	Skotnicki, T.	D-1-1	Sulthoni, M. A.	P-9-7
		Saito, S.	I-8-4, I-8-5	Shih, T. -L.	B-8-2	Sminov, V.	L-2-1	Sumarlina A. B. S.	A-2-3
		Saito, S.	P-1-3	Shima, A.	A-1-4	Smith, C. G.	J-7-5	Sumida, Y.	A-1-5
		Saito, S.	P-13-5	Shimada, A.	H-4-1	Sofue, Y.	KM-7-3	Sumiya, K.	M-3-4
		Saito, T.	L-3-3	Shimada, T.	B-2-5	Soga, T.	P-10-16	Summerfelt, S. R.	F-2-1
		Saitoh, E.	N-9-4	Shimada, T.	M-1-2	Sogawa, T.	J-5-1, P-9-8, P-9-18, P-13-5	Sun, D. -M.	K-3-3
		Saitoh, K.	P-2-14	Shimada, T.	P-10-10	Sohn, C. W.	P-6-1, P-13-2	Sun, M. -C.	D-4-2
		Saitoh, M.	D-7-2, D-8-4	Shimamoto, H.	C-5-2, P-2-2	Someya, T.	B-3-4, B-6-6, B-8-5, B-8-6, B-9-1, B-9-4	Sun, X.	C-5-4
		Sakai, H.	P-10-19L	Shimazaki, T.	P-8-9	Son, J. -W.	P-4-2	Sun, X.	P-13-25
		Sakai, M.	B-2-4, B-9-5	Shimizu, H.	I-1-4	Son, K. S.	P-13-9	Sun, Y. C.	P-7-28
		Sakai, S.	F-3-1	Shimizu, Y.	C-4-2	Song, S. H.	P-2-6	Sung, M. M.	B-2-1
		Sakai, S.	P-13-11	Shimizu, Y.	P-10-15	Song, C. K.	P-10-20L	Suwa, T.	E-3-3, P-1-8
		Sakai, T.	P-8-24	Shimo, Y.	L-8-5	Song, D.	P-4-12	Suzuki, A.	P-10-18
		Sakakibara, K.	D-1-3	Shimoda, T.	F-2-2			Suzuki, A.	P-14-7
		Sakakibara, Y.	P-7-16						
		Sakamoto, K.	E-1-3, E-1-5						

S

Saba, K.	A-4-4
Sadaf, S. M.	F-6-3, F-8-5
Sadana, D. K.	M-8-7, D-7-1
Sadoh, T.	E-6-1
Sagong, H. C.	P-6-1
Saha, D.	P-6-5
Sahari, S. K.	P-1-4
Sahoo, A. K.	F-9-2
Saigusa, S.	G-7-1
Saito, H.	A-4-1
Saito, H.	N-7-2, P-12-15
Saito, K.	N-6-1
Saito, M.	C-8-4
Saito, M.	E-2-4
Saito, M.	G-6-5L
Saito, M.	I-4-1
Saito, S.	I-8-4, I-8-5
Saito, S.	P-1-3
Saito, S.	P-13-5
Saito, T.	L-3-3
Saitoh, E.	N-9-4
Saitoh, K.	P-2-14
Saitoh, M.	D-7-2, D-8-4
Sakai, H.	P-10-19L
Sakai, M.	B-2-4, B-9-5
Sakai, S.	F-3-1
Sakai, S.	P-13-11
Sakai, T.	P-8-24
Sakakibara, K.	D-1-3
Sakakibara, Y.	P-7-16
Sakamoto, K.	E-1-3, E-1-5

Suzuki, D. -----N-8-2
 Suzuki, H. -----D-5-1
 Suzuki, H. -----L-1-3, M-3-2
 Suzuki, H. -----P-11-1
 Suzuki, J. -----A-8-2
 Suzuki, J. -----P-1-13
 Suzuki, J. -----KM-7-4
 Suzuki, K. -----E-2-3
 Suzuki, K. -----P-13-21, P-13-23
 Suzuki, K. -----P-13-27
 Suzuki, M. -----P-11-9
 Suzuki, R. -----E-8-3, E-8-4
 Suzuki, S. -----J-7-5
 Suzuki, S. -----P-8-19
 Suzuki, T. -----A-1-6, A-8-6
 Suzuki, T. -----C-8-5
 Suzuki, T. -----N-7-1
 Suzuki, T. -----N-9-2
 Suzuki, T. -----P-8-3
 Suzuki, Y. -----A-1-4
 Suzuki, Y. -----F-1-4
 Suzuki, Y. -----N-7-1, N-8-5
 Suzuki, Y. -----P-13-21
 Suzuno, M. -----L-3-4
 Sverdlov, V. -----P-12-13
 Swerts, J. -----F-2-3
 Syu, Y. C. -----P-7-11

T

Tōkei, Z. -----C-4-1
 Tabata, H. -----P-11-7
 Tabata, T. -----E-1-2, E-6-3
 Tabe, M. -----J-6-5, J-7-4
 Tabei, T. -----P-11-4
 Tachibana, T. -----L-9-3, P-14-1, P-14-2
 Tackeuchi, A. -----P-12-16L
 Tada, T. -----E-2-3, P-1-10, P-3-18
 Taguchi, D. -----B-6-5, B-7-5, BL-1-2, BL-1-3, BL-2-5, B-5-2
 Taguchi, Y. -----H-3-2
 Taiji, T. -----C-3-3
 Taima, T. -----BL-1-4
 Taira, T. -----N-6-3
 Taira, Y. -----I-3-3
 Tajima, Y. -----P-10-11
 Takaba, H. -----P-14-7
 Takada, N. -----B-2-2
 Takada, T. -----M-9-4L
 Takada, T. -----P-4-4
 Takada, Y. -----J-4-1
 Takagi, H. -----B-1-7L
 Takagi, J. -----N-7-3
 Takagi, K. -----P-10-5
 Takagi, K. -----P-10-11
 Takagi, S. -----D-4-1, E-8-3, E-8-4, E-8-5
 Takagi, S. -----P-4-4
 Takagi, Y. -----K-8-5
 Takahagi, T. -----P-11-1
 Takahashi, K. -----M-9-2

Takahashi, K. -----P-2-1
 Takahashi, K. -----P-14-1, P-14-2
 Takahashi, M. -----C-3-2
 Takahashi, M. -----F-3-1
 Takahashi, M. -----P-1-6
 Takahashi, M. -----P-2-5
 Takahashi, N. -----P-12-2
 Takahashi, R. -----KM-6-2
 Takahashi, S. -----L-8-2, L-8-3, P-14-18
 Takahashi, T. -----C-3-3
 Takahashi, T. -----I-5-1
 Takahashi, T. -----L-9-2
 Takahashi, T. -----P-3-21L
 Takahashi, T. -----P-11-9
 Takahashi, Y. -----J-4-2, P-9-17
 Takahashi, Y. -----BL-2-6
 Takahasi, M. -----L-1-3, M-3-2
 Takai, H. -----I-9-2
 Takai, I. -----GH-1-2
 Takakura, H. -----L-3-2, P-14-9
 Takakuwa, Y. -----C-1-2, C-1-3, KM-6-4
 Takamura, T. -----H-3-4
 Takamura, Y. -----J-4-4
 Takanashi, K. -----N-6-1, P-12-5, P-12-10
 Takano, K. -----D-1-5
 Takano, T. -----P-2-4
 Takano, Y. -----P-7-9
 Takao, H. -----GH-2-3
 Takeda, K. -----C-1-5L, C-9-1, L-2-6, P-6-4, P-8-3, P-13-19
 Takeda, K. -----C-3-3
 Takeda, Y. -----P-14-13
 Takehara, H. -----H-4-4, H-6-2
 Takehi, J. -----D-2-3
 Takei, M. -----E-7-3
 Takei, R. -----P-7-16
 Takenaka, M. -----D-4-1, E-8-3, E-8-4, E-8-5
 Takenobu, T. -----B-6-2
 Takenoshita, S. -----P-9-1
 Takeuchi, K. -----B-8-5, F-3-1, F-8-1, G-4-3, P-4-1, F-4-1
 Takeuchi, K. -----P-8-1
 Takeuchi, M. -----P-7-6
 Takeuchi, T. -----P-2-4
 Takikawa, M. -----A-8-2
 Takimiya, K. -----B-3-4, B-6-6, B-7-2, B-8-6
 Takimoto, T. -----I-4-2
 Takinai, K. -----I-8-6
 Tanaka, H. -----M-2-1
 Tamaki, H. -----M-9-3
 Tamari, K. -----P-10-7
 Tamotsu, H. -----P-14-6
 Tamura, K. -----B-7-3
 Tamura, Y. -----A-8-4
 Tamura, Y. -----J-6-4
 Tan, C. S. -----C-5-1
 Tanabe, S. -----D-2-3
 Tanabe, S. -----K-9-1
 Tanaka, C. -----D-7-2, D-8-4

Tanaka, D. -----J-7-5
 Tanaka, D. -----P-8-24
 Tanaka, H. -----B-6-2, B-6-4
 Tanaka, H. -----E-3-4
 Tanaka, H. -----H-6-3, H-6-4
 Tanaka, K. -----B-1-5, B-5-5L
 Tanaka, M. -----J-8-4
 Tanaka, M. -----P-2-5
 Tanaka, N. -----M-9-3, P-2-14
 Tanaka, S. -----KM-6-1
 Tanaka, T. -----A-1-2
 Tanaka, T. -----C-5-2, C-8-3, CI-7-2, G-4-2, H-4-2, P-2-2, P-5-3, P-5-5, P-11-3
 Tanaka, Y. -----B-6-3
 Tanaka, Y. -----I-9-1
 Tanaka, Y. -----P-12-2
 Tanamoto, T. -----J-8-2
 Tanemura, M. -----P-13-26
 Tanemura, T. -----P-7-18
 Tang, C. -C. -----P-9-13
 Tang, D. -M. -----K-1-1
 Tang, J. -----P-9-2
 Tang, S. H. -----P-6-9
 Tani, K. -----I-8-4, I-8-5
 Tani, M. -----A-5-2
 Tanida, K. -----P-2-1
 Tanigawa, H. -----N-9-2
 Taniguchi, K. -----D-5-4
 Taniyasu, Y. -----A-1-3
 Tanoi, S. -----G-5-2, G-5-3, G-7-3
 Tanoi, S. -----P-5-10
 Tanoue, F. -----P-8-2
 Taoka, N. -----D-4-1, E-8-3, E-8-4
 Tarun, A. -----M-9-1
 Tateno, K. -----P-13-5
 Tatsumi, T. -----P-2-9
 Taucha, S. -----J-7-2
 Taue, S. -----I-1-6, P-7-23
 Tavernier, C. -----P-2-17
 Tawara, T. -----I-5-4
 Taylor, R. J. -----I-2-2
 Tayurskii, D. A. -----J-7-1
 Tazawa, K. -----I-1-4
 Teehan, S. -----E-4-3
 Temmyo, J. -----K-8-6L, P-8-25, P-13-18
 Teng, K. -N. -----H-6-5
 Terada, S. -----I-1-2
 Terada, Y. -----BL-1-1
 Teramoto, A. -----A-8-1, D-2-4, D-5-1, E-3-3, E-3-4, P-1-8, P-3-16
 Teranishi, T. -----J-7-5
 Teraoka, S. -----J-7-2
 Teraoka, Y. -----KM-6-4
 Tezcan, D. S. -----C-3-1, H-6-3
 Tezuka, T. -----D-2-1, D-6-2, E-4-2
 Tezuka, T. -----E-8-6
 Thanh, P. V. -----F-2-2
 Theodoropoulou, N. -----M-2-5
 Tian, Y. -----K-3-3

Tielens, H. -----F-7-2
 Tien, T. C. -----P-4-16L
 Timmermans, M. Y. -----K-3-3
 Toan, D. T. -----P-10-19L
 Tobe, K. -----D-2-2
 Togashi, S. -----P-5-4
 Toh, E. -H. -----D-4-4
 Toh, K. -----L-3-3
 Toko, K. -----L-3-3, L-3-4, M-8-4
 Toko, K. -----P-9-1
 Tokuda, H. -----AL-6-5
 Tokuda, M. -----B-1-7L, P-13-12
 Tokuda, T. -----GH-2-5, H-4-3
 Tokuda, Y. -----P-6-11
 Tokuhara, T. -----B-9-1
 Tokuhisa, H. -----E-9-3, F-4-3
 Tokumitsu, E. -----F-2-2
 Tokumoto, K. -----P-13-12
 Tokunaga, H. -----P-11-9
 Tokuno, T. -----C-8-1, P-2-12
 Tokura, N. -----L-8-2, L-8-3, P-14-18
 Tokura, Y. -----P-9-18
 Tomida, K. -----F-2-3
 Tomiki, M. -----P-7-15
 Tominaga, J. -----F-6-1
 Tomioka, K. -----D-4-3, P-3-10, P-13-1, P-13-4
 Tomita, H. -----N-8-5
 Tomita, M. -----E-7-2
 Tomori, H. -----J-3-2, J-3-4
 Tomura, M. -----P-11-11
 Torimitsu, K. -----H-4-1, H-7-1
 Torimoto, T. -----P-8-19
 Toriumi, A. -----AL-6-2, E-1-2, E-4-4, E-6-2, E-6-3, K-8-2, K-8-4
 Toyota, Y. -----J-3-2, J-3-4
 Tozawa, K. -----P-12-4
 Trampert, A. -----M-3-1
 Tria, M. C. -----B-2-3
 Trigueros, S. -----P-11-12
 Trinh, B. N.Q. -----F-2-2
 Trinh, H. D. -----P-6-9
 Tsai, C. -C. -----A-5-4
 Tsai, C. -C. -----L-8-4
 Tsai, C. H. -----D-5-2
 Tsai, C. -M. -----P-7-29
 Tsai, C. T. -----D-5-2
 Tsai, F. -S. -----KM-4-4
 Tsai, H. -L. -----P-10-4
 Tsai, L. -C. -----H-6-5
 Tsai, M. -A. -----L-2-4, P-14-5, P-14-8
 Tsai, M. -J. -----F-6-4, F-9-1, F-9-2
 Tsai, M. -S. -----G-4-1, P-4-8, P-4-16L
 Tsai, N. C. -----P-3-3
 Tsai, T. -H. -----P-14-3
 Tssi, W. -C. -----P-8-20
 Tsai, Y. -J. -----P-7-7
 Tsai, Y. -L. -----L-2-4, P-14-5, P-14-8
 Tseng, K. -H. -----P-9-12
 Tseng, P. -C. -----P-14-8

Tseng, P. -C. -----L-2-4
 Tseng, T. -Y. -----J-5-5
 Tseng, Y. -M. -----F-8-3
 Tsuboi, H. -----P-14-7
 Tsubouchi, Y. -----G-7-1
 Tsuchida, Y. -----B-2-5
 Tsuchiya, H. -----K-3-1, P-3-17
 Tsuchiya, T. -----P-3-2
 Tsuchizawa, T. -----CI-7-1, I-8-6
 Tsuji, H. -----D-5-4
 Tsuji, K. -----B-2-6
 Tsuji, K. -----P-10-9
 Tsuji, M. -----KM-6-5
 Tsuji, S. -----I-1-1
 Tsujioka, T. -----P-10-9
 Tsukada, J. -----E-9-3, F-4-3
 Tsukagoshi, K. -----J-3-2, J-3-4, K-9-3, K-9-4
 Tsunoda, M. -----N-6-4
 Tsurumachi, N. -----P-9-3, P-12-2
 Tsurumi, N. -----A-1-2
 Tsuruta, K. -----P-7-23
 Tsutsui, K. -----B-1-7L, P-13-12
 Tsutsui, K. -----E-3-1, E-3-2, M-9-2, P-1-11
 Tsutsumi, J. -----P-7-15
 Tsuya, D. -----J-3-2
 Tu, B. -M. -----P-7-8
 Tu, C. -C. -----P-7-2
 Tu, C. -H. -----P-5-16
 Tu, K. -C. -----P-3-15
 Tu, P. -M. -----I-2-4, I-2-5, M-1-6, P-7-2
 Tu, Y. -C. -----KM-4-4
 Tue, P. T. -----F-2-2
 Tutunjan, N. -----H-6-3

U

Uang, K. M. -----P-14-16
 Uchida, K. -----C-9-2
 Uchida, K. -----D-8-4, K-2-4, P-3-21L
 Uchiyama, N. -----B-6-6
 Uda, Y. -----P-12-2
 Udayakumar, K. R. -----F-2-1
 Udhiarto, A. -----J-6-5
 Ueda, H. -----A-8-1
 Ueda, K. -----N-6-4, P-12-4, P-12-6
 Ueda, K. -----N-9-2
 Ueda, N. -----G-3-3
 Ueda, S. -----P-1-14
 Ueda, T. -----A-1-2
 Ueda, T. -----C-8-2
 Ueda, T. -----P-2-10
 Ueda, Y. -----P-10-3
 Uehara, K. -----I-1-4
 Uemura, S. -----B-2-2
 Uemura, T. -----N-6-3, N-7-4, P-12-9
 Ueno, K. -----B-1-6
 Ueno, T. -----E-1-4
 Uenuma, M. -----P-11-13
 Ueyama, H. -----I-5-1
 Ueyama, Y. -----I-1-3

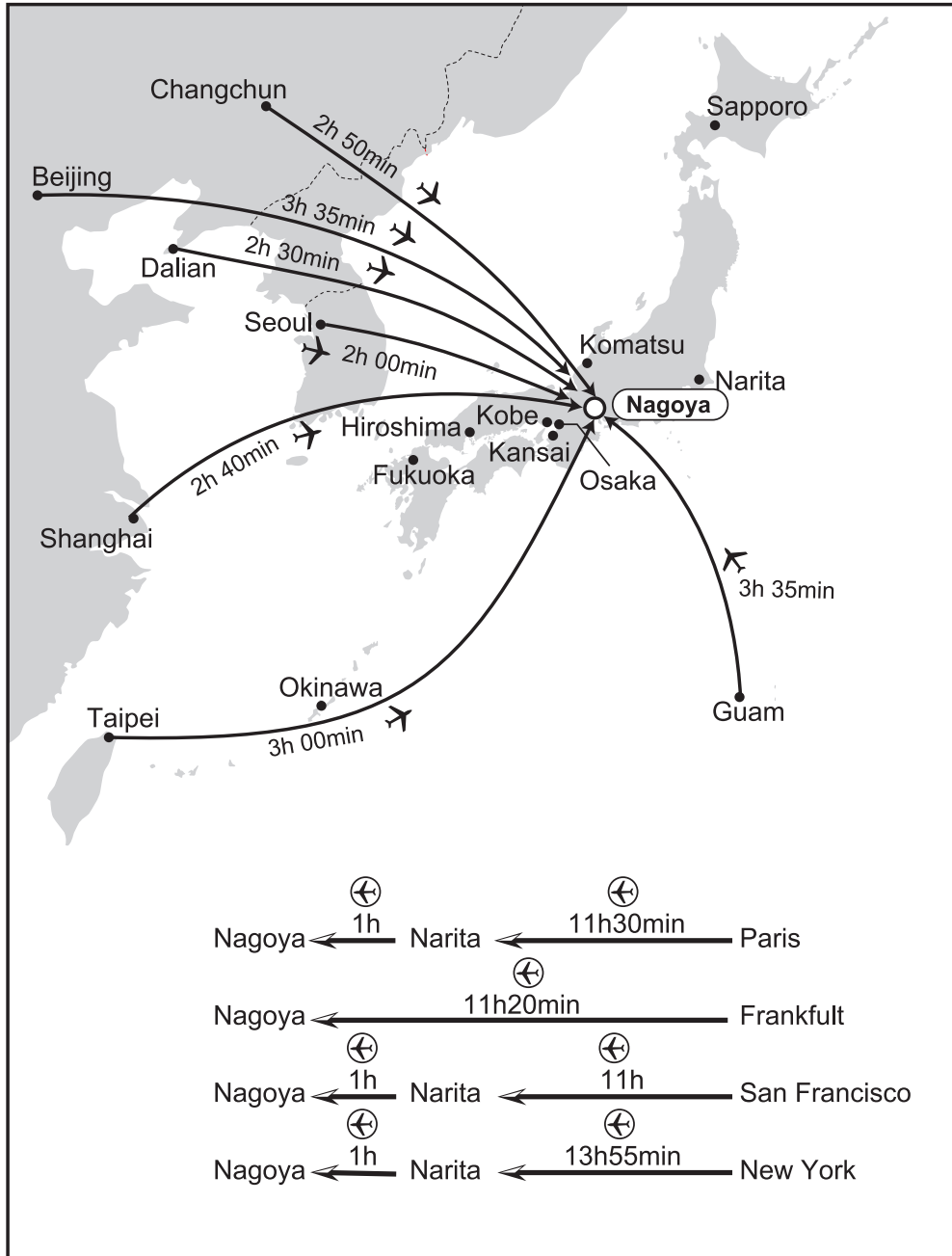
Ujihara, T.	P-8-11	Wang, J.	P-13-25	Wei, A.	D-6-1	Yagisawa, T.	P-2-9	Yamanouchi, T.	A-8-2
Umeda, M.	P-10-16	Wang, J. C.	P-1-20L	Wei, H.	C-1-4	Yagishita, A.	D-7-1	Yamao, T.	P-10-6
Umehara, M.	P-14-13	Wang, J. F.	P-9-10, P-9-12	Wei, K. L.	P-3-19	Yagyū, E.	A-1-4	Yamasaki, J.	M-9-3
Umeno, M.	KM-6-6	Wang, J. L.	P-8-20	Wei, O. Y.	B-7-1	Yahagi, T.	P-13-24	Yamasaki, N.	P-10-2
Umezawa, S.	P-9-6	Wang, J. R.	BL-2-3	Wei, X.	P-13-24	Yakata, S.	P-12-14	Yamasaki, S.	P-11-11
Uno, S.	J-4-5, P-5-1	Wang, J. Y.	P-2-8	Weiss, M.	B-7-1, B-7-5, BL-2-5	Yamada, A.	L-8-3	Yamashima, M.	P-9-3
Uno, Y.	GH-1-4	Wang, K. L.	P-3-7	Weng, S. -C.	P-9-16	Yamada, A.	L-9-5	Yamashiro, Y.	K-9-2
Urabe, Y.	B-2-4	Wang, L.	F-2-1	Weng, W. C.	P-10-4	Yamada, H.	E-2-2	Yamashita, I.	H-6-3, H-6-4
Urabe, Y.	E-8-5	Wang, M.	D-7-1	Wernersson, L. -E.	KM-4-3L	Yamada, H.	E-8-4, E-8-5	Yamashita, I.	H-7-3, P-11-10,
Uraoka, Y.	A-5-2, A-5-3, P-11-10,	Wang, M.	F-9-3	Whang, D.	P-13-9	Yamada, H.	I-1-3		P-11-13, P-11-14
	P-11-13, P-11-14	Wang, P. H.	P-7-4, P-14-16	Whitten, J. L.	M-2-3	Yamada, H.	I-3-3, I-4-1, CI-7-3	Yamashita, N.	G-6-4
Urbanczyk, A.	KM-5-1	Wang, P. R.	P-7-4	Williams, D. M.	P-10-16	Yamada, I.	P-10-16	Yamashita, T.	P-7-15
Urteaga, M.	A-2-1	Wang, R. L.	P-5-16	Wilmart, Q.	J-5-2	Yamada, K.	C-8-4	Yamashita, T.	P-9-6
Uryu, K.	P-9-14	Wang, S. C.	I-2-5, P-7-3	Wilson, A. F.	AL-7-5	Yamada, K.	D-7-3	Yamauchi, H.	B-2-4, B-9-5
Uryu, N.	GH-1-3	Wang, S. J.	A-5-5, KM-4-4, P-1-18,	Witters, L.	E-1-1	Yamada, K.	I-8-6, CI-7-1	Yamauchi, H.	E-9-3, F-4-3
Usami, N.	L-3-3, L-3-4, M-8-4		P-7-4, P-14-16	Won, C. -H.	AL-6-6, P-6-2	Yamada, S.	D-6-4	Yan, H. C.	B-4-3
Usuda, K.	E-7-2	Wang, S. K.	E-1-2	Wong, H. -S. P.	C-1-4, F-6-2	Yamada, S.	E-5-3	Yan, H. J.	B-8-2
Usui, H.	B-1-5, B-2-3, B-5-5L	Wang, S.	P-8-4	Woo, J.	F-6-3, F-8-2, F-8-5	Yamada, S.	BL-2-6	Yan, W. S.	P-12-3
Utsumi, H.	P-10-2	Wang, T. C.	P-14-16	Wouters, D. J.	F-7-2	Yamada, T.	B-9-3	Yanagisawa, Y.	P-11-11
Uwai, K.	P-7-12	Wang, W.	F-9-3	Wu, C. H.	A-5-5, P-1-18	Yamada, T.	P-7-20	Yang, H. X.	P-4-11
		Wang, W.	P-1-12	Wu, C. M.	P-10-4	Yamada, T.	KM-6-4	Yang, C. H.	L-1-4
	V	Wang, W. C.	F-2-3	Wu, C. W.	G-4-1	Yamada, Y.	K-3-1	Yang, C. H.	P-9-12
Van Elshocht, S.	F-2-3	Wang, W. Y.	B-1-4	Wu, C. Y.	P-3-3	Yamada, Y.	L-9-1	Yang, C. L.	P-1-18
Van der Cingel, J.	A-5-3	Wang, X.	F-6-1	Wu, C. Y.	P-8-20	Yamada, Y.	P-6-11	Yang, C. M.	AL-6-6
Vandeweyer, T.	F-7-2	Wang, X.	P-1-12	Wu, G. -Y.	P-4-9	Yamada, Y.	P-9-4	Yang, F. J.	P-12-5
Vangoidsenhoven, D.	F-7-2	Wang, X. -Y.	A-8-4	Wu, H. T.	M-2-4, P-2-13, BL-1-5,	Yamagata, Y.	P-10-11	Yang, H.	E-1-3, E-1-5
Vanslette, D.	C-8-2	Wang, Y.	F-9-3		BL-1-7, BL-2-4	Yamagishi, M.	J-8-6L	Yang, H. C.	P-7-3, P-7-8
Vegso, K.	BL-2-5	Wang, Y.	L-1-2	Wu, J. C.	M-2-4	Yamagiwa, H.	C-8-4, P-2-4	Yang, H. J.	P-9-15
Verbrugge, B.	F-7-2	Wang, Y.	P-13-16	Wu, J. J.	L-8-4	Yamaguchi, H.	A-4-4, J-5-1, J-5-2, KM-6-3	Yang, J. W.	P-4-2
Vereecke, B.	H-7-2	Wang, Y. C.	P-9-2	Wu, J. R.	P-1-19L, P-2-18L	Yamaguchi, M.	L-1-3, L-1-5, P-8-17,	Yang, P. Y.	P-8-20
Vijayashree, P. S.	K-9-5	Wang, Y. S.	P-7-5, P-9-12	Wu, J. Y.	P-1-18		P-10-8, P-14-11, P-14-12	Yang, S. D.	B-3-3
Vincent, B.	E-1-1	Wang, Y. Y.	E-7-4	Wu, K.	M-2-3	Yamaguchi, M.	P-13-7	Yang, S. H.	B-1-3
Vinet, M.	E-9-2	Wang, Z.	B-1-1, BL-2-1	Wu, M. C.	BL-1-6, P-9-2	Yamaguchi, N.	P-2-1	Yang, S. R. E.	J-4-2
Vivien, L.	K-2-6, CI-6-2	Washio, K.	J-7-3	Wu, M. L.	P-1-19L, P-2-18L	Yamaguchi, R.	P-12-16L	Yang, W. L.	F-5-3
Vrancken, E.	E-1-1	Watahiki, T.	L-2-3	Wu, N. J.	P-7-7	Yamaguchi, T.	E-4-1	Yang, Y.	D-4-4
van Hoof, C.	H-6-3	Watanabe, A.	P-7-19	Wu, S. C.	P-9-13	Yamaguchi, T.	E-7-3	Yang, Y.	H-3-4
van Otten, Frank W. M.	KM-5-1	Watanabe, E.	J-3-2	Wu, S. H.	BL-1-7, BL-2-4, M-2-4, P-2-13	Yamaguchi, T.	P-9-19	Yang, Y.	P-13-16
		Watanabe, H.	G-3-3	Wu, S. L.	P-3-3, P-3-6	Yamaguchi, T. J.	P-5-13	Yang, Y. C.	P-3-7
	W	Watanabe, H.	P-7-15	Wu, T. -H.	P-9-16	Yamaha, T.	E-7-1	Yang, Y. S.	H-6-5
Wada, A.	P-1-1, P-11-11	Watanabe, H.	P-11-13	Wu, T. B.	P-4-7	Yamamoto, A.	L-3-2	Yano, K.	A-5-3
Wada, K.	I-8-3, I-8-6	Watanabe, K.	J-6-4, P-13-6	Wu, T. T.	P-7-11	Yamamoto, H.	A-4-2	Yao, I. C.	J-5-5
Wada, S.	P-14-11	Watanabe, K.	GH-2-4	Wu, T. Y.	P-4-8	Yamamoto, H.	C-9-1	Yao, Y. C.	L-1-4
Wada, T.	P-14-10	Watanabe, M.	P-9-14	Wu, Y. C.	P-2-8	Yamamoto, K.	E-1-3, E-1-5	Yashiro, T.	A-8-2
Wada, Y.	B-1-7L, P-13-12	Watanabe, N.	C-5-3	Wu, Y. C.	P-14-3	Yamamoto, M.	L-8-3	Yasuda, M.	G-3-2, G-6-3
Wakahara, A.	P-6-8, P-8-16	Watanabe, O.	G-7-1	Wu, Y. H.	P-1-19L, P-2-18L	Yamamoto, M.	N-6-3, N-7-4, P-12-9	Yasuda, T.	E-8-3, E-8-4, E-8-5, M-9-4L
Wakejima, A.	AL-7-5	Watanabe, S.	B-6-2	Wu, Y. K.	P-8-14	Yamamoto, N.	I-9-2, P-8-2	Yasui, K.	B-4-1
Wakita, K.	KM-6-6	Watanabe, S.	K-2-2	Wu, Y. L.	I-2-5	Yamamoto, T.	B-3-4, B-6-6, B-8-6	Yasui, Y.	M-3-3
Wallace, R. M.	E-8-1	Watanabe, S.	N-7-2	Wu, Y. S.	J-4-3	Yamamoto, T.	D-7-1	Yasuoka, K.	P-1-7
Wang, B. C.	P-3-6	Watanabe, S.	P-2-3			Yamamoto, T.	I-9-1	Yasutomi, K.	GH-1-2
Wang, C. -W.	CI-6-4, P-7-30	Watanabe, T.	J-5-1		X	Yamamoto, T.	K-2-2	Yatabe, R.	P-9-1
Wang, C. H.	P-7-3	Watanabe, T.	CI-7-1, I-8-6	Xiang, J.		Yamamoto, Y.	P-8-11	Yatago, M.	KM-5-2
Wang, C. L.	P-8-20	Watanabe, Y.	H-4-2	Xie, H. W.	P-1-12	Yamamura, A.	P-12-11	Ye, M. R.	F-5-3
Wang, D.	B-1-2	Watanabe, Y.	L-9-5	Xu, H.	P-3-14	Yamana, K.	P-4-4	Ye, T.	P-1-12
Wang, D.	E-1-3, E-1-5	Watanabe, Y.	N-9-3	Xu, Y.	P-13-25	Yamanaka, K.	A-1-4	Yeh, C. C.	A-5-4
Wang, G.	B-8-3	Watarai, M.	C-3-3			Yamanaka, T.	E-1-5	Yeh, C. C.	A-5-4
Wang, G.	E-1-1	Watts, M. R.	CI-6-1		Y	Yamanashi, Y.	J-8-3	Yeh, K. L.	D-5-3
Wang, H.	B-6-6	Webb, B.	C-8-2	Yabe, K.		Yamane, K.	P-8-16	Yen, S. F.	P-7-29
Wang, H.	P-8-4	Weber, K.	B-1-6	Yafune, N.	AL-6-5	Yamane, K.	P-10-7	Yen, S. S.	M-1-6, P-7-2, P-7-8
Wang, I. -S.	H-7-4L	Weber, O.	E-2-1	Yagi, S.	A-1-5	Yamane, T.	P-3-2	Yen, W. Y.	P-7-1

Yeo, Y. C. ----- A-2-4, A-8-5, D-4-4, P-4-10
 Yi, X. ----- K-2-3
 Yin, L. C. ----- K-1-1
 Yoh, K. ----- P-13-3
 Yokoi, J. ----- E-5-1
 Yokota, T. ----- B-3-4, B-6-6, B-8-5, B-8-6, B-9-1
 Yokoyama, H. ----- A-2-2, I-1-5
 Yokoyama, M. ----- B-1-4, BL-2-3, P-10-4
 Yokoyama, M. ----- D-4-1, E-8-3, E-8-4
 Yokoyama, N. ----- C-1-2, C-1-3, C-3-2, K-9-4
 Yokoyama, S. ----- B-5-1
 Yokoyama, S. ----- CI-6-5, P-4-4, P-7-22,
 P-11-4, P-11-9
 Yokoyama, T. ----- P-7-9
 Yonemura, H. ----- BL-2-6
 Yonezawa, A. ----- D-5-1
 Yoo, H. ----- F-4-2
 Yoo, H. W. ----- P-2-6
 Yoo, W. S. ----- C-8-2, P-2-6
 Yoon, J. ----- B-8-3
 Yoon, Y. T. ----- J-4-1
 Yoshida, A. ----- I-8-6
 Yoshida, A. ----- P-14-20
 Yoshida, H. ----- P-10-2, P-10-15
 Yoshida, H. ----- P-14-1, P-14-2
 Yoshida, M. ----- B-2-2
 Yoshida, M. ----- E-6-3
 Yoshida, M. ----- L-1-1
 Yoshida, M. ----- PL-2-1
 Yoshida, T. ----- P-6-6
 Yoshida, Y. ----- N-8-4
 Yoshida, Y. ----- BL-1-4
 Yoshigoe, A. ----- KM-6-4
 Yoshikawa, M. ----- P-14-21L
 Yoshikawa, N. ----- J-8-3
 Yoshiki, K. ----- P-2-5
 Yoshimasu, T. ----- G-7-4
 Yoshimizu, Y. ----- C-9-2
 Yoshimura, M. ----- P-3-10
 Yoshioka, Y. ----- I-9-2
 Yotsuhashi, S. ----- L-9-1
 You, H. W. ----- P-4-3
 You, J. ----- BL-2-6
 Yu, C. H. ----- J-4-3
 Yu, C. J. ----- P-6-7
 Yu, C. W. ----- P-7-13
 Yu, H. C. ----- B-4-3
 Yu, P. ----- L-2-4, P-14-4, P-14-5, P-14-8
 Yu, R. ----- P-3-12
 Yu, X. ----- P-8-4, P-12-3
 Yuan, C. T. ----- P-9-2
 Yuasa, S. ----- N-7-2, N-8-5, P-12-15
 Yue, H. ----- N-6-5
 Yukita, Y. ----- P-11-3
 Yun, C. S. ----- P-14-18
 Yun, H. J. ----- B-3-3
 Yun, J. Y. ----- P-6-3

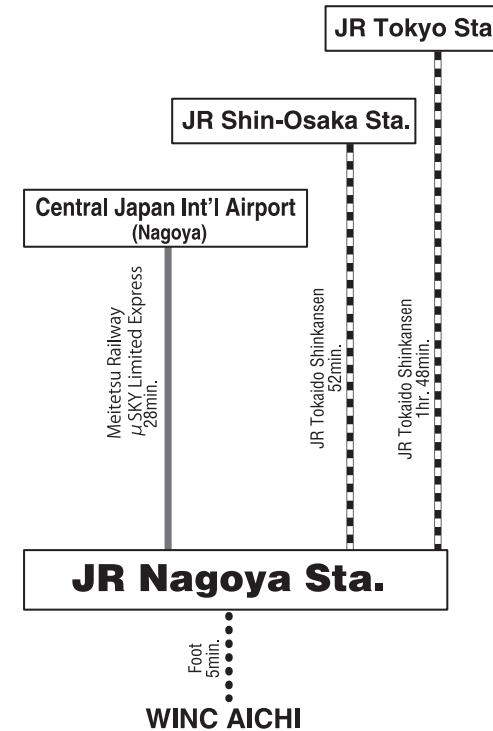
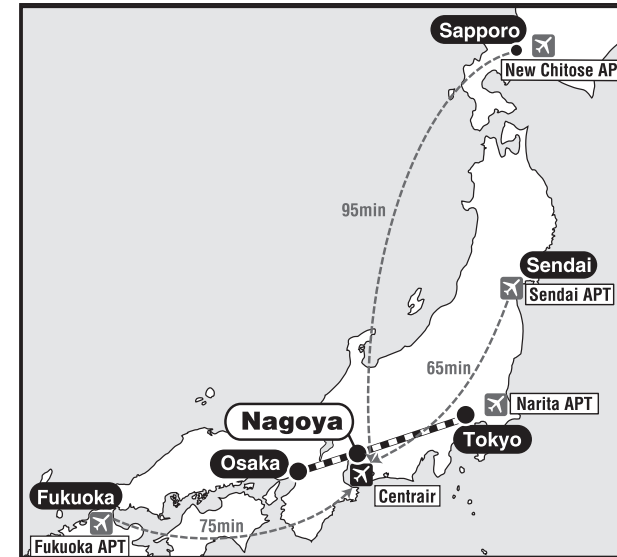
Z

Zaima, S. ----- E-5-1, E-6-4, E-7-1, P-1-5
 Zaitso, M. ----- P-7-18
 Zamdmer, N. ----- D-7-1
 Zamri, M. ----- P-13-26
 Zan, H. W. ----- A-5-4, B-3-5, I-2-4
 Zayets, V. ----- P-12-15
 Zeller, D. ----- L-2-2, M-2-3, P-4-13L
 Zenitani, Y. ----- L-9-1
 Zhan, C. ----- D-4-4
 Zhang, F. ----- F-7-3
 Zhang, G. ----- P-13-5
 Zhang, G. ----- P-14-17
 Zhang, J. ----- P-1-12
 Zhang, J. ----- P-3-14
 Zhang, K. W. ----- F-9-3
 Zhang, L. ----- B-6-5, BL-2-5
 Zhang, L. ----- C-5-1
 Zhang, R. ----- P-5-8
 Zhang, W. ----- C-5-4
 Zhang, X. ----- A-8-5
 Zhang, X. ----- F-3-1
 Zhang, X. H. ----- N-6-5
 Zhang, Y. ----- M-1-3
 Zhang, Y. ----- P-13-16
 Zhang, Z. ----- D-7-1
 Zhang, Z. ----- P-4-13L
 Zhao, R. ----- P-4-11
 Zhao, D. D. ----- E-6-2
 Zhao, F. ----- P-6-7
 Zhao, J. H. ----- P-8-4, N-6-5, P-12-3
 Zhao, Y. ----- B-9-4
 Zhao, Y. G. ----- P-12-3
 Zheng, B. ----- P-11-13
 Zhou, C. ----- AL-7-1
 Zhou, Q. ----- AL-7-1
 Zhou, Y. K. ----- P-12-8
 Zhu, L. J. ----- P-12-3
 Zhu, Y. ----- D-7-1
 Zhu, Y. G. ----- N-6-5
 Zhu, Z. ----- A-2-4
 Zhu, Z. ----- D-7-1, M-8-7
 Ziebell, M. ----- CI-6-2
 Zous, N. K. ----- F-3-2
 Zschieschang, U. - B-3-4, B-6-6, B-8-5, B-8-6

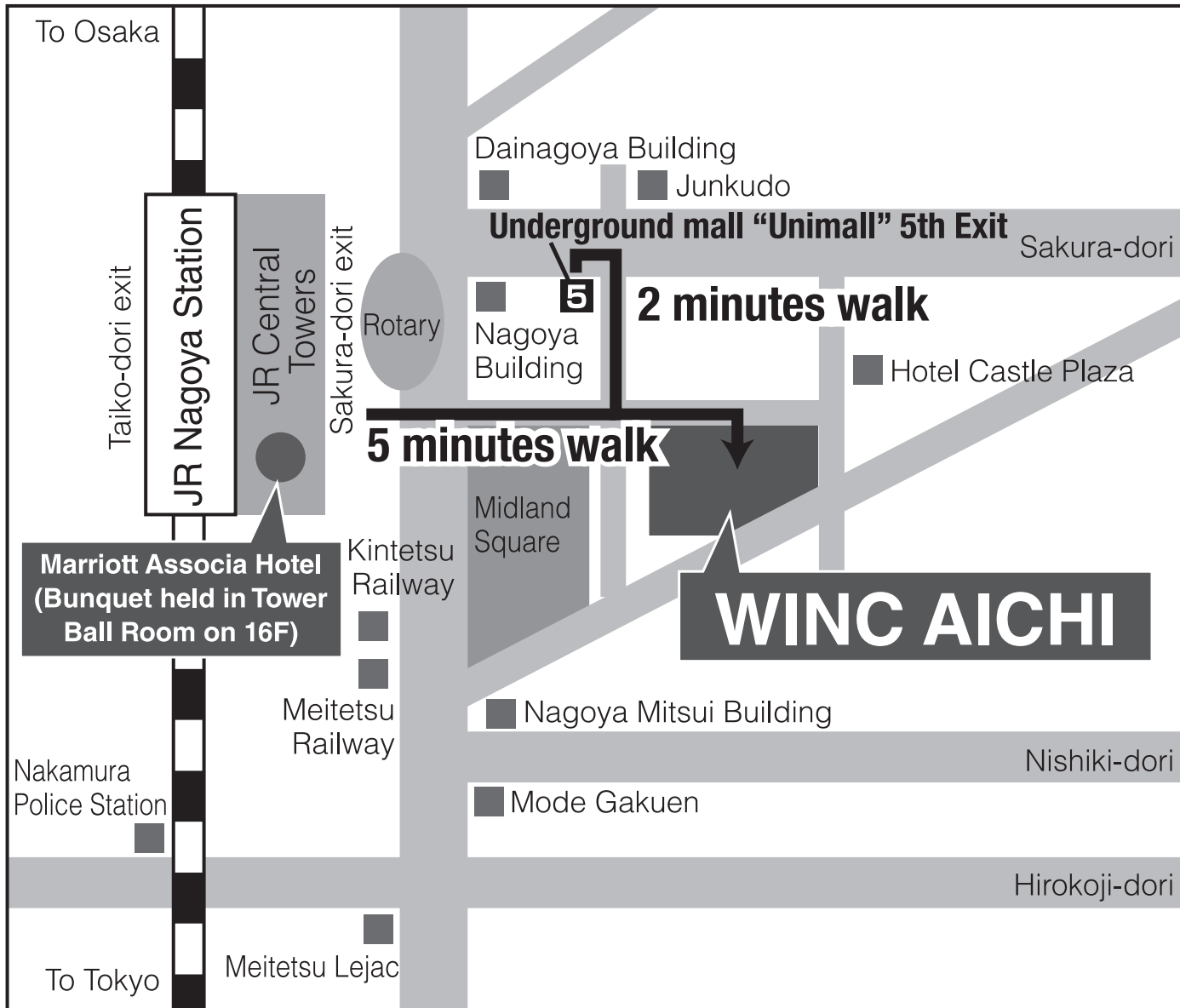
Flying in to Central Japan Int'l Airport Nagoya, from Abroad



ACCESS TO WINC AICHI

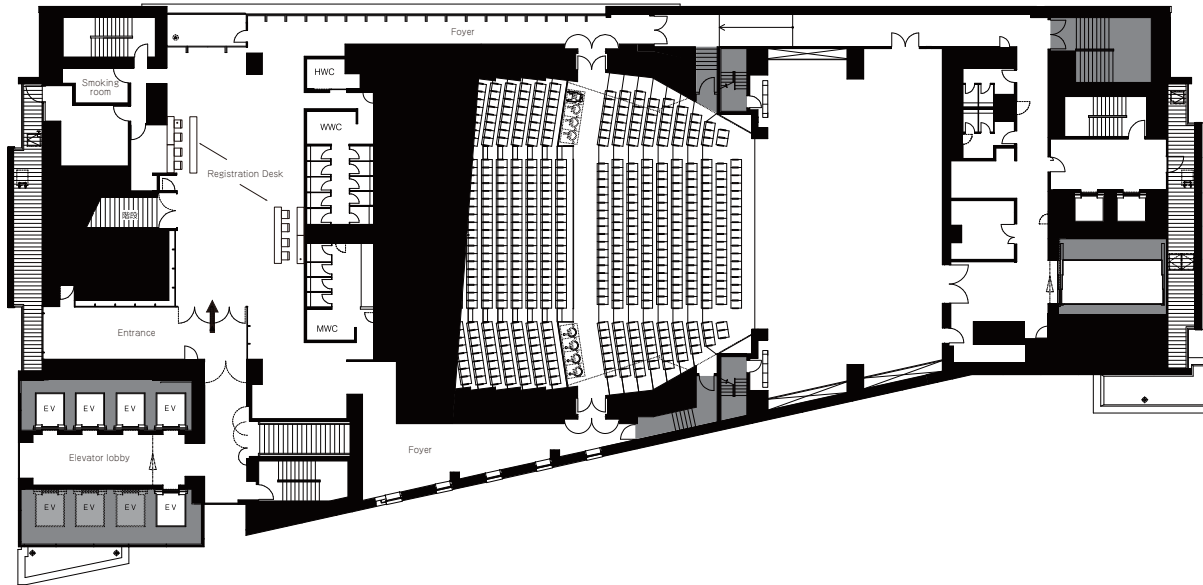


ACCESS TO WINC AICHI

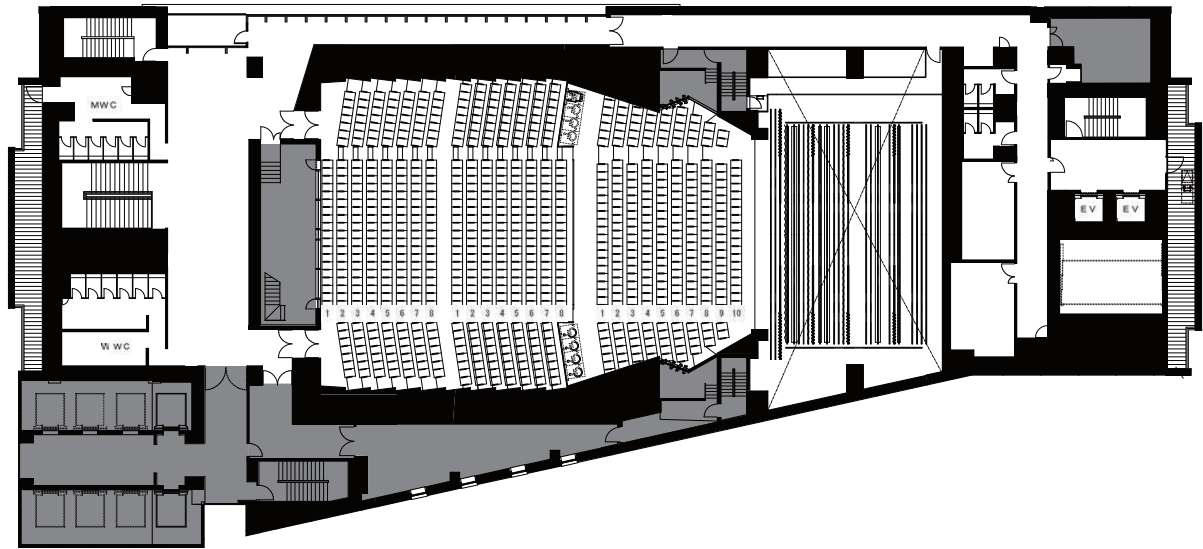


FLOOR GUIDE

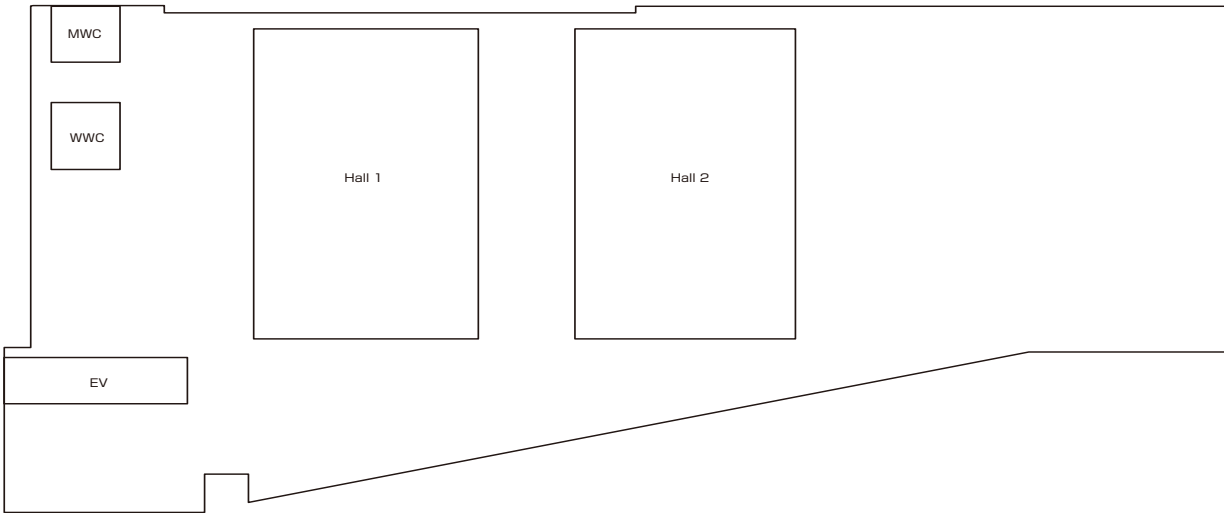
2F WING HALL



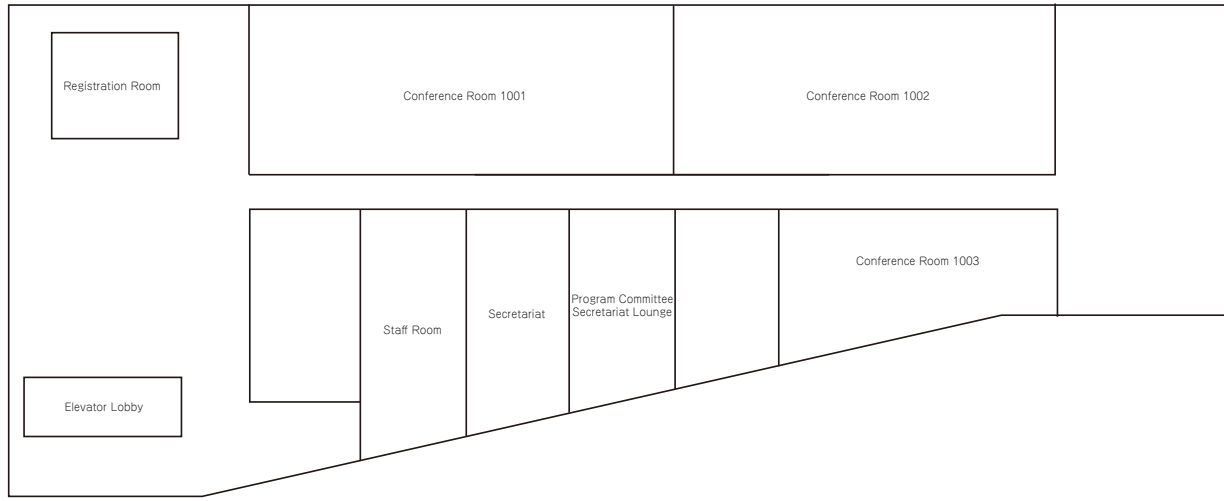
3F WING HALL



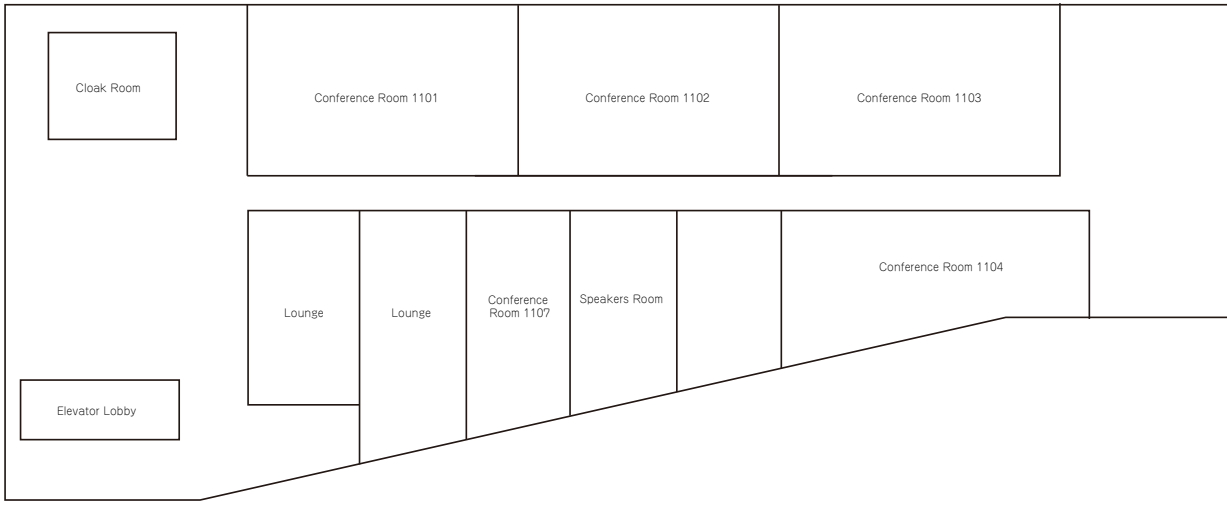
5F HALL



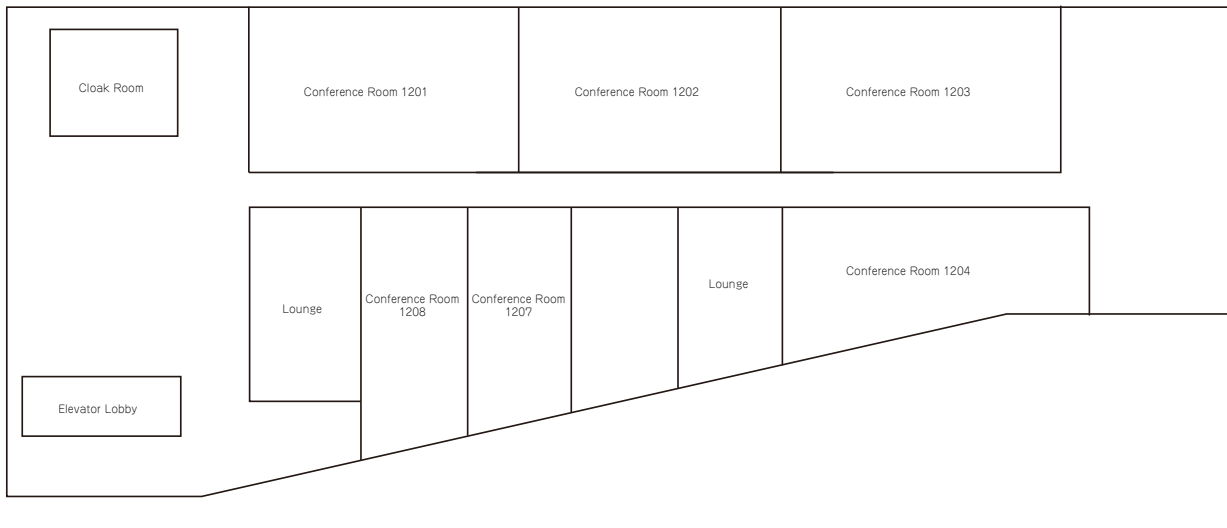
10F



11F



12F



MEMO

PROGRAM TIME TABLE

Wednesday, September 28						
9:30-12:15 Opening & Plenary Sessions (2F WINC HALL)						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
13:30-15:15 Area 6: A-1: GaN FET Technologies	13:30-15:15 Area 10&14: BL-1: Organic Photovoltaics (1)	13:30-15:15 Area 10: B-1: OLEDs	13:30-15:15 Area 2: C-1: Future Interconnect	13:30-15:10 Area 3: D-1: Modeling and Circuits	13:30-15:20 Area 1: E-1: Ge-MOS	13:30-15:00 Area 4: F-1: STT-RAM
15:40-16:55 Area 6: A-2: III-V HBTs and FETs	15:40-17:25 Area 10&14: BL-2: Organic Photovoltaics (2)	15:40-17:25 Area 10: B-2: Organic device fabrication process and interface control		15:40-17:00 Area 3: D-2: Device & Characteristics	15:45-17:15 Area 1: E-2: Characterization in Gate Stacks	15:40-17:30 Area 4: F-2: FeRAM/DRAM/SRAM
19:00-21:00 《Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)》						
Thursday, September 29						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
		9:00-10:15 Area 10: B-3: Novel structure and fabrication process for OTFT	9:00-10:00 Area 2: C-3: Memory Application		9:00-10:20 Area 1: E-3: Process Technology and Analysis	9:00-10:00 Area 4: F-3: NAND
10:45-12:00 Short Presentation Area 6		10:45-12:00 Short Presentation Area 10	10:45-12:00 Short Presentation Area 2	10:45-12:00 Short Presentation Area 3	10:45-12:00 Short Presentation Area 1	10:45-12:00 Short Presentation Area 4
13:30-15:00 《Poster Session》 6F Exhibition Hall						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
15:25-16:25 Area 6: A-4: Novel III-V Devices and Applications	15:25-16:40 Area 8&13: KM-4: Nanowire Growth and Characterization	15:25-16:40 Area 10: B-4: Organic memory and photonic devices (1)	15:25-16:35 Area 2: C-4: Characterization (1)	15:25-16:45 Area 3: D-4: Tunnel-FET	15:25-16:55 Area 1: E-4: Junction Technology and Physics	15:25-16:25 Area 4: F-4: e-Flash
17:05-18:20 Area 6: A-5: Oxide Devices	17:05-18:20 Area 8&13: KM-5: Nanowire and Quantum Structures	17:05-18:20 Area 10: B-5: Organic memory and photonic devices (2)	17:05-18:25 Area 2: C-5: 3D Interconnect (1)	17:05-18:25 Area 3: D-5: Noise and Fluctuation	17:20-18:20 Area 1: E-5: Ge Metallization	17:05-18:05 Area 4: F-5: CT-Flash
19:00-21:00 《Rump Sessions》 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”						
Friday, September 30						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
9:00-10:45 Area 6&14: AL-6: SiC&GaN Power Switching Devices (1)	9:00-10:45 Area 8&13: KM-6: Graphene Synthesis	9:00-10:45 Area 10: B-6: Device physics and characterization of OTFT (1)		9:00-10:30 Area 3: D-6: Advanced CMOS Devices	9:00-10:20 Area 1: E-6: Ge Process Technology (1)	9:00-10:50 Area 4: F-6: PRAM/ReRAM (1)
11:15-12:30 Area 6&14: AL-7: SiC&GaN Power Switching Devices (2)	11:15-12:30 Area 8&13: KM-7: Graphene Application	11:15-12:30 Area 10: B-7: Device physics and characterization of OTFT (2)		11:15-12:25 Area 3: D-7: ET-SOI and Nanowire Devices	10:45-12:05 Area 1: E-7: Ge Process Technology (2)	11:15-12:40 Area 4: F-7: ReRAM (2)
14:00-15:30 Area 6: A-8: Processing and Characterization Technologies		14:00-15:45 Area 10: B-8: OTFT application (1)	14:00-15:50 Area 2: C-8: 3D Interconnect (2) and Characterization (2)	14:00-15:30 Area 3: D-8: Device Reliability	13:35-15:55 Area 1: E-8: III-V CMOS Technology	14:00-15:40 Area 4: F-8: ReRAM (3)
		16:10-17:25 Area 10: B-9: OTFT application (2)	16:10-17:30 Area 2: C-9: Characterization (3)		16:10-17:25 Area 1: E-9: Advanced Si Technology	16:10-17:10 Area 4: F-9: ReRAM (4)

- | | |
|---|---|
| <p>Area Scope</p> <ul style="list-style-type: none"> Area 1: Advanced LSI Processing & Materials Science Area 2: Advanced Interconnect / Materials Technology and Characterization Area 3: CMOS Devices / Device Physics Area 4: Advanced Memory Technology Area 5: Advanced Circuits and Systems | <ul style="list-style-type: none"> Area 6: Compound Semiconductor Electron Devices and Related Technologies Area 7: Photonic Devices and Optoelectronic Integration Area 8: Advanced Material Synthesis and Crystal Growth Technology Area 9: Physics and Application of Novel Functional Devices and Materials Area 10: Organic Materials Science, Device Physics, and Applications |
|---|---|

PROGRAM TIME TABLE

Wednesday, September 28							
9:30-12:15 Opening & Plenary Sessions (2F WINC HALL)							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
13:30-15:10 Area 5&11: GH-1: Image Sensor and MEMS Technology (1)		13:30-15:15 Area 7: I-1: Optical Link and Related Devices		13:30-15:15 Area 13: K-1: CNT Property	13:30-15:15 Area 14: L-1: Quantum Well& III-V Solar Cell	13:30-15:15 Area 8: M-1: Nitrides	
15:40-17:20 Area 5&11: GH-2: Image Sensor and MEMS Technology (2)		15:40-17:10 Area 7: I-2: Photonic Crystals		15:40-17:10 Area 13: K-2: CNT Device	15:40-17:25 Area 14: L-2: Thin-Film Silicon Solar Cells	15:40-17:25 Area 8: M-2: Oxides	
19:00-21:00 《Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)》							
Thursday, September 29							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
9:00-10:15 Area 5: G-3: Variation and Reliability	9:00-10:15 Area 11: H-3: Electric, Magnetic and Optical Biosensing	9:00-10:15 Area 7: I-3: Plasmonics and Nonlinear Devices	9:00-10:15 Area 9: J-3: Graphene Quantum Transport	9:00-10:00 Area 13: K-3: Nanowire/Nanotube FET	9:00-10:15 Area 14: L-3: Compound Thin Film Solar Cells	9:00-10:15 Area 8: M-3: III-V Compounds	
10:45-12:00 Short Presentation Area 5	10:45-12:00 Short Presentation Area 11	10:45-12:00 Short Presentation Area 7	10:45-12:00 Short Presentation Area 9	10:45-12:00 Short Presentation Area 13	10:45-12:00 Short Presentation Area 14	10:45-12:00 Short Presentation Area 8	10:45-12:00 Short Presentation Area 12
13:30-15:00 《Poster Session》 6F Exhibition Hall							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
15:25-16:35 Area 5: G-4: Circuits for 3D Structure	15:25-16:40 Area 11: H-4: Neural Interface Technology	15:25-16:25 Area 7: I-4: Novel Optical Devices	15:25-16:40 Area 9: J-4: Advanced MOS-FETs and Transport				
17:05-18:20 Area 5: G-5: RF Circuits (1)		17:05-18:05 Area 7: I-5: Er-Doped Devices	17:05-18:20 Area 9: J-5: MEMS & Thin-Film Devices				
19:00-21:00 《Rump Sessions》 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”							
Friday, September 30							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
9:00-10:50 Area 5: G-6: Analog and Digital Circuits	9:00-10:45 Area 11: H-6: Micro Fabrication and Micro fluidic Devices	9:00-10:45 Area 2&7: CI-6: Optical Interconnect (1)	9:00-10:45 Area 9: J-6: Photon & Spin in Nanostructures				9:00-10:45 Area 12: N-6: Spintronics materials and devices
11:15-12:35 Area 5: G-7: RF Circuits (2)	11:15-12:15 Area 11: H-7: Nano fabrication and Application	11:15-12:25 Area 2&7: CI-7: Optical Interconnect (2)	11:15-12:30 Area 9: J-7: Quantum Transport in Nanostructures				11:15-12:30 Area 12: N-7: Spin transport in semiconductors
		14:00-15:30 Area 7: I-8: SiGe-Based Optical Devices	14:00-15:45 Area 9: J-8: Qubit and Novel Functional Devices	14:00-15:45 Area 13: K-8: Graphene Property	14:00-15:45 Area 14: L-8: Power Devices & ICs	14:00-15:45 Area 8: M-8: Growth techniques of Si and Ge	14:00-15:30 Area 12: N-8: Circuit application of spintronics devices
		16:10-17:25 Area 7: I-9: Quantum-Dot Devices		16:10-17:25 Area 13: K-9: Graphene Device	16:10-17:25 Area 14: L-9: Novel Concepts	16:10-17:10 Area 8: M-9: Characterization of group IV related materials	16:10-17:25 Area 12: N-9: Physics of spintronics devices

Area 11: Micro/Nano Electromechanical Systems and Bio/Medical Analyses
 Area 12: Spintronics Materials and Devices
 Area 13: Application of Nanotubes, Nanowires, and Graphene
 Area 14: Photovoltaics & Power Semiconductor Devices

2011 International Conference on Solid State Devices and Materials (SSDM 2011)

SECRETARIAT

c/o Inter Group Corp.

NBF Akasaka Sanno Square Bldg.,

2-2-12, Akasaka, Minato-ku,

Tokyo 107-0052, Japan

Phone : +81-3-5549-6909

F a x : +81-3-5549-3201

E-mail : ssdm_secretariat@intergroup.co.jp

U R L : <http://www.ssdm.jp>

